ISSN 0022-0248

JOURNAL OF CRYSTAL GROWTH

VOLUME 200, pp. 635–720
(1999)

MASTER INDEX

Volumes 191–200

EDITORS:

G.B. STRINGFELLOW (Principal Editor), University of Utah

M. SCHIEBER (Founding Editor), Hebrew University

R.S. FEIGELSON, Stanford University

D.T.J. HURLE, University of Bristol

R. KERN, Université Aix–Marseille

T. NISHINAGA, University of Tokyo

CO-FOUNDERS: N. CABRERA, B. CHALMERS, F.C. FRANK
FORMER ADVISOR: R.A. LAUDISE†

Last Issue of this Volume

NOW included in your subscription:
ELECTRONIC ACCESS
www.elsevier.nl/locate/elecacc

North-Holland

http://www.elsevier.nl/locate/jcrysgro

Journal of Crystal Growth

EDITORIAL BOARD

G.B. STRINGFELLOW (Principal Editor)
College of Eng., Univ. Utah
1495 East 100 South, Room 214
Salt Lake City, UT 84112-1109, USA
Fax: +1 801 581 8692
E-mail: stringfellow@eng.utah.edu

M. SCHIEBER (Founding Editor)
The Fredy and Nadine Herrmann
Graduate School of Appl. Sci.
Hebrew University, Jerusalem 91904, Israel
Fax: +972 2 566 3878
E-mail: schieber@vms.huji.ac.il

R.S. FEIGELSON
Ctr. Materials Res., Press Warehouse
Stanford University
Stanford, CA 94305-4045, USA
Fax: +1 650 723 3752/3044
E-mail: feigel@soe.stanford.edu

D.T.J. HURLE
H.H. Wills Phys. Lab.
University of Bristol
Tyndall Avenue
Bristol BS8 1TL, UK

R. KERN
CRMC², CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Fax: +33 4 91 418 916
E-mail: kern@crmc2.univ-mrs.fr

T. NISHINAGA
Dept. Electron. Eng., University of Tokyo
7-3-1, Hongo, Bunkyo-ku, Tokyo 113, Japan
Fax: +81 3 5684 3974
E-mail: tatau@ee.t.u-tokyo.ac.jp

ASSOCIATE EDITORS

C.R. ABERNATHY (*Chemical Beam Epitaxy, III-Nitrides, Novel Dielectrics*)
K.W. BENZ (*Microgravity, Electronic Materials*)
N.E. CHAYEN (*Crystallization of Biological Macromolecules*)
A.A. CHERNOV (*Kinetics of Crystallization, Protein Crystallization*)
A.Y. CHO (*Molecular Beam Epitaxy*)
S.R. CORIELL (*Theory*)
J.J. DERBY (*Computational Models*)
M.E. GLICKSMAN (*Solidification*)
M.S. GOORSKY (*XRD Characterization, Epitaxy for Devices*)
T. HIBIYA (*Oxides, Melt Thermophysical Properties, Microgravity*)
S. HIYAMIZU (*Molecular Beam Epitaxy*)
R. JAMES (*II–VI Semiconductors, Radiation Sensors*)
T.F. KUECH (*Thin Films and Electronic and Optical Devices*)
A. McPHERSON (*Protein Growth*)
P.A. MORRIS HOTSENPILLER (*Electrooptical Crystals, Oxide Thin Films, Book Reviews*)
J.B. MULLIN (*Semiconductors*)
K. NAKAJIMA (*Liquid and Vapor Phase Epitaxy*)
H. OHNO (*Epitaxy*)
K. PLOOG (*Molecular Beam Epitaxy*)
R.W. ROUSSEAU (*Solution Growth, Industrial Crystallization*)
K. SATO (*Biocrystallization and Organic Crystals*)
L.F. SCHNEEMEYER (*Superconductivity, Oxides, Novel Materials, Priority Communications*)
D.W. SHAW (*Semiconductors, Epitaxy, Devices*)
M. UWAHA (*Growth Kinetics*)
A.F. WITT (*Semiconductor Crystals*)
A. ZANGWILL (*Theory (Epitaxy)*)

Scope of the journal

Experimental and theoretical contributions are invited in the following fields: Theory of nucleation and growth, molecular kinetics and transport phenomena, crystallization in viscous media such as polymers and glasses. Crystal growth of metals, minerals, semiconductors, magnetics, inorganic, organic and biological substances in bulk or as thin films. Apparatus, instrumentation and techniques for crystal growth, and purification methods. Characterization of single crystals by physical and chemical methods.

Abstracted/indexed in:

Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineered Materials Abstracts; Engineering Index; INSPEC; Metals Abstracts.

Subscription information 1999

Volumes 195–207 of Journal of Crystal Growth (ISSN 0022-0248) are scheduled for publication. (Frequency: semimonthly.) Prices are available from the publishers upon request. Subscriptions are accepted on a prepaid basis only. Issues are sent by SAL (Surface Air Lifted) mail wherever this service is available. Airmail rates are available upon request.

Orders, claims, and product enquiries

Please contact the Customer Support Department at the Regional Sales Office nearest to you:

New York: Elsevier Science, P.O. Box 945, New York, NY 10159-0945, USA; tel.: +1 212 633 3730 [toll free number for North American customers: 1-888-4ES-INFO (437-4636)]; fax: +1 212 633 3680; e-mail: usinfo-f@elsevier.com.

Amsterdam: Elsevier Science, P.O. Box 211, 1000 AE Amsterdam, The Netherlands; tel.: +31 20 485 3757; fax: +31 20 485 3432; e-mail: nlinfo-f@elsevier.nl.

Tokyo: Elsevier Science, 9-15 Higashi-Azabu 1-chome, Minato-ku, Tokyo 106-0044, Japan; tel.: +81 3 5561 5033; fax: +81 3 5561 5047; e-mail: info@elsevier.co.jp.

Singapore: Elsevier Science, No. 1 Temasek Avenue, #17-1 Millenia Tower, Singapore 039192; tel.: +65 434 3727; fax: +65 337 2230; e-mail: asiainfo@elsevier.com.sg.

Rio de Janeiro: Elsevier Science, Rua Sete de Setembro 111/16 Andar, 20050-002 Centro, Rio de Janeiro – RJ, Brazil; tel.: +55 21 509 5340; fax: +55 21 507 1991; e-mail: elsevier@campus.com.br. [Note: (Latin America): for orders, claims and help desk information, please contact the Regional Sales Office in New York as listed above.]

Claims for issues not received should be made within six months of our publication (mailing) date.

Advertising information

Advertising orders and enquiries can be sent to:

USA, Canada and South America: Mr. Tino de Carlo, The Advertising Department, Elsevier Science Inc., 655 Avenue of the Americas, New York, NY 10010-5107, USA; tel.: +1 212 633 3815; fax: +1 212 633 3820; e-mail: t.decarlo@elsevier.com.

Japan: The Advertising Department, Elsevier Science K.K., 9-15 Higashi-Azabu 1-chome, Minato-ku, Tokyo 106-0044, Japan; tel.: +81 3 5561 5033; fax: +81 3 5561 5047.

Europe and ROW: Rachel Gresle-Farthing, The Advertising Department, Elsevier Science Ltd., The Boulevard, Langford Lane, Kidlington, Oxford OX5 1GB, UK; tel.: +44 1865 843565; fax: +44 1865 843976; e-mail: r.gresle-farthing@elsevier.co.uk.

US mailing notice – *Journal of Crystal Growth* (ISSN 0022-0248) is published semimonthly by Elsevier Science B.V., Molenwerf 1, P.O. Box 211, 1000 AE Amsterdam, The Netherlands. Annual subscription price in the USA is US$ 7545 (valid in North, Central and South America only), including air speed delivery. Periodicals postage paid at Jamaica, NY 11431, USA.

US postmasters: Send address changes to Journal of Crystal Growth, Publications Expediting, Inc., 200 Meacham Avenue, Elmont, NY 11003, USA. Airfreight and mailing in the USA by Publications Expediting.

The paper used in this publication meets the requirements of ANSI/NISO Z39.48-1992 (Permanence of Paper)

PRINTED IN THE NETHERLANDS

North-Holland, an imprint of Elsevier Science

EDITORIAL BOARD

G.B. STRINGFELLOW (Principal Editor)
College of Eng., Univ. Utah
1495 East 100 South, Room 214
Salt Lake City, UT 84112-1109, USA
Fax: +1 801 581 8692
E-mail: stringfellow@eng.utah.edu

M. SCHIEBER (Founding Editor)
The Fredy and Nadine Herrmann
Graduate School of Appl. Sci.
Hebrew University, Jerusalem 91904, Israel
Fax: +972 2 566 3878
E-mail: schieber@vms.huji.ac.il

R.S. FEIGELSON
Ctr. Materials Res., Press Warehouse
Stanford University
Stanford, CA 94305-4045, USA
Fax: +1 650 723 3752/3044
E-mail: feigel@soe.stanford.edu

D.T.J. HURLE
H.H. Wills Phys. Lab.
University of Bristol
Tyndall Avenue
Bristol BS8 1TL, UK

R. KERN
CRMC^2, CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Fax: +33 4 91 418 916
E-mail: kern@crmc2.univ-mrs.fr

T. NISHINAGA
Dept. Electron. Eng., University of Tokyo
7-3-1, Hongo, Bunkyo-ku, Tokyo 113, Japan
Fax: +81 3 5684 3974
E-mail: tatau@ee.t.u-tokyo.ac.jp

ASSOCIATE EDITORS

C.R. ABERNATHY (*Chemical Beam Epitaxy, III-Nitrides, Novel Dielectrics*)
Dept. Mater. Sci. Eng., Univ. Florida
Rhines Hall, Gainesville, FL 32606, USA
Fax: +1 352 846 1182
E-mail: caber@mse.ufl.edu

K.W. BENZ (*Microgravity, Electronic Materials*)
Kristallographisches Inst., Universität
Hebelstr. 25, D-79104 Freiburg, Germany
Fax: +49 761 203 4369
E-mail: benz@ruf.uni-freiburg.de

N.E. CHAYEN (*Crystallization of Biological Macromolecules*)
Biophysics Section, Physics Dept.
Imperial College, London SW7 2BZ, UK
Fax: +44 171 589 0191
E-mail: n.chayen@ic.ac.uk

A.A. CHERNOV (*Kinetics of Crystallization, Protein Crystallization*)
Inst. Crystallography, Acad. of Sciences
Leninskii Prosp., Moscow 117333
Russian Fed.
Fax: +7 095 135 1011
Univ. Space Res. Assoc., 4950 Corp. Dr.
Ste. 100, Huntsville, AL 35805, USA
Fax: +1 205 544 8762
E-mail: alex.chernov@msfc.nasa.gov

A.Y. CHO (*Molecular Beam Epitaxy*)
Lucent Technol., Room 6H-422
600 Mountain Ave.
Murray Hill, NJ 07974-0636, USA
Fax: +1 908 582 2043
E-mail: ayc@lucent.com

S.R. CORIELL (*Theory*)
A153 Mater.
Nat. Inst. of Standards & Technol.
Gaithersburgh, MD 20899-0001, USA
Fax: +1 301 975 4553
E-mail: coriell@nist.gov

J.J. DERBY (*Computational Models*)
Dept. Chem. Eng. & Mater. Sci.
Univ. Minnesota, 151 Amundson Hall
421 Washington Ave. S.E.
Minneapolis, MN 55455-0132, USA
Fax: +1 612 626 7246
E-mail: derby@maroon.tc.umn.edu

E. GLICKSMAN (*Solidification*)
School of Eng., Mater. Eng. Dept.
Rensselaer Polytechnic Inst.
Troy, NY 12180-3590, USA
Fax: +1 518 276 2198
E-mail: glickm@rpi.edu

M.S. GOORSKY (*XRD Characterization, Epitaxy for Devices*)
Dept. Mater. Sci. Eng., Univ. California
Los Angeles, CA 90095-1595, USA
Fax: +1 310 206 7353
E-mail: goorsky@seas.ucla.edu

T. HIBIYA (*Oxides, Melt Thermophysical Properties, Microgravity*)
Fundamental Res. Labs., NEC Corp.
34, Miyukigaoka, Tsukuba 305, Japan
Fax: +81 298 566 136
E-mail: hibiya@frl.cl.nec.co.jp

S. HIYAMIZU (*Molecular Beam Epitaxy*)
Dept. Phys. Sci., Graduate School Eng. Sci.
Osaka Univ., Toyonaka, Osaka 560, Japan
Fax: +81 6 845 4632
E-mail: hiyamizu@mp.es.osaka-u.ac.jp

R. JAMES (*II–VI Semiconductors, Radiation Sensors*)
Sandia National Labs., MS 9405
7011 East Ave., Livermore, CA 94550, USA
Fax: +1 925 294 3870
E-mail: rbjames@sandia.gov

T.F. KUECH (*Thin Films and Electronic and Optical Devices*)
Dept. Chem. Eng.
Univ. Wisconsin-Madison
Madison, WI 53706, USA
Fax: +1 608 265 3782
E-mail: kuech@engr.wisc.edu

A. McPHERSON (*Protein Growth*)
Dept. Mol. Biol. & Biochem.
Univ. California
Irvine, CA 92697-3900, USA
Fax: +1 949 824 1954
E-mail: amcphers@uci.edu

P.A. MORRIS HOTSENPILLER (*Electrooptical Crystals, Oxide Thin Films, Book Reviews*)
DuPont Central Res. & Devel., Exp. Station
P.O. Box 80356
Wilmington, DE 19880-0356, USA
Fax: +1 302 695 1664; E-mail: patricia.a.morris_hotsenpiller@usa.dupont.com

J.B. MULLIN (*Semiconductors*)
EMC, "The Hoo", Brockhill Road
West Malvern, Worcs. WR14 4DL, UK
Fax: +44 1684 575 591
E-mail: brian.mullin@btinternet.com

K. NAKAJIMA (*Liquid and Vapor Phase Epitaxy*)
Inst. Mater. Res., Tohoku Univ.
Katahira 2-1-1, Sendai 980-8577, Japan
Fax: +81 22 215 2011
E-mail: nakajima@imr.tohoku.ac.jp

H. OHNO (*Epitaxy*)
Research Inst. of Electrical Commun.
Tohoku Univ., Sendai 980-8577, Japan
Fax: +81 22 217 5553
E-mail: ohno@riec.tohoku.ac.jp

K. PLOOG (*Molecular Beam Epitaxy*)
Paul-Drude-Inst. für Festkörperelektronik
Hausvogteiplatz 5–7
D-10117 Berlin, Germany
Fax: +49 30 203 77201
E-mail: ploog@pdi-berlin.de

R.W. ROUSSEAU (*Solution Growth, Industrial Crystallization*)
School of Chem. Eng.
Georgia Inst. of Technol.
Atlanta, GA 30332-0100, USA
Fax: +1 404 894 2866
E-mail: ronald.rousseau@che.gatech.edu

K. SATO (*Biocrystallization and Organic Crystals*)
Fac. Appl. Biol. Sci., Hiroshima Univ.
Higashi-Hiroshima 724, Japan
Fax: +81 824 227 062
E-mail: kyosato@ipc.hiroshima-u.ac.jp

L.F. SCHNEEMEYER (*Superconductivity, Oxides, Novel Materials, Priority Communications*)
Room 1A-363, AT&T Bell Labs.
Murray Hill, NJ 07974-2070, USA
Fax: +1 908 582 2521
E-mail: schneemeyer@bell-labs.com

D.W. SHAW (*Semiconductors, Epitaxy, Devices*)
Univ. Texas, 10009 Apple Creek Dr.
Dallas, TX 75243, USA
Fax: +1 972 234 2648
E-mail: dnsw@worldnet.att.net

M. UWAHA (*Growth Kinetics*)
Dept. Physics, Nagoya Univ.
Furo-cho, Chikusa-ku, Nagoya 464-8602
Japan
Fax: +81 52 789 2928
E-mail: uwaha@phys.nagoya-u.ac.jp

A.F. WITT (*Semiconductor Crystals*)
Dept. of Metall. & Mater. Sci.
Massachusetts Inst. of Technol.
Cambridge, MA 02139, USA
Fax: +1 617 253 5827

A. ZANGWILL (*Theory (Epitaxy)*)
School of Physics, Georgia Inst. of Technol.
Atlanta, GA 30332, USA
Fax: +1 404 894 9958
E-mail: andrew.zangwill@physics.gatech.edu

© 1999 Elsevier Science B.V. All rights reserved

This journal and the individual contributions contained in it are protected under copyright by Elsevier Science B.V., and the following terms and conditions apply to their use:

Photocopying
Single photocopies of single articles may be made for personal use as allowed by national copyright laws. Permission of the Publisher and payment of a fee is required for all other photocopying, including multiple or systematic copying, copying for advertising or promotional purposes, resale, and all forms of document delivery. Special rates are available for educational institutions that wish to make photocopies for non-profit educational classroom use.
Permissions may be sought directly from Elsevier Science Rights & Permissions Department, P.O. Box 800, Oxford OX5 1DX, UK; tel.: +44 1865 843830, fax: +44 1865 853333, e-mail: permissions@elsevier.co.uk. You may also contact Rights & Permissions directly through Elsevier's home page (http://www.elsevier.nl), selecting first 'Customer Support', then 'General Information', then 'Permissions Query Form'.
In the USA, users may clear permissions and make payments through the Copyright Clearing Center, Inc., 222 Rosewood Drive, Danvers, MA 01923, USA; tel.: +1 978 7508400, fax: +1 978 7504744, and in the UK through the Copyright Licensing Agency Rapid Clearance Service (CLARCS), 90 Tottenham Court Road, London W1P 0LP, UK; tel.: +44 171 631 5555, fax: +44 171 631 5500. Other countries may have a local reprographic rights agency for payments.

Derivative works
Subscribers may reproduce tables of contents or prepare lists of articles including abstracts for internal circulation within their institutions. Permission of the Publisher is required for resale or distribution outside the institution.
Permission of the Publisher is required for all other derivative works, including compilations and translations.

Electronic storage or usage
Permission of the Publisher is required to store or use electronically any material contained in this journal, including any article or part of an article.
Except as outlined above, no part of this publication may be reproduced, stored in a retrieval system or transmitted in any form or by any means, electronic, mechanical, photocopying, recording or otherwise, without prior written permission of the Publisher.
Address permissions requests to: Elsevier Science Rights & Permissions Department, at the mail, fax and e-mail addresses noted above.

Notice
No responsibility is assumed by the Publisher for any injury and/or damage to persons or property as a matter of products liability, negligence or otherwise, or from any use or operation of any methods, products, instructions or ideas contained in the material herein. Because of rapid advances in the medical sciences, in particular, independent verification of diagnoses and drug dosages should be made. Although all advertising material is expected to conform to ethical (medical) standards, inclusion in this publication does not constitute a guarantee or endorsement of the quality of such product or of the claims made of it by its manufacturer.

⊙ The paper used in this publication meets the requirements of ANSI/NISO Z39.48-1992 (Permanence of Paper)

PRINTED IN THE NETHERLANDS

ELSEVIER

Journal of Crystal Growth 200 (1999) 635–708

JOURNAL OF CRYSTAL GROWTH

Author index to volumes 191–200

Abakumov, A.M., see Stefan, M. 200 (1999) 148
Abbaschian, R., see López, C.R. 200 (1999) 1
Abe, K., see Nakanishi, H. 191 (1998) 711
Abe, K., see Maeda, S. 192 (1998) 117
Abe, K., see Maeda, S. 194 (1998) 70
Abramof, E., see Rappl, P.H.O. 191 (1998) 466
Abrutis, A., J.P. Sénateur, F. Weiss, V. Bigelyte, A. Teiserskis, V. Kubilius, V. Galindo and S. Balevicius, High quality $YBa_2Cu_3O_7$ films grown on $LaAlO_3$ by single source pulsed metalorganic chemical vapor deposition 191 (1998) 79
Achtziger, N., see Reislöhner, U. 197 (1999) 576
Adachi, G., see Dąbkowski, A. 197 (1999) 879
Adachi, G., see Imanaka, N. 200 (1999) 169
Adachi, H., Y. Takahashi, J. Yabuzaki, Y. Mori and T. Sasaki, Growth of high quality nonlinear optical crystal 4-dimethylamino-N-methyl-4-stilbazolium tosylate (DAST) 198/199 (1999) 568
Adcock-Downey, L., see Carter, D.C. 196 (1999) 602
Adcock-Downey, L., see Carter, D.C. 196 (1999) 610
Addadi, L., see Bromberg, R. 193 (1998) 656
Addai-Mensah, J., see Barnes, M.C. 200 (1999) 251
Adinolfi, S., see Sica, F. 196 (1999) 305
Agarwal, M.K., see Deshpande, M.P. 197 (1999) 833
Agert, C., see Höhnsdorf, F. 195 (1998) 391
Agethen, M., see Velling, P. 195 (1998) 117
Aggarwal, M.D., see Wang, W.S. 198/199 (1999) 578
Aguiar, R., see Trtík, V. 192 (1998) 175
Ahe, M. v.d., see Schmidt, R. 195 (1998) 124
Ahilea, T. and E. Zolotoyabko, SiO_2 formation in oxygen-implanted silicon 198/199 (1999) 414
Ahmed, M.U., see Irvine, S.J.C. 197 (1999) 616
Aiga, M., see Takemi, M. 191 (1998) 18
Aina, L., see Ferguson, I.T. 195 (1998) 648
Aitken, N.M., M.D.G. Potter, D.J. Buckley, J.T. Mullins, J. Carles, D.P. Halliday, K. Durose, B.K. Tanner and A.W. Brinkman, Characterisation of cadmium telluride bulk crystals grown by a novel "multi-tube" vapour growth technique 198/199 (1999) 984
Akabori, M., J. Motohisa and T. Fukui, Formation and characterization of modulated two-dimensional electron gas on GaAs multiatomic steps grown by metalorganic vapor phase epitaxy 195 (1998) 579
Akaishi, M., see Hong, S.M. 200 (1999) 326
Akasaka, T., see Nishida, T. 195 (1998) 41
Akasaka, T., see Kobayashi, Y. 195 (1998) 187
Akasaka, T., see Nishida, T. 195 (1998) 459
Akasaki, I., Progress in crystal growth and future prospects of group III nitrides by metalorganic vapor-phase epitaxy 195 (1998) 248
Akasaki, I., see Yamaguchi, S. 195 (1998) 309
Akasaki, I., Renaissance and progress in crystal growth of nitride semiconductors 198/199 (1999) 885
Al-Muhanna, A., see Mawst, L.J. 195 (1998) 609
Ala, P., see Carter, D.C. 196 (1999) 610
Alamo, J., see Sochinskii, N.V. 192 (1998) 342
Alatalo, H., see Sha, Z.L. 198/199 (1999) 692
Alexander, W.B., see Lang, A.R. 200 (1999) 446
Alexandru, H., see Stanculescu, A. 198/199 (1999) 572
Alkemper, J., S. Sous, C. Stöcker and L. Ratke, Directional solidification in an aerogel furnace with high resolution optical temperature measurements 191 (1998) 252
Allerman, A.A., see Biefeld, R.M. 195 (1998) 356
Allieri, B., see Sangaletti, L. 198/199 (1999) 454
Allieri, B., see Depero, L.E. 198/199 (1999) 516
Allieri, B., see Sangaletti, L. 198/199 (1999) 1240
Allwood, D.A., N.J. Mason and P.J. Walker, In situ characterisation of MOVPE by surface photoabsorption. I. Substrate oxide desorption 195 (1998) 163
Alvarez, F.D., see Mawst, L.J. 195 (1998) 609

0022-0248/99/$ – see front matter © 1999 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(99)00165-7

Amano, C., K. Tateno, H. Takenouchi and Y. Ohiso, MOVPE growth of C-doped GaAs/AlAs DBRs for wafer fusion 193 (1998) 460
Amano, H., see Yamaguchi, S. 195 (1998) 309
Ambacher, O., see Off, J. 195 (1998) 286
Amberg, G., see Tönhardt, R. 194 (1998) 406
Amelinckx, S., see Pauwels, B. 200 (1999) 126
Amir, N., see Levy, M. 197 (1999) 626
Amir, N., see Stolyarova, S. 198/199 (1999) 1157
Amir, N., see Cohen, K. 198/199 (1999) 1174
Ammerahl, U., G. Dhalenne, A. Revcolevschi, J. Berthon and H. Moudden, Crystal growth and characterization of the spin-ladder compound $(Sr,Ca)_{14}Cu_{24}O_{41}$ 193 (1998) 55
Ammerahl, U. and A. Revcolevschi, Crystal growth of the spin-ladder compound $(Ca,La)_{14}Cu_{24}O_{41}$ and observation of one-dimensional disorder 197 (1999) 825
Ammerahl, U., see Revcolevschi, A. 198/199 (1999) 593
Amon, J., P. Berwian and G. Müller, Computer-assisted growth of low-EPD GaAs with 3″ diameter by the vertical gradient-freeze technique 198/199 (1999) 361
Amon, J., J. Härtwig, W. Ludwig and G. Müller, Analysis of types of residual dislocations in the VGF growth of GaAs with extremely low dislocation density (EPD$\ll$ 1000 cm^{-2}) 198/199 (1999) 367
An, H.G., see Lee, H. 191 (1998) 59
Anderson, T.J., see Prasad, S.R. 198/199 (1999) 194
Ando, Y., see Zhao, X. 198/199 (1999) 934
Andreeta, M.R.B., A.C. Hernandes, S.L. Cuffini, J.A. Guevara and Y.P. Mascarenhas, Laser heated pedestal growth of orthorhombic $SrHfO_3$ single crystal fiber 200 (1999) 621
Andrukhiv, A., G. Khlyap and M. Andrukhiv, Some properties of heterostructures based on new semiconductor ZnCdHgTe 198/199 (1999) 1162
Andrukhiv, M., see Andrukhiv, A. 198/199 (1999) 1162
Angermeier, D., R. Monna, A. Slaoui and J.C. Muller, Analysis of thin film polysilicon on graphite substrates deposited in a thermal CVD system 191 (1998) 386
Anton, R., see Franke, T. 193 (1998) 451
Antonov, P.I., see Krymov, V.M. 198/199 (1999) 210
Anuratha, H., see Shanthi, S. 194 (1998) 369
Anzai, H., S. Maki, S. Takasaki, S. Tanaka, S. Nakatsuji, J.-i. Yamada, K. Nozaki, A. Negishi and M. Harusawa, Effect of electrode-materials for electrocrystallization of organic charge-transfer complex $(TMTSF)_2ClO_4$ 191 (1998) 148
Aoki, T., see Niraula, M. 200 (1999) 90
Aoyagi, Y., see Hwang, J. 200 (1999) 63
Aoyama, T., see Yap, Y.K. 198/199 (1999) 1028
Apostol, E., see Vasile, E. 198/199 (1999) 806
Aquilano, D., see Sgualdino, G. 192 (1998) 290
Aquilano, D., see Rubbo, M. 194 (1998) 156
Arafune, K. and A. Hirata, Thermal and solutal Marangoni convection in In–Ga–Sb system 197 (1999) 811
Arai, E., see Ichimura, M. 198/199 (1999) 308
Ard, C.K., see Maxey, C.D. 197 (1999) 427
Arens, M., see Kurpas, P. 195 (1998) 217
Arès, R., see Gupta, J.A. 195 (1998) 205
Arès, R., J. Hu, P. Yeo and S.P. Watkins, Time-resolved reflectance difference spectroscopy of InAs growth under alternating flow conditions 195 (1998) 234
Arkenbout, G.J., see van den Berg, E.P.G. 191 (1998) 169
Arnold, S., see Izmailov, A.F. 196 (1999) 234
Arnoux, B., see Vidal, O. 196 (1999) 559
Arnoux, T., see von Bardeleben, H.J. 197 (1999) 718
Arsenov, A., see Shulyatev, D. 198/199 (1999) 511
As, D.J., see Lima, A.P. 197 (1999) 31
Asaba, S., see Nakanishi, H. 191 (1998) 711
Asano, T., see Saito, T. 191 (1998) 723
Asanov, A., see Guo, B. 196 (1999) 424
Asher, S.E., see Bertness, K.A. 196 (1999) 13
Asomoza, R., see Salazar-Hernández, B. 197 (1999) 783
Assmus, W., see Langsdorf, A. 192 (1998) 152
Assmus, W., see Gross, C. 198/199 (1999) 188
Asthagiri, D., see Neal, B.L. 196 (1999) 377
Astier, J.-P., see Budayova, M. 196 (1999) 297
Aswal, D.K., M. Shinmura, Y. Hayakawa and M. Kumagawa, In situ observation of melting/dissolution, nucleation and growth of $NdBa_2Cu_3O_x$ by high temperature optical microscopy 193 (1998) 61
Aswal, D.K., M. Shinmura, Y. Hayakawa and M. Kumagawa, In situ measurement of the growth rate of $YBa_2Cu_3O_x$ single crystals 197 (1999) 379
Aswal, D.K., M. Shinmura, Y. Hayakawa and M. Kumagawa, Direct observations of pseudo-binary $NdBa_2Cu_3O_x$–$Ba_3Cu_{10}O_{13}$ phase diagram and $NdBa_2Cu_3O_x$ crystallization under reduced oxygen atmosphere 200 (1999) 427

Ataev, B.M., A.M. Bagamadova, V.V. Mamedov, A.K. Omaev and M.R. Rabadanov, Highly conductive and transparent thin ZnO films prepared in situ in a low pressure system 198/199 (1999) 1222
Ataka, M., see Soga, T. 196 (1999) 291
Ataka, M., see Sakurazawa, S. 196 (1999) 325
Ataka, M., see Michinomae, M. 197 (1999) 257
Ataka, M., see Tachibana, M. 198/199 (1999) 661
Ataka, M., see Niimura, N. 200 (1999) 265
Atherton, J., see Zaitseva, N. 197 (1999) 911
Atroshchenko, L.V., L.P. Gal'chinetskii, S.N. Galkin, V.D. Ryzhikov, V.I. Silin and N.I. Shevtsov, Distribution of tellurium in melt-grown ZnSe(Te) crystals 197 (1999) 471
Atroshchenko, L.V., L.P. Gal'chinetskii, S.N. Galkin, V.D. Ryzhikov and V.I. Silin, Structure defects and phase transition in tellurium-doped ZnSe crystals 197 (1999) 475
Atroshchenko, L.V., L.P. Gal'chinetskii, S.N. Galkin, V.D. Ryzhikov, N.I. Shevtsov and V.I. Silin, Structural perfection and mechanical properties of $ZnSe_{1-x}Te_x$ crystals grown by the Bridgman technique 198/199 (1999) 292
Aubert, P., see Veignant, F. 196 (1999) 141
Aubry, A., see Taleb, M. 200 (1999) 575
Ausloos, M., see Vandewalle, N. 197 (1999) 317
Auvray, L., see Dumont, H. 197 (1999) 755
Averous, M., see Breton, G. 200 (1999) 112
Avrahami, Y., D. Shilo, N. Mainzer and E. Zolotoyabko, Study of atomic diffusion in crystalline structures by high-resolution X-ray diffraction 198/199 (1999) 264
Avrov, D.D., A.S. Bakin, S.I. Dorozhkin, V.P. Rastegaev and Yu.M. Tairov, The analysis of mass transfer in system β-SiC–α-SiC under silicon carbide sublimation growth 198/199 (1999) 1011
Azzi, A., see Zhu, D.-W. 196 (1999) 356

Baars, T., see Höfling, E. 191 (1998) 607
Babcock, S.E., see Hansen, D.M. 195 (1998) 144
Babinski, A., see Li, G. 195 (1998) 54
Babonas, G.-J., see Shvanskaya, L. 198/199 (1999) 600
Babonas, G.-J., see Leonyuk, L. 198/199 (1999) 619
Babonas, G.-J., see Maltsev, V. 198/199 (1999) 626
Babu, S.M., see Senguttuvan, N. 191 (1998) 130
Babu, S.M., see Mohan, P. 200 (1999) 96
Bacchin, G. and T. Nishinaga, Dependence of the degree of selectivity on the Al content during the selective area growth of AlGaAs on GaAs(0 0 1) by PSE/MBE 191 (1998) 599
Bacchin, G. and T. Nishinaga, A detailed comparison of the degree of selectivity, morphology and growth mechanisms between PSE/MBE and conventional MBE 198/199 (1999) 1130
Bachem, K.H., see Obloh, H. 195 (1998) 270
Back, J.T., see Kwon, K.S. 198/199 (1999) 1039
Backofen, R., see Mühe, A. 198/199 (1999) 409
Backov, R., see Whipps, S. 192 (1998) 243
Badens, E., S. Veesler and R. Boistelle, Crystallization of gypsum from hemihydrate in presence of additives 198/199 (1999) 704
Bagamadova, A.M., see Ataev, B.M. 198/199 (1999) 1222
Bahir, G., see Mainzer, N. 197 (1999) 542
Bai, C.L., see Gong, Q. 192 (1998) 376
Baik, H.K., see Choi, D.J. 191 (1998) 718
Baird, J.K., S.C. Hill and J.C. Clunie, Kinetics of protein crystal nucleation and growth in the batch method 196 (1999) 220
Bajcar, R.C., see Krasnov, A.N. 194 (1998) 53
Bąk-Misiuk, J., see Mycielski, A. 197 (1999) 423
Baker, N., see Barber, P. 198/199 (1999) 815
Bakin, A.S., see Avrov, D.D. 198/199 (1999) 1011
Bakin, A.S., S.I. Dorozhkin, A.O. Lebedev, B.A. Kirillov, A.A. Ivanov and Yu.M. Tairov, Stress and misoriented area formation under large silicon carbide boule growth 198/199 (1999) 1015
Bakovets, V.V., Growth and wetting angles as the control parameters of crystal shape in Czochralski method 193 (1998) 720
Balaban, N.P., see Kuranova, I.P. 196 (1999) 313
Balakumar, S. and H.C. Zeng, Preparation of orthorhombic molybdenum trioxide crystals using a semi-open flux growth system 194 (1998) 195
Balakumar, S. and H.C. Zeng, Growth modes in vapour-phase prepared orthorhombic molybdenum trioxide crystals 197 (1999) 186
Baldochi, S.L., see Shimamura, K. 197 (1999) 896
Baldochi, S.L., see Santo, A.M.E. 198/199 (1999) 466
Baldochi, S.L., K. Shimamura, K. Nakano, N. Mujilatu and T. Fukuda, Growth and optical characteristics of Ce-doped and Ce:Na-codoped $BaLiF_3$ single crystals 200 (1999) 521
Baldock, P.F.M., see Stewart, P.D.S. 196 (1999) 665
Balevicius, S., see Abrutis, A. 191 (1998) 79
Ballif, C., see Regula, M. 193 (1998) 109
Balykov, L.N., M. Kitamura, I.L. Maksimov and K. Nishioka, Growth and dissolution kinetics of step structure 198/199 (1999) 32

Banas, M.A., see Han, J. 195 (1998) 291

Bancel, P.A., V.B. Cajipe, F. Rodier and J. Witz, Laser seeding for bi-omolecular crystallization 191 (1998) 537

Bancel, P.A., V.B. Cajipe and F. Rodier, Manipulating crystals with light 196 (1999) 685

Bandeira, I.N., see Rappl, P.H.O. 191 (1998) 466

Bao, C.L., see Cai, L.C. 197 (1999) 364

Baran, M., see Barilo, S.N. 198/199 (1999) 636

Barat, C., T. Duffar and J.-P. Garandet, Estimation of the curvature of the solid–liquid interface during Bridgman crystal growth 194 (1998) 149

Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). III. Growth process 194 (1998) 101

Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). IV. Characterisation of the final product 194 (1998) 109

Barbé, M., see Mora-Seró, I. 197 (1999) 497

Barbé, M., see Triboulet, R. 198/199 (1999) 968

Barber, P., C. Hayes, N. Baker and W. Rosch, Estimating crystal quality in semiconductors using voltammetry 198/199 (1999) 815

Barilo, S.N., see Leonyuk, N.I. 191 (1998) 135

Barilo, S.N., see Koporulina, E.V. 198/199 (1999) 460

Barilo, S.N., see Zhigunov, D.I. 198/199 (1999) 605

Barilo, S.N., see Shiryaev, S.V. 198/199 (1999) 631

Barilo, S.N., S.V. Shiryaev, V.I. Gatalskaya, D.I. Zhigunov, A.V. Pushkarev, V.V. Fedotova, H. Szymczak, R. Szymczak, M. Baran, J.W. Lynn, N. Rosov and S. Skanthakumar, A new method for growing $Ba_{1-x}K_xBiO_3$ single crystals and investigation of their properties 198/199 (1999) 636

Barilo, S.N., G.L. Bychkov, L.A. Kurnevich, N.I. Leonuk, V.P. Mikhailov, S.V. Shiryaev, V.T. Koyava and T.V. Smirnova, Controlled crystallization of emerald from the fluxed melt 198/199 (1999) 716

Barmin, I.V., see Senchenkov, A.S. 197 (1999) 552

Barnes, M.C., J. Addai-Mensah and A.R. Gerson, The kinetics of desilication of synthetic spent Bayer liquor seeded with cancrinite and cancrinite/sodalite mixed-phase crystals 200 (1999) 251

Bartram, M.E., see Han, J. 195 (1998) 291

Barvinschi, F., J.-L. Santailler, T. Duffar and H. Le Gal, Modelling of Verneuil process for the sapphire crystal growth 198/199 (1999) 239

Barz, A., see Dold, P. 192 (1998) 125

Baskar, K., see Saravanan, S. 192 (1998) 23

Battaile, C.C., D.J. Srolovitz and J.E. Butler, Atomic-scale simulations of chemical vapor deposition on flat and vicinal diamond substrates 194 (1998) 353

Batur, C., see Seidensticker, R.G. 198/199 (1999) 988

Baucom, K.C., see Biefeld, R.M. 195 (1998) 356

Bauhuis, G.J., P.R. Hageman and P.K. Larsen, Heavily doped p-type AlGaInP grown by metalorganic chemical vapor deposition 191 (1998) 313

Bauhuis, G.J., see Hageman, P.R. 194 (1998) 270

Baumeister, H., see Kröner, P. 195 (1998) 660

Baumstark, M.W., see Ritter, S. 196 (1999) 344

Bawendi, M.G., see Heine, J.R. 195 (1998) 564

Bayender, B., N. Maraşli, E. Çadirli, H. Şişman and M. Gündüz, Solid–liquid surface energy of pivalic acid 194 (1998) 119

Bayer, M., see Höfling, E. 191 (1998) 607

Bazarova, G.G., see Pylneva, N.A. 198/199 (1999) 546

Bchetnia, A., see Rebey, A. 194 (1998) 286

Bchetnia, A., see Rebey, A. 194 (1998) 292

Beaumont, B., see Nataf, G. 192 (1998) 73

Beccard, R., H. Protzmann, D. Schmitz, G. Strauch, M. Heuken and H. Juergensen, A novel reactor concept for multiwafer growth of III–V semiconductors 198/199 (1999) 1049

Becker, R., see Leu, S. 195 (1998) 98

Beckermann, C., see Pines, V. 197 (1999) 355

Beckman, C., see Ferguson, I.T. 195 (1998) 648

Beckmann, W., Nucleation phenomena during the crystallisation and precipitation of Abecarnil 198/199 (1999) 1307

Becla, P., see Bryja, L. 197 (1999) 694

Beerbom, M.M., see Giesen, Ch. 195 (1998) 85

Begarney, M.J., M.L. Warddrip, M.J. Kappers and R.F. Hicks, Kinetics of carbon tetrachloride decomposition during the metalorganic vapor-phase epitaxy of gallium arsenide and indium arsenide 193 (1998) 305

Begarney, M.J., see Li, L. 195 (1998) 28

Behr, G., W. Löser, G. Graw, H. Bitterlich, J. Freudenberger, J. Fink and L. Schultz, Growth of $RENi_2B_2C$ single crystals by RF-zone melting 198/199 (1999) 642

Behres, A., see Xu, J. 193 (1998) 50

Behres, A., see Xu, J. 193 (1998) 738

Behres, A., D. Püttjer and K. Heime, Low-pressure metal organic vapour-phase epitaxy and characterization of strained InAs(P)/InAsSb superlattices for infrared emitters 195 (1998) 373

Bejarano, J.M.Z., see Mota, M.A. 198/199 (1999) 850
Béji, L., see Rebey, A. 191 (1998) 734
Belaich, A., see Budayova, M. 196 (1999) 297
Belas, E., see Franc, J. 197 (1999) 593
Belenchuk, A., O. Shapoval, V. Kantser, A. Fedorov, P. Schunk, Th. Schimmel and Z. Dashevsky, Growth of (111)-oriented PbTe thin films on vicinal Si(111) and on Si(100) using fluoride buffers 198/199 (1999) 1216
Belenko, S.V., see Kurlov, V.N. 191 (1998) 520
Belenko, S.V., see Kurlov, V.N. 191 (1998) 779
Beling, C.D., see Fleischer, S. 196 (1999) 53
Bello, I., see Zhang, Y.F. 197 (1999) 136
Belloni, L., see Tardieu, A. 196 (1999) 193
Belogorokhov, A.I., L.I. Belogorokhova and S. Gavrilov, Investigation of properties of porous silicon embedded with ZnSe and CdSe 197 (1999) 702
Belogorokhova, L.I., see Belogorokhov, A.I. 197 (1999) 702
Belov, A.I., see Yelisseyev, A.P. 198/199 (1999) 555
Ben-Dor, L. and J.H. Greenberg, Equilibrium composition in II–VI telluride MOCVD systems 198/199 (1999) 1151
Ben-Yoseph, E. and R.W. Hartel, Computer modeling of sugar crystallization during drying of thin sugar films 198/199 (1999) 1294
Bender, H., see Jin, S. 194 (1998) 189
Bendriss, A., see Mansori, M. 197 (1999) 141
Benjeddou, Ch., see Rebey, A. 194 (1998) 292
Benkaddour, M., see Fougères, P. 197 (1999) 641
Benndorf, G., see Pietzonka, I. 196 (1999) 33
Bennema, P., see Bögels, G. 191 (1998) 446
Bennema, P., see Grimbergen, R.F.P. 191 (1998) 846
Bennema, P., see van Hoof, P.J.C.M. 191 (1998) 861
Bennema, P., see Millan, A. 192 (1998) 215
Bennema, P., see van Hoof, P.J.C.M. 192 (1998) 307
Bennema, P., see Sweegers, C. 197 (1999) 244
Bennema, P., see van Veenendaal, E. 198/199 (1999) 22
Bennett, B.R., see Twigg, M.E. 191 (1998) 651
Benz, K.W., see Cröll, A. 191 (1998) 365
Benz, K.W., see Dold, P. 192 (1998) 125
Benz, K.W., see Fiederle, M. 197 (1999) 635
Ber, B.Ya., see Orton, J.W. 197 (1999) 7
Berdiskihk, T., see Mei, X. 193 (1998) 148
Berenschot, J.W., see Nijdam, A.J. 198/199 (1999) 430
Berg, A., see Ritter, S. 196 (1999) 344
Bergmans, R.H., see Moest, B. 192 (1998) 410
Bergsma-Schutter, W., see Brisson, A. 196 (1999) 456
Berisio, R., see Sica, F. 196 (1999) 305
Berman, A. and D. Charych, Oriented nucleation of inorganic salts on polymeric long chain acid monolayers 198/199 (1999) 796
Bermingham, S.K., see Neumann, A.M. 198/199 (1999) 723
Bermingham, S.K., see Kramer, H.J.M. 198/199 (1999) 729
Bermúdez, V., F. Caccavale, C. Sada, F. Segato and E. Diéguez, Etching effect on periodic domain structures of lithium niobate crystals 191 (1998) 589
Bermúdez, V., M.D. Serrano and E. Diéguez, Growth and characterization of $LiNbO_3$ thin films obtained by liquid phase epitaxy on $Li_xNb_{1-x}O_3$ substrates 198/199 (1999) 526
Bermúdez, V., M.D. Serrano and E. Diéguez, Bulk periodic poled lithium niobate crystals doped with Er and Yb 200 (1999) 185
Bernaerts, D., see Pauwels, B. 200 (1999) 126
Bernard, M.C., see Furlong, M.J. 193 (1998) 114
Berner, A., see Mainzer, N. 197 (1999) 542
Berner, A., see Lisiansky, M. 197 (1999) 630
Berrigan, R.A., N. Maung, S.J.C. Irvine, D.J. Cole-Hamilton and D. Ellis, Thin films of CdTe/CdS grown by MOCVD for photovoltaics 195 (1998) 718
Berthon, J., see Ammerahl, U. 193 (1998) 55
Bertness, K.A., S.R. Kurtz, S.E. Asher and R.C. Reedy Jr., AlInP benchmarks for growth of AlGaInP compounds by organometallic vapor-phase epitaxy 196 (1999) 13
Bertone, D., R. Campi and G. Morello, Etching of InP-based MQW laser structure in a MOCVD reactor by chlorinated compounds 195 (1998) 624
Berwian, P., see Amon, J. 198/199 (1999) 361
Beserman, R., see Levy, M. 197 (1999) 626
Beserman, R., see Cohen, K. 198/199 (1999) 1174
Beserman, R., see Chack, A. 198/199 (1999) 1179
Bettinelli, M., see Sangaletti, L. 198/199 (1999) 454
Bettini, J., see de Castro, M.P.P. 193 (1998) 510
Bhat, A.P., see Nagaraja, H.S. 193 (1998) 674
Bhat, I.B., see Hitchcock, C.W. 195 (1998) 363
Bhat, I.B., see Ehsani, H. 195 (1998) 385
Bhat, R., C. Caneau, L. Salamanca-Riba, W. Bi and C. Tu, Growth of GaAsN/GaAs, GaInAsN/GaAs and GaInAsN/GaAs quantum wells by low-pressure organometallic chemical vapor deposition 195 (1998) 427
Bi, R.-C., see Shu, Z.-Y. 192 (1998) 282
Bi, R.-C., see Cang, H.-X. 194 (1998) 133
Bi, R.-C., see Cang, H.-X. 196 (1999) 442
Bi, W., see Bhat, R. 195 (1998) 427
Biasiol, G., F. Lelarge, K. Leifer and E. Kapon, Mechanisms of self-ordering of nanostructures in nonplanar OMCVD growth 195 (1998) 596
Biblemont, S., see Décobert, J. 195 (1998) 681

Bickermann, M., see Hofmann, D. 198/199 (1999) 1005
Biefeld, R.M., see Han, J. 195 (1998) 291
Biefeld, R.M., A.A. Allerman, S.R. Kurtz and K.C. Baucom, Progress in the growth of mid-infrared InAsSb emitters by metal-organic chemical vapor deposition 195 (1998) 356
Bieg, B., see Cederberg, J.G. 195 (1998) 63
Bieg, B., see Cederberg, J.G. 195 (1998) 105
Bieg, B., see Szatkowski, J. 197 (1999) 684
Bigelyte, V., see Abrutis, A. 191 (1998) 79
Bimberg, D., see Dadgar, A. 195 (1998) 69
Bimberg, D., see Heinrichsdorff, F. 195 (1998) 540
Bimberg, D., see Kappelt, M. 195 (1998) 552
Bimberg, D., see Pohl, U.W. 195 (1998) 569
Birch, J., see Sandström, P. 197 (1999) 849
Birkholz, M., W. Bohne, J. Röhrich, A. Jäger-Waldau and M.C. Lux-Steiner, Stoichiometry and impurity concentrations in II–VI compounds measured by elastic recoil detection analysis (ERDA) 197 (1999) 571
Birkholz, M., see Weiss, T. 198/199 (1999) 1190
Bischoff, J.L., see Dentel, D. 191 (1998) 697
Bitterlich, H., see Behr, G. 198/199 (1999) 642
Biwa, G., H. Yaguchi, K. Onabe and Y. Shiraki, Photoluminescence and photoluminescence-excitation spectroscopy of GaPAsN/GaP lattice-matched multiple quantum well structures 195 (1998) 574
Blagojević I., D. Blečić and R. Vasiljevic Influence of decomposition parameters on agglomeration process and total soda content in precipitated $Al(OH)_3$ 200 (1999) 558
Blagova, E.V., see Kuranova, I.P. 196 (1999) 313
Blanco, A., see Yates, H.M. 193 (1998) 9
Blečić, D., see Blagojević I. 200 (1999) 558
Bleuse, J., J. Bonnet-Gamard, G. Mula, N. Magnea and J.-L. Pautrat, Laser emission in HgCdTe in the 2–3.5 μm range 197 (1999) 529
Bleyhl, S., see Weiss, T. 198/199 (1999) 1190
Bliss, D.F., see Dudley, M. 192 (1998) 1
Bloch, D.G., see Granberg, R.A. 198/199 (1999) 1287
Blumin, M., see Mogilyanski, D. 198/199 (1999) 1070
Bocelli, G., see Koporulina, E.V. 198/199 (1999) 460
Bočkowski, M., see Prystawko, P. 198/199 (1999) 1061
Boeck, T., T. Teubner, K. Schmidt and P.-M. Wilde, A method to grow silicon crystallites on glass 198/199 (1999) 420
Boeck, T., see Teubner, T. 198/199 (1999) 425
Boettinger, W.J., see Coriell, S.R. 191 (1998) 573
Boettinger, W.J. and J.A. Warren, Simulation of the cell to plane front transition during directional solidification at high velocity 200 (1999) 583
Bögels, G., see van den Berg, E.P.G. 191 (1998) 169
Bögels, G., H. Meekes, P. Bennema and D. Bollen, The role of {100} side faces for lateral growth of tabular silver bromide crystals 191 (1998) 446
Bohne, W., see Birkholz, M. 197 (1999) 571
Bohne, W., see Oertel, J. 198/199 (1999) 1205
Boistelle, R., see Seyssiecq, I. 196 (1999) 174
Boistelle, R., see Budayova, M. 196 (1999) 297
Boistelle, R., see Badens, E. 198/199 (1999) 704
Boistelle, R., see Garcia, E. 198/199 (1999) 1360
Boiton, P., N. Giacometti, J.L. Santailler, T. Duffar and J.P. Nabot, Experimental determination and numerical modelling of solid–liquid interface shapes for vertical Bridgman grown GaSb crystals 194 (1998) 43
Boiton, P., see Duffar, T. 198/199 (1999) 374
Bollen, D., see Bögels, G. 191 (1998) 446
Bollen, D., see Millan, A. 192 (1998) 215
Bolognesi, C.R., see Xu, X.G. 195 (1998) 687
Bondar, V., see Burachas, S. 198/199 (1999) 881
Bondarenko, E.A., see Kovalenko, S.I. 191 (1998) 553
Bonnet-Gamard, J., see Bleuse, J. 197 (1999) 529
Bonneté, F., see Boyer, M. 196 (1999) 185
Bonneté, F., see Tardieu, A. 196 (1999) 193
Bonneté, F., see Budayova, M. 196 (1999) 210
Bonneté, F., S. Finet and A. Tardieu, Second virial coefficient: variations with lysozyme crystallization conditions 196 (1999) 403
Bontempi, E., see Depero, L.E. 198/199 (1999) 516
Bontempi, E., see Sangaletti, L. 198/199 (1999) 1240
Borc, J., see Sangwal, K. 194 (1998) 214
Borodenko, Yu., see Burachas, S. 198/199 (1999) 881
Borodin, A.V., V.A. Borodin, V.V. Sidorov and I.S. Pet'kov, Influence of growth process parameters on weight sensor readings in the Stepanov (EFG) technique 198/199 (1999) 215
Borodin, A.V., V.A. Borodin and A.V. Zhdanov, Simulation of the pressure distribution in the melt for sapphire ribbon growth by the Stepanov (EFG) technique 198/199 (1999) 220
Borodin, V.A., V.V. Sidorov, S.N. Rossolenko, T.A. Steriopolo and T.N. Yalovets, Development of the Stepanov (edge-defined film-fed growth) method: variable shaping technique and local dynamic shaping technique 198/199 (1999) 201
Borodin, V.A., see Borodin, A.V. 198/199 (1999) 215
Borodin, V.A., see Borodin, A.V. 198/199 (1999) 220
Borusík, O., see Ivlev, G. 198/199 (1999) 1066

Börzsönyi, T., see González-Cinca, R. 193 (1998) 712
Bosch, R., see Pletser, V. 196 (1999) 638
Boschetti, C., see Rappl, P.H.O. 191 (1998) 466
Botez, D., see Mawst, L.J. 195 (1998) 609
Böttcher, K., P. Rudolph, M. Neubert, M. Kurz, A. Pusztai and G. Müller, Global temperature field simulation of the vapour pressure controlled Czochralski (VCZ) growth of 3″–4″ gallium arsenide crystals 198/199 (1999) 349
Bouchoule, S., see Sik, H. 195 (1998) 479
Boudeulle, M., see Métrat, G. 197 (1999) 883
Boué, F., see Vidal, O. 192 (1998) 257
Boué, F., see Vidal, O. 192 (1998) 271
Bouillé, A., see Nataf, G. 192 (1998) 73
Bouix, J., see Dumont, H. 197 (1999) 755
Boulet, P., see Sik, H. 195 (1998) 479
Boulon, G., see Ferriol, M. 197 (1999) 221
Boulon, G., see Métrat, G. 197 (1999) 883
Boulouz, A., A. Giani, F. Pascal-Delannoy, M. Boulouz, A. Foucaran and A. Boyer, Preparation and characterization of MOCVD bismuth telluride thin films 194 (1998) 336
Boulouz, M., see Boulouz, A. 194 (1998) 336
Bousquet, V., E. Tournié and J.-P. Faurie, Defect density in ZnSe pseudomorphic layers grown by molecular beam epitaxy on to various GaAs buffer layers 192 (1998) 102
Boyer, A., see Boulouz, A. 194 (1998) 336
Boyer, M., M.-O. Roy, M. Jullien, F. Bonneté and A. Tardieu, Protein interactions in concentrated ribonuclease solutions 196 (1999) 185
Brandon, S., see Virozub, A. 193 (1998) 592
Brandon, S., see Rotstein, H.G. 198/199 (1999) 1256
Brandt, O., see Yang, Q.K. 192 (1998) 28
Braski, D.N., see Gao, Y. 191 (1998) 439
Braslavsky, I., see Notcovich, A.G. 198/199 (1999) 10
Braslavsky, I. and S.G. Lipson, The double-pyramid structure of dendritic ice growing from supercooled water 198/199 (1999) 56
Bray, K.L., see Koporulina, E.V. 191 (1998) 767
Bray, K.L., see Cederberg, J.G. 195 (1998) 105
Brecht, E., C. Træholt, R. Schneider and G. Linker, Transmission electron microscopy study of the interface of $Bi_2Sr_2CaCu_2O_{8+\delta}$ thin films on (110) oriented $SrTiO_3$ substrates 191 (1998) 421
Breiland, W.G., see Vineis, C.J. 195 (1998) 181
Breiland, W.G., see Hou, H.Q. 195 (1998) 199
Brémond, G., see Zerrai, A. 197 (1999) 646
Brémond, G., see Zumbiehl, A. 197 (1999) 670
Brémond, G., see Zerrai, A. 197 (1999) 729
Brenier, A., see Métrat, G. 197 (1999) 883
Bretherton, T. and A. Rodgers, Crystallization of calcium oxalate in minimally diluted urine 192 (1998) 448
Breton, G., M. Nouaoura, X. Gratens, O. Laire, F. Touhari, S. Charar and M. Averous, Effect of chemical preparation of Si(1 1 1) surfaces on the CaF_2 growth 200 (1999) 112
Briat, B., F. Ramaz, B. Farid, K. Shcherbin and H.J. von Bardeleben, Spectroscopic characterization of photorefractive CdTe:Ge 197 (1999) 724
Briggs, G.A.D., see Goldfarb, I. 198/199 (1999) 1032
Brinkman, A.W., see Aitken, N.M. 198/199 (1999) 984
Brion, P., see Sauter, C. 196 (1999) 365
Brisson, A., W. Bergsma-Schutter, F. Oling, O. Lambert and I. Reviakine, Two-dimensional crystallization of proteins on lipid monolayers at the air–water interface and transfer to an electron microscopy grid 196 (1999) 456
Brisson, O., A. Simonnet and B. Darriet and J.-C. Launay, Transmission electron microscopy investigation of $AgGaSe_2$ single crystals and study of annealing efficiency by electrical conductivity measurements 193 (1998) 597
Bromberg, R., N. Kessler and L. Addadi, Antibody recognition of specific crystal faces of 1,4-dinitrobenzene 193 (1998) 656
Bronfenbrener, L. and E. Korin, Two-phase zone formation conditions under freezing of porous media 198/199 (1999) 89
Brongersma, H.H., see Moest, B. 192 (1998) 410
Brown, I., see Shima, R. 198/199 (1999) 957
Brown, J.D., see Yu, Z. 195 (1998) 333
Brown, M.G., see Tran, C.A. 195 (1998) 397
Bruinsma, O.S.L., see Wubbolts, F.E. 198/199 (1999) 767
Bryja, L., M. Ciorga, J. Misiewicz, A. Zaleski, P. Becla and W.C. Chou, Magneto-optical studies of quaternary diluted magnetic semiconductors 197 (1999) 694
Buchanan, M., see Mei, X. 193 (1998) 148
Buckley, D.J., see Aitken, N.M. 198/199 (1999) 984
Budayova, M., F. Bonneté, A. Tardieu and P. Vachette, Interactions in solution of a large oligomeric protein 196 (1999) 210
Budayova, M., J.-P. Astier, S. Veesler, M. Czjzek, A. Belaich and R. Boistelle, Characterization and crystallization of the Endoglucanase A from Clostridium Cellulolyticum in solution 196 (1999) 297

Buff, W., see Piechotka, M. 193 (1998) 80
Bugge, F., A. Knauer, U. Zeimer, J. Sebastian, V.B. Smirnitski, A. Klehr, G. Erbert and M. Weyers, MOVPE growth of tunable DBR laser diode emitting at 1060 nm 195 (1998) 676
Bugge, F., see Knauer, A. 195 (1998) 694
Buka, Á., see González-Cinca, R. 193 (1998) 712
Bulutcu, A.N., see Tanrikulu, S.Ü. 194 (1998) 220
Bunick, G., see Carter, D.C. 196 (1999) 602
Burachas, S., see Nagornaya, L. 198/199 (1999) 877
Burachas, S., V. Bondar, Yu. Borodenko, K. Katrunov, V. Martinov, L. Nagornaya, V. Ryzhikov, G. Tamulaitis, H. Gutbrod and V. Manko, Lead tungstate $PbWO_4$ crystals for high energy physics 198/199 (1999) 881
Burachek, V.R., see Savitsky, A.V. 192 (1998) 196
Burchard, A., see Desnica, U.V. 197 (1999) 612
Burger, A., see Chattopadhyay, K. 191 (1998) 377
Burger, A., K. Chattopadhyay, H. Chen, J.O. Ndap, X. Ma, S. Trivedi, S.W. Kutcher, R. Chen and R.D. Rosemeier, Crystal growth, fabrication and evaluation of cadmium manganese telluride gamma ray detectors 198/199 (1999) 872
Burk Jr., A.A., M.J. O'Loughlin and H.D. Nordby Jr., SiC epitaxial layer growth in a novel multi-wafer vapor-phase epitaxial (VPE) reactor 200 (1999) 458
Burkhalter, R., see Egger, P. 200 (1999) 515
Burkhard, H., see Jochum, S. 195 (1998) 637
Buschmann, V., M. Rodewald, H. Fuess, G. Van Tendeloo and C. Schäffer, Hetero-epitaxial growth of $CoSi_2$ thin films on Si(100): template effects and epitaxial orientations 191 (1998) 430
Buschmann, V., S. Klein, H. Fueß and H. Hahn, HREM study of 3C–SiC nanoparticles: influence of growth conditions on crystalline quality 193 (1998) 335
Busse, P., F. Deuerler and J. Pötschke, The stability of the ODS alloy CMSX6-Al_2O_3 during melting and solidification under low gravity 193 (1998) 413
Butendeich, R., M. Hurich and H. Heinecke, Material localisation at GaInAsP-ridge-structures selectively grown by MOMBE 195 (1998) 510
Butkute, R., see Kleptsyn, V. 196 (1999) 122
Butler, J.E., see Battaile, C.C. 194 (1998) 353
Butler, J.E., see Lang, A.R. 200 (1999) 446
Butz, R. and H. Lüth, Strain dependent growth of silicon on Ge/Si–C heterostructures 200 (1999) 407
Bychkov, G.L., see Leonyuk, N.I. 191 (1998) 135
Bychkov, G.L., see Koporulina, E.V. 198/199 (1999) 460
Bychkov, G.L., see Barilo, S.N. 198/199 (1999) 716
Čabrić B., T. Pavlović and A. Janićijević, Regulation of the crystallization in a crucible furnace 200 (1999) 339
Caccavale, F., see Bermúdez, V. 191 (1998) 589
Çadirli, E., see Bayender, B. 194 (1998) 119
Cadoret, R., see Trassoudaine, A. 192 (1998) 402
Cahen, D., see Lyahovitskaya, V. 197 (1999) 106
Cahen, D., see Lyahovitskaya, V. 197 (1999) 177
Cahen, D., O. Melamed and I. Lubomirski, Can percolation control doping, diffusion and phase segregation in (Hg,Cd)Te? 197 (1999) 537
Cai, L.C., H. Chen, C.L. Bao, Q. Huan and J.M. Zhou, RHEED characterization of InAs/GaAs grown by MBE 197 (1999) 364
Cai, S.J., see Liu, J.L. 200 (1999) 106
Cajipe, V.B., see Bancel, P.A. 191 (1998) 537
Cajipe, V.B., see Bancel, P.A. 196 (1999) 685
Camassel, J., see Duffar, T. 192 (1998) 63
Camel, D., see Leroux, S. 198/199 (1999) 911
Campbell, R.L., see Zhu, D.-W. 196 (1999) 356
Campi, R., see Bertone, D. 195 (1998) 624
Campion, R.P., see Cheng, T.S. 197 (1999) 12
Caneau, C., see Bhat, R. 195 (1998) 427
Cang, H.-X., W.-D. Huang and Y.-H. Zhou, Effects of organic solvents on the morphology of the meta-nitroaniline crystal 192 (1998) 236
Cang, H.-X. and R.-C. Bi, Numerical studies on the pre-nucleation transport in the liquid/liquid diffusion crystallization of proteins 194 (1998) 133
Cang, H.-X. and R.-C. Bi, Influence of various factors on the liquid/liquid diffusion crystallization of proteins 196 (1999) 442
Canselier, J.P., see Lin, C.H. 191 (1998) 791
Canselier, J.P., see Lin, C.H. 191 (1998) 803
Capelle, B., see Fourme, R. 196 (1999) 535
Capelle, B., see Otalora, F. 196 (1999) 546
Capelle, B., see Vidal, O. 196 (1999) 559
Capelle, B., see Taleb, M. 200 (1999) 575
Capper, P., see Maxey, C.D. 197 (1999) 427
Capper, P., see Lane, D.W. 197 (1999) 743
Caram, R. and S. Milenkovic, Microstructure of Ni–Ni_3Si eutectic alloy produced by directional solidification 198/199 (1999) 844
Caram, R., see Mota, M.A. 198/199 (1999) 850
Cardenas, J., see Joelsson, K.B. 196 (1999) 97
Carles, J., see Aitken, N.M. 198/199 (1999) 984

Carlsson, N., T. Junno, L. Montelius, M.-E. Pistol, L. Samuelson and W. Seifert, Growth of self-assembled InAs and $InAs_xP_{1-x}$ dots on InP by metalorganic vapour phase epitaxy 191 (1998) 347
Carlsson, N., see Seifert, W. 197 (1999) 19
Carman, L., see Zaitseva, N. 197 (1999) 911
Caro, P., see Menéndez, J.L. 192 (1998) 164
Carter, D.C., see Declercq, J.-P. 196 (1999) 595
Carter, D.C., B. Wright, T. Miller, J. Chapman, P. Twigg, K. Keeling, K. Moody, M. White, James Click, J.R. Ruble, J.X. Ho, L. Adcock-Downey, G. Bunick and J. Harp, Diffusion-controlled crystallization apparatus for microgravity (DCAM): flight and ground-based applications 196 (1999) 602
Carter, D.C., B. Wright, T. Miller, J. Chapman, P. Twigg, K. Keeling, K. Moody, M. White, J. Click, J.R. Ruble, J.X. Ho, L. Adcock-Downey and T. Dowling, C.-H. Chang, P. Ala, J. Rose, B.C. Wang, J.-P. Declercq, C. Evrard, J. Rosenberg, J.-P. Wery, D. Clawson, M. Wardell, W. Stallings and A. Stevens, PCAM: a multi-user facility-based protein crystallization apparatus for microgravity 196 (1999) 610
Carter, D.C., K. Lim, J.X. Ho, B.S. Wright, P.D. Twigg, T.Y. Miller, J. Chapman, K. Keeling, J. Ruble, P.G. Vekilov, B.R. Thomas, F. Rosenberger and A.A. Chernov, Lower dimer impurity incorporation may result in higher perfection of HEWL crystal grown in microgravity. A case study 196 (1999) 623
Casademunt, J., see González-Cinca, R. 193 (1998) 712
Castaño, J.L., see Plaza, J.L. 198/199 (1999) 379
Castelluci, D., see Trassoudaine, A. 192 (1998) 402
Catalano, M., see Passaseo, A. 197 (1999) 777
Caylor, C., see Dobrianov, I. 196 (1999) 511
Cebollada, A., see Menéndez, J.L. 192 (1998) 164
Cederberg, J.G., B. Bieg, J.-W. Huang, S.A. Stockman, M.J. Peanasky and T.F. Kuech, Intrinsic and oxygen-related deep level defects in $In_{0.5}(Al_xGa_{1-x})_{0.5}P$ grown by metal-organic vapor phase epitaxy 195 (1998) 63
Cederberg, J.G., T.D. Culp, B. Bieg, D. Pfeiffer, C.H. Winter, K.L. Bray and T.F. Kuech, Erbium-doped GaAs grown using the novel precursor tris(3,5-di-tert-butylpyrazolato)bis(4-tert-butylpyridine) erbium 195 (1998) 105
Černý, R., see Ivlev, G. 198/199 (1999) 1066
Cháb, V., see Ivlev, G. 198/199 (1999) 1066
Chack, A., see Cohen, K. 198/199 (1999) 1174
Chack, A., K. Cohen, S. Stolyarova, Y. Nemirovsky, R. Beserman and R. Weil, Dielectric and pyroelectric properties of ordered CdZnTe layers grown by MOCVD 198/199 (1999) 1179
Chai, B.H.T., see Morris, R.C. 191 (1998) 108
Chai, B.H.T., see Ye, Q. 197 (1999) 228
Chait, A., see Pines, V. 197 (1999) 355
Champness, C.H., see Shukri, Z.A. 191 (1998) 97
Chang, C.-H., see Carter, D.C. 196 (1999) 610
Chang, D.-G., see Kim, I. 195 (1998) 138
Chang, L.-B., H.-T. Wang, Y.-C. Cheng, T.-W. Shong and E.-K. Lin, Praseodymium added GaAs liquid phase epitaxy and its Schottky diode application 198/199 (1999) 1092
Chang, Y.S., S. Naritsuka and T. Nishinaga, Optimization of growth condition for wide dislocation-free GaAs on Si substrate by micro-channel epitaxy 192 (1998) 18
Chani, V.I., K. Nagata, T. Kawaguchi, M. Imaeda and T. Fukuda, Segregation and uniformity of $K_3Li_2(Ta,Nb)_5O_{15}$ fiber crystals grown by micro-pulling-down method 194 (1998) 374
Chani, V.I., see Takeda, H. 197 (1999) 204
Chapman, J., see Carter, D.C. 196 (1999) 602
Chapman, J., see Carter, D.C. 196 (1999) 610
Chapman, J., see Carter, D.C. 196 (1999) 623
Charach, Ch. and P.C. Fife, Phase field models of solidification in binary alloys: capillarity and solute trapping effects 198/199 (1999) 1267
Charache, G.W., see Wang, C.A. 195 (1998) 346
Charache, G.W., see Hitchcock, C.W. 195 (1998) 363
Charache, G.W., see Ehsani, H. 195 (1998) 385
Charar, S., see Breton, G. 200 (1999) 112
Charbonnier, J.-B., see Stura, E.A. 196 (1999) 250
Charych, D., see Berman, A. 198/199 (1999) 796
Chatterjee, A., see Chen, Q.S. 198/199 (1999) 710
Chattopadhyay, K., S. Feth, H. Chen, A. Burger and C.-H. Su, Characterization of semi-insulating CdTe crystals grown by horizontal seeded physical vapor transport 191 (1998) 377
Chattopadhyay, K., see Burger, A. 198/199 (1999) 872
Chaudhuri, J., see Gao, Y. 191 (1998) 439
Chayen, N.E., Crystallization with oils: a new dimension in macromolecular crystal growth 196 (1999) 434

Chayen, N.E., Recent advances in methodology for the crystallization of biological macromolecules 198/199 (1999) 649
Cheema, S.N., see Gao, Y. 191 (1998) 439
Chen, C.-M., L.T. Zhang and W.C. Zhou, Characterization of LaB_6–ZrB_2 eutectic composite grown by the floating zone method 191 (1998) 873
Chen, H., see Chattopadhyay, K. 191 (1998) 377
Chen, H., see Cai, L.C. 197 (1999) 364
Chen, H., see Burger, A. 198/199 (1999) 872
Chen, J., see Yang, Q. 194 (1998) 31
Chen, J.-C., L.-T. Liu and C.-C. Young, A study of the growth mechanism of bismuth silicon oxide during LHPG method 198/199 (1999) 476
Chen, J.-C., see Lai, Y.-J. 198/199 (1999) 531
Chen, J.X., A.Z. Li, Q.K. Yang, C. Lin, Y.C. Ren, S.R. Jin, C.C. Li and M. Qi, Novel $In_{0.49}Ga_{0.51}P$/(In)GaAs/GaAs p-type modulation doped heterostructure grown by gas source molecular beam epitaxy 193 (1998) 28
Chen, N., see Lin, L. 191 (1998) 586
Chen, Q.S., V. Prasad, A. Chatterjee and J. Larkin, A porous media-based transport model for hydrothermal growth 198/199 (1999) 710
Chen, R., see Burger, A. 198/199 (1999) 872
Chen, S.W., see Ferguson, I.T. 195 (1998) 648
Chen Xingda, see Zhou Guoqing 191 (1998) 517
Chen, Y., L.P. Guo, D.J. Johnson and R.H. Prince, Plasma-induced low-temperature growth of graphitic nanofibers on nickel substrates 193 (1998) 342
Chen, Z., see Shi, W. 197 (1999) 905
Cheng, J., X. Meng, P. Yang and J. Chu, Preparation and characterization of Pt/MgO/Si multilayer thin films 194 (1998) 89
Cheng, L., Z. Zhang, G. Zhang and Z. Yang, Microstructures of GaN films grown by low pressure metal-organic vapor phase epitaxy on $(0\,1\,\bar{1})$ sapphire substrates 191 (1998) 641
Cheng, L.-S., see Yang, H.-F. 193 (1998) 478
Cheng, L., see Wang, L. 193 (1998) 484
Cheng, R., see Zhang, H. 200 (1999) 335
Cheng, T.S., see Orton, J.W. 197 (1999) 7
Cheng, T.S., S.V. Novikov, V.B. Lebedev, R.P. Campion, N.J. Jeffs, Yu.V. Melnik, D.V. Tsvetkov, S.I. Stepanov, A.E. Cherenkov, V.A. Dmitriev, D. Korakakis, O.H. Hughes and C.T. Foxon, The initiation of GaN growth by molecular beam epitaxy on GaN composite substrates 197 (1999) 12
Cheng, X.J., see Xu, J. 193 (1998) 50
Cheng, X.J., see Xu, J. 193 (1998) 636
Cheng, X.J., see Xu, J. 193 (1998) 738
Cheng, Y.-C., see Chang, L.-B. 198/199 (1999) 1092
Cheong, S.-W., see Kloc, Ch. 191 (1998) 294
Chepurov, A.I., I.I. Fedorov, V.M. Sonin and A.A. Tomilenko, Experimental study of intake of gases by diamonds during crystallization 198/199 (1999) 963
Cherenkov, A.E., see Cheng, T.S. 197 (1999) 12
Cherkaoui, K., see Zerrai, A. 197 (1999) 646
Cherkaoui, K., see Zumbiehl, A. 197 (1999) 670
Chernikov, V., see Ryzhikov, V. 197 (1999) 655
Chernov, A.A., Estimates of internal stress and related mosaicity in solution grown crystals: proteins 196 (1999) 524
Chernov, A.A., see Carter, D.C. 196 (1999) 623
Chi, G.-C., see Yang, C.-C. 200 (1999) 32
Chi, G.-C., see Yang, C.-C. 200 (1999) 39
Chiba, K.-i., see Obara, K. 198/199 (1999) 894
Chibani, L., see Fougères, P. 197 (1999) 641
Chichibu, S.F., see Keller, S. 195 (1998) 258
Cho, S., see Sanz-Hervás, A. 195 (1998) 558
Choi, D.J., Y.H. Kim, D.W. Han, H.K. Baik and S.I. Kim, Formation of polycrystalline silicon films on glass substrates at low-temperatures by a direct negative Si ion beam deposition system 191 (1998) 718
Choi, D.Y. and S.J. Chung, Annealing behaviors of lattice misfit in YIG and La-doped YIG films grown on GGG substrates by LPE method 191 (1998) 754
Choi, H.K., see Wang, C.A. 195 (1998) 346
Choi, J., see Wang, W.S. 198/199 (1999) 578
Choi, W.-J., see Kim, I. 193 (1998) 293
Choi, W.-J. and P.D. Dapkus, Selective growth and regrowth of high Al content AlGaAs for use in BH lasers 195 (1998) 495
Choi, Y.D., see Nam, S. 194 (1998) 61
Chong, T.C., see Xu, X.W. 198/199 (1999) 536
Chong, T.C., see Shi, L.P. 198/199 (1999) 551
Chou, W.C., see Bryja, L. 197 (1999) 694
Choubey, A., see Murthy, R.V.A. 197 (1999) 865
Chow, Y.T., see Zhang, H. 193 (1998) 370
Chow, Y.T., see Meng, X. 200 (1999) 199
Christopher, G.K., A.G. Phipps and R.J. Gray, Temperature-dependent solubility of selected proteins 191 (1998) 820
Chu, J., see Cheng, J. 194 (1998) 89
Chua, S.J., see Li, G. 191 (1998) 357
Chua, S.J., see Halliwell, M.A.G. 192 (1998) 456
Chua, S.J., see Li, G. 195 (1998) 54

Chun, C.-H., see Lee, Y.-S. 197 (1999) 297
Chun, C.-H., see Lee, Y.-S. 197 (1999) 307
Chun, C.-H., see Lee, Y.-S. 198/199 (1999) 147
Chung, H., see Dudley, M. 192 (1998) 1
Chung, S.J., see Choi, D.Y. 191 (1998) 754
Chung, S.J., see Lee, Y.K. 192 (1998) 350
Chung, S.J., see Lee, Y.K. 196 (1999) 151
Chung, S.K. and E.H. Trinh, Containerless protein crystal growth in rotating levitated drops 194 (1998) 384
Ciach, R., M.V. Demich, P.M. Gorley, Z. Kuznicki, V.P. Makhniy, I.V. Malimon and Z. Swiatek, Photo and X-ray sensitive heterostructures based on cadmium telluride 197 (1999) 675
Cibert, J., see Siviniant, J. 197 (1999) 680
Cingolani, R., see Passaseo, A. 197 (1999) 777
Ciorga, M., see Bryja, L. 197 (1999) 694
Clawson, D., see Carter, D.C. 196 (1999) 610
Click, J., see Carter, D.C. 196 (1999) 602
Click, J., see Carter, D.C. 196 (1999) 610
Cloots, R., see Vandewalle, N. 197 (1999) 317
Closs, H., see Rappl, P.H.O. 191 (1998) 466
Clunie, J.C., see Baird, J.K. 196 (1999) 220
Cockayne, B., see Lane, P.A. 192 (1998) 423
Coelho, A.A., see Mota, M.A. 198/199 (1999) 850
Cohen, K., S. Stolyarova, N. Amir, A. Chack, R. Beserman, R. Weil and Y. Nemirovsky, MOCVD growth of ordered $Cd_{(1-x)}Zn_xTe$ epilayers 198/199 (1999) 1174
Cohen, K., see Chack, A. 198/199 (1999) 1179
Cohen, R.M., see Tandon, A. 192 (1998) 47
Cole-Hamilton, D.J., see Berrigan, R.A. 195 (1998) 718
Combs, L.L., see Guo, B. 196 (1999) 424
Conibeer, G.J., see Lane, D.W. 197 (1999) 743
Considine, L., E.J. Thrush, J.A. Crawley, K. Jacobs, W. Van der Stricht, I. Moerman, P. Demeester, G.H. Park, S.J. Hwang and J.J. Song, Growth and in situ monitoring of GaN using IR interference effects 195 (1998) 192
Considine, L., see Vanhollebeke, K. 195 (1998) 644
Constantino, M.E., M.A. Vidal, B. Salazar-Hernández, H. Navarro-Contreras, M. López-López, M. Meléndez and I. Hernández-Calderon, Dislocation densities in MBE grown ZnSe epitaxial layers on GaAs by HRXRD 194 (1998) 301
Constantino, M.E., see Salazar-Hernández, B. 197 (1999) 783
Conti, M., Oscillatory instabilities and banded structures in rapidly solidified alloys 198/199 (1999) 1251
Contreras, S., see Duffar, T. 192 (1998) 63
Cook, M.J., see Wankerl, A. 191 (1998) 8
Cook Jr., J.W., see Yu, Z. 195 (1998) 333
Cooke, P., see Partin, D.L. 195 (1998) 378
Coquillat, D., see Siviniant, J. 197 (1999) 680
Coriell, S.R., G.B. McFadden, R.F. Sekerka and W.J. Boettinger, Multiple similarity solutions for solidification and melting 191 (1998) 573
Coriell, S.R., see Seidensticker, R.G. 198/199 (1999) 988
Coriell, S.R., see Singh, N.B. 198/199 (1999) 995
Coriell, S.R., G.B. McFadden and R.F. Sekerka, Selection mechanisms for multiple similarity solutions for solidification and melting 200 (1999) 276
Cortès, R., see Furlong, M.J. 193 (1998) 114
Cotta, M.A., see Soares, L.S.M. 191 (1998) 44
Crawford, M.H., see Han, J. 195 (1998) 291
Crawley, J.A., see Considine, L. 195 (1998) 192
Crawley, J.A., see Vanhollebeke, K. 195 (1998) 644
Cristiani, G., see Konuma, M. 198/199 (1999) 1045
Cristiani, G., see Czech, E. 198/199 (1999) 1087
Cröll, A., Th. Kaiser, M. Schweizer, A.N. Danilewsky, S. Lauer, A. Tegetmeier and K.W. Benz, Floating-zone and floating-solution-zone growth of GaSb under microgravity 191 (1998) 365
Crosbie, M.J., see Lane, P.A. 192 (1998) 423
Crozier, E.D., see Gupta, J.A. 195 (1998) 34
Cuffini, S.L., see Andreeta, M.R.B. 200 (1999) 621
Cui, D., see Gao, S. 192 (1998) 89
Cui, F.Z., see Luo, Z.S. 197 (1999) 939
Cui, F.Z., see Feng, Q.L. 200 (1999) 550
Cui, L., see Zhu, H. 197 (1999) 372
Cui, W., see Guan, Q. 197 (1999) 1012
Cuisinier, F.J.G., see Ngankam, P.A. 197 (1999) 927
Culp, T.D., see Cederberg, J.G. 195 (1998) 105
Curreri, P.A., see Sen, S. 193 (1998) 692
Cussó, F., see Fedorov, V.A. 194 (1998) 94
Czech, E., see Konuma, M. 198/199 (1999) 1045
Czech, E., G. Götz, G. Cristiani and M. Konuma, Residual impurities in high purity GaAs layers grown by liquid phase epitaxy in H_2–Ar atmosphere 198/199 (1999) 1087
Czjzek, M., see Budayova, M. 196 (1999) 297

D'Hondt, M., Z.-Q. Yu, B. Depreter, C. Sys, I. Moerman, P. Demeester and P. Mijlemans, High quality InGaAs/AlGaAs lasers grown on Ge substrates 195 (1998) 655
Dabkowska, H.A., see Dabkowski, A. 197 (1999) 879
Dabkowska, H.A., see Imanaka, N. 200 (1999) 169

Dabkowski, A., H.A. Dabkowska, J.E. Greedan, G. Adachi, Y. Kobayashi, S. Tamura, M. Hiaraiwa and N. Imanaka, Crystal growth of aluminum tungstate $Al_2(WO_4)_3$ by the Czochralski method from non-stoichiometric melt 197 (1999) 879
Dabkowski, A., see Imanaka, N. 200 (1999) 169
Dadgar, A., O. Stenzel, L. Köhne, A. Näser, M. Straßburg, W. Stolz, D. Bimberg and H. Schumann, Growth of Ru doped semi-insulating InP by low pressure metalorganic chemical vapor deposition 195 (1998) 69
Dalecki, W., see Hruban, A. 198/199 (1999) 282
Dammak, M., see Zerrai, A. 197 (1999) 729
Daniels-Race, T., see Li, H. 200 (1999) 321
Danilewsky, A.N., see Cröll, A. 191 (1998) 365
Danilov, D.A., see Galenko, P.K. 197 (1999) 992
Danilov, V.I., see Pylneva, N.A. 198/199 (1999) 546
Dapkus, P.D., see Kim, I. 193 (1998) 293
Dapkus, P.D., see Kim, I. 195 (1998) 138
Dapkus, P.D., see Kobayashi, J.T. 195 (1998) 252
Dapkus, P.D., see Choi, W.-J. 195 (1998) 495
Darcy, P.A. and J.M. Wiencek, Identifying nucleation temperatures for lysozyme via differential scanning calorimetry 196 (1999) 243
Dariel, M.P., see Shimony, Y. 198/199 (1999) 583
Darriet, B., see Brisson, O. 193 (1998) 597
Dashevsky, Z., see Belenchuk, A. 198/199 (1999) 1216
Datcu, M., see Vasile, E. 198/199 (1999) 806
David, D., see Papaioannou, V. 194 (1998) 342
David, J.P.R., see Roberts, J.S. 195 (1998) 668
Davis, A.M.J., see Hadji, L. 191 (1998) 889
Davis, S.H., see Golovin, A.A. 198/199 (1999) 1245
Davydov, A.A., see Melnikov, A.A. 197 (1999) 666
Dawes, J., see Zhang, H. 193 (1998) 370
Dawes, J., see Zhang, H. 200 (1999) 335
Dazord, J., see Dumont, H. 197 (1999) 755
De Boer, W.B., see Zhao, Q.X. 193 (1998) 328
De Carvalho, M.M.G., see Soares, L.S.M. 191 (1998) 44
De Carvalho, M.M., see de Castro, M.P.P. 193 (1998) 510
De Castro, M.P.P., N.C. Frateschi, J. Bettini and M.M. de Carvalho, $In_{0.49}Ga_{0.51}P$ growth on pre-patterned GaAs substrates by chemical beam epitaxy 193 (1998) 510
De Cogan, D., see Rak, M. 197 (1999) 944
De Graauw, J., see van der Ham, F. 198/199 (1999) 744
De Lorenzo, C., see Sica, F. 196 (1999) 305
De los Angeles Hernández-Hernández, M., see Moreno, A. 196 (1999) 587
De Smet, T.M.F., see van Geelen, A. 195 (1998) 79
De Theije, F.K., A.R.A. Zauner, P.R. Hageman, W.J.P. van Enckevort and P.K. Larsen, An atomic force microscopy study of a temperature dependent morphology transition of GaN grown on sapphire by MOCVD 197 (1999) 37
Declercq, J.-P., C. Evrard, D.C. Carter, B.S. Wright, G. Etienne and J. Parello, A crystal of a typical EF-hand protein grown under microgravity diffracts X-rays beyond 0.9 Å resolution 196 (1999) 595
Declercq, J.-P., see Carter, D.C. 196 (1999) 610
Décobert, J., G. Rondeau, H. Maher, C. Ladner, A. Falcou, S. Biblemont and G. Post, Doping optimizations for InGaAs/InP composite channel HEMTs 195 (1998) 681
Deicher, M., see Desnica, U.V. 197 (1999) 612
Dekker, P., see Zhang, H. 200 (1999) 335
Delepine, J., see Krymov, V.M. 198/199 (1999) 210
Delepine, J., see Gurjiyants, P.A. 198/199 (1999) 227
Demeester, P., see Considine, L. 195 (1998) 192
Demeester, P., see Vanhollebeke, K. 195 (1998) 644
Demeester, P., see D'Hondt, M. 195 (1998) 655
Demich, M.V., see Ciach, R. 197 (1999) 675
Demo, P., see Kožíšek, Z. 194 (1998) 239
DenBaars, S.P., see Keller, S. 195 (1998) 258
DenBaars, S.P., see Kozodoy, P. 195 (1998) 265
DenBaars, S.P., see Marchand, H. 195 (1998) 328
Deng Peizhen, see Zhou Gueqing 191 (1998) 517
Deng Peizhen, see Xu Jianwei 193 (1998) 123
Deng Peizhen, see Xu Ke 193 (1998) 127
Deng Yuanming, see Zhao Qian 200 (1999) 603
Denier van der Gon, A.W., see Moest, B. 192 (1998) 410
Dennis, M., see Yeckel, A. 191 (1998) 206
Dentel, D., J.L. Bischoff, L. Kubler, J. Werckmann and M. Romeo, Surface smoothing induced by epitaxial Si capping of rough and strained Ge or $Si_{1-x}Ge_x$ morphologies: A RHEED and TEM study 191 (1998) 697
Depero, L.E., see Sangaletti, L. 198/199 (1999) 454
Depero, L.E., L. Sangaletti, B. Allieri, E. Bontempi, A. Marino and M. Zocchi, Correlation between crystallite sizes and microstrains in TiO_2 nanopowders 198/199 (1999) 516
Depero, L.E., see Sangaletti, L. 198/199 (1999) 1240
Depreter, B., see D'Hondt, M. 195 (1998) 655
Derby, J.J., see Yeckel, A. 191 (1998) 206
Derby, J.J., see Rojo, J.C. 198/199 (1999) 154
Derby, J.J., see Rojo, J.C. 200 (1999) 329

Deshpande, M.P., P.D. Patel, M.N. Vashi and M.K. Agarwal, Effect of intercalating indium in WSe_2 single crystals 197 (1999) 833

DeSisto, W.J. and B.J. Rappoli, Ultraviolet absorption sensors for precursor delivery rate control for metalorganic chemical vapor deposition of multiple component oxide thin films 191 (1998) 290

Desnica-Franković, I.D., see Desnica, U.V. 197 (1999) 612

Desnica, U.V., I.D. Desnica-Franković, R. Magerle, A. Burchard and M. Deicher, Experimental evidence of the self-compensation mechanism in CdS 197 (1999) 612

DeTitta, G.T., see Luft, J.R. 196 (1999) 447

DeTitta, G.T., see Luft, J.R. 196 (1999) 450

Deuerler, F., see Busse, P. 193 (1998) 413

DeWitt, C.R., see Edmundson, A.B. 196 (1999) 276

Dhalenne, G., see Ammerahl, U. 193 (1998) 55

Dhalenne, G., see Revcolevschi, A. 198/199 (1999) 593

Dhindaw, B.K., see Sen, S. 193 (1998) 692

Di Cioccio, L., see Papaioannou, V. 194 (1998) 342

Di Forte-Poisson, M.A., F. Huet, A. Romann, M. Tordjman, D. Lancefield, E. Pereira, J. Di Persio and B. Pecz, Relationship between physical properties and gas purification in GaN grown by metalorganic vapor phase epitaxy 195 (1998) 314

Di Persio, J., see di Forte-Poisson, M.A. 195 (1998) 314

Didier, G., see Lemasson, P. 197 (1999) 462

Didierjean, C., see Taleb, M. 200 (1999) 575

Diederichs, K., see Ritter, S. 196 (1999) 344

Diéguez, E., see Bermúdez, V. 191 (1998) 589

Diéguez, E., see Plaza, J.L. 198/199 (1999) 379

Diéguez, E., see Bermúdez, V. 198/199 (1999) 526

Diéguez, E., see Bermúdez, V. 200 (1999) 185

Diéguez, E., see Rojo, J.C. 200 (1999) 329

Dieker, Ch., see Schmidt, R. 195 (1998) 124

Dieker, Ch., see Gerthsen, D. 200 (1999) 353

Dimitrova, S., see Tsekova, D. 196 (1999) 226

Dimitrova, Zl., see Gogova, D. 198/199 (1999) 1230

Dinculescu, I., C. Logofătu, N. Mincu and B. Iliescu, Fluoride crystals for IR optics, grown by the PVGF method 198/199 (1999) 999

Dinescu, M., see Verardi, P. 197 (1999) 523

Ding, D., see Gong, Q. 192 (1998) 376

Dinger, A., M. Hetterich, M. Göppert, M. Grün, C. Klingshirn, B. Weise, J. Liang, V. Wagner and J. Geurts, Growth of CdS/ZnS strained layer superlattices on GaAs(0 0 1) by molecular-beam epitaxy with special reference to their structural properties and lattice dynamics 200 (1999) 391

Dinu, R., see Verardi, P. 197 (1999) 523

Dmitriev, V.A., see Cheng, T.S. 197 (1999) 12

Dobrianov, I., C. Caylor, S.G. Lemay, K.D. Finkelstein and R.E. Thorne, X-ray diffraction studies of protein crystal disorder 196 (1999) 511

Döhler, G.H., see Velling, P. 195 (1998) 490

Dohnke, I., M. Mühlberg and W. Neumann, ZnSe single-crystal growth with SnSe as solvent 198/199 (1999) 287

Doi, Y., see Iijima, M. 193 (1998) 182

Dold, P., A. Barz, S. Recha, K. Pressel, M. Franz and K.W. Benz, Growth and characterization of $Ge_{1-x}Si_x$ ($x \leqslant 10$ at%) single crystals 192 (1998) 125

Dolle, J., see Schulz, D. 198/199 (1999) 1024

Domagała, J., see Szczerbakow, A. 191 (1998) 673

Domagała, J., see Mycielski, A. 197 (1999) 423

Domagała, J., see Prystawko, P. 198/199 (1999) 1061

Domingo, C., F.E. Wubbolts, R. Rodríguez-Clemente and G.M. van Rosmalen, Solid crystallization by rapid expansion of supercritical ternary mixtures 198/199 (1999) 760

Domopoulou, A., A. Michaelides, S. Skoulika and D. Kovala-Demertzi, Crystallization of an unstable molecular compound using a tailor-made additive 191 (1998) 166

Dong Jianrong, see Zhou Hongwei 191 (1998) 361

Dornberger, E., see Von Ammon, W. 198/199 (1999) 390

Dornberger, E., see Mühe, A. 198/199 (1999) 409

Dorozhkin, S.I., see Avrov, D.D. 198/199 (1999) 1011

Dorozhkin, S.I., see Bakin, A.S. 198/199 (1999) 1015

Dour, G., E. Ehret, A. Laugier, D. Sarti, M. Garnier and F. Durand, Continuous solidification of photovoltaic multicrystalline silicon from an inductive cold crucible 193 (1998) 230

Dowling, T., see Carter, D.C. 196 (1999) 610

Drebushchak, V.A., T.A. Kravchenko and V.S. Pavlyuchenko, Synthesis of pure pentlandite in bulk 193 (1998) 728

Drenth, J., see Haas, C. 196 (1999) 388

Drevet, B., see Eustathopoulos, N. 191 (1998) 268

Drevet, B., see Leroux, S. 198/199 (1999) 911

Drozdowski, M., see Pajaczkowska, A. 198/199 (1999) 440

Du, J., see Li, Y.X. 191 (1998) 282

Du, J., see Wu, G. 192 (1998) 417

Duan, L.H., see Xu, D.P. 191 (1998) 646

Duan, S., X. Teng, P. Han and D.-C. Lu, Growth and characterization of GaN on $LiGaO_2$ 195 (1998) 304

Duan, S.-K., see Yang, H.-F. 193 (1998) 478

Duan, X.F., see Wang, Z.M. 192 (1998) 97
Dubois, C., see Ketata, M. 194 (1998) 297
Ducruix, A., see Fourme, R. 196 (1999) 535
Dudarev, S.L., see Mitura, Z. 198/199 (1999) 905
Dudley, M., B. Raghothamachar, Y. Guo, X.R. Huang, H. Chung, D.T.J. Hurle and D.F. Bliss, The influence of polarity on twinning in zinc-blende structure crystals: new insights from a study of magnetic liquid encapsulated, Czochralski grown InP single crystals 192 (1998) 1
Duffar, T., M.D. Serrano, C.D. Moore, J. Camassel, S. Contreras, P. Dusserre, A. Rivoallant and B.K. Tanner, Bridgman solidification of GaSb in space 192 (1998) 63
Duffar, T., see Boiton, P. 194 (1998) 43
Duffar, T., see Barat, C. 194 (1998) 149
Duffar, T., see Gondet, S. 198/199 (1999) 129
Duffar, T., see Théodore, F. 198/199 (1999) 232
Duffar, T., see Barvinschi, F. 198/199 (1999) 239
Duffar, T., P. Dusserre, N. Giacometti, P. Boiton, J.P. Nabot and N. Eustathopoulos, Effect of crucible–sample adhesion on grain germination 198/199 (1999) 374
Dujardin, C., see Petrosyan, A.G. 198/199 (1999) 492
Dumont, H., L. Auvray, J. Dazord, V. Souliere, Y. Monteil, J. Bouix and A. Ougazzaden, Surface morphology of InGaAs and InP materials grown with trimethylarsenic and arsine on vicinal InP substrates 197 (1999) 755
Dunn, K.A., see Hansen, D.M. 195 (1998) 144
Dupuis, R.D., J. Park, P.A. Grudowski, C.J. Eiting and Z. Liliental-Weber, Selective-area and lateral epitaxial overgrowth of III-N materials by metalorganic chemical vapor deposition 195 (1998) 340
Durand, F., see Dour, G. 193 (1998) 230
Durbin, S.D., see Sazaki, G. 196 (1999) 204
Durbin, S.D., see Kurihara, K. 196 (1999) 285
Durbin, S.D., see Yanagiya, S.-i. 196 (1999) 319
Durbin, S.D., see Nakada, T. 196 (1999) 503
Durose, K., see Szczerbakow, A. 191 (1998) 673
Durose, K., P.R. Edwards and D.P. Halliday, Materials aspects of CdTe/CdS solar cells 197 (1999) 733
Durose, K., see Aitken, N.M. 198/199 (1999) 984
Dusserre, P., see Duffar, T. 192 (1998) 63
Dusserre, P., see Duffar, T. 198/199 (1999) 374
Dutta, P.S. and A.G. Ostrogorsky, Nearly diffusion controlled segregation of tellurium in GaSb 191 (1998) 904
Dutta, P.S. and A.G. Ostrogorsky, Suppression of cracks in $In_xGa_{1-x}Sb$ crystals through forced convection in the melt 194 (1998) 1
Dutta, P.S. and A.G. Ostrogorsky, Strong band gap narrowing in quasi-binary $(GaSb)_{1-x}(InAs)_x$ crystals grown from melt 197 (1999) 1
Dutta, P.S. and A.G. Ostrogorsky, Segregation of tellurium in GaSb single crystals and associated diffusion coefficient in the solute layer 197 (1999) 749
Dutta, P.S. and A.G. Ostrogorsky, Melt growth of quasi-binary $(GaSb)_{1-x}(InAs)_x$ crystals 198/199 (1999) 384
Duval, W.M.B., see Seidensticker, R.G. 198/199 (1999) 988
Dynowska, E., see Miotkowska, S. 200 (1999) 483

Ebel, C., P. Faou and G. Zaccai, Protein–solvent and weak protein–protein interactions in halophilic malate dehydrogenase 196 (1999) 395
Ebert, S., see Künzel, H. 192 (1998) 56
Eckstein, R., see Hofmann, D. 198/199 (1999) 1005
Edgar, J.H., see Gao, Y. 191 (1998) 439
Edmundson, A.B., C.R. DeWitt, B.Z. Goldsteen and P.A. Ramsland, Packing motifs as predictors of the propensity of antibody fragments to crystallize 196 (1999) 276
Edwards, P.R., see Durose, K. 197 (1999) 733
Efremenko, I., M. Sheintuch, I. Gouzman and A. Hoffman, Cluster model of DC-glow discharge enhanced diamond nucleation 198/199 (1999) 951
Egger, P., R. Burkhalter and J. Hulliger, Czochralski growth of $Ba_2Y_{1-x}Er_xCl_7$ $(0 < x \leqslant 1)$ using growth equipment integrated into a dry-box 200 (1999) 515
Eguchi, M., see Watanabe, M. 193 (1998) 402
Ehret, E., see Dour, G. 193 (1998) 230
Ehsani, H., see Hitchcock, C.W. 195 (1998) 363
Ehsani, H., I. Bhat, C. Hitchcock, R.J. Gutmann, G. Charache and M. Freeman, p-Type and n-type doping in GaSb and $Ga_{0.8}In_{0.2}Sb$ layers grown by metalorganic vapor phase epitaxy 195 (1998) 385
Eisener, B., M. Wagner, D. Wolf and G. Müller, Study of the intrinsic defects in solution grown $CuInSe_2$ crystals depending on the path of crystallization 198/199 (1999) 321
Eiting, C.J., see Dupuis, R.D. 195 (1998) 340
El Jani, B., see Rebey, A. 191 (1998) 734
El Jani, B., see Rebey, A. 194 (1998) 286

El Jani, B., see Rebey, A. 194 (1998) 292
El-Masry, N.A., see Yu, Z. 195 (1998) 333
Eliashevich, I., see Tran, C.A. 195 (1998) 397
Elliott, R., see Liu, J. 191 (1998) 261
Ellis, D., see Berrigan, R.A. 195 (1998) 718
Ellmer, K., see Oertel, J. 198/199 (1999) 1205
Ellmers, C., S. Leu, R. Rettig, M. Hofmann, W.W. Rühle and W. Stolz, GaAs-based VCSEL-structures with strain-compensated (GaIn)As/Ga(PAs)-MQWH active regions grown by using TBAs and TBP 195 (1998) 630
Elwenspoek, M., see Nijdam, A.J. 198/199 (1999) 430
Emerson, D.T., see Wankerl, A. 191 (1998) 8
Enculescu, I., see Iliescu, B. 198/199 (1999) 507
Endoh, Y., see Kaneko, N. 197 (1999) 818
Engelhardt, R., see Pohl, U.W. 195 (1998) 569
Enoki, Y., see Osawa, S. 198/199 (1999) 444
Epelbaum, B.M., A. Yoshikawa, K. Shimamura, T. Fukuda, K. Suzuki and Y. Waku, Microstructure of $Al_2O_3/Y_3Al_5O_{12}$ eutectic fibers grown by μ-PD method 198/199 (1999) 471
Erbert, G., see Bugge, F. 195 (1998) 676
Eremenko, V.V., see Kovalenko, S.I. 191 (1998) 553
Erkoç, Ş and Ş. Katircioğlu, Dependence of energy levels and optical transitions on layer thicknesses in InSe/GaSe superlattices 194 (1998) 331
Eroğlu, I., see Tanrikulu, S.Ü. 194 (1998) 220
Esser, N., see Pristovsek, M. 195 (1998) 1
Etienne, G., see Declercq, J.-P. 196 (1999) 595
Eustathopoulos, N., B. Drevet and E. Ricci, Temperature coefficient of surface tension for pure liquid metals 191 (1998) 268
Eustathopoulos, N., see Duffar, T. 198/199 (1999) 374
Evrard, C., see Declercq, J.-P. 196 (1999) 595
Evrard, C., see Carter, D.C. 196 (1999) 610

Fainberg, J., see Mühe, A. 198/199 (1999) 409
Falcou, A., see Décobert, J. 195 (1998) 681
Falster, R., see Voronkov, V.V. 194 (1998) 76
Falster, R., see Voronkov, V.V. 198/199 (1999) 399
Fan Feidi, see Song Youting 194 (1998) 379
Fan, S., R. Sun, Y. Lin and J. Wu, Bridgman growth of lead potassium niobate crystals 198/199 (1999) 542
Fan, X.W., see Yu, G. 196 (1999) 77
Fang Zujie, see Xu Ke 193 (1998) 127
Faou, P., see Ebel, C. 196 (1999) 395
Faqir, H., see Mansori, M. 197 (1999) 141
Farid, B., see Briat, B. 197 (1999) 724
Faschinger, W., Doping and contacting of wide gap II–VI compounds 197 (1999) 557
Faurie, J.-P., see Bousquet, V. 192 (1998) 102
Fawell, P.D., see Rossiter, D.S. 191 (1998) 525
Fediv, V.I., see Savchuk, A.I. 197 (1999) 698
Fedorov, A.G., I.A. Shneiderman, A.Yu. Sipatov and E.V. Kaidalova, X-ray diffraction investigation of diffusion in PbTe–PbSe superlattices 198/199 (1999) 1211
Fedorov, A.G., see Belenchuk, A. 198/199 (1999) 1216
Fedorov, I.I., see Chepurov, A.I. 198/199 (1999) 963
Fedorov, V.A., Yu.N. Korkishko, F. Vereda, G. Lifante and F. Cussó, Structural characterisation of vapour Zn-diffused waveguides in lithium niobate 194 (1998) 94
Fedotova, V.V., see Shiryaev, S.V. 198/199 (1999) 631
Fedotova, V.V., see Barilo, S.N. 198/199 (1999) 636
Feichouk, P., see Vacková, S. 197 (1999) 599
Feigelson, R.S., see Lee, M. 193 (1998) 347
Feigelson, R.S., see Lee, M. 193 (1998) 355
Felicelli, S.D., J.C. Heinrich and D.R. Poirier, Three-dimensional simulations of freckles in binary alloys 191 (1998) 879
Feltgen, T., see Fiederle, M. 197 (1999) 635
Feng, J., W.D. Huang, X. Lin, Q.Y. Pan, T. Li and Y.H. Zhou, Primary cellular/dendritic spacing selection of Al–Zn alloy during unidirectional solidification 197 (1999) 393
Feng, J., see Zou, X. 200 (1999) 441
Feng, Q.L., H. Wang, F.Z. Cui and T.N. Kim, Controlled crystal growth of calcium phosphate on titanium surface by NaOH-treatment 200 (1999) 550
Feng, S., see Zhu, H. 197 (1999) 372
Feng, S.L., see Wang, Z.M. 192 (1998) 97
Feng Songlin, see Zhao Qian 200 (1999) 603
Feng, Z.C., see Ferguson, I.T. 195 (1998) 648
Ferguson, I.T., see Tran, C.A. 195 (1998) 397
Ferguson, I.T., C. Beckman, Z.C. Feng, A.G. Thompson, R. Stall, H.Q. Hou, K. Seipel, S.W. Chen and L. Aina, MOCVD growth of high power 0.5 W 35 GHz MMICs 195 (1998) 648
Fernández-González, A., R. Martín-Díaz and M. Prieto, Crystallisation of $Ba(SO_4, CrO_4)$ solid solutions from aqueous solutions 200 (1999) 227
Fernelius, N.C., see Singh, N.B. 198/199 (1999) 588
Ferrari, C., see Henderson, R. 194 (1998) 8
Ferrater, C., see Trtík, V. 192 (1998) 175
Ferreira, S.O., see Rappl, P.H.O. 191 (1998) 466
Ferriol, M., Y. Terada, T. Fukuda and G. Boulon, Laser heated pedestal growth and characterization of zinc lithium niobate crystals 197 (1999) 221
Feth, S., see Chattopadhyay, K. 191 (1998) 377
Feth, S., see Su, C.-H. 192 (1998) 386

Fetzer, C., see Lee, S.H. 195 (1998) 13
Feychuk, P., see Panchuk, O. 197 (1999) 607
Fiederle, M., T. Feltgen, J. Meinhardt, M. Rogalla and K.W. Benz, State of the art of (Cd,Zn)Te as gamma detector 197 (1999) 635
Fife, P.C., see Charach, Ch. 198/199 (1999) 1267
Figiel, J.J., see Han, J. 195 (1998) 291
Filz, T., see Ostheimer, V. 198/199 (1999) 1184
Finet, S., see Tardieu, A. 196 (1999) 193
Finet, S., see Bonneté, F. 196 (1999) 403
Fini, P.T., see Marchand, H. 195 (1998) 328
Fink, J., see Behr, G. 198/199 (1999) 642
Finkelstein, K.D., see Dobrianov, I. 196 (1999) 511
Fischer, B., J. Friedrich, H. Weimann and G. Müller, The use of time-dependent magnetic fields for control of convective flows in melt growth configurations 198/199 (1999) 170
Fissel, A., see Schenk, H.P.D. 200 (1999) 45
Fix, W., see Velling, P. 195 (1998) 490
Flade, T., M. Jurisch, A. Kleinwechter, A. Köhler, U. Kretzer, J. Prause, Th. Reinhold and B. Weinert, State of the art 6″ SI GaAs wafers made of conventionally grown LEC-crystals 198/199 (1999) 336
Flade, T., see Korb, J. 198/199 (1999) 343
Flade, T., see Gärtner, G. 198/199 (1999) 355
Fleischer, S., C. Surya, Y.F. Hu, C.D. Beling, S. Fung, T.L. Smith, K.M. Moulding and M. Missous, A study of the vacancy-defect distribution in a GaAs/$Al_xGa_{1-x}As$ multi-layer structure grown at low temperature 196 (1999) 53
Flisch, A., see Piechotka, M. 193 (1998) 90
Flueraru, C., see Verardi, P. 197 (1999) 523
Fochuk, P., O. Korovyanko and O. Panchuk, High-temperature point defect equilibrium in CdTe modelling 197 (1999) 603
Fochuk, P., see Panchuk, O. 197 (1999) 607
Földvári, I., Á. Péter, O. Szakács and A. Munoz F., Improvement in quality and performance of photorefractive Bi_2TeO_5 198/199 (1999) 482
Folman, M., see Shima, R. 198/199 (1999) 957
Forbes, I., see Miles, R.W. 198/199 (1999) 316
Forchel, A., see Höfling, E. 191 (1998) 607
Forsythe, E.L., E.H. Snell, C.C. Malone and M.L. Pusey, Crystallization of chicken egg white lysozyme from assorted sulfate salts 196 (1999) 332
Foucaran, A., see Boulouz, A. 194 (1998) 336
Fougères, P., L. Chibani, M. Hageali, J.M. Koebel, G. Hennard, A. Zumbiehl, P. Siffert and M. Benkadour, Zinc segregation in HPB grown nuclear detector grade $Cd_{1-x}Zn_xTe$ 197 (1999) 641
Fougères, P., see Zerrai, A. 197 (1999) 646
Fougères, P., see Zumbiehl, A. 197 (1999) 650
Fougères, P., see Zumbiehl, A. 197 (1999) 670
Fourme, R., A. Ducruix, M. Riès-Kautt and B. Capelle, Probing the quality of crystals of biological macromolecules using maximum resolution of diffraction data, Bragg reflection profiles and X-ray topographs 196 (1999) 535
Foxon, C.T., see Orton, J.W. 197 (1999) 7
Foxon, C.T., see Cheng, T.S. 197 (1999) 12
Franc, J., E. Belas, A.L. Toth, H. Sitter, P. Hlídek, P. Moravec and P. Höschl, Diffusion length of minority carriers in (CdZn)Te and (HgCd)Te single crystals measured by EBIC method 197 (1999) 593
François, C.J.P., see Tracy, S.L. 193 (1998) 374
Franke, D., F.W. Reier and N. Grote, Post-growth Zn diffusion into InGaAs/InP in a LP-MOVPE reactor 195 (1998) 112
Franke, T., P. Kreutzer, Th. Zacher, W. Naumann and R. Anton, In situ RHEED, AFM, and REM investigations of the surface recovery of MBE-grown GaAs(0 0 1)-layers during growth interruptions 193 (1998) 451
Franz, M., see Dold, P. 192 (1998) 125
Franzheld, R., see Pietzonka, I. 195 (1998) 21
Franzheld, R., see Pietzonka, I. 196 (1999) 33
Frasunyak, V.M., see Savchuk, A.I. 197 (1999) 698
Frateschi, N.C., see de Castro, M.P.P. 193 (1998) 510
Frazier, D.O., see Wang, W.S. 198/199 (1999) 578
Freeman, M.J., see Hitchcock, C.W. 195 (1998) 363
Freeman, M.J., see Ehsani, H. 195 (1998) 385
Freiberg, M., see Schönherr, E. 197 (1999) 455
Freij, S., see Reyhani, M.M. 198/199 (1999) 258
Freudenberger, J., see Behr, G. 198/199 (1999) 642
Frey, I., see Ritter, S. 196 (1999) 344
Frey, T., see Lima, A.P. 197 (1999) 31
Frey, V., see Winterhoff, R. 195 (1998) 132
Friedman, D.J., see Geisz, J.F. 195 (1998) 401
Friedman, D.J., J.F. Geisz, S.R. Kurtz and J.M. Olson, 1-eV solar cells with GaInNAs active layer 195 (1998) 409
Friedman, D.J., J.F. Geisz, S.R. Kurtz, J.M. Olson and R. Reedy, Nonlinear dependence of N incorporation on In content in GaInNAs 195 (1998) 438
Friedrich, J., see Fischer, B. 198/199 (1999) 170
Frolow, F., see Lyahovitskaya, V. 197 (1999) 177
Froment, M., see Furlong, M.J. 193 (1998) 114

Fu, H., see Zhang, W. 194 (1998) 263
Fu, R.-H., see Zhang, J.-P. 192 (1998) 93
Fu, Y.-J., Z.-S. Gao, J.-M. Liu, Y.-P. Li, H. Zeng and M.-H. Jiang, The effects of anionic impurities on the growth habit and optical properties of KDP 198/199 (1999) 682
Fu, Z., B. Lin, G. Liao and Z. Wu, The effect of Zn buffer layer on growth and luminescence of ZnO films deposited on Si substrates 193 (1998) 316
Fuess, H., see Buschmann, V. 191 (1998) 430
Fuess, H., see Buschmann, V. 193 (1998) 335
Fujii, N., see Miyashita, M. 192 (1998) 79
Fujii, T., see Sekijima, T. 193 (1998) 446
Fujino, H., see Migita, S. 200 (1999) 161
Fujisawa, Y., see Kubota, N. 197 (1999) 388
Fujita, K., see Koizumi, K. 198/199 (1999) 1136
Fujita, Sg., see Tachibana, H. 196 (1999) 41
Fujita, Sg., see Ogata, K. 198/199 (1999) 1170
Fujita, Sz., see Tachibana, H. 196 (1999) 41
Fujita, Sz., see Ogata, K. 198/199 (1999) 1170
Fujiwara, S., Y. Watanabe, Y. Namikawa, T. Keishi, K. Matsumoto and T. Kotani, Numerical simulation on dumping of convection by rotating a horizontal cylinder during crystal growth from vapor 192 (1998) 328
Fujiwara, S., Y. Namikawa, Y. Hirota, M. Irikura, K. Matsumoto and T. Kotani, Growth of ZnSe single crystal by CVT method with self-moving convection shield 196 (1999) 83
Fujiwara, S., see Niimura, N. 200 (1999) 265
Fukuda, T., see Kaigawa, K. 191 (1998) 119
Fukuda, T., see Kawaguchi, T. 191 (1998) 125
Fukuda, T., see Sato, J. 191 (1998) 746
Fukuda, T., see Ko, J.M. 192 (1998) 157
Fukuda, T., see Lan, C.W. 193 (1998) 552
Fukuda, T., see Kawaguchi, T. 193 (1998) 605
Fukuda, T., see Shimamura, K. 194 (1998) 203
Fukuda, T., see Shimamura, K. 194 (1998) 209
Fukuda, T., see Chani, V.I. 194 (1998) 374
Fukuda, T., see Takeda, H. 197 (1999) 204
Fukuda, T., see Ferriol, M. 197 (1999) 221
Fukuda, T., see Shimamura, K. 197 (1999) 896
Fukuda, T., see Epelbaum, B.M. 198/199 (1999) 471
Fukuda, T., see Ko, J.M. 200 (1999) 490
Fukuda, T., see Baldochi, S.L. 200 (1999) 521
Fukui, T., see Oda, Y. 195 (1998) 6
Fukui, T., see Akabori, M. 195 (1998) 579
Fukuyama, T., see Obara, K. 198/199 (1999) 77
Funato, M., see Tachibana, H. 196 (1999) 41
Fung, S., see Fleischer, S. 196 (1999) 53
Füredi-Milhofer, H., N. Garti and A. Kamyshny, Crystallization from microemulsions – a novel method for the preparation of new crystal forms of aspartame 198/199 (1999) 1365
Furlong, M.J., M. Froment, M.C. Bernard, R. Cortès, A.N. Tiwari, M. Krejci, H. Zogg and D. Lincot, Aqueous solution epitaxy of CdS layers on $CuInSe_2$ 193 (1998) 114
Furukawa, Y., see Nabetani, Y. 193 (1998) 470
Furukawa, Y., K. Kitamura, E. Suzuki and K. Niwa, Stoichiometric $LiTaO_3$ single crystal growth by double crucible Czochralski method using automatic powder supply system 197 (1999) 889
Furuya, H., M. Yoshimura, T. Kobayashi, K. Murase, Y. Mori and T. Sasaki, Crystal growth and characterization of $Gd_xY_{1-x}Ca_4O(BO_3)_3$ crystal 198/199 (1999) 560
Furuya, T., see Shibata, M. 196 (1999) 47

Gabas, N., see Lin, C.H. 191 (1998) 791
Gabas, N., see Lin, C.H. 191 (1998) 803
Gabrielli, C., G. Maurin, G. Poindessous and R. Rosset, Nucleation and growth of calcium carbonate by an electrochemical scaling process 200 (1999) 236
Gajbhiye, N.S., see Panda, R.N. 191 (1998) 92
Gal, M., see Li, G. 195 (1998) 54
Gal'chinetskii, L.P., see Atroshchenko, L.V. 197 (1999) 471
Gal'chinetskii, L.P., see Atroshchenko, L.V. 197 (1999) 475
Gal'chinetskii, L.P., see Ryzhikov, V. 197 (1999) 655
Gal'chinetskii, L.P., see Atroshchenko, L.W. 198/199 (1999) 292
Galenko, P.K. and D.A. Danilov, Model for free dendritic alloy growth under interfacial and bulk phase nonequilibrium conditions 197 (1999) 992
Galindo, V., see Abrutis, A. 191 (1998) 79
Galkin, S.N., see Atroshchenko, L.V. 197 (1999) 471
Galkin, S.N., see Atroshchenko, L.V. 197 (1999) 475
Galkin, S.N., see Ryzhikov, V. 197 (1999) 655
Galkin, S.N., see Atroshchenko, L.W. 198/199 (1999) 292
Gallagher, D.T., Q. Pan and G.L. Gilliland, Mechanism of ionic strength dependence of crystal growth rates in a subtilisin variant 193 (1998) 665
Gallagher, H.G., see Ryu, G. 191 (1998) 492
Gama, S., see Mota, M.A. 198/199 (1999) 850
Gamarnik, M.Y., Crystallization of high molecular weight urokinase 197 (1999) 254
Gan Fuxi, see Zhou Guoqing 191 (1998) 517
Gandais, M., see Veignant, F. 196 (1999) 141
Gao, J., see Zeng, J. 197 (1999) 874

Gao, S., D. Cui, B. Huang and M. Jiang, Study on the factors affecting the particles size of GaP nanocrystalline materials 192 (1998) 89
Gao, S., see Wu, G. 192 (1998) 417
Gao, Y., J.H. Edgar, J. Chaudhuri, S.N. Cheema, M.V. Sidorov and D.N. Braski, Low-temperature chemical vapor deposition of 3C–SiC films on Si(1 0 0) using SiH_4–C_2H_4–HCl–H_2 191 (1998) 439
Gao, Z.-S., see Fu, Y.-J. 198/199 (1999) 682
Garandet, J.-P., see Barat, C. 194 (1998) 149
Garcia, E., S. Veesler, R. Boistelle and C. Hoff, Crystallization and dissolution of pharmaceutical compounds. An experimental approach 198/199 (1999) 1360
Garcia, J.A., A. Remón, V. Muñoz and R. Triboulet, Photoluminescence study of radiative transitions in ZnTe bulk crystals 191 (1998) 685
Garcia, J.A., A. Remón, V. Muñoz and R. Triboulet, Effect of plastic deformation on photoluminescence of ZnTe bulk monocrystals 197 (1999) 794
García-Ruiz, J.-M., see Otálora, F. 196 (1999) 546
García-Ruiz, J.-M., see Otálora, F. 196 (1999) 649
García-Ruiz, J.-M., M.L. Novella and F. Otálora, Supersaturation patterns in counter-diffusion crystallisation methods followed by Mach–Zehnder interferometry 196 (1999) 703
Gardeniers, J.G.E., see Nijdam, A.J. 198/199 (1999) 430
Gardner, J.S., B.D. Gaulin and D.McK. Paul, Single crystal growth by the floating-zone method of a geometrically frustrated pyrochlore antiferromagnet, $Tb_2Ti_2O_7$ 191 (1998) 740
Garnier, M., see Dour, G. 193 (1998) 230
Garrault-Gauffinet, S. and A. Nonat, Experimental investigation of calcium silicate hydrate (C-S-H) nucleation 200 (1999) 565
Garry, G., see Veignant, F. 196 (1999) 141
Garti, N., see Füredi-Milhofer, H. 198/199 (1999) 1365
Gärtner, G., T. Flade, M. Jurisch, A. Köhler, J. Korb, U. Kretzer and B. Weinert, Oxygen incorporation in undoped LEC-GaAs 198/199 (1999) 355
Gartsman, K., see Lyahovitskaya, V. 197 (1999) 177
Gartstein, E., see Mogilyanski, D. 198/199 (1999) 1070
Gatalskaya, V.I., see Barilo, S.N. 198/199 (1999) 636
Gatskevitch, E., see Ivlev, G. 198/199 (1999) 1066
Gauer, D., see Schmidt, R. 195 (1998) 124
Gaulin, B.D., see Gardner, J.S. 191 (1998) 740
Gavira, J.A., see Otalora, F. 196 (1999) 546
Gavrilov, S., see Belogorokhov, A.I. 197 (1999) 702
Gaye, H., see Rocabois, P. 198/199 (1999) 838
Gayral, B., see Sagnes, I. 195 (1998) 524
Ge, W., see Lu, L. 194 (1998) 25
Gebhardt, W., see Hahn, B. 191 (1998) 65
Gebre, T., see Wang, W.S. 198/199 (1999) 578
Geertman, R.M., see Oosterhof, H. 198/199 (1999) 754
Geertman, R.M., see ter Horst, J.H. 198/199 (1999) 773
Geiger, M., see Porsche, J. 195 (1998) 591
Geißelbrecht, W., see Velling, P. 195 (1998) 490
Geisz, J.F., D.J. Friedman, J.M. Olson, S.R. Kurtz and B.M. Keyes, Photocurrent of 1 eV GaInNAs lattice-matched to GaAs 195 (1998) 401
Geisz, J.F., see Friedman, D.J. 195 (1998) 409
Geisz, J.F., see Friedman, D.J. 195 (1998) 438
Gelabert, M.C., R.A. Laudise and R.E. Riman, Phase stability, solubility and hydrothermal crystal growth of $PbTiO_3$ 197 (1999) 195
Gelfgat, Yu.M., Rotating magnetic fields as a means to control the hydrodynamics and heat/mass transfer in the processes of bulk single crystal growth 198/199 (1999) 165
Gentscheva, G., see Manuilov, N. 196 (1999) 181
Gérard, J.M., see Sagnes, I. 195 (1998) 524
Gerbeth, G., see Mößner, R. 197 (1999) 341
Gerson, A.R., see Barnes, M.C. 200 (1999) 251
Gerthsen, D., B. Neubauer, Ch. Dieker, R. Lantie, A. Rizzi and H. Lüth, Molecular beam epitaxy (MBE) growth and structural properties of GaN and AlN on 3C-SiC(0 0 1) substrates 200 (1999) 353
Gesheva, K., see Gogova, D. 198/199 (1999) 1230
Gesheva, K., see Szekeres, A. 198/199 (1999) 1235
Geurts, J., see Dinger, A. 200 (1999) 391
Gherasim, C., see Verardi, P. 197 (1999) 523
Ghica, C., see Verardi, P. 197 (1999) 523
Giacometti, N., see Boiton, P. 194 (1998) 43
Giacometti, N., see Duffar, T. 198/199 (1999) 374
Giani, A., see Boulouz, A. 194 (1998) 336
Gibart, P., see Rebey, A. 191 (1998) 734
Gibart, P., see Nataf, G. 192 (1998) 73
Gibart, P., see Rebey, A. 194 (1998) 292
Gibis, R., see Künzel, H. 192 (1998) 56
Giegé, R., see Sauter, C. 196 (1999) 365
Gierse, J.K., see Stevens, A.M. 196 (1999) 350
Giesen, Ch., see Xu, X.G. 191 (1998) 341
Giesen, Ch., M.M. Beerbom, X.G. Xu and K. Heime, MOVPE of AlAsSb using tritertiarybutylaluminum 195 (1998) 85
Gil-Lafon, E., see Trassoudaine, A. 192 (1998) 402
Gill, W.N., see Naik, M.B. 193 (1998) 133
Gilliland, G.L., see Gallagher, D.T. 193 (1998) 665

Givand, J.C., R.W. Rousseau and P.J. Ludovice, Characterization of L-isoleucine crystal morphology from molecular modeling 194 (1998) 228

Givand, J.C., A.S. Teja and R.W. Rousseau, Manipulating crystallization variables to enhance crystal purity 198/199 (1999) 1340

Givoli, D., see Vigdergauz, S. 198/199 (1999) 125

Gladki, A., see Hruban, A. 198/199 (1999) 282

Glans, P.-A., see Syväjärvi, M. 198/199 (1999) 1019

Glebovsky, V.G., see Moest, B. 192 (1998) 410

Glicksman, M.E., see LaCombe, J.C. 194 (1998) 143

Glikin, A.E., see Kiryanova, E.V. 198/199 (1999) 697

Gogova, D., A. Iossifova, T. Ivanova, Zl. Dimitrova and K. Gesheva, Electrochromic behavior in CVD grown tungsten oxide films 198/199 (1999) 1230

Gogova, D., see Szekeres, A. 198/199 (1999) 1235

Goldfarb, I. and G.A.D. Briggs, The effect of mismatch strain on Stranski–Krastanow transition in epitaxial Ge_xSi_{1-x}/Si(0 0 1) gas-source growth 198/199 (1999) 1032

Goldsteen, B.Z., see Edmundson, A.B. 196 (1999) 276

Golovin, A.A., S.H. Davis and A.A. Nepomnyashchy, Modeling the formation of facets and corners using a convective Cahn–Hilliard model 198/199 (1999) 1245

Golyshev, V.D., M.A. Gonik and V.B. Tsvetovsky, Problems of $Bi_4Ge_3O_{12}$ and $Li_2B_4O_7$ single crystal growth by crusibleless variant of AHP method 198/199 (1999) 501

Gondet, S., T. Duffar, G. Jacob, N. Van den Bogaert and F. Louchet, Thermal stress simulation and interface destabilisation in indium phosphide grown by LEC process 198/199 (1999) 129

Gong, H.-Y., see Shu, Z.-Y. 192 (1998) 282

Gong, Q., J.B. Liang, B. Xu, D. Ding, H.X. Li, C. Jiang, W. Zhou, F.Q. Liu, Z.G. Wang, X.H. Qiu, G.Y. Shang and C.L. Bai, Analysis of atomic force microscopic results of InAs islands formed by molecular beam epitaxy 192 (1998) 376

Gong, Q., see Xu, H. 200 (1999) 70

Gong, Q., see Liu, J.P. 200 (1999) 617

Gonik, M.A., see Golyshev, V.D. 198/199 (1999) 501

Gonzalez, A., see Scripa, R.N. 198/199 (1999) 825

González-Cinca, R., L. Ramírez-Piscina, J. Casademunt, A. Hernández-Machado, T. Tóth-Katona, T. Börzsönyi and Á. Buka, Heat diffusion anisotropy in dendritic growth: phase field simulations and experiments in liquid crystals 193 (1998) 712

González-Ramírez, L.A., see Moreno, A. 196 (1999) 587

Goorsky, M.S., see Koontz, E.M. 198/199 (1999) 1104

Göppert, M., see Dinger, A. 200 (1999) 391

Gorbenko, O., see Kleptsyn, V. 196 (1999) 122

Goriletsky, V.I., Evolution of structural state in massive CsI-based single crystals pulled from melt 198/199 (1999) 860

Goriletsky, V.I., see Panova, A.N. 198/199 (1999) 865

Gorley, P.M., see Ciach, R. 197 (1999) 675

Gorochov, O., see Thiandoume, C. 197 (1999) 805

Goswami, J., see Lyahovitskaya, V. 197 (1999) 106

Goto, F., see Ichimura, M. 198/199 (1999) 308

Goto, T., see Iijima, M. 193 (1998) 182

Gotoh, Y., see Kawanowa, H. 197 (1999) 163

Gottschalch, V., see Pietzonka, I. 195 (1998) 21

Gottschalch, V., see Pietzonka, I. 196 (1999) 33

Götz, G., see Czech, E. 198/199 (1999) 1087

Goumet, E., see Trassoudaine, A. 192 (1998) 402

Gouzman, I., see Efremenko, I. 198/199 (1999) 951

Gower, J.E., see Maxey, C.D. 197 (1999) 427

Gower, L.A. and D.A. Tirrell, Calcium carbonate films and helices grown in solutions of poly(aspartate) 191 (1998) 153

Gramlich, S., see Knauer, A. 195 (1998) 694

Granberg, R.A., D.G. Bloch and Å.C. Rasmuson, Crystallization of paracetamol in acetone–water mixtures 198/199 (1999) 1287

Granier, J., see Leroux, S. 198/199 (1999) 911

Grasza, K., Computational modeling of the low supersaturation nucleation in crystal growth by "contactless" physical vapor transport 193 (1998) 426

Gratens, X., see Breton, G. 200 (1999) 112

Graw, G., see Behr, G. 198/199 (1999) 642

Gray, R.J., see Christopher, G.K. 191 (1998) 820

Grebennik, A., see Lott, K. 197 (1999) 489

Greedan, J.E., see Dąbkowski, A. 197 (1999) 879

Green, L., see Partin, D.L. 195 (1998) 378

Greenberg, J.H., Vapor pressure scanning implications of CdTe crystal growth 197 (1999) 406

Greenberg, J.H., see Ben-Dor, L. 198/199 (1999) 1151

Greiling, A., see Leu, S. 195 (1998) 98

Grein, C.H., see Oh, J. 193 (1998) 241

Griebl, E., see Hahn, B. 191 (1998) 65

Grimbergen, R.F.P., see Vogels, L.J.P. 191 (1998) 563

Grimbergen, R.F.P., P.J.C.M. van Hoof, H. Meekes and P. Bennema, Morphology of orthorhombic n-paraffin crystals: the influence of multiple connected nets 191 (1998) 846

Grimbergen, R.F.P., see van Hoof, P.J.C.M. 191 (1998) 861

Grinyov, B.V., see Zaslavsky, B.G. 198/199 (1999) 856

Grinyova, T.B., see Panova, A.N. 198/199 (1999) 865
Groppelli, S., see Sangaletti, L. 198/199 (1999) 1240
Gross, C., W. Assmus, A. Muiznieks, A. Mühlbauer, C. Stenzel and O. Schulz, Possible use of Skull melting under microgravity 198/199 (1999) 188
Grossmann, J.G., see Shekunov, B.Yu. 198/199 (1999) 1335
Grote, N., see Franke, D. 195 (1998) 112
Grudowski, P.A., see Dupuis, R.D. 195 (1998) 340
Grün, M., see Dinger, A. 200 (1999) 391
Grundmann, M., see Heinrichsdorff, F. 195 (1998) 540
Guan, Q., X. Hu, J. Wei, J. Wang, L. Tian, W. Cui and Y. Liu, Growth, etching, polarization and second harmonic generation of potassium lithium tantalate niobate crystals 197 (1999) 1012
Guéneau, C., see Leroux, S. 198/199 (1999) 911
Guenrikhson, V., see Kleptsyn, V. 196 (1999) 122
Guerasimov, V., see Murthy, R.V.A. 197 (1999) 865
Guérin, R., C. Le Marec and P. Haldenwang, Striation in Bridgman directional solidification 194 (1998) 247
Guevara, J.A., see Andreeta, M.R.B. 200 (1999) 621
Gui, X., see Rak, M. 197 (1999) 944
Guillén-Cervantes, A., see López-López, M. 193 (1998) 528
Gündüz, M., see Bayender, B. 194 (1998) 119
Guo, B., S. Kao, H. McDonald, A. Asanov, L.L. Combs and W.W. Wilson, Correlation of second virial coefficients and solubilities useful in protein crystal growth 196 (1999) 424
Guo, J.Q., T.J. Sato, T. Hirano and A.P. Tsai, Solid–liquid interface in the growth of a decagonal Al-72 Co-16 Ni-12 quasi crystal 197 (1999) 963
Guo, L.P., see Chen, Y. 193 (1998) 342
Guo, Y., see Dudley, M. 192 (1998) 1
Guo, Z., S. Maruyama and S. Togawa, Combined heat transfer in floating zone growth of large silicon crystals with radiation on diffuse and specular surfaces 194 (1998) 321
Gupta, J.A., J.C. Woicik, S.P. Watkins, K.E. Miyano, J.G. Pellegrino and E.D. Crozier, An X-ray standing wave study of ultrathin InAs films in GaAs(0 0 1) grown by atomic layer epitaxy 195 (1998) 34
Gupta, J.A., S.P. Watkins, R. Arès and G. Soerensen, MOVPE growth of single monolayers of InAs in GaAs studied by time-resolved reflectance difference spectroscopy 195 (1998) 205
Gupta, V., see Mihopoulos, T.G. 195 (1998) 733
Gurin, V.S., Nucleation and growth of PbS nanocrystals and simulation of X-ray diffraction patterns 191 (1998) 161
Gurjiyants, P.A., M.Yu. Starostin, V.N. Kurlov, F. Theodore and J. Delepine, Effect of growth conditions on the strength of shaped sapphire 198/199 (1999) 227
Gustafsson, A., see Seifert, W. 197 (1999) 19
Gutbrod, H., see Burachas, S. 198/199 (1999) 881
Gutmann, R.J., see Hitchcock, C.W. 195 (1998) 363
Gutmann, R.J., see Ehsani, H. 195 (1998) 385
Gutsche, D., see Kurpas, P. 195 (1998) 217
Guttzeit, A., see Schineller, B. 195 (1998) 274
Guzmán, A., see Sánchez, J.J. 192 (1998) 363

Haas, C. and J. Drenth, Understanding protein crystallization on the basis of the phase diagram 196 (1999) 388
Habelitz, S., see Höche, T. 192 (1998) 185
Haberland, K., see Zettler, J.-T. 195 (1998) 151
Haberland, K., see Steimetz, E. 195 (1998) 530
Hadji, L. and A.M.J. Davis, The influence of insoluble spherical particles on the stability of a planar solidifying interface 191 (1998) 889
Haffouz, S., see Nataf, G. 192 (1998) 73
Hage-Ali, M., see Fougères, P. 197 (1999) 641
Hage-Ali, M., see Zerrai, A. 197 (1999) 646
Hage-Ali, M., see Zumbiehl, A. 197 (1999) 650
Hage-Ali, M., see Zumbiehl, A. 197 (1999) 670
Hageman, P.R., see Bauhuis, G.J. 191 (1998) 313
Hageman, P.R., G.J. Bauhuis and S.M. Olsthoorn, Influence of Ga precursor choice on ordering degree of MOVPE grown $Ga_{0.5}In_{0.5}P$ 194 (1998) 270
Hageman, P.R., see de Theije, F.K. 197 (1999) 37
Hahn, B., E. Pschorr-Schoberer, E. Griebl, M. Kastner and W. Gebhardt, Metalorganic chemical vapor deposition of ZnSe films on glass and GaAs(1 1 1) substrates 191 (1998) 65
Hahn, H., see Buschmann, V. 193 (1998) 335
Hahn, S.-H., T. Tsukada, M. Hozawa, S. Maruyama, N. Imaishi and S. Kitagawa, Global analysis of heat transfer in Si CZ furnace with specular and diffuse surfaces 191 (1998) 413
Hähnert, I., see Kappelt, M. 195 (1998) 552
Haidoux, A., see Tomasini, P. 193 (1998) 572
Haldenwang, P., see Guérin, R. 194 (1998) 247
Halliday, D.P., see Durose, K. 197 (1999) 733
Halliday, D.P., see Aitken, N.M. 198/199 (1999) 984
Halliwell, M.A.G. and S.J. Chua, Determining substrate orientation using a high-resolution diffractometer 192 (1998) 456

Hamadeh, H., see Taudt, W. 191 (1998) 663
Hamamoto, K., see Mori, K. 195 (1998) 466
Hamann, J., see Ostheimer, V. 198/199 (1999) 1184
Hammons, B.E., see Hou, H.Q. 195 (1998) 199
Han, B.-K., see Li, L. 195 (1998) 28
Han, D.W., see Choi, D.J. 191 (1998) 718
Han, E.-M., see Yoshida, Y. 198/199 (1999) 923
Han, J., J.J. Figiel, M.H. Crawford, M.A. Banas, M.E. Bartram, R.M. Biefeld, Y.K. Song and A.V. Nurmikko, OMVPE growth and gas-phase reactions of AlGaN for UV emitters 195 (1998) 291
Han, M.S., T.W. Kang and T.W. Kim, Structural and electrical properties of the arsenic planar-doped $Hg_{1-x}Cd_xTe$ epilayers grown on p-$Cd_{0.96}Zn_{0.04}Te$ substrates 200 (1999) 101
Han, P., see Duan, S. 195 (1998) 304
Han, P.D., see Wang, Z.M. 192 (1998) 97
Han, P.-D., see Yang, H.-F. 193 (1998) 478
Han, Q., see Zhu, D.-W. 196 (1999) 356
Han, T.P.J., see Ryu, G. 191 (1998) 492
Hanada, T., see Yoshida, Y. 198/199 (1999) 923
Handschuh, M., see Pietzonka, I. 196 (1999) 33
Hanna, M., see Shekunov, B.Yu. 198/199 (1999) 1345
Hansen, D., see Koporulina, E.V. 191 (1998) 767
Hansen, D.M., P.D. Moran, K.A. Dunn, S.E. Babcock, R.J. Matyi and T.F. Kuech, Development of a glass-bonded compliant substrate 195 (1998) 144
Hansson, G.V., see Joelsson, K.B. 196 (1999) 97
Hansson, P.O., see Von Ammon, W. 198/199 (1999) 390
Hao, M.S., see Wang, J. 197 (1999) 48
Happo, Y., see Katsumata, T. 198/199 (1999) 1226
Hara, K., see Hirose, S. 194 (1998) 16
Hara, M., see Nakamura, F. 195 (1998) 280
Hardikar, S., see Modak, P. 193 (1998) 501
Hardt, A., see Taudt, W. 191 (1998) 663
Hardtdegen, H., see Schmidt, R. 195 (1998) 124
Hardtdegen, H., M. Pristovsek, H. Menhal, J.-T. Zettler, W. Richter and D. Schmitz, In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere 195 (1998) 211
Harp, J., see Carter, D.C. 196 (1999) 602
Harris Jr., J.S., see Huang, T.F. 200 (1999) 362
Hartel, R.W., see Ben-Yoseph, E. 198/199 (1999) 1294
Härtwig, J., see Amon, J. 198/199 (1999) 367
Harusawa, M., see Anzai, H. 191 (1998) 148
Hasegawa, F., see Tsuchiya, H. 198/199 (1999) 1056
Haselhoff, M., K. Reimann and H.-J. Weber, Optical determination of the size distribution of CuCl nanocrystals in NaCl 196 (1999) 135
Hashimoto, S., see Nakamura, F. 195 (1998) 280
Hasznosné-Nezdei, M., see Liszi, I. 198/199 (1999) 1330
Hatakeyama, H., see Mori, K. 195 (1998) 466
Hatanaka, Y., see Niraula, M. 200 (1999) 90
Hauck, T., see Schmidt, R. 195 (1998) 124
Hawksworth, A., W.M. Rainforth and H. Jones, Solidification microstructure selection in the Al-rich Al–La, Al–Ce and Al–Nd systems 197 (1999) 286
Hayakawa, Y., see Aswal, D.K. 193 (1998) 61
Hayakawa, Y., see Aswal, D.K. 197 (1999) 379
Hayakawa, Y., see Iida, S. 200 (1999) 368
Hayakawa, Y., see Aswal, D.K. 200 (1999) 427
Hayashi, Y., see Saito, T. 191 (1998) 723
Hayes, C., see Barber, P. 198/199 (1999) 815
Hearne, S., see Lane, D.W. 197 (1999) 743
Heime, K., see Xu, X.G. 191 (1998) 341
Heime, K., see Xu, J. 193 (1998) 50
Heime, K., see Xu, J. 193 (1998) 738
Heime, K., see Giesen, Ch. 195 (1998) 85
Heime, K., see Schineller, B. 195 (1998) 274
Heime, K., see Behres, A. 195 (1998) 373
Heime, K., see Liu, Q. 197 (1999) 507
Heine, J.R., J. Rodriguez-Viejo, M.G. Bawendi and K.F. Jensen, Synthesis of CdSe quantum dot–ZnS matrix thin films via electrospray organometallic chemical vapor deposition 195 (1998) 564
Heinecke, H., see Butendeich, R. 195 (1998) 510
Heinecke, H., see Kröner, P. 195 (1998) 660
Heinrich, J.C., see Felicelli, S.D. 191 (1998) 879
Heinrichsdorff, F., M. Grundmann, O. Stier, A. Krost and D. Bimberg, Influence of In/Ga intermixing on the optical properties of InGaAs/GaAs quantum dots 195 (1998) 540
Henderson, R., F. Walters, C.L. Reynolds, Jr., V. Swaminathan, L.C. Luther, G. Salviati and C. Ferrari, Structural and optical characterization of strained and strain-compensated InGaAsP/InP quantum well laser structures 194 (1998) 8
Hennard, G., see Fougères, P. 197 (1999) 641
Hennessy, A.J., A. Neville and K.J. Roberts, An examination of additive-mediated wax nucleation in oil pipeline environments 198/199 (1999) 830
Henningsen, T., see Singh, N.B. 198/199 (1999) 995
Henry, A., see Syväjärvi, M. 197 (1999) 155
Henry, A., see Syväjärvi, M. 198/199 (1999) 1019
Heremans, J., see Partin, D.L. 195 (1998) 378
Hernandes, A.C., see Andreeta, M.R.B. 200 (1999) 621
Hernández-Calderón, I., see López-López, M. 193 (1998) 528

Hernández-Calderón, I., see Constantino, M.E. 194 (1998) 301
Hernández-Machado, A., see González-Cinca, R. 193 (1998) 712
Hetterich, M., see Dinger, A. 200 (1999) 391
Heuken, M., see Xu, X.G. 191 (1998) 341
Heuken, M., see Taudt, W. 191 (1998) 663
Heuken, M., see Schineller, B. 195 (1998) 274
Heuken, M., see Schoen, O. 195 (1998) 297
Heuken, M., see Liu, Q. 197 (1999) 507
Heuken, M., see Beccard, R. 198/199 (1999) 1049
Hiaraiwa, M., see Dąbkowski, A. 197 (1999) 879
Hibiya, T., see Watanabe, M. 193 (1998) 402
Hicks, R.F., see Kappers, M.J. 191 (1998) 332
Hicks, R.F., see Begarney, M.J. 193 (1998) 305
Hicks, R.F., see Li, L. 195 (1998) 28
Hidaka, Y., see Kaneko, N. 197 (1999) 818
Hidalgo, P., see Plaza, J.L. 198/199 (1999) 379
Hiei, F., see Tsukamoto, H. 191 (1998) 679
Hill, S.C., see Baird, J.K. 196 (1999) 220
Hirabayashi, I., see Takagi, A. 193 (1998) 71
Hiraiwa, M., see Imanaka, N. 200 (1999) 169
Hiralal, I.D.K., see Sweegers, C. 197 (1999) 244
Hirano, M., see Xu, X.W. 198/199 (1999) 536
Hirano, T., see Sato, T.J. 191 (1998) 545
Hirano, T., see Guo, J.Q. 197 (1999) 963
Hirata, A., see Arafune, K. 197 (1999) 811
Hirose, F. and H. Sakamoto, Prediction of concentration profile for P doping in Si gas-source molecular beam epitaxy 196 (1999) 115
Hirose, S., M. Yamaura, A. Yoshida, H. Ibuka, K. Hara and H. Munekata, Mechanism of atomic layer epitaxy of AlAs 194 (1998) 16
Hirota, Y., see Fujiwara, S. 196 (1999) 83
Hirsch, L.S., see Ziemer, K.S. 191 (1998) 594
Hisa, Y., see Kizuki, H. 194 (1998) 277
Hitchcock, C.W., R.J. Gutmann, H. Ehsani, I.B. Bhat, C.A. Wang, M.J. Freeman and G.W. Charache, Ternary and quaternary antimonide devices for thermophotovoltaic applications 195 (1998) 363
Hitchcock, C.W., see Ehsani, H. 195 (1998) 385
Hlídek, P., see Franc, J. 197 (1999) 593
Ho, J.X., see Carter, D.C. 196 (1999) 602
Ho, J.X., see Carter, D.C. 196 (1999) 610
Ho, J.X., see Carter, D.C. 196 (1999) 623
Höche, T., S. Habelitz and I.I. Khodos, Origin of unusual fluorophlogopite morphology in mica glass-ceramics of the system SiO_2–Al_2O_3–MgO–K_2O–Na_2O–F_2 192 (1998) 185
Hodgkiess, T., see Morizot, A. 198/199 (1999) 738
Hoff, C., see Garcia, E. 198/199 (1999) 1360
Hoffman, A., see Efremenko, I. 198/199 (1999) 951
Hoffman, A., see Shima, R. 198/199 (1999) 957
Höfling, E., J.P. Reithmaier, T. Baars, M. Bayer and A. Forchel, Optical and structural properties of GaInAs/InP single quantum wells grown by solid-source MBE with a GaP decomposition source 191 (1998) 607
Hofmann, D., M. Bickermann, R. Eckstein, M. Kölbl, St.G. Müller, E. Schmitt, A. Weber and A. Winnacker, Sublimation growth of silicon carbide bulk crystals: experimental and theoretical studies on defect formation and growth rate augmentation 198/199 (1999) 1005
Hofmann, L., A. Knauer, I. Rechenberg and M. Weyers, Overgrowth of trenches with (AlGa)As using metalorganic vapor-phase epitaxy (MOVPE) 195 (1998) 485
Hofmann, M., see Ellmers, C. 195 (1998) 630
Hofstra, P.G., see Krasnov, A.N. 194 (1998) 53
Hogg, S., see Jin, S. 194 (1998) 189
Höhnsdorf, F., see Leu, S. 195 (1998) 91
Höhnsdorf, F., see Leu, S. 195 (1998) 98
Höhnsdorf, F., J. Koch, C. Agert and W. Stolz, Investigations of (GaIn)(NAs) bulk layers and (GaIn)(NAs)/GaAs multiple quantum well structures grown using tertiarybutylarsine (TBAs) and 1,1-dimethylhydrazine (UDMHy) 195 (1998) 391
Hollman, R.J.A.J., see Zijlema, T.G. 198/199 (1999) 789
Holmbäck, X. and Å.C. Rasmuson, Size and morphology of benzoic acid crystals produced by drowning-out crystallisation 198/199 (1999) 780
Holmes, D.M., E.S. Tok, J.L. Sudijono, T.S. Jones and B.A. Joyce, Surface evolution in GaAs(1 1 0) homoepitaxy; from microscopic to macroscopic morphology 192 (1998) 33
Holmes, R.R., see Scripa, R.N. 198/199 (1999) 825
Holtz, P.O., see Zhao, Q.X. 193 (1998) 328
Honda, T., A. Inoue, M. Mori, T. Shirasawa, N. Mochida, K. Saotome, T. Sakaguchi, A. Ohtomo, M. Kawasaki, H. Koinuma, F. Koyama and K. Iga, GaN growth on ozonized sapphire(0001) substrates by MOVPE 195 (1998) 319
Hondoh, T., see Salamatin, A.N. 193 (1998) 197
Hong, C.H., see Kim, S.T. 194 (1998) 37
Hong, K.J., see Lee, H. 191 (1998) 59

Hong, S.K., B.J. Kim, H.S. Park, Y. Park, S.Y. Yoon and T.I. Kim, Evaluation of nanopipes in MOCVD grown (0001)GaN/Al_2O_3 by wet chemical etching 191 (1998) 275

Hong, S.M., M. Akaishi and S. Yamaoka, Nucleation of diamond in the system of carbon and water under very high pressure and temperature 200 (1999) 326

Hong, X., K. Lu, L. Li and D. Tang, Viscosity and density of BaB_2O_4, BaB_2O_4–NaF and BaB_2O_4–Na_2O melts 193 (1998) 610

Hong, X. and K. Lu, Physical properties of Li_2O–$4B_2O_3$ melt 200 (1999) 172

Hoogesteger, F.J., see ten Grotenhuis, E. 191 (1998) 834

Hooper, S.E., see Orton, J.W. 197 (1999) 7

Hopkins, F.K., see Singh, N.B. 198/199 (1999) 588

Hopkins, R.H., see Seidensticker, R.G. 198/199 (1999) 988

Hopkins, R.H., see Singh, N.B. 198/199 (1999) 995

Hopkinson, M., see Sánchez, J.J. 192 (1998) 363

Horikawa, H., see Yamauchi, Y. 195 (1998) 74

Höschl, P., see Franc, J. 197 (1999) 593

Hoshikawa, K., see Maeda, S. 192 (1998) 117

Hoshikawa, K., see Maeda, S. 194 (1998) 70

Hoshizaki, H., see Ueno, Y. 197 (1999) 376

Hosokawa, E., see Kishida, S. 192 (1998) 136

Hosoya, S., see Kaneko, N. 197 (1999) 818

Hosseini, M.W., see Sauter, C. 196 (1999) 365

Hou, H.Q., B.E. Hammons and W.G. Breiland, In situ etching of GaAs by $AsCl_3$ for regrowth on AlGaAs in metalorganic vapor-phase epitaxy 195 (1998) 199

Hou, H.Q., see Ferguson, I.T. 195 (1998) 648

Hovakimian, L.B. and S.-i. Tanaka, Involvement of image forces in dynamics of epitaxial dislocation arrays 198/199 (1999) 900

Hövel, R., see Xu, X.G. 191 (1998) 341

Howard, J., see McPherson, A. 196 (1999) 572

Hozawa, M., see Hahn, S.-H. 191 (1998) 413

Hozman, J., see Kubínek, R. 193 (1998) 174

Hruban, A., W. Dalecki, K. Nowysz, S. Strzelecka and A. Gładki, Synthesis and crystallization of ZnSe by the liquid encapsulation technique 198/199 (1999) 282

Hsieh, J.-Y., see Lee, S.-C. 200 (1999) 305

Hsu, C.-T., Variation with composition of the properties in ZnS_xSe_{1-x} 193 (1998) 33

Hsu, T.C., Y. Hsu and G.B. Stringfellow, Effect of P precursor on surface structure and ordering in GaInP 193 (1998) 1

Hsu, Y., see Hsu, T.C. 193 (1998) 1

Hu, B., see Wu, G. 192 (1998) 417

Hu, E., see Keller, S. 195 (1998) 258

Hu, J., see Arès, R. 195 (1998) 234

Hu, J., see Xu, X.G. 195 (1998) 687

Hu, W.R., see Tang, Z.M. 192 (1998) 335

Hu, X., see Guan, Q. 197 (1999) 1012

Hu, Y.F., see Fleischer, S. 196 (1999) 53

Hu, Z., see Zhang, W. 194 (1998) 263

Huan, Q., see Cai, L.C. 197 (1999) 364

Huang, B., see Gao, S. 192 (1998) 89

Huang, C.-K., see Yang, C.-C. 200 (1999) 32

Huang, C.-K., see Yang, C.-C. 200 (1999) 39

Huang, D.D., see Liu, J.P. 193 (1998) 535

Huang, D.D., see Liu, J.P. 194 (1998) 426

Huang, D.D., see Liu, J.P. 200 (1999) 613

Huang, D.D., see Liu, J.P. 200 (1999) 617

Huang, J.F., see Jin, P. 191 (1998) 285

Huang, J.-W., see Cederberg, J.G. 195 (1998) 63

Huang, J.Y., see Wu, H.Z. 191 (1998) 72

Huang, T.F., A. Marshall, S. Spruytte and J.S. Harris Jr., Optical and structural properties of epitaxial GaN films grown by pulsed laser deposition 200 (1999) 362

Huang, W.-D., see Cang, H.-X. 192 (1998) 236

Huang, W.D., see Feng, J. 197 (1999) 393

Huang, X.R., see Dudley, M. 192 (1998) 1

Huang, Y., see Xu, G.-Y. 200 (1999) 143

Huber, G., see Rogin, P. 198/199 (1999) 564

Hudait, M.K., see Modak, P. 193 (1998) 501

Huet, F., see di Forte-Poisson, M.A. 195 (1998) 314

Hufgard, E., see Leu, S. 195 (1998) 91

Hughes, O.H., see Cheng, T.S. 197 (1999) 12

Hull, R., see Xu, J. 196 (1999) 26

Hulliger, J., see Rogin, P. 198/199 (1999) 564

Hulliger, J., see Egger, P. 200 (1999) 515

Hultman, L., see Joelsson, K.B. 196 (1999) 97

Hummel, S.G., see Mihopoulos, T.G. 195 (1998) 725

Humphreys, C.J., see Walther, T. 197 (1999) 113

Hunt, J.D., see Maraşli, N. 191 (1998) 558

Huppert, H.E., see Spencer, B.J. 200 (1999) 287

Hurich, M., see Butendeich, R. 195 (1998) 510

Hurle, D.T.J., see Dudley, M. 192 (1998) 1

Hwang, C.-C., see Lee, S.-C. 200 (1999) 305

Hwang, J., S. Tanaka, S. Iwai, Y. Aoyagi and S. Seong, High quality GaN film growth on AlN buffer layer, pretreated with alternating pulsative supply of TMG and NH_3 200 (1999) 63

Hwang, N.M. and H.M. Jang, Nucleation behavior of cage structure of carbon in the presence of charge 198/199 (1999) 929

Hwang, N.M., Crystal growth by charged cluster focused on CVD diamond process 198/199 (1999) 945

Hwang, S.J., see Considine, L. 195 (1998) 192

Hwang, Y.G., see Kim, K.C. 197 (1999) 841

Ibbetson, J.P., see Marchand, H. 195 (1998) 328
Ibuka, H., see Hirose, S. 194 (1998) 16
Ichimura, M., F. Goto, Y. Ono and E. Arai, Deposition of CdS and ZnS from aqueous solutions by a new photochemical technique 198/199 (1999) 308
Ichino, K., see Inoue, R. 198/199 (1999) 1196
Iga, K., see Honda, T. 195 (1998) 319
Iga, K., see Miyamoto, T. 195 (1998) 421
Iga, K., see Ohnoki, N. 195 (1998) 603
Iga, K., see Schlenker, D. 196 (1999) 67
Iga, K., see Miyamoto, T. 197 (1999) 67
Iga, R., see Yamamoto, N. 193 (1998) 16
Iida, K., see Takiguchi, H. 193 (1998) 641
Iida, S., Y. Hayakawa, T. Koyama and M. Kumagawa, Effect of trench structure on the quality of InGaAs layers grown on patterned GaAs (1 1 1) A substrates 200 (1999) 368
Iijima, M., H. Kamemizu, N. Wakamatsu, T. Goto, Y. Doi and Y. Moriwaki, Effects of Ca addition on the formation of octacalcium phosphate and apatite in solution at pH 7.4 and at 37°C 193 (1998) 182
Iijima, M. and Y. Moriwaki, Lengthwise and oriented growth of octacalcium phosphate crystal in polyacrylamide gel in a model system of tooth enamel apatite formation 194 (1998) 125
Iijima, M. and Y. Moriwaki, Effects of ionic inflow and organic matrix on crystal growth of octacalcium phosphate; relevant to tooth enamel formation 198/199 (1999) 670
Ikeda, M., see Tsukamoto, H. 191 (1998) 679
Ikeda, M., see Nakamura, F. 195 (1998) 280
Ilashchuk, M.I., see Savitsky, A.V. 192 (1998) 196
Ilaschouk, M.I., see Vacková, S. 197 (1999) 599
Ilashchuk, M.I., see Panchuk, O. 197 (1999) 607
Iliescu, B., I. Enculescu, F. Vasiliu and M. Secu, Growth of metal structures in quartz crystals by electrodiffusion 198/199 (1999) 507
Iliescu, B., see Dinculescu, I. 198/199 (1999) 999
Ilievski, D., see Rossiter, D.S. 191 (1998) 525
Imaeda, M., see Kaigawa, K. 191 (1998) 119
Imaeda, M., see Kawaguchi, T. 191 (1998) 125
Imaeda, M., see Kawaguchi, T. 193 (1998) 605
Imaeda, M., see Chani, V.I. 194 (1998) 374
Imaishi, N., see Hahn, S.-H. 191 (1998) 413
Imaishi, N., see Jing, C.J. 200 (1999) 204
Imanaga, S., see Nakamura, F. 195 (1998) 280
Imanaka, N., see Dąbkowski, A. 197 (1999) 879
Imanaka, N., M. Hiraiwa, S. Tamura, G. Adachi, H. Dabkowska and A. Dabkowski, Single-crystal growth of aluminum tungstate–scandium tungstate solid solution samples by the modified Czochralski method 200 (1999) 169
Inatomi, Y., A. Takada and K. Kuribayashi, Morphological change of semiconductor growth interface from solution in a magnetic field 198/199 (1999) 176
Inoue, A., see Honda, T. 195 (1998) 319
Inoue, R., M. Kitagawa, T. Nishigaki, D. Morita, K. Ichino, H. Kobayashi, M. Ohishi and H. Saito, Growth and luminescence of $Zn_xMg_{1-x}S:Mn$ ternary compound crystal films 198/199 (1999) 1196
Iossifova, A., see Gogova, D. 198/199 (1999) 1230
Irie, S., S. Isoda, K. Kuwamoto, M.J. Miles, T. Kobayashi and Y. Yamashita, Monolayer epitaxy of a triangular molecule on graphite 198/199 (1999) 939
Irikura, M., see Fujiwara, S. 196 (1999) 83
Irisawa, T., see Yoshioka, Y. 198/199 (1999) 71
Irmscher, K., see Schulz, D. 198/199 (1999) 1024
Irvine, S.J.C., see Berrigan, R.A. 195 (1998) 718
Irvine, S.J.C., A. Stafford and M.U. Ahmed, Substrate/layer relationships in II–VIs 197 (1999) 616
Isaenko, L.I., see Yelisseyev, A.P. 198/199 (1999) 555
Ishibashi, A., see Okuyama, H. 193 (1998) 43
Ishida, M., see Jung, Y.-C. 196 (1999) 88
Ishido, T., see Tachibana, H. 196 (1999) 41
Ishii, H., see Matsuoka, M. 198/199 (1999) 1299
Ishikawa, H., see Nishijima, Y. 197 (1999) 769
Ishikawa, Y., see Wang, J. 197 (1999) 48
Ishikawa, Y., see Wang, J. 200 (1999) 85
Ishimaru, M., S. Munetoh, T. Motooka, K. Moriguchi and A. Shintani, Behavior of impurity atoms during crystal growth from melted silicon: carbon atoms 194 (1998) 178
Ishizu, T., see Kitamura, M. 192 (1998) 225
Islam, M.R., see Saghir, M.Z. 193 (1998) 623
Isoda, S., see Irie, S. 198/199 (1999) 939
Isshiki, M., see Miki, T. 200 (1999) 399
Itai, K., see Kubota, N. 196 (1999) 156
Itaya, A., see Nagai, Y. 193 (1998) 732
Ito-Landers, K.M., see Soares, L.S.M. 191 (1998) 44
Ivanchuk, D.D., see Savitsky, A.V. 192 (1998) 196
Ivanchuk, R.D., see Savitsky, A.V. 192 (1998) 196
Ivanov, A.A., see Bakin, A.S. 198/199 (1999) 1015
Ivanov, I.G., see Syväjärvi, M. 197 (1999) 147
Ivanov, V.Yu., see Szczerbakow, A. 191 (1998) 673
Ivanov, Yu.M., The growth of single crystals by the self-seeding technique 194 (1998) 309
Ivanova, T., see Gogova, D. 198/199 (1999) 1230

Ivlev, G., E. Gatskevitch, O. Borusík, V. Cháb, P. Přikryl and R. Černý, Pulsed laser assisted recrystallisation of monocrystalline InSb surfaces 198/199 (1999) 1066
Iwai, S., see Hwang, J. 200 (1999) 63
Iwanov, D. and D. Nenow, Equilibrium form of camphene crystals 198/199 (1999) 96
Iyoda, T., see Osawa, S. 198/199 (1999) 444
Izmailov, A.F., A.S. Myerson and S. Arnold, A statistical understanding of nucleation 196 (1999) 234
Izpura, I., see Sánchez, J.J. 192 (1998) 363
Izuta, S., see Kaito, C. 200 (1999) 271

Jackson, K.A., Computer modeling of atomic scale crystal growth processes 198/199 (1999) 1
Jacob, G., see Gondet, S. 198/199 (1999) 129
Jacob, K.I., see Möller, J. 197 (1999) 973
Jacobi, K., see Pristovsek, M. 195 (1998) 1
Jacobs, K., see Considine, L. 195 (1998) 192
Jadhav, V.K., see Tavare, N.S. 198/199 (1999) 1320
Jagadish, C., see Li, G. 191 (1998) 357
Jagadish, C., see Li, G. 195 (1998) 54
Jäger-Waldau, A., see Birkholz, M. 197 (1999) 571
Jäger-Waldau, A., see Weiss, T. 198/199 (1999) 1190
Jakabovič, J., see Kečkéš, J. 192 (1998) 84
James, L., see Zaitseva, N. 197 (1999) 911
Jang, H.M., see Hwang, N.M. 198/199 (1999) 929
Jang, K.-Y., Y. Okada and M. Kawabe, Effect of hydrogen in AlGaAs grown by atomic hydrogen-assisted molecular beam epitaxy 197 (1999) 54
Janićijević, A., see Čabrić, B. 200 (1999) 339
Janßen, G., see Velling, P. 195 (1998) 117
Janzén, E., see Tuominen, M. 193 (1998) 101
Janzén, E., see Syväjärvi, M. 197 (1999) 147
Janzén, E., see Syväjärvi, M. 197 (1999) 155
Janzén, E., see Syväjärvi, M. 198/199 (1999) 1019
Jayavel, R., see Ushasree, P.M. 197 (1999) 216
Jeffs, N.J., see Cheng, T.S. 197 (1999) 12
Jeganathan, K., see Saravanan, S. 192 (1998) 23
Jeganathan, K., S. Saravanan, P. Ramasamy and J. Kumar, Effect of bismuth on liquid-phase epitaxy (LPE) grown GaAs layer using Ga–As–Bi melt 200 (1999) 341
Jelsch, C., see Taleb, M. 200 (1999) 575
Jenkins, G., see McPherson, A. 196 (1999) 572
Jenneskens, L.W., see ten Grotenhuis, E. 191 (1998) 834
Jennings, H.M., see Tracy, S.L. 193 (1998) 374
Jennings, H.M., see Tracy, S.L. 193 (1998) 382
Jensen, K.F., see Vineis, C.J. 195 (1998) 181
Jensen, K.F., see Heine, J.R. 195 (1998) 564
Jensen, K.F., see Mihopoulos, T.G. 195 (1998) 725
Jensen, K.F., see Mihopoulos, T.G. 195 (1998) 733
Jeong, T.S., see Lee, H. 191 (1998) 59
Jia, K., see Wu, G. 192 (1998) 417
Jia, W., H. Yuan, L. Lu, H. Liu and W.M. Yen, Crystal growth and characterization of Eu^{2+}, Dy^{3+} : $SrAl_2O_4$ and Eu^{2+}, Nd^{3+} : $CaAl_2O_4$ by the LHPG method 200 (1999) 179
Jiang, C., see Gong, Q. 192 (1998) 376
Jiang, H., see Ning, Y. 191 (1998) 39
Jiang, M., see Gao, S. 192 (1998) 89
Jiang, M.-H., see Fu, Y.-J. 198/199 (1999) 682
Jiang Rihong, see Yang Shangfeng 197 (1999) 383
Jiang, W., see Xu, H. 200 (1999) 70
Jiang, X.B., see Wu, H.Z. 191 (1998) 72
Jiang Xue-yin, Jin Yang, Zhang Zhi-lin and Xu Shao-hong, Mn-doped nanometer-size ZnS clusters in chitosan film matrix prepared by ion-coordination reaction 191 (1998) 692
Jie, W.Q., see Ma, D. 194 (1998) 398
Jimbo, T., see Saravanan, S. 192 (1998) 23
Jiménez-González, A.E., J.A. Soto Urueta and R. Suárez-Parra, Optical and electrical characteristics of aluminum-doped ZnO thin films prepared by solgel technique 192 (1998) 430
Jin, G.L., see Liu, J.L. 200 (1999) 106
Jin, P., M. Tazawa, J.F. Huang and S. Tanemura, Growth of samarium monosulfide thin films by co-sputtering deposition 191 (1998) 285
Jin, S., H. Bender, M.F. Wu, A. Vantomme, S. Hogg, H. Pattyn and G. Langouche, Growth of high-quality buried Y- and (Y, Nd)-silicide layers prepared by channelled ion implantation 194 (1998) 189
Jin, S.R., see Chen, J.X. 193 (1998) 28
Jin, W., Z. Pan and Z. Liu, Effect of buoyancy-driven convection upon crystal growth of $KNbO_3$ in the melt 191 (1998) 760
Jin, Y., see Ning, Y. 191 (1998) 39
Jin Yan, see Jiang Xue-yin 191 (1998) 692
Jing, C.J., N. Imaishi, S. Yasuhiro and Y. Miyazawa, Three-dimensional numerical simulation of spoke pattern in oxide melt 200 (1999) 204
Jochum, S., E. Kuphal, V. Piataev and H. Burkhard, Very high compositional homogeneity of 1.55 μm strain-compensated InGaAsP MQW structures by MOVPE under N_2 atmosphere 195 (1998) 637

Joelsson, K.B., L. Hultman, W.-X Ni, J. Cardenas, B.G. Svensson, E. Olsson and G.V. Hansson, Er doping of Si and $Si_{0.88}Ge_{0.12}$ using Er_2O_3 and ErF_3 evaporation during molecular beam epitaxy: a transmission electron microscopy study 196 (1999) 97
Johansson, J., W. Seifert, T. Junno and L. Samuelson, Sizes of self-assembled quantum dots – effects of deposition conditions and annealing 195 (1998) 546
Johansson, J., see Seifert, W. 197 (1999) 19
Johansson, L.I., see Syväjärvi, M. 198/199 (1999) 1019
Johnson, D.J., see Chen, Y. 193 (1998) 342
Johnson, M.A.L., see Yu, Z. 195 (1998) 333
Johnson, R., see Mawst, L.J. 195 (1998) 609
Johnston, M.B., see Li, G. 195 (1998) 54
Johnstone, J., C. Peacock and K.J. Roberts, Application of polarised NEXAFS spectroscopy to the structural characterisation of condensed molecular surfaces and interfaces 198/199 (1999) 275
Jones, A.C., see Lane, P.A. 192 (1998) 423
Jones, H., see Hawksworth, A. 197 (1999) 286
Jones, T.S., see Holmes, D.M. 192 (1998) 33
Joo, H.-B., G.M. Yang, D.H. Lim, J.-H. Kim, K.S. Kim, K.Y. Lim and E.-K. Suh, Self-organized growth of InGaAs/GaAs/AlGaAs quantum dot heterostructures by metalorganic chemical vapor deposition 194 (1998) 161
Joutsensaari, J., see Pauwels, B. 200 (1999) 126
Joyce, B.A., see Holmes, D.M. 192 (1998) 33
Ju, Y.L., see Li, Y.X. 191 (1998) 282
Juergensen, H., see Schoen, O. 195 (1998) 297
Juergensen, H., see Beccard, R. 198/199 (1999) 1049
Jullien, M., see Boyer, M. 196 (1999) 185
Jung, Y.-C., H. Miura, K. Ohtani and M. Ishida, High-quality silicon/insulator heteroepitaxial structures formed by molecular beam epitaxy using Al_2O_3 and Si 196 (1999) 88
Junno, T., see Carlsson, N. 191 (1998) 347
Junno, T., see Johansson, J. 195 (1998) 546
Jurisch, M., see Rudolph, P. 198/199 (1999) 325
Jurisch, M., see Flade, T. 198/199 (1999) 336
Jurisch, M., see Korb, J. 198/199 (1999) 343
Jurisch, M., see Gärtner, G. 198/199 (1999) 355

Ka, O., see Thiandoume, C. 197 (1999) 805
Kachniarz, J., see Miotkowska, S. 200 (1999) 483
Kadota, Y., see Yamamoto, N. 193 (1998) 16
Kagawa, H., see Kanie, H. 197 (1999) 504
Kageyama, T., see Miyamoto, T. 197 (1999) 67
Kaidalova, E.V., see Fedorov, A.G. 198/199 (1999) 1211
Kaigawa, K., T. Kawaguchi, M. Imaeda, H. Sakai and T. Fukuda, Crystal structure of LPE-grown $LiNb_{1-x}Ta_xO_3$ epitaxial films 191 (1998) 119
Kaiser, R., see Künzel, H. 192 (1998) 56
Kaiser, Th., see Cröll, A. 191 (1998) 365
Kaiser, U., see Schenk, H.P.D. 200 (1999) 45
Kaishita, Y., see Nishioka, K. 200 (1999) 592
Kaito, C., H. Suzuki, S. Izuta, N. Tsuda, Y. Saito, T. Nakada and S. Kimura, Spontaneous growth of singular morphology of a comet-like fine particle 200 (1999) 271
Kajikawa, Y., see Kizuki, H. 194 (1998) 277
Kakanakova-Georgieva, A., see Tuominen, M. 193 (1998) 101
Kakanakova-Georgieva, A., see Syväjärvi, M. 197 (1999) 155
Kakimoto, K., S. Kikuchi and H. Ozoe, Molecular dynamics simulation of oxygen in silicon melt 198/199 (1999) 114
Kalanda, N.A., see Zhigunov, D.I. 198/199 (1999) 605
Kaldis, E., see Piechotka, M. 193 (1998) 80
Kaldis, E., see Piechotka, M. 193 (1998) 90
Kaler, E.W., see Neal, B.L. 196 (1999) 377
Kam, C.H., see Shi, W. 197 (1999) 89
Kamada, H., see Temmyo, J. 195 (1998) 516
Kamemizu, H., see Iijima, M. 193 (1998) 182
Kameta, M., see Saito, T. 191 (1998) 723
Kamiya, N., see Sugiyama, N. 191 (1998) 84
Kamp, M., see Prystawko, P. 198/199 (1999) 1061
Kamyshny, A., see Füredi-Milhofer, H. 198/199 (1999) 1365
Kaneko, F., K. Tashiro and M. Kobayashi, Polymorphic transformations during crystallization processes of fatty acids studied with FT-IR spectroscopy 198/199 (1999) 1352
Kaneko, N., S. Ueno, J. Yano, T. Katsuragi and K. Sato, Impurity effects on crystallization rates of n-hexadecane in oil-in-water emulsions 197 (1999) 263
Kaneko, N., Y. Hidaka, S. Hosoya, K. Yamada, Y. Endoh, S. Takekawa and K. Kitamura, Optimum crucible material for growth of $Pr_{2-x}Ce_xCuO_4$ crystal 197 (1999) 818
Kang, G.Y. and J.K. Yoon, The growth of potassium lithium niobate (KLN) with low Nb_2O_5 content 193 (1998) 615
Kang, T.W., see Han, M.S. 200 (1999) 101
Kanie, H., H. Kagawa and T. Kato, Crystal growth of SrS from Te solution and its optical properties 197 (1999) 504
Kantser, V., see Belenchuk, A. 198/199 (1999) 1216
Kao, S., see Guo, B. 196 (1999) 424
Kaplan, L., see Lyahovitskaya, V. 197 (1999) 106
Kaplan, L., see Lyahovitskaya, V. 197 (1999) 177

Kapon, E., see Biasiol, G. 195 (1998) 596
Kappelt, M., V. Türck, D. Bimberg, H. Kirmse, I. Hähnert and W. Neumann, InGaAs and InAsP V-groove quantum wires using arsenic/phosphorus exchange preparation 195 (1998) 552
Kappers, M.J., M.L. Warddrip and R.F. Hicks, Ligand exchange reactions in InGaAs metalorganic vapor-phase epitaxy 191 (1998) 332
Kappers, M.J., see Begarney, M.J. 193 (1998) 305
Kar, T., see Mukerji, S. 200 (1999) 543
Karabashev, S., see Shulyatev, D. 198/199 (1999) 511
Kariya, M., see Yamaguchi, S. 195 (1998) 309
Karlicek Jr., R.F., see Tran, C.A. 195 (1998) 397
Kasai, Y., see Migita, S. 200 (1999) 161
Kasprowicz, D., see Pajaczkowska, A. 198/199 (1999) 440
Kastner, M., see Hahn, B. 191 (1998) 65
Kasuga, M., see Yoshioka, Y. 198/199 (1999) 71
Katagiri, K.-i., see Kubota, N. 196 (1999) 156
Katırcıoğlu, Ş., see Erkoç, Ş. 194 (1998) 331
Kato, H., see Yamaguchi, S. 195 (1998) 309
Kato, M., see Maeda, S. 192 (1998) 117
Kato, M., see Maeda, S. 194 (1998) 70
Kato, T., see Kanie, H. 197 (1999) 504
Katoh, Y., see Kubota, E. 191 (1998) 501
Katrunov, K., see Burachas, S. 198/199 (1999) 881
Katsumata, T., see Osawa, S. 198/199 (1999) 444
Katsumata, T., see Kawasaki, M. 198/199 (1999) 449
Katsumata, T., R. Sakai, S. Komuro, T. Morikawa and H. Kimura, Growth and characteristics of long duration phosphor crystals 198/199 (1999) 869
Katsumata, T., T. Murakami, Y. Happo and S. Komuro, Preparation of rare-earth oxide films by a pyrolysis technique from acetylacetonates 198/199 (1999) 1226
Katsuragi, T., see Kaneko, N. 197 (1999) 263
Katz, J.L., see Parsiegla, K.I. 200 (1999) 213
Kauerauf, B., G. Zimmermann, L. Murmann and S. Rex, Planar to cellular transition in the system succinonitrile–acetone during directional solidification of a bulk sample 193 (1998) 701
Kaufmann, U., see Obloh, H. 195 (1998) 270
Kaukler, W.F., see Sen, S. 193 (1998) 692
Kaul, A., see Kleptsyn, V. 196 (1999) 122
Kauppinen, E.I., see Pauwels, B. 200 (1999) 126
Kavokin, A.V., see Siviniant, J. 197 (1999) 680
Kawabe, M., see Jang, K.-Y. 197 (1999) 54
Kawaguchi, T., see Kaigawa, K. 191 (1998) 119
Kawaguchi, T., K. Mizuuchi, K. Yamamoto, T. Yoshino, M. Imaeda and T. Fukuda, Fabrication of thin-film waveguide QPM-SHG devices by domain-inverted liquid-phase epitaxy 191 (1998) 125
Kawaguchi, T., M. Imaeda and T. Fukuda, Selective edge-growth with controlled ferroelectric-domain structure by liquid-phase epitaxy 193 (1998) 605
Kawaguchi, T., see Chani, V.I. 194 (1998) 374
Kawahara, A., see Saito, T. 191 (1998) 723
Kawai, H., see Nakamura, F. 195 (1998) 280
Kawanowa, H. and Y. Gotoh, Crystal growth of WSi_2 on a W(1 1 0) surface 197 (1999) 163
Kawasaki, K., see Sawada, T. 191 (1998) 225
Kawasaki, M., see Honda, T. 195 (1998) 319
Kawasaki, M., T. Katsumata, Y. Oshiba and M. Koshiji, Flux growth of thulium vanadate single crystals 198/199 (1999) 449
Kayama, M. and J. Kuwano, Effects of the phosphorus-ion additive on the crystal habit of the emerald crystals grown from the V_2O_5–Li_2O–P_2O_5 fluxes 193 (1998) 648
Kečkéš, J., B. Ortner, J. Jakabovič and J. Kováč, Orientation relationship between indium films and GaSb(1 1 1)B: annealing-induced transformation of fibre texture into heteroepitaxy 192 (1998) 84
Keeling, K., see Carter, D.C. 196 (1999) 602
Keeling, K., see Carter, D.C. 196 (1999) 610
Keeling, K., see Carter, D.C. 196 (1999) 623
Keiper, D., R. Westphalen and G. Landgren, Comparison of carbon doping of InGaAs and GaAs by CBr_4 using hydrogen or nitrogen as carrier gas in LP-MOVPE 197 (1999) 25
Keir, A.M., see Mizuno, K. 198/199 (1999) 1146
Keishi, T., see Fujiwara, S. 192 (1998) 328
Keith, G., see Sauter, C. 196 (1999) 365
Keller, S., S.F. Chichibu, M.S. Minsky, E. Hu, U.K. Mishra and S.P. DenBaars, Effect of the growth rate and the barrier doping on the morphology and the properties of InGaN/GaN quantum wells 195 (1998) 258
Keller, S., see Kozodoy, P. 195 (1998) 265
Keller, S., see Marchand, H. 195 (1998) 328
Kennedy, R.J., see Stampe, P.A. 191 (1998) 472
Kennedy, R.J., see Stampe, P.A. 191 (1998) 478
Kern, R., see Müller, P. 193 (1998) 257
Kessler, N., see Bromberg, R. 193 (1998) 656
Ketata, K., see Ketata, M. 194 (1998) 297

Ketata, M., K. Ketata, S. Koumetz, P. Martin, J. Marcon and C. Dubois, Be diffusion in InGaAs layers grown by gas source molecular beam epitaxy 194 (1998) 297
Keul, J., see Ritter, S. 196 (1999) 344
Keyes, B.M., see Geisz, J.F. 195 (1998) 401
Khan, S.R., see Whipps, S. 192 (1998) 243
Khanin, E., see Levy, M. 197 (1999) 626
Kharachenko, L., see Murthy, R.V.A. 197 (1999) 865
Khlyap, G., see Andrukhiv, A. 198/199 (1999) 1162
Khodos, I.I., see Höche, T. 192 (1998) 185
Khoo, B.C., see Ma, W.J. 193 (1998) 430
Kida, S., see Yap, Y.K. 198/199 (1999) 1028
Kijima, S., see Okuyama, H. 193 (1998) 43
Kikuchi, S., see Kakimoto, K. 198/199 (1999) 114
Kikuma, I., see Udono, H. 193 (1998) 39
Kikuma, I., see Udono, H. 197 (1999) 466
Kilpiö, T., see Koiranen, T. 198/199 (1999) 749
Kim, B.J., see Hong, S.K. 191 (1998) 275
Kim, B.W., see Sanz-Hervás, A. 195 (1998) 558
Kim, C.-S., see Lee, C.-R. 193 (1998) 300
Kim, D.-J., see Paek, J.-S. 200 (1999) 55
Kim, D.H., see Wang, J.H. 198/199 (1999) 120
Kim, D.H., see Kwon, S.K. 198/199 (1999) 1039
Kim, H.-G., see Paek, J.-S. 200 (1999) 55
Kim, H.S., see Kim, Y.K. 192 (1998) 109
Kim, I., K. Uppal, W.-J. Choi and P.D. Dapkus, Composition control of InGaAsP in metalorganic chemical vapor deposition using tertiarybutylphosphine and tertiarybutylarsine 193 (1998) 293
Kim, I., D.-G. Chang and P.D. Dapkus, Growth of InGaAsP in a stagnation flow vertical reactor using TBP and TBA 195 (1998) 138
Kim, J., see Sanz-Hervás, A. 195 (1998) 558
Kim, J.-H., see Joo, H.-B. 194 (1998) 161
Kim, J.H., see Kim, T.W. 197 (1999) 799
Kim, J.Y., see Lee, H. 191 (1998) 59
Kim, K., see Lee, H.J. 191 (1998) 621
Kim, K.C., K.S. Nahm, E.-K. Suh and Y.G. Hwang, The surface modification of Si(1 1 1) substrates with SiN_x for the growth of high quality β-SiC epilayers 197 (1999) 841
Kim, K.-K., see Paek, J.-S. 200 (1999) 55
Kim, K.S., see Joo, H.-B. 194 (1998) 161
Kim, S.I., see Choi, D.J. 191 (1998) 718
Kim, S.T., Y.J. Lee, D.C. Moon, C.H. Hong and T.K. Yoo, Preparation and properties of free-standing HVPE grown GaN substrates 194 (1998) 37
Kim, T.I., see Hong, S.K. 191 (1998) 275
Kim, T.N., see Feng, Q.L. 200 (1999) 550
Kim, T.S., see Lee, H. 191 (1998) 59
Kim, T.W., D.U. Lee and Y.S. Yoon, The interfacial layer formation of the Ag/InP heterointerfaces 193 (1998) 496
Kim, T.W., J.H. Kim, H.L. Park and J.Y. Lee, Structural property and interband transition studies on $Cd_xZn_{1-x}Te/ZnTe$ coupled step and rectangular quantum wells 197 (1999) 799
Kim, T.W., see Han, M.S. 200 (1999) 101
Kim, T.W., see Lim, Y.S. 200 (1999) 421
Kim, Y.H., see Choi, D.J. 191 (1998) 718
Kim, Y.K., J.Y. Lee, H.S. Kim, J.-H. Song and S.-H. Suh, An electron microscopy study on the formation mechanism of hillocks on the (1 0 0)CdTe/GaAs 192 (1998) 109
Kimmel, G., see Shimony, Y. 198/199 (1999) 583
Kimura, H., see Katsumata, T. 198/199 (1999) 869
Kimura, S., see Yoshimura, J. 191 (1998) 483
Kimura, S., see Kaito, C. 200 (1999) 271
Kipshidze, G.D., see Schenk, H.P.D. 200 (1999) 45
Kirchner, C., see Prystawko, P. 198/199 (1999) 1061
Kirillov, B.A., see Bakin, A.S. 198/199 (1999) 1015
Kirmse, H., see Kappelt, M. 195 (1998) 552
Kiryanova, E.V. and A.E. Glikin, The laws of fluorite and calcite habit formation in terms of the morphogenetic structural-chemical concept 198/199 (1999) 697
Kishi, K., see Yamamoto, N. 193 (1998) 16
Kishida, S. and E. Hosokawa, Optimum growth condition of $Bi_2Sr_2CaCu_2O_y$ single crystals in a vertical Bridgman method 192 (1998) 136
Kishida, Y. and K. Okazawa, Geostrophic turbulence in CZ silicon crucible 198/199 (1999) 135
Kisil, I.I., see Zaslavsky, B.G. 198/199 (1999) 856
Kitagawa, M., see Inoue, R. 198/199 (1999) 1196
Kitagawa, S., see Hahn, S.-H. 191 (1998) 413
Kitamura, K., see Kaneko, N. 197 (1999) 818
Kitamura, K., see Furukawa, Y. 197 (1999) 889
Kitamura, M. and T. Ishizu, Kinetic effect of L-phenylalanine on growth process of L-glutamic acid polymorph 192 (1998) 225
Kitamura, M., see Balykov, L.N. 198/199 (1999) 32
Kizuki, H., see Künzel, H. 192 (1998) 56
Kizuki, H., see Miyashita, M. 192 (1998) 79
Kizuki, H., Y. Kajikawa, Y. Hisa and Y. Mihashi, Observation of quasiperiodic faceting both on MOCVD-grown and on gas-etched surfaces of vicinal (1 1 0)GaAs substrates 194 (1998) 277
Klehr, A., see Bugge, F. 195 (1998) 676
Klein, S., see Buschmann, V. 193 (1998) 335

Kleinwechter, A., see Flade, T. 198/199 (1999) 336
Klemenz, C. and H.J. Scheel, Solubility of $YBa_2Cu_3O_{7-\delta}$ and $Nd_{1+x}Ba_{2-x}Cu_3O_{7+\delta}$ in the BaO/CuO flux 200 (1999) 435
Klepetsanis, P.G. and P.G. Koutsoukos, Kinetics of calcium sulfate formation in aqueous media: effect of organophosphorus compounds 193 (1998) 156
Kleptsyn, V., V. Guenrikhson, V. Lisauskas, R. Butkute, B. Vengalis, S. Samojlenkov, O. Gorbenko and A. Kaul, High temperature superconducting thin films on CaGdAlO$_4$ substrates 196 (1999) 122
Klingshirn, C., see Dinger, A. 200 (1999) 391
Klipstein, P.C., S.G. Lyapin, N.J. Mason and P.J. Walker, In situ characterisation of MOVPE by surface photoabsorption. II. Interface monitoring 195 (1998) 168
Kloc, Ch., S.-W. Cheong and P. Matl, Floating-zone crystal growth of perovskite manganites with colossal magnetoresistance 191 (1998) 294
Kloc, Ch. and R.A. Laudise, Vapor pressures of organic semiconductors: α-hexathiophene and α-quaterthiophene 193 (1998) 563
Klos, A., see Pajaczkowska, A. 198/199 (1999) 440
Klotz, S., see Munoz, V. 196 (1999) 71
Knauer, A., see Hofmann, L. 195 (1998) 485
Knauer, A., see Bugge, F. 195 (1998) 676
Knauer, A., G. Oelgart, A. Oster, S. Gramlich, F. Bugge and M. Weyers, Ordering in $Ga_xIn_{1-x}As_yP_{1-y}$ grown on GaAs by metalorganic vapour-phase epitaxy 195 (1998) 694
Kniest, A., see Off, J. 195 (1998) 286
Ko, H.J., see Ko, J.M. 192 (1998) 157
Ko, J.M., Y. Terada, H.J. Ko, K. Shimamura, T. Yao and T. Fukuda, Epitaxial growth of $NdF_3:Er^{3+}$ film on CaF_2(1 1 1) substrate by molecular beam epitaxy 192 (1998) 157
Ko, J.M. and T. Fukuda, Molecular beam epitaxy of $Ca_{1-x}R_xF_{2+x}$ (R = Nd, Er) layers: study of RHEED pattern and lattice mismatch 200 (1999) 490
Kobayashi, H., see Inoue, R. 198/199 (1999) 1196
Kobayashi, J.T., N.P. Kobayashi, X. Zhang, P.D. Dapkus and D.H. Rich, Structural and optical emission characteristics of InGaN thin layers and the implications for growing high-quality quantum wells by MOCVD 195 (1998) 252
Kobayashi, M., see Kaneko, F. 198/199 (1999) 1352
Kobayashi, N., see Nishida, T. 195 (1998) 41
Kobayashi, N., see Kobayashi, Y. 195 (1998) 187
Kobayashi, N., Surface photoabsorption monitoring of III–V and GaN MOVPE surfaces 195 (1998) 228
Kobayashi, N., see Saito, H. 195 (1998) 416
Kobayashi, N., see Nishida, T. 195 (1998) 459
Kobayashi, N.P., see Kobayashi, J.T. 195 (1998) 252
Kobayashi, T., see Watanabe, N. 195 (1998) 48
Kobayashi, T., see Furuya, H. 198/199 (1999) 560
Kobayashi, T., see Irie, S. 198/199 (1999) 939
Kobayashi, T., see Watanabe, N. 200 (1999) 599
Kobayashi, Y., T. Akasaka and N. Kobayashi, In-situ monitoring of GaN MOVPE by shallow-angle reflectance using ultraviolet light 195 (1998) 187
Kobayashi, Y., see Dąbkowski, A. 197 (1999) 879
Kobayashi, Y., see Tachibana, M. 198/199 (1999) 661
Koch, J., see Höhnsdorf, F. 195 (1998) 391
Kochurikhin, V.V., see Shimamura, K. 194 (1998) 203
Kochurikhin, V.V., see Shimamura, K. 194 (1998) 209
Kodama, S., K. Nakajima, Y. Suzuki, O. Ohtsuki and H. Sakai, Compositional variation in AlGaAs crystals grown by LPE under microgravity and terrestrial conditions 194 (1998) 166
Koebel, J.M., see Fougères, P. 197 (1999) 641
Koebel, J.M., see Zerrai, A. 197 (1999) 646
Koebel, J.M., see Zumbiehl, A. 197 (1999) 650
Koebel, J.M., see Zumbiehl, A. 197 (1999) 670
Köhler, A., see Flade, T. 198/199 (1999) 336
Köhler, A., see Korb, J. 198/199 (1999) 343
Köhler, A., see Gärtner, G. 198/199 (1999) 355
Kohler, R., see Mogilyanski, D. 198/199 (1999) 1070
Köhler, U., see Lima, A.P. 197 (1999) 31
Köhne, L., see Dadgar, A. 195 (1998) 69
Koinuma, H., see Honda, T. 195 (1998) 319
Koiranen, T., T. Kilpiö, J. Nurmi and H.V. Nordén, The modelling and simulation of dissolution of sucrose crystals 198/199 (1999) 749
Koizumi, K., P.O. Vaccaro, K. Fujita, M. Tateuchi and T. Ohachi, Lateral wet oxidation of AlAs layer in GaAs/AlAs heterostructures grown by MBE on GaAs (n 1 1)A substrates 198/199 (1999) 1136
Kojima, K., see Tachibana, M. 198/199 (1999) 661
Kojima, K., see Tachibana, M. 198/199 (1999) 665
Kokh, A.E., Crystal growth through forced stirring of melt or solution in Czochralski configuration 191 (1998) 774
Kokh, A.E. and N.G. Kononova, II. Crystal growth through forced stirring of melt or solution in Czochralski configuration 198/199 (1999) 161

Kölbl, M., see Hofmann, D. 198/199 (1999) 1005
Kolodziejski, L.A., see Koontz, E.M. 198/199 (1999) 1104
Komatsu, H., see Sazaki, G. 196 (1999) 204
Komatsu, H., see Kurihara, K. 196 (1999) 285
Komatsu, H., see Yanagiya, S.-i. 196 (1999) 319
Komatsu, H., see Nakada, T. 196 (1999) 503
Komatsu, K., see Mori, K. 195 (1998) 466
Komatsu, K., see Koui, T. 195 (1998) 503
Komatsu, R., see Sugawara, T. 193 (1998) 364
Komuro, S., see Osawa, S. 198/199 (1999) 444
Komuro, S., see Katsumata, T. 198/199 (1999) 869
Komuro, S., see Katsumata, T. 198/199 (1999) 1226
Kondo, S., see Shindo, H. 198/199 (1999) 253
Kondo, S., see Sugiura, H. 200 (1999) 13
Kondo, Y., see Yamamoto, N. 193 (1998) 16
Kong, M., see Li, X. 191 (1998) 31
Kong, M., see Li, X. 191 (1998) 34
Kong, M., see Wang, H. 191 (1998) 627
Kong, M.Y., see Liu, J.P. 193 (1998) 535
Kong, M.Y., see Liu, J.P. 194 (1998) 426
Kong, M.Y., see Zhuang, Q.D. 200 (1999) 375
Kong, M.Y., see Liu, J.P. 200 (1999) 613
Kong, M.Y., see Liu, J.P. 200 (1999) 617
Kong, M.-Y., see Zhang, J.-P. 192 (1998) 93
Kong, M.-Y., see Zhang, J.-P. 192 (1998) 471
Kong, M.-Y., see Zhang, J.-P. 197 (1999) 368
Kong Meiying, see Zhou Hongwei 191 (1998) 361
Kono, K., see Tachibana, M. 198/199 (1999) 665
Kononova, N.G., see Kokh, A.E. 198/199 (1999) 161
Kononova, N.G., see Pylneva, N.A. 198/199 (1999) 546
Konstantinov, V.I., see Yakimovich, V.N. 198/199 (1999) 975
Konstantinov, V.I., see Levchenko, V.I. 198/199 (1999) 980
Konuma, M., G. Cristiani, E. Czech and I. Silier, Liquid phase epitaxy of Si from Pb solutions 198/199 (1999) 1045
Konuma, M., see Czech, E. 198/199 (1999) 1087
Koontz, E.M., G.D. U'Ren, M.H. Lim, L.A. Kolodziejski, M.S. Goorsky, G.S. Petrich and H.I. Smith, Overgrowth of (In,Ga)(As,P) on rectangular-patterned surfaces using gas source molecular beam epitaxy 198/199 (1999) 1104
Koporulina, E.V., see Leonyuk, N.I. 191 (1998) 135
Koporulina, E.V., N.I. Leonyuk, D. Hansen and K.L. Bray, Flux growth and luminescence of Ho : $YAl_3(BO_3)_4$ and $PrAl_3(BO_3)_4$ crystals 191 (1998) 767
Koporulina, E.V., N.I. Leonyuk, S.N. Barilo, L.A. Kurnevich, G.L. Bychkov, A.V. Mokhov, G. Bocelli and L. Righi, Flux growth, composition, structural and thermal characteristics of $(R_xY_{1-x})Al_3(BO_3)_4$ (R = Nd, Gd; $x = 1$, 0.6, 0.65, 0.7 and 0.75) crystals 198/199 (1999) 460
Korakakis, D., see Cheng, T.S. 197 (1999) 12
Korb, J., T. Flade, M. Jurisch, A. Köhler, Th. Reinhold and B. Weinert, Carbon, oxygen, boron, hydrogen and nitrogen in the LEC growth of SI GaAs: a thermochemical approach 198/199 (1999) 343
Korb, J., see Gärtner, G. 198/199 (1999) 355
Korbutjak, N.D., see Korbutyak, D.V. 197 (1999) 659
Korbutyak, D.V., S.G. Krylyuk, P.M. Tkachuk, V.I. Tkachuk, N.D. Korbutjak and M.D. Raransky, Growth and characterization of high-resistivity CdTe⟨Cl⟩ 197 (1999) 659
Korchnoi, V., see Lisiansky, M. 197 (1999) 630
Körfer, H., see Taudt, W. 191 (1998) 663
Korin, E., see Bronfenbrener, L. 198/199 (1999) 89
Korkishko, Yu.N., see Fedorov, V.A. 194 (1998) 94
Korostelin, Yu.V., V.I. Kozlovsky, A.S. Nasibov and P.V. Shapkin, Vapour growth and doping of ZnSe single crystals 197 (1999) 449
Korovyanko, O., see Fochuk, P. 197 (1999) 603
Korsukova, M.M., see Otani, S. 194 (1998) 430
Korzun, B.V., V.A. Virchenko and V.N. Yakimovich, ^{57}Fe and ^{119}Sn Mössbauer spectroscopy of the $CuAlS_2$ chalcopyrite semiconductor 198/199 (1999) 821
Koshiji, M., see Kawasaki, M. 198/199 (1999) 449
Koss, M.B., see LaCombe, J.C. 194 (1998) 143
Koszelak, S., see McPherson, A. 196 (1999) 572
Kotani, T., see Fujiwara, S. 192 (1998) 328
Kotani, T., see Fujiwara, S. 196 (1999) 83
Kotlyarchuk, B., see Zaginey, A. 194 (1998) 317
Kou, S., see Lin, M.H. 193 (1998) 443
Koui, T., Y. Sakata, Y. Sasaki, T. Matsumoto and K. Komatsu, Mass-transport effect on InP corrugation shape control of DFB-LDs under atmospheric pressure MOVPE 195 (1998) 503
Koukitu, A., T. Taki, N. Takahashi and H. Seki, Thermodynamic study on the role of hydrogen during the MOVPE growth of group III nitrides 197 (1999) 99
Koukitu, A., T. Taki, K. Narita and H. Seki, In situ monitoring of arsenic desorption on GaAs (1 1 1)B surface in atomic layer epitaxy 198/199 (1999) 1111
Koumetz, S., see Ketata, M. 194 (1998) 297
Koumoto, K., see Lin, H. 192 (1998) 250
Kousai, S., A. Yamashiki, T. Ogura and T. Nishinaga, Real-time observations of mesa shrinkage process in MBE of GaAs on (1 1 1)B patterned substrates and theoretical analysis 198/199 (1999) 1119

Koutsoukos, P.G., see Spanos, N. 191 (1998) 783
Koutsoukos, P.G., see Klepetsanis, P.G. 193 (1998) 156
Kováč, J., see Kečkéš, J. 192 (1998) 84
Kovala-Demertzi, D., see Domopoulou, A. 191 (1998) 166
Kovalenko, S.I., D.D. Solnyshkin, E.A. Bondarenko, E.T. Verkhovtseva and V.V. Eremenko, Electron diffraction study on the rise of crystal phase in rare-gas and nitrogen clusters 191 (1998) 553
Kowalczyk, L., see Mycielski, A. 197 (1999) 423
Koyama, F., see Honda, T. 195 (1998) 319
Koyama, F., see Miyamoto, T. 195 (1998) 421
Koyama, F., see Ohnoki, N. 195 (1998) 603
Koyama, F., see Schlenker, D. 196 (1999) 67
Koyama, F., see Miyamoto, T. 197 (1999) 67
Koyama, T., see Iida, S. 200 (1999) 368
Koyava, V.T., see Barilo, S.N. 198/199 (1999) 716
Kožíšek, Z. and P. Demo, Transient nucleation of ethanol–hexanol vapour 194 (1998) 239
Kozlovsky, V.I., see Korostelin, Yu.V. 197 (1999) 449
Kozodoy, P., S. Keller, S.P. DenBaars and U.K. Mishra, MOVPE growth and characterization of Mg-doped GaN 195 (1998) 265
Kramer, H.J.M., see Neumann, A.M. 198/199 (1999) 723
Kramer, H.J.M., S.K. Bermingham and G.M. van Rosmalen, Design of industrial crystallisers for a given product quality 198/199 (1999) 729
Krapukhin, V.V., see Senchenkov, A.S. 197 (1999) 552
Krasnov, A.N., R.C. Bajcar and P.G. Hofstra, Threshold voltage trends in ZnS : Mn-based alternating-current thin-film electroluminescent devices: role of native defects 194 (1998) 53
Kräußlich, J., see Schenk, H.P.D. 200 (1999) 45
Kravchenko, T.A., see Drebushchak, V.A. 193 (1998) 728
Krejci, M., see Furlong, M.J. 193 (1998) 114
Krempl, P.W., see Wallnöfer, W. 198/199 (1999) 487
Kretzer, U., see Flade, T. 198/199 (1999) 336
Kretzer, U., see Gärtner, G. 198/199 (1999) 355
Kreutzer, P., see Franke, T. 193 (1998) 451
Krishnamurthy, D., see Kumaragurubaran, S. 197 (1999) 210
Krispel, F., see Wallnöfer, W. 198/199 (1999) 487
Kröner, P., H. Baumeister, J. Rieger, E. Veuhoff, M. Popp and H. Heinecke, Optimization of p-dopant profiles for GaInAsP MQW laser structures in MOMBE 195 (1998) 660
Krost, A., see Heinrichsdorff, F. 195 (1998) 540
Krupanidhi, S.B., see Modak, P. 193 (1998) 501
Krylyuk, S.G., see Korbutyak, D.V. 197 (1999) 659
Krymov, V.M., V.N. Kurlov, P.I. Antonov, F. Theodore and J. Delepine, Temperature distribution near the interface in sapphire crystals grown by EFG and GES methods 198/199 (1999) 210
Kubalek, E., see Liu, Q. 197 (1999) 507
Kubilius, V., see Abrutis, A. 191 (1998) 79
Kubínek, R., J. Hozman and J. Vařenka, Dendritic growth in viscous solutions containing organic molecules 193 (1998) 174
Kubler, L., see Dentel, D. 191 (1998) 697
Kubota, E., M. Shimokozono and Y. Katoh, LPE growth of yttrium–lutetium, indium–gallium garnet films for optical waveguide formation on a GGG substrate 191 (1998) 501
Kubota, N., K.-i. Katagiri, M. Yokota, A. Sato, H. Yashiro and K. Itai, Impurity effect of iron(III) on the growth of potassium sulfate crystal in aqueous solution 196 (1999) 156
Kubota, N., Y. Fujisawa, M. Yokota and J.W. Mullin, Pseudo-solubilities of potassium sulfate in water in the presence of crystal-growth and -dissolution suppressor iron(III) impurities 197 (1999) 388
Kubota, T., see Sakurazawa, S. 196 (1999) 325
Kudin, A.M., see Zaslavsky, B.G. 198/199 (1999) 856
Kudriavtsev, Yu.A., see Orton, J.W. 197 (1999) 7
Kuech, T.F., see Cederberg, J.G. 195 (1998) 63
Kuech, T.F., see Cederberg, J.G. 195 (1998) 105
Kuech, T.F., see Hansen, D.M. 195 (1998) 144
Kuech, T.F., see Li, J. 195 (1998) 617
Kuech, T.F., see Sun, J. 195 (1998) 711
Kuleshov, N.V., see Levchenko, V.I. 198/199 (1999) 980
Kuma, S., see Shibata, M. 196 (1999) 47
Kumagai, H., see Xu, X.W. 198/199 (1999) 536
Kumagawa, M., see Aswal, D.K. 193 (1998) 61
Kumagawa, M., see Aswal, D.K. 197 (1999) 379
Kumagawa, M., see Iida, S. 200 (1999) 368
Kumagawa, M., see Aswal, D.K. 200 (1999) 427
Kumar, J., see Jeganathan, K. 200 (1999) 341
Kumaragurubaran, S., D. Krishnamurthy, C. Subramanian and P. Ramasamy, Investigations on the growth of Bi_2TeO_5 and TeO_2 crystals 197 (1999) 210
Kumaresan, R., S. Moorthy Babu and P. Ramasamy, Investigations on electrochemical growth and properties of mercury cadmium telluride semiconductor thin films for device fabrication 198/199 (1999) 1165
Kunst, M., see Weiss, T. 198/199 (1999) 1190

Künzel, H., S. Ebert, R. Gibis, R. Kaiser, H. Kizuki, S. Malchow and G. Urmann, Selective MOMBE growth of InP-based waveguide/laser butt-joints 192 (1998) 56
Kunzer, M., see Obloh, H. 195 (1998) 270
Kuphal, E., see Jochum, S. 195 (1998) 637
Kuramochi, E., see Temmyo, J. 195 (1998) 516
Kuranova, I.P., E.V. Blagova, V.M. Levdikov, G.N. Rudenskaya, N.P. Balaban and E.V. Shakirov, Crystal growth and preliminary X-ray study of glutamic acid specific serine protease from *Bacillus intermedius* 196 (1999) 313
Kuribayashi, K., see Inatomi, Y. 198/199 (1999) 176
Kuribayashi, K., see Nagashio, K. 200 (1999) 118
Kurihara, K., S. Miyashita, G. Sazaki, T. Nakada, S. Durbin, H. Komatsu, T. Ohba and K. Ohki, Incorporation of impurity to a tetragonal lysozyme crystal 196 (1999) 285
Kuriyama, K., R. Taguchi, K. Kushida and K. Ushiyama, Growth and band gap of the filled tetrahedral semiconductor LiZnN 198/199 (1999) 802
Kurlov, V.N., S.N. Rossolenko and S.V. Belenko, Growth of sapphire core-doped fibers 191 (1998) 520
Kurlov, V.N. and S.V. Belenko, Growth of sapphire shaped crystals with continuously modulated dopants 191 (1998) 779
Kurlov, V.N., see Krymov, V.M. 198/199 (1999) 210
Kurlov, V.N., see Gurjiyants, P.A. 198/199 (1999) 227
Kurnevich, L.A., see Leonyuk, N.I. 191 (1998) 135
Kurnevich, L.A., see Koporulina, E.V. 198/199 (1999) 460
Kurnevich, L.A., see Zhigunov, D.I. 198/199 (1999) 605
Kurnevich, L.A., see Barilo, S.N. 198/199 (1999) 716
Kurobe, A., see Sugiyama, N. 192 (1998) 395
Kurochkin, L.A., see Zhigunov, D.I. 198/199 (1999) 605
Kurochkin, L.A., see Shiryaev, S.V. 198/199 (1999) 631
Kuroda, Y., see Miyazaki, N. 196 (1999) 62
Kurpas, P., see Zettler, J.-T. 195 (1998) 151
Kurpas, P., M. Arens, D. Gutsche, E. Richter and M. Weyers, Growth monitoring of GaInP/GaAs heterojunction bipolar transistors by reflectance anisotropy spectroscopy 195 (1998) 217
Kurpas, P., see Zorn, M. 195 (1998) 223
Kurtz, S.R., see Biefeld, R.M. 195 (1998) 356
Kurtz, S.R., see Geisz, J.F. 195 (1998) 401
Kurtz, S.R., see Friedman, D.J. 195 (1998) 409
Kurtz, S.R., see Friedman, D.J. 195 (1998) 438
Kurtz, S.R., see Bertness, K.A. 196 (1999) 13
Kurumbail, R.G., see Stevens, A.M. 196 (1999) 350
Kurz, M., A. Pusztai and G. Müller, Development of a new powerful computer code CrysVUN++ especially designed for fast simulation of bulk crystal growth processes 198/199 (1999) 101
Kurz, M., see Böttcher, K. 198/199 (1999) 349
Kusakabe, K., see Saito, T. 191 (1998) 723
Kushida, K., see Kuriyama, K. 198/199 (1999) 802
Kutas, A.A., see Yakimovich, V.N. 198/199 (1999) 975
Kutcher, S.W., see Burger, A. 198/199 (1999) 872
Kuwabara, K., see Lin, H. 192 (1998) 250
Kuwamoto, K., see Irie, S. 198/199 (1999) 939
Kuwano, J., see Kayama, M. 193 (1998) 648
Kuznetsov, V.A., T.M. Okhrimenko and M. Rak, Growth promoting effect of organic impurities on growth kinetics of KAP and KDP crystals 193 (1998) 164
Kuznetsov, Yu.G., see Malkin, A.J. 196 (1999) 471
Kuznetsov, Yu.G., A.J. Malkin and A. McPherson, AFM studies of the nucleation and growth mechanisms of macromolecular crystals 196 (1999) 489
Kuznetsov, Yu.G., see McPherson, A. 196 (1999) 572
Kuznicki, Z., see Ciach, R. 197 (1999) 675
Kwon, M.S. and J.Y. Lee, Formation of CuPt-type ordered (Cd, Zn)Te at CdTe/ZnTe interface 191 (1998) 51
Kwon, S.K., D.H. Kim and J.T. Baek, Silicon epitaxial film growth on silicon substrate exposed to UV-excited NF_3/H_2 gas for native oxide removal 198/199 (1999) 1039
Kwon, Y.-S., see Leem, J.-Y. 193 (1998) 491

Lacey, G., see Mizuno, K. 198/199 (1999) 1146
Lachab, M., see Wang, J. 200 (1999) 85
LaCombe, J.C., M.B. Koss, L.A. Tennenhouse, E.A. Winsa and M.E. Glicksman, The Clapeyron effect in succinonitrile: applications to crystal growth 194 (1998) 143
Ladeinde, F., see Zhang, T. 198/199 (1999) 141
Ladner, C., see Décobert, J. 195 (1998) 681
Lai, Y.-J., J.-C. Chen and K.-C. Liao, Investigations of ferroelectric domain structures in the MgO:$LiNbO_3$ fibers by LHPG 198/199 (1999) 531
Laire, O., see Breton, G. 200 (1999) 112
Lakatos, B.G., see Liszi, I. 198/199 (1999) 1330
Lakeenkov, V.M., V.B. Ufimtsev, N.I. Shmatov and Yu.F. Schelkin, Numeric simulation of vertical Bridgman growth of $Cd_{1-x}Zn_xTe$ melts 197 (1999) 443
Lakin, E., see Mainzer, N. 197 (1999) 542
Lakner, H., see Taudt, W. 191 (1998) 663
Lakner, H., see Liu, Q. 197 (1999) 507
Lakshmanan, S.K., see Naik, M.B. 193 (1998) 133

Lal, K., see Murthy, R.V.A. 197 (1999) 865
Lam, W.W., see Wang, H.P. 200 (1999) 137
Lambert, O., see Brisson, A. 196 (1999) 456
Lan, C.W., S. Uda and T. Fukuda, Theoretical analysis of the micro-pulling-down process for Ge_xSi_{1-x} fiber crystal growth 193 (1998) 552
Lan, C.W., Effects of ampoule rotation on flows and dopant segregation in vertical Bridgman crystal growth 197 (1999) 983
Lancefield, D., see di Forte-Poisson, M.A. 195 (1998) 314
Landgren, G., see Silfvenius, C. 195 (1998) 700
Landgren, G., see Keiper, D. 197 (1999) 25
Lane, D.W., G.J. Conibeer, D.A. Wood, K.D. Rogers, P. Capper, S. Romani and S. Hearne, Sulphur diffusion in CdTe and the phase diagram of the CdS–CdTe pseudo-binary alloy 197 (1999) 743
Lane, P.A., P.J. Wright, M.J. Crosbie, A.D. Pitt, C.L. Reeves, B. Cockayne, A.C. Jones and T.J. Leedham, Liquid injection metal organic chemical vapour deposition of nickel zinc ferrite thin films 192 (1998) 423
Lang, A.R., A.P.W. Makepeace, W.B. Alexander, T. McCormick, P.E. Pehrsson and J.E. Butler, Optical microscopic, synchrotron X-ray topographic and reticulographic study of homoepitaxial CVD diamond 200 (1999) 446
Langouche, G., see Jin, S. 194 (1998) 189
Langsdorf, A. and W. Assmus, Growth of large single grains of the icosahedral quasicrystal ZnMgY 192 (1998) 152
Lantie, R., see Gerthsen, D. 200 (1999) 353
LaPierre, R.R., B.J. Robinson and D.A. Thompson, Growth mechanisms of III–V compounds by atomic hydrogen-assisted epitaxy 191 (1998) 319
Larkin, J., see Chen, Q.S. 198/199 (1999) 710
Larsen, P.K., see Bauhuis, G.J. 191 (1998) 313
Larsen, P.K., see de Theije, F.K. 197 (1999) 37
Larson Jr., D.J., see Zheng, L.L. 191 (1998) 243
Lasbley, A., see Munoz, V. 196 (1999) 71
Lascaray, J-P., see Siviniant, J. 197 (1999) 680
Lauck, R. and E. Schönherr, Isotopically pure ZnSe crystals grown from the vapor 197 (1999) 513
Laudise, R.A., see Kloc, Ch. 193 (1998) 563
Laudise, R.A., see Gelabert, M.C. 197 (1999) 195
Lauer, S., see Cröll, A. 191 (1998) 365
Lauer, St., see Ostheimer, V. 198/199 (1999) 1184
Laugier, A., see Dour, G. 193 (1998) 230
Launey, J.C., see Brisson, O. 193 (1998) 597
Launay, J.C., see von Bardeleben, H.J. 197 (1999) 718
Law, D., see Li, L. 195 (1998) 28
Lawson, G., see McPherson, A. 196 (1999) 572
Laxmanan, V., The limiting behavior of the gradient function for an isolated paraboloid growing in a positive temperature gradient 191 (1998) 298
Le Bellego, Y., see Sik, H. 195 (1998) 479
Le Gal, H., see Barvinschi, F. 198/199 (1999) 239
Le Marec, C., see Guérin, R. 194 (1998) 247
Le Mestreallan, G., see Sik, H. 195 (1998) 479
Le Roux, G., see Sagnes, I. 195 (1998) 524
Le Verge, A., see Tardieu, A. 196 (1999) 193
Lebbou, K., see Sangaletti, L. 198/199 (1999) 454
Lebedev, A.O., see Bakin, A.S. 198/199 (1999) 1015
Lebedev, V.B., see Cheng, T.S. 197 (1999) 12
Lee, C.-R., see Lee, H.J. 191 (1998) 621
Lee, C.-R., J.-Y. Leem, S.-K. Noh, S.-E. Park, J.-I. Lee, C.-S. Kim, S.-J. Son and K.-Y. Leem, Characteristics of Mg-doped GaN epilayers grown with the variation of Mg incorporation 193 (1998) 300
Lee, C.-R., see Leem, J.-Y. 193 (1998) 491
Lee, C.-R., J.-Y. Leem, S.K. Noh, S.-J. Son and K.-Y. Leem, Doping behavior of $In_{0.1}Ga_{0.9}$ codoped with Si and Zn 197 (1999) 78
Lee, C.-R., see Leem, J.-Y. 197 (1999) 84
Lee, C.S., see Zhang, Y.F. 197 (1999) 136
Lee, C.-Y., M.-C. Wu and W. Lin, The influence of window layers on the performance of 650 nm AlGaInP/GaInP multi-quantum-well light-emitting diodes 200 (1999) 382
Lee, D.U., see Kim, T.W. 193 (1998) 496
Lee, H., T.S. Kim, T.S. Jeong, H.G. An, J.Y. Kim, C.J. Youn, P.Y. Yu, K.J. Hong, H.J. Lee and Y.J. Shin, Growth of zinc selenide single crystal by the modified Piper and Polich sublimation method 191 (1998) 59
Lee, H.J., see Lee, H. 191 (1998) 59
Lee, H.J., H. Ryu, C.-R. Lee and K. Kim, Polytypes in GaN films grown by metalorganic chemical vapor deposition on (0 0 0 1) sapphire substrate 191 (1998) 621
Lee, J.-I., see Lee, C.-R. 193 (1998) 300
Lee, J.-I., see Leem, J.-Y. 193 (1998) 491
Lee, J.-M., see Paek, J.-S. 200 (1999) 55
Lee, J.-S., M. Sugisaki, H.-W. Ren, S. Sugou and Y. Masumoto, Spontaneous lateral alignment of multi-stacked $In_{0.45}Ga_{0.55}As$ quantum dots on GaAs(3 1 1)B substrate 200 (1999) 77

Lee, J.Y., see Kwon, M.S. 191 (1998) 51
Lee, J.Y., see Kim, Y.K. 192 (1998) 109
Lee, J.Y., see Kim, T.W. 197 (1999) 799
Lee, J.Y., see Lim, Y.S. 200 (1999) 421
Lee, K.-S., see Nam, S. 194 (1998) 61
Lee, K.-Y., see Lee, S.-C. 200 (1999) 305
Lee, M., R.S. Feigelson and R.K. Route, Growth of lead barium niobate ($Pb_{1-x}Ba_xNb_2O_6$) crystals by the vertical Bridgman method. I. Self-seeded growth 193 (1998) 347
Lee, M. and R.S. Feigelson, Growth of lead barium niobate ($Pb_{1-x}Ba_xNb_2O_6$) crystals by the vertical Bridgman method. II. $Sr_{0.61}Ba_{0.39}Nb_2O_6$ seeded growth 193 (1998) 355
Lee, M.-y. and G.M. Parkinson, Growth rates of gibbsite single crystals determined using in situ optical microscopy 198/199 (1999) 270
Lee, R.T., see Liu, Z. 191 (1998) 1
Lee, S.-C., C.-C. Hwang, J.-Y. Hsieh and K.-Y. Lee, Morphological instabilities in rapid directional solidifications under local noneqilibrium conditions 200 (1999) 305
Lee, S.H., C. Fetzer and G.B. Stringfellow, Effect of Te doping on step structure and ordering in GaInP 195 (1998) 13
Lee, S.T., see Zhang, Y.F. 197 (1999) 136
Lee, Y.J., see Kim, S.T. 194 (1998) 37
Lee, Y.K. and S.J. Chung, Hydrothermal growth of calcite single crystal in NH_4Cl solution 192 (1998) 350
Lee, Y.K. and S.J. Chung, The dependence of cobalt concentration on the growth temperature in synthetic blue quartz 196 (1999) 151
Lee, Y.-S. and C.-H. Chun, Transition from regular to irregular thermal wave by coupling of natural convection with rotating flow in Czochralski crystal growth 197 (1999) 297
Lee, Y.-S. and C.-H. Chun, Effects of a cusp magnetic field on the oscillatory convection coupled with crucible rotation in Czochralski crystal growth 197 (1999) 307
Lee, Y.-S. and C.-H. Chun, Experiments on the oscillatory convection of low Prandtl number liquid in Czochralski crystal growth under an axial magnetic field 198/199 (1999) 147
Leedham, T.J., see Lane, P.A. 192 (1998) 423
Leem, J.-Y., see Lee, C.-R. 193 (1998) 300
Leem, J.-Y., C.-R. Lee, J.-I. Lee, S.K. Noh, Y.-S. Kwon, Y.-H. Ryu and S.-J. Son, Characteristics of Si-doped GaN compensated with Mg 193 (1998) 491
Leem, J.-Y., see Lee, C.-R. 197 (1999) 78
Leem, J.-Y., C.-R. Lee, S.K. Noh and J.-S. Son, RHEED oscillation studies of pseudomorphic InGaAs strained layers on GaAs substrate 197 (1999) 84
Leem, K.-Y., see Lee, C.-R. 193 (1998) 300
Leem, K.-Y., see Lee, C.-R. 197 (1999) 78
Legrand, B., see Roussel, J.-M. 198/199 (1999) 83
Lehmann, J., see Rocabois, P. 198/199 (1999) 838
Lehn, J.-M., see Sauter, C. 196 (1999) 365
Lehoczky, S.L., see Su, C.-H. 192 (1998) 386
Lehoczky, S.L., see Price, M.W. 198/199 (1999) 297
Lehoczky, S.L., see Price, M.W. 198/199 (1999) 303
Leifer, K., see Biasiol, G. 195 (1998) 596
Lelarge, F., see Biasiol, G. 195 (1998) 596
Lemaître, A., see Sagnes, I. 195 (1998) 524
Lemasson, P., A. Rivière, G. Didier, A. Tromson-Carli and R. Triboulet, Low resistive ZnSe substrates 197 (1999) 462
Lemasson, P., see Rzepka, E. 197 (1999) 480
Lemasson, P., see Triboulet, R. 198/199 (1999) 968
Lemay, S.G., see Dobrianov, I. 196 (1999) 511
Lenhoff, A.M., see Neal, B.L. 196 (1999) 377
Leonyuk, L., see Shvanskaya, L. 198/199 (1999) 600
Leonyuk, L., G.-J. Babonas, V. Maltsev, A. Vetkin, V. Rybakov and A. Reza, Structural features and anomalies in the temperature dependence of resistance in superconducting Bi-2212 single crystals 198/199 (1999) 619
Leonyuk, L., see Maltsev, V. 198/199 (1999) 626
Leonyuk, N.I., E.V. Koporulina, S.N. Barilo, L.A. Kurnevich and G.L. Bychkov, Crystal growth of solid solutions based on the $YAl_3(BO_3)_4$, $NdAl_3(BO_3)_4$ and $GdAl_3(BO_3)_4$ borates 191 (1998) 135
Leonyuk, N.I., see Koporulina, E.V. 191 (1998) 767
Leonyuk, N.I., see Koporulina, E.V. 198/199 (1999) 460
Leonyuk, N.I., see Barilo, S.N. 198/199 (1999) 716
Lereah, Y. and I. Zarudi, The kinetics of Ge branches growth in Al : Ge crystallization 198/199 (1999) 62
Leroux, S., J.Le Ny, C. Guéneau, J. Granier, B. Drevet and D. Camel, Condensation and flowing of silver–copper alloys in a solid–liquid domain of the phase diagram 198/199 (1999) 911
Leszczyński, M., see Prystawko, P. 198/199 (1999) 1061
Leu, S., H. Protzmann, F. Höhnsdorf, W. Stolz, J. Steinkirchner and E. Hufgard, Si-doping of MOVPE grown InP and GaAs by using the liquid Si source ditertiarybutyl silane 195 (1998) 91

Leu, S., F. Höhnsdorf, W. Stolz, R. Becker, A. Salzmann and A. Greiling, C- and O-incorporation in (AlGa)As epitaxial layers grown by MOVPE using TBAs 195 (1998) 98
Leu, S., see Ellmers, C. 195 (1998) 630
Levade, C. and G. Vanderschaeve, Electron-irradiation enhanced dislocation glide in II–VI semiconductors 197 (1999) 565
Levchenko, V.I., see Yakimovich, V.N. 198/199 (1999) 975
Levchenko, V.I., V.N. Yakimovich, L.I. Postnova, V.I. Konstantinov, V.P. Mikhailov and N.V. Kuleshov, Preparation and properties of bulk ZnSe : Cr single crystals 198/199 (1999) 980
Levdikov, V.M., see Kuranova, I.P. 196 (1999) 313
Lévy, F., see Regula, M. 193 (1998) 109
Levy, M., N. Amir, E. Khanin, Y. Nemirovsky and R. Beserman, Characterization of CdTe substrates and MOCVD $Cd_{1-x}Zn_xTe$ epilayers 197 (1999) 626
Leys, M.R., see Verschuren, C.A. 200 (1999) 19
Li, A.Z., see Yang, Q.K. 192 (1998) 28
Li, A.Z., see Chen, J.X. 193 (1998) 28
Li, A.Z., see Yang, Q.K. 194 (1998) 31
Li, C.C., see Chen, J.X. 193 (1998) 28
Li, G., K.E. Prince, M. Petravic, S.J. Chua and C. Jagadish, Substrate orientation effect on Zn δ-doping in GaAs grown by metal organic vapour-phase epitaxy 191 (1998) 357
Li, G., M.B. Johnston, A. Babinski, S. Yuan, M. Gal, S.J. Chua and C. Jagadish, Si and C δ-doping for device applications 195 (1998) 54
Li, H.X., see Gong, Q. 192 (1998) 376
Li, H.X., see Wu, J. 197 (1999) 95
Li, H.X., T. Daniels-Race and Z. Wang, Structural and optical characterization of InAs nanostructures grown on high-index InP substrates 200 (1999) 321
Li, H.X., see Zhuang, Q.D. 200 (1999) 375
Li, J., A. Mirabedini, L.J. Mawst, D.E. Savage, R.J. Matyi and T.F. Kuech, Effect of interface roughness on performance of AlGaAs/InGaAs/GaAs resonant tunneling diodes 195 (1998) 617
Li, J.-B., see Xu, G.-Y. 200 (1999) 143
Li, J.F., Y.C. Liu, Y.L. Lu, G.C. Yang and Y.H. Zhou, Structural evolution of undercooled Ni–Cu alloys 192 (1998) 462
Li, J.-M., see Zhang, J.-P. 192 (1998) 471
Li, J.-M., see Zhang, J.-P. 197 (1999) 368
Li, J.M., see Zhuang, Q.D. 200 (1999) 375
Li, J.P., see Liu, J.P. 193 (1998) 535
Li, J.P., see Liu, J.P. 194 (1998) 426
Li, J.P., see Liu, J.P. 200 (1999) 613
Li, J.P., see Liu, J.P. 200 (1999) 617
Li, J.-S. and K. Nishioka, Generalized kinetic potential and mechanism of the ridge crossing in binary nucleation 198/199 (1999) 27
Li, L., see Hong, X. 193 (1998) 610
Li, L., B.-K. Han, D. Law, M. Begarney and R.F. Hicks, Gallium arsenide and indium arsenide surfaces produced by metalorganic vapor-phase epitaxy 195 (1998) 28
Li, L., see Xu, X.W. 198/199 (1999) 536
Li, S., see Ning, Y. 191 (1998) 39
Li, T., see Feng, J. 197 (1999) 393
Li, W.Z., see Luo, Z.S. 197 (1999) 939
Li, X., D. Sun, J. Zhang and M. Kong, GaN epilayers grown at high growth rate using gas source molecular beam epitaxy method 191 (1998) 31
Li, X., D. Sun, J. Zhang, S. Zhu and M. Kong, Properties of GaN epilayers with various growth conditions grown by gas source molecular beam epitaxy 191 (1998) 34
Li, X.-B., see Zhang, J.-P. 192 (1998) 93
Li, X.-B., see Zhang, J.-P. 192 (1998) 471
Li, Y., see Wu, G. 192 (1998) 417
Li, Y., see Ma, D. 194 (1998) 398
Li, Y., see Tran, C.A. 195 (1998) 397
Li, Y., see Liu, C. 196 (1999) 111
Li, Y.-P., see Fu, Y.-J. 198/199 (1999) 682
Li, Y.X., Y.L. Ju, H.M. Wang, P.J. Niu, C.C. Tang, J. Du, and G.H. Wu The effect of orientation deviation on pattern distortion in epitaxial buried layer on p-type $\langle 1\,0\,0 \rangle$ silicon substrate 191 (1998) 282
Li Zhengdong, see Yang Shangfeng 197 (1999) 383
Liang, J., see Dinger, A. 200 (1999) 391
Liang, J.B., see Gong, Q. 192 (1998) 376
Liao, G., see Fu, Z. 193 (1998) 316
Liao, K.-C., see Lai, Y.-J. 198/199 (1999) 531
Lifante, G., see Fedorov, V.A. 194 (1998) 94
Lifshitz, E., M. Sirota and H. Porteanu, Continuous and time-resolved photoluminescence study of lead sulfide nanocrystals, embedded in polymer film 196 (1999) 126
Lifshitz, E., see Litvin, I.D. 198/199 (1999) 313
Liliental-Weber, Z., see Dupuis, R.D. 195 (1998) 340
Lim, D.H., see Joo, H.-B. 194 (1998) 161
Lim, K., see Carter, D.C. 196 (1999) 623
Lim, K.Y., see Joo, H.-B. 194 (1998) 161
Lim, M.H., see Koontz, E.M. 198/199 (1999) 1104

Lim, P.H., see Schineller, B. 195 (1998) 274
Lim, Y.S., J.Y. Lee and T.W. Kim, The strain relaxation in a lattice-mismatched heterostructure 200 (1999) 421
Lima, A.P., T. Frey, U. Köhler, C. Wang, D.J. As, B. Schöttker, K. Lischka and D. Schikora, Surface irregularities of MBE grown cubic GaN layers 197 (1999) 31
Lin, B., see Fu, Z. 193 (1998) 316
Lin, C., see Chen, J.X. 193 (1998) 28
Lin, C., see Zeng, J. 197 (1999) 874
Lin, C.H., N. Gabas, J.P. Canselier and G. Pèpe, Prediction of the growth morphology of aminoacid crystals in solution. I. α-Glycine 191 (1998) 791
Lin, C.H., N. Gabas and J.P. Canselier, Prediction of the growth morphology of aminoacid crystals in solution. II. γ-Aminobutyric acid 191 (1998) 803
Lin, C.-H., see Lu, S.-Y. 200 (1999) 527
Lin, E.-K., see Chang, L.-B. 198/199 (1999) 1092
Lin, H., H. Sakamoto, W.S. Seo, K. Kuwabara and K. Koumoto, Crystal growth of lepidocrocite and magnetite under Langmuir monolayers 192 (1998) 250
Lin, H., see Vekilov, P.G. 196 (1999) 261
Lin, H.-C., see Lu, S.-Y. 200 (1999) 527
Lin, H.-H., see Liu, J.-S. 192 (1998) 372
Lin, L., X. Zhong and N. Chen, Improvement of stoichiometry in semi-insulating gallium arsenide grown under microgravity 191 (1998) 586
Lin, L., see Liu, X. 193 (1998) 23
Lin, L.-Y., see Zhang, J.-P. 192 (1998) 471
Lin, L.-Y., see Zhang, J.-P. 197 (1999) 368
Lin, L.Y., see Zhuang, Q.D. 200 (1999) 375
Lin, M.H. and S. Kou, Czochralski pulling of InSb single crystals from a molten zone on a solid feed 193 (1998) 443
Lin, S.-X., see Zhu, D.-W. 196 (1999) 356
Lin, W., see Lee, C.-Y. 200 (1999) 382
Lin, X., see Feng, J. 197 (1999) 393
Lin, Y., see Fan, S. 198/199 (1999) 542
Lincot, D., see Furlong, M.J. 193 (1998) 114
Linker, G., see Brecht, E. 191 (1998) 421
Lipenkov, V.Y., see Salamatin, A.N. 193 (1998) 197
Lipovskii, A.A., see Litvin, I.D. 198/199 (1999) 313
Lipson, S.G., see Notcovich, A.G. 198/199 (1999) 10
Lipson, S.G., see Braslavsky, I. 198/199 (1999) 56
Lisauskas, V., see Kleptsyn, V. 196 (1999) 122
Lischka, K., see Lima, A.P. 197 (1999) 31
Lisetskaya, E., see Ryzhikov, V. 197 (1999) 655
Lisiansky, M., V. Korchnoi, A. Berner, E. Muranevich and R. Weil, Improvement of CdTe substrate quality by acoustic treatment 197 (1999) 630
Liszi, I., M. Hasznosné-Nezdei, B.G. Lakatos, Ts.J. Sapundzhiev and R.G. Popov, Determination of the crystal growth mechanism of KCl in ethanol–water system 198/199 (1999) 1330
Litvin, I.D., H. Porteanu, E. Lifshitz and A.A. Lipovskii, Optically detected magnetic resonance studies of CdS nanoparticles grown in phosphate glass 198/199 (1999) 313
Liu, C., H. Wang, Y. Li, Q. Wang, B. Ren, Y. Xu and D. Que, Study on the oxygen concentration reduction in heavily Sb-doped silicon 196 (1999) 111
Liu, F.Q., see Gong, Q. 192 (1998) 376
Liu, F.-Q., Z.-G. Wang, J. Wu, B. Xu, W. Zhou and J.-J. Qian, Size quantization effects in InAs self-assembled islands on InP(0 0 1) at the onset of 2D-to-3D transition 197 (1999) 789
Liu, F.Q., see Zhou, W. 200 (1999) 608
Liu, H., see Jia, W. 200 (1999) 179
Liu Hongbin, see Song Youting 194 (1998) 379
Liu, J. and R. Elliott, Numerical modelling of the solidification of ductile iron 191 (1998) 261
Liu, J.-M., see Fu, Y.-J. 198/199 (1999) 682
Liu, J.-S., J.-S. Wang and H.-H. Lin, Very thin layers of TlP grown on InP using gas source molecular beam epitaxy 192 (1998) 372
Liu, J.L., S.J. Cai, G.L. Jin, S.G. Thomas and K.L. Wang, Growth of Si whiskers on Au/Si(1 1 1) substrate by gas source molecular beam epitaxy (MBE) 200 (1999) 106
Liu, J.P., M.Y. Kong, J.P. Li, X.F. Liu, D.D. Huang and D.Z. Sun, Low-temperature growth properties of $Si_{1-x}Ge_x$ by disilane and solid-Ge molecular beam epitaxy 193 (1998) 535
Liu, J.P., M.Y. Kong, D.D. Huang, J.P. Li and D.Z. Sun, Structural characterization of SiGe/Si single wells grown by disilane and solid-Ge molecular beam epitaxy with varied disilane cracking temperature 194 (1998) 426
Liu, J.P., D.D. Huang, J.P. Li, D.Z. Sun and M.Y. Kong, High phosphorous doping and morphological evolution during Si growth by gas source molecular beam epitaxy (GSMBE) 200 (1999) 613
Liu, J.P., Q. Gong, D.D. Huang, J.P. Li, D.Z. Sun and M.Y. Kong, Evolution of height distribution of Ge islands on Si(1 0 0) 200 (1999) 617
Liu, L.-T., see Chen, J.-C. 198/199 (1999) 476

Liu, N., see Shi, W. 197 (1999) 905
Liu, N.-n., see Wang, R.-p. 200 (1999) 505
Liu, Q., see Taudt, W. 191 (1998) 663
Liu, Q., H. Lakner, W. Taudt, M. Heuken, C. Mendorf, K. Heime and E. Kubalek, Structural properties of MOVPE-grown ZnSe studied by X-ray diffractometry, atomic force microscopy and electron microscopy 197 (1999) 507
Liu, S., see Ma, D. 194 (1998) 398
Liu, X., D.-C. Lu, L. Wang, X. Wang, D. Wang and L. Lin, The dependence of growth rate of GaN buffer layer on growth parameters by metalorganic vapor-phase epitaxy 193 (1998) 23
Liu, X., see Wang, L. 193 (1998) 484
Liu, X., see Zhang, H. 200 (1999) 335
Liu, X.F., see Liu, J.P. 193 (1998) 535
Liu, X.Y., Principles for predicting the morphology of crystals and application to n-paraffin crystals 198/199 (1999) 1281
Liu, Y., see Lu, T. 193 (1998) 577
Liu, Y., see Guan, Q. 197 (1999) 1012
Liu, Y.C., see Li, J.F. 192 (1998) 462
Liu, Z., R.T. Lee and G.B. Stringfellow, Pyrolysis of tertiarybutylamine alone and with trimethylgallium for GaN growth 191 (1998) 1
Liu, Z., see Jin, W. 191 (1998) 760
Liu, Z., see Shimamura, K. 197 (1999) 896
Loduca, J.Y., see Stevens, A.M. 196 (1999) 350
Logofătu, C., see Dinculescu, I. 198/199 (1999) 999
Longo, M., see Passaseo, A. 197 (1999) 777
López, C., see Yates, H.M. 193 (1998) 9
López, C.R., J. R. Mileham and R. Abbaschian, Microgravity growth of GaSb single crystals by the liquid encapsulated melt zone (LEMZ) technique 200 (1999) 1
López-López, M., A. Guillén-Cervantes, Z. Rivera-Alvarez and I. Hernández-Calderón, Hillocks formation during the molecular beam epitaxial growth of ZnSe on GaAs substrates 193 (1998) 528
López-López, M., see Constantino, M.E. 194 (1998) 301
Lorber, B., see Sauter, C. 196 (1999) 365
Löser, W., see Behr, G. 198/199 (1999) 642
Lott, K. and T. Nirk, High temperature electrical conductivity in the phase transition region 197 (1999) 485
Lott, K., M. Raukas, A. Vishnjakov and A. Grebennik, High temperature electrical conductivity in the Cu solubility limit range in ZnS : Cu 197 (1999) 489
Lott, K. and L. Türn, A method for the calculation of defect equilibrium 197 (1999) 493
Louchet, F., see Gondet, S. 198/199 (1999) 129
Louchet, F., see Théodore, F. 198/199 (1999) 232
Louhi-Kultanen, M., see Sha, Z.L. 198/199 (1999) 692
Lowndes, D.H., see Park, J.-W. 193 (1998) 516
Lu, C.J., H.M. Shen and Y.N. Wang, The growth and phase transitions of epitaxial $Pb(Zr_{0.95}Ti_{0.05})O_3$ thin films prepared by sputter deposition combined with post-annealing on $SrTiO_3(1\,0\,0)$ 191 (1998) 113
Lu, D.-C., see Liu, X. 193 (1998) 23
Lu, D.-C., see Wang, L. 193 (1998) 484
Lu, D.-C., see Duan, S. 195 (1998) 304
Lu, H.-b., see Wang, R.-p. 200 (1999) 505
Lu, K., see Hong, X. 193 (1998) 610
Lu, K., see Hong, X. 200 (1999) 172
Lu, L., Y. Zhang, G. Yang, J. Wang and W. Ge, Threshold reduction in strained-layer InGaAs/GaAs quantum well lasers by liquid phase epitaxy regrowth 194 (1998) 25
Lu, L., see Jia, W. 200 (1999) 179
Lu, M., see Meng, X. 200 (1999) 199
Lu, S.-Y., H.-C. Lin and C.-H. Lin, Modeling particle growth and deposition in a tubular CVD reactor 200 (1999) 527
Lu, T., Y. Liu, J. Shigley, T. Moses and I.M. Reinitz, Characterization of a notable historic gem diamond showing the alexandrite effect 193 (1998) 577
Lu, Y.L., see Li, J.F. 192 (1998) 462
Lu, Y.M., see Yu, G. 196 (1999) 77
Lu, Z.D., see Wang, Z.M. 192 (1998) 97
Lubomirski, I., see Cahen, D. 197 (1999) 537
Lüdge, A., see Mühlbauer, A. 198/199 (1999) 107
Ludovice, P.J., see Givand, J.C. 194 (1998) 228
Ludwig, W., see Amon, J. 198/199 (1999) 367
Luft, J.R., D.M. Rak and G.T. DeTitta, Microbatch macromolecular crystallization on a thermal gradient 196 (1999) 447
Luft, J.R., D.M. Rak and G.T. DeTitta, Microbatch macromolecular crystallization in micropipettes 196 (1999) 450
Lui, P.Y., see Yoon, S.F. 197 (1999) 59
Łukasiewicz, T., see Sokólska, I. 198/199 (1999) 521
Lundager Madsen, H.E., see Suvorova, E.I. 198/199 (1999) 677
Luo, Z.S., F.Z. Cui and W.Z. Li, Abnormal refinement of grains in calcium phosphate films during a low temperature crystallization 197 (1999) 939
Łusakowska, E., see Mycielski, A. 197 (1999) 423
Lusson, A., see Thiandoume, C. 197 (1999) 805

Lüth, H., see Gerthsen, D. 200 (1999) 353
Lüth, H., see Butz, R. 200 (1999) 407
Luther, L.C., see Henderson, R. 194 (1998) 8
Lux-Steiner, M.C., see Birkholz, M. 197 (1999) 571
Lux-Steiner, M.C., see Weiss, T. 198/199 (1999) 1190
Luysberg, M., see Schmidt, R. 195 (1998) 124
Lyahovitskaya, V., L. Kaplan, J. Goswami and D. Cahen, Post-growth, In doping of CdTe single crystals via vapor phase 197 (1999) 106
Lyahovitskaya, V., S. Richter, F. Frolow, L. Kaplan, Y. Manassen, K. Gartsman and D. Cahen, Growth of single $CuInSe_2$ crystals by the traveling heater method and their characterization 197 (1999) 177
Lyapin, S.G., see Klipstein, P.C. 195 (1998) 168
Lynn, J.W., see Barilo, S.N. 198/199 (1999) 636

Ma, D., W.Q. Jie, W. Xu, Y. Li and S. Liu, Unidirectional solidification of Al–Cu eutectic with the accelerated crucible rotation technique 194 (1998) 398
Ma, W.J., B.C. Khoo and D. Xu, Influence of Coriolis force on bulk flows during horizontal Bridgman growth on a centrifuge: a numerical study 193 (1998) 430
Ma, X., see Burger, A. 198/199 (1999) 872
MacMillan, M.F., see Tuominen, M. 193 (1998) 101
MacMillan, M.F., see Syväjärvi, M. 197 (1999) 155
MacMillan, M.F., see Syväjäyrvi, M. 198/199 (1999) 1019
Madsen, L.D., see McCaffrey, J.P. 200 (1999) 498
Maeda, H., see Saito, T. 191 (1998) 723
Maeda, N., see Nishida, T. 195 (1998) 41
Maeda, S., see Nakanishi, H. 191 (1998) 711
Maeda, S., K. Abe, M. Kato, H. Nakanishi, K. Hoshikawa and K. Terashima, Oxygen concentration in Czochralski silicon crystals depending on silicon monoxide evaporation from boron doped silicon melts 192 (1998) 117
Maeda, S., K. Takeuchi, M. Kato, K. Abe, H. Nakanishi, K. Hoshikawa and K. Terashima, Morphology variations on inner surface of silica crucibles depending on oxygen concentration in silicon melts 194 (1998) 70
Maffei, N., see Saghir, M.Z. 193 (1998) 623
Magerle, R., see Desnica, U.V. 197 (1999) 612
Magnea, N., see Bleuse, J. 197 (1999) 529
Magno, R., see Twigg, M.E. 191 (1998) 651
Mah, K.W., see Yoon, S.F. 191 (1998) 613
Maher, H., see Décobert, J. 195 (1998) 681
Maier, M., see Obloh, H. 195 (1998) 270
Mainzer, N., E. Zolotoyabko, A. Berner, E. Lakin, G. Bahir and A. Sher, Influence of structural defects on lattice parameter and measured composition of $Hg_{1-x}Cd_xTe$ 197 (1999) 542
Mainzer, N., see Avrahami, Y. 198/199 (1999) 264
Maiwa, K., see Plomp, M. 198/199 (1999) 246
Majerfeld, A., see Sanz-Hervás, A. 195 (1998) 558
Makepeace, A.P.W., see Lang, A.R. 200 (1999) 446
Makhniy, V.P., see Ciach, R. 197 (1999) 675
Maki, S., see Anzai, H. 191 (1998) 148
Makimoto, T., see Saito, H. 195 (1998) 416
Maksimov, I.L., see Balykov, L.N. 198/199 (1999) 32
Maksimov, I.L., see Sanada, M. 198/199 (1999) 67
Maksimov, I.L., see Mori, A. 200 (1999) 297
Małąg, A., see Strupiński, W. 195 (1998) 474
Malchow, S., see Künzel, H. 192 (1998) 56
Malfois, M., see Tardieu, A. 196 (1999) 193
Malimon, I.V., see Ciach, R. 197 (1999) 675
Malkin, A.J., Yu.G. Kuznetsov and A. McPherson, In situ atomic force microscopy studies of surface morphology, growth kinetics, defect structure and dissolution in macromolecular crystallization 196 (1999) 471
Malkin, A.J., see Kuznetsov, Yu.G. 196 (1999) 489
Malkin, A.J., see McPherson, A. 196 (1999) 572
Mallika, C., see Prasad, S.R. 198/199 (1999) 194
Malm, J.-O., see Seifert, W. 197 (1999) 19
Malone, C.C., see Forsythe, E.L. 196 (1999) 332
Maltsev, V., see Leonyuk, L. 198/199 (1999) 619
Maltsev, V., L. Leonyuk, G.-J. Babonas, A. Vetkin and A. Reza, A use of the melt decanting method for the separation of co-crystallizing phases in the system Bi(Pb)–Sr–Ca(Y,RE)–Cu–O 198/199 (1999) 626
Mamedov, V.V., see Ataev, B.M. 198/199 (1999) 1222
Mamiya, M., T. Suzuki and H. Takei, A phase relation study of Bi-based copper oxide super conductors as a function of partial oxygen pressure 198/199 (1999) 611
Manassen, Y., see Lyahovitskaya, V. 197 (1999) 177
Mangeot, J.P., see Taleb, M. 200 (1999) 575
Manko, V., see Burachas, S. 198/199 (1999) 881
Mansori, M., H. Faqir, P. Satre, A. Bendriss, Y. Syono and A. Sebaoun, A new single crystal growth method of $(Bi,Pb)_2Sr_2CaCu_2O_z$ superconductor 197 (1999) 141
Mantovani, G., see Sgualdino, G. 192 (1998) 290
Manuilov, N., V. Nikolov, G. Gentscheva and P. Peshev, Study of some $K_2W_2O_7$–$KGd_{1-x}Ln_x(WO_4)_2$ systems to be used for flux growth of doped $KGd(WO_4)_2$ single crystals 196 (1999) 181

Marable, M., see Singh, N.B. 198/199 (1999) 588
Maraşli, N. and J.D. Hunt, The use of measured values of surface energies to test heterogeneous nucleation theory 191 (1998) 558
Maraşli, N., see Bayender, B. 194 (1998) 119
Marangoni, A.G., see Narine, S.S. 198/199 (1999) 1315
Marchand, H., J.P. Ibbetson, P.T. Fini, S. Keller, S.P. DenBaars, J.S. Speck and U.K. Mishra, Mechanisms of lateral epitaxial overgrowth of gallium nitride by metalorganic chemical vapor deposition 195 (1998) 328
Marcon, J., see Ketata, M. 194 (1998) 297
Marfaing, Y., State of the art and prospects of photorefractive CdTe 197 (1999) 707
Marfaing, Y., see Zerrai, A. 197 (1999) 729
Marino, A., see Depero, L.E. 198/199 (1999) 516
Marone, P.A., P. Thiyagarajan, A.M. Wagner and D.M. Tiede, The association state of a detergent-solubilized membrane protein measured during crystal nucleation and growth by small-angle neutron scattering 191 (1998) 811
Marrakchi, G., see Zerrai, A. 197 (1999) 646
Marrakchi, G., see Zumbiehl, A. 197 (1999) 670
Marrakchi, G., see Zerrai, A. 197 (1999) 729
Marshall, A., see Huang, T.F. 200 (1999) 362
Marsman, A.W., see ten Grotenhuis, E. 191 (1998) 834
Martin, P., see Ketata, M. 194 (1998) 297
Martín-Díaz, R., see Fernández-González, A. 200 (1999) 227
Martinez-Tomas, C., V. Muñoz and R. Triboulet, Heat transfer simulation in a vertical Bridgman CdTe growth configuration 197 (1999) 435
Martinov, V., see Burachas, S. 198/199 (1999) 881
Marty, O., see Sánchez, J.J. 192 (1998) 363
Martynov, V., see Nagornaya, L. 198/199 (1999) 877
Maruyama, S., see Hahn, S.-H. 191 (1998) 413
Maruyama, S., see Guo, Z. 194 (1998) 321
Mascarenhas, Y.P., see Andreeta, M.R.B. 200 (1999) 621
Mascher, P., see Tessaro, G. 197 (1999) 581
Mason, N.J., see Allwood, D.A. 195 (1998) 163
Mason, N.J., see Klipstein, P.C. 195 (1998) 168
Masuda, M. and T. Nishinaga, Macrostep formation and growth condition dependence in MBE of GaAs on GaAs (1 1 1)B vicinal surface 198/199 (1999) 1098
Masumoto, K., see Niwa, E. 192 (1998) 354
Masumoto, Y., see Lee, J.S. 200 (1999) 77
Mateescu, D.C., see Stefan, M. 200 (1999) 148
Matl, P., see Kloc, Ch. 191 (1998) 294
Matsuda, Y., see Sato, K. 197 (1999) 413
Matsuhata, H., see Wang, X.-L. 195 (1998) 586
Matsui, T., see Yoshioka, Y. 198/199 (1999) 71
Matsumoto, K., see Fujiwara, S. 192 (1998) 328
Matsumoto, K., see Fujiwara, S. 196 (1999) 83
Matsumoto, S., see Yamamoto, N. 193 (1998) 16
Matsumoto, T., see Mori, K. 195 (1998) 466
Matsumoto, T., see Koui, T. 195 (1998) 503
Matsuoka, M., see Takiyama, H. 192 (1998) 439
Matsuoka, M., M. Yamanobe, N. Tezuka, H. Takiyama and H. Ishii, Polymorphism, morphologies and bulk densities of DL-methionine agglomerate crystals 198/199 (1999) 1299
Matsushita, H. and T. Takizawa, Se vapor pressure dependence of the phase diagram of the $CuGa_{1-x}In_xSe_2$ system 191 (1998) 455
Matsushita, H., T. Mihira and T. Takizawa, Chemical reaction process and the single crystal growth of $CuInS_2$ compound 197 (1999) 169
Matyi, R.J., see Hansen, D.M. 195 (1998) 144
Matyi, R.J., see Li, J. 195 (1998) 617
Maung, N., see Berrigan, R.A. 195 (1998) 718
Maurin, G., see Gabrielli, C. 200 (1999) 236
Maurin, M., see Tomasini, P. 193 (1998) 572
Mawatari, H., see Yamamoto, N. 193 (1998) 16
Mawst, L.J., H. Yang, M. Nesnidal, A. Al-Muhanna, D. Botez, T.A. Vang, F.D. Alvarez and R. Johnson, High-power, single-mode, Al-free InGaAs(P)/InGaP/GaAs distributed feedback diode lasers 195 (1998) 609
Mawst, L.J., see Li, J. 195 (1998) 617
Maxey, C.D., J.E. Gower, P. Capper, E.S. O'Keefe, T. Skauli and C.K. Ard, Zn concentration determination in CdZnTe by NIR spectroscopy 197 (1999) 427
Mazelsky, R., see Seidensticker, R.G. 198/199 (1999) 988
Mazelsky, R., see Singh, N.B. 198/199 (1999) 995
Mazzarella, L., see Sica, F. 196 (1999) 305
McCaffrey, J.P., E.B. Svedberg, J.R. Phillips and L.D. Madsen, Epitaxial variations of Ni films grown on MgO(0 0 1) 200 (1999) 498
McCormick, T., see Lang, A.R. 200 (1999) 446
McDonald, H., see Guo, B. 196 (1999) 424
McFadden, G.B., see Coriell, S.R. 191 (1998) 573
McFadden, G.B., see Coriell, S.R. 200 (1999) 276
McLaughlin, S., see Xu, X.G. 195 (1998) 687
McPherson, A., see Malkin, A.J. 196 (1999) 471
McPherson, A., see Kuznetsov, Yu.G. 196 (1999) 489
McPherson, A., A.J. Malkin, Yu.G. Kuznetsov, S. Koszelak, M. Wells, G. Jenkins, J. Howard and G. Lawson, The effects of microgravity on protein crystallization: evidence for concentration gradients around growing crystals 196 (1999) 572

Meekes, H., see Bögels, G. 191 (1998) 446
Meekes, H., see Grimbergen, R.F.P. 191 (1998) 846
Meekes, H., see van Hoof, P.J.C.M. 191 (1998) 861
Meekes, H., see Sweegers, C. 197 (1999) 244
Meertens, D., see Schmidt, R. 195 (1998) 124
Mei, X., H.E. Ruda, T. Berdiskihk and M. Buchanan, Liquid phase epitaxial growth of GaP layers on textured GaP (1 1 1)B substrates 193 (1998) 148
Meinhardt, J., see Fiederle, M. 197 (1999) 635
Melamed, O., see Cahen, D. 197 (1999) 537
Meléndez, M., see Constantino, M.E. 194 (1998) 301
Melnik, Yu.V., see Cheng, T.S. 197 (1999) 12
Melnikov, A.A., CdZnTe radiation detectors 197 (1999) 663
Melnikov, A.A., A.S. Sigov, K.A. Vorotilov, A.A. Davydov, L.I. Topalova and N.V. Zhavoronkov, Growth of CdZnTe single crystals for radiation detectors 197 (1999) 666
Méndez, B., see Plaza, J.L. 198/199 (1999) 379
Mendonça, C.A.C., see Soares, L.S.M. 191 (1998) 44
Mendorf, C., see Liu, Q. 197 (1999) 507
Menéndez, J.L., P. Caro and A. Ceballada, Epitaxy, strain and morphology of low Ar pressure sputtered Pt thin films 192 (1998) 164
Meng, X., see Zhang, H. 193 (1998) 370
Meng, X., see Cheng, J. 194 (1998) 89
Meng, X., L. Zhu, H. Zhang, C. Wang, Y.T. Chow and M. Lu, Growth, morphology and laser performance of Nd : YVO_4 crystal 200 (1999) 199
Meng, X., see Zhang, H. 200 (1999) 335
Menhal, H., see Pristovsek, M. 195 (1998) 1
Menhal, H., see Hardtdegen, H. 195 (1998) 211
Merai, V., see Tran, C.A. 195 (1998) 397
Mergui, S., see Paul, N. 197 (1999) 547
Merkulov, A., see Salazar-Hernández, B. 197 (1999) 783
Merkulov, A.A., see Yelisseyev, A.P. 198/199 (1999) 555
Meseguer, F., see Yates, H.M. 193 (1998) 9
Métrat, G., M. Boudeulle, N. Muhlstein, A. Brenier and G. Boulon, Nucleation, morphology and spectroscopic properties of Yb^{3+}-doped $KY(WO_4)_2$ crystals grown by the top nucleated floating crystal method 197 (1999) 883
Meyer, R., see Singh, N.B. 198/199 (1999) 588
Miao, X., Use of natural topaz as a transporting agent in the vapor growth of potassium tungsten oxide bronze fibres 197 (1999) 1008
Michaelides, A., see Domopoulou, A. 191 (1998) 166
Michinomae, M., M. Mochizuki and M. Ataka, Electron microscopic studies on the initial process of lysozyme crystal growth 197 (1999) 257
Migita, S., H. Ota, H. Fujino, Y. Kasai and S. Sakai, Epitaxial $Bi_4Ti_3O_{12}$ thin film growth using Bi self limiting function 200 (1999) 161
Miguez, H., see Yates, H.M. 193 (1998) 9
Mihashi, Y., see Takemi, M. 191 (1998) 18
Mihashi, Y., see Miyashita, M. 192 (1998) 79
Mihashi, Y., see Kizuki, H. 194 (1998) 277
Mihira, T., see Matsushita, H. 197 (1999) 169
Mihopoulos, T.G., S.G. Hummel and K.F. Jensen, Simulation of flow and growth phenomena in a close-spaced reactor 195 (1998) 725
Mihopoulos, T.G., V. Gupta and K.F. Jensen, A reaction-transport model for AlGaN MOVPE growth 195 (1998) 733
Mijlemans, P., see D'Hondt, M. 195 (1998) 655
Mikhailov, V.P., see Barilo, S.N. 198/199 (1999) 716
Mikhailov, V.P., see Levchenko, V.I. 198/199 (1999) 980
Miki, T., J.F. Wang, A. Omino and M. Isshiki, Growth and annealing effect of high-quality ZnSe:N/ZnSe by MOCVD 200 (1999) 399
Mileham, J.R., see López, C.R. 200 (1999) 1
Milenkovic, S., see Caram, R. 198/199 (1999) 844
Miles, M.J., see Jrie, S. 198/199 (1999) 939
Miles, R.W., K.T. Ramakrishna Reddy and I. Forbes, Formation of polycrystalline thin films of $CuInS_2$ by a two step process 198/199 (1999) 316
Millan, A., P. Bennema, A. Verbeeck and D. Bollen, Morphology of silver bromide crystals from KBr–AgBr–DMSO–water systems 192 (1998) 215
Miller, T., see Carter, D.C. 196 (1999) 602
Miller, T., see Carter, D.C. 196 (1999) 610
Miller, T., see Carter, D.C. 196 (1999) 623
Minato, A., see Ueno, S. 198/199 (1999) 1326
Mincu, N., see Dinculescu, I. 198/199 (1999) 999
Minezaki, Y., see Niimura, N. 200 (1999) 265
Minsky, M.S., see Keller, S. 195 (1998) 258
Miotkowska, S., E. Dynowska, I. Miotkowski, A. Szczerbakow, B. Witkowska, J. Kachniarz and W. Paszkowicz, The lattice constants of ternary and quaternary alloys in the PbTe–SnTe–MnTe system 200 (1999) 483
Miotkowski, I., see Miotkowska, S. 200 (1999) 483
Mirabedini, A., see Li, J. 195 (1998) 617
Mishra, U.K., see Keller, S. 195 (1998) 258
Mishra, U.K., see Kozodoy, P. 195 (1998) 265
Mishra, U.K., see Marchand, H. 195 (1998) 328
Misiewicz, J., see Bryja, L. 197 (1999) 694
Missous, M., see Pilkington, S.J. 196 (1999) 1
Missous, M., see Fleischer, S. 196 (1999) 53

Mitichkin, A.I., see Zaslavsky, B.G. 198/199 (1999) 856

Mitrović, M.M., A.A. Žekić and Lj.S. Petruševski, Growth rate dispersion of small KDP crystals 198/199 (1999) 687

Mitsuhara, M., see Sugiura, H. 200 (1999) 13

Mitsuhashi, T., see Otani, S. 194 (1998) 430

Mitura, Z., S.L. Dudarev and M.J. Whelan, Interpretation of reflection high-energy electron diffraction oscillation phase 198/199 (1999) 905

Miura, H., see Jung, Y.-C. 196 (1999) 88

Miyamoto, T., S. Sato, Z. Pan, D. Schlenker, F. Koyama and K. Iga, GaNAs/GaInAs short-period superlattice quantum well structures grown by MOCVD using TBAs and DMHy 195 (1998) 421

Miyamoto, T., see Schlenker, D. 196 (1999) 67

Miyamoto, T., K. Takeuchi, T. Kageyama, F. Koyama and K. Iga, Chemical beam epitaxy of GaInNAs/GaAs quantum wells and its optical absorption property 197 (1999) 67

Miyano, K.E., see Gupta, J.A. 195 (1998) 34

Miyasaka, H., see Nagai, Y. 193 (1998) 732

Miyashita, M., H. Kizuki, M. Tsugami, N. Fujii, Y. Mihashi and S. Takamiya, Metalorganic chemical vapor deposition growth of high-quality AlGaAs using dimethylethylamine alane and triethylgallium–dimethylethylamine adduct 192 (1998) 79

Miyashita, S., see Sazaki, G. 196 (1999) 204

Miyashita, S., see Kurihara, K. 196 (1999) 285

Miyashita, S., see Yanagiya, S.-i. 196 (1999) 319

Miyashita, S., see Nakada, T. 196 (1999) 503

Miyazaki, N. and Y. Kuroda, Finite element analysis of dislocation density during bulk single crystal growth (effect of doping atoms in InP single crystal) 196 (1999) 62

Miyazawa, S. and T. Tabata, Bi_2O_3–TiO_2 binary phase diagram study for TSSG pulling of $Bi_{12}TiO_{20}$ single crystals 191 (1998) 512

Miyazawa, Y., see Jing, C.J. 200 (1999) 204

Mizuno, K., P. Möck, B.K. Tanner, G. Lacey, C.R. Whitehouse, G.W. Smith and A.M. Keir, Partial strain relaxation in (In,Ga)As epilayers on GaAs by means of twin formation 198/199 (1999) 1146

Mizutani, U., see Takagi, A. 193 (1998) 71

Mizuuchi, K., see Kawaguchi, T. 191 (1998) 125

Mo, Q.W., see Wu, J. 197 (1999) 95

Mo, Y., Y. Xia and W. Wu, A nucleation mechanism for diamond film deposited on alumina substrates by microwave plasma CVD 191 (1998) 459

Möck, P., see Mizuno, K. 198/199 (1999) 1146

Mochida, N., see Honda, T. 195 (1998) 319

Mochizuki, M., see Michinomae, M. 197 (1999) 257

Modak, P., M.K. Hudait, S. Hardikar and S.B. Krupanidhi, OMVPE growth of undoped and Si-doped GaAs epitaxial layers on Ge 193 (1998) 501

Moerman, I., see Considine, L. 195 (1998) 192

Moerman, I., see Vanhollebeke, K. 195 (1998) 644

Moerman, I., see D'Hondt, M. 195 (1998) 655

Moest, B., V.G. Glebovsky, H.H. Brongersma, R.H. Bergmans, A.W. Denier van der Gon and V.N. Semenov, Study of Pd single crystals grown by crucibleless zone melting 192 (1998) 410

Mogilyanski, D., M. Blumin, E. Gartstein, R. Opitz and R. Kohler, Structural characterization of LPOMVPE grown AlAs/GaAs multilayers 198/199 (1999) 1070

Mohan, P., see Senguttuvan, N. 191 (1998) 130

Mohan, P., N. Senguttuvan, S.M. Babu, P. Santhanaraghavan and P. Ramasamy, Bulk growth of InSb crystals for infrared device applications 200 (1999) 96

Mohan Rao, P., see Nagaraja, H.S. 193 (1998) 674

Mokhov, A.V., see Koporulina, E.V. 198/199 (1999) 460

Möller, J. and K.I. Jacob, Instability in competitive crystallization in porous viscoelastic materials 197 (1999) 973

Moncorgé, R., see Sangaletti, L. 198/199 (1999) 454

Monna, R., see Angermeier, D. 191 (1998) 386

Monteil, Y., see Dumont, H. 197 (1999) 755

Montelius, L., see Carlsson, N. 191 (1998) 347

Moody, K., see Carter, D.C. 196 (1999) 602

Moody, K., see Carter, D.C. 196 (1999) 610

Moon, D.C., see Kim, S.T. 194 (1998) 37

Moore, C.D., see Duffar, T. 192 (1998) 63

Moorthy Babu, S., see Kumaresan, R. 198/199 (1999) 1165

Mora-Seró, I., V. Muñoz, M. Barbé and R. Triboulet, Study of the chemically activated sublimation of ZnSe 197 (1999) 497

Mora-Seró, I., see Triboulet, R. 198/199 (1999) 968

Moran, P.D., see Hansen, D.M. 195 (1998) 144

Morato, S.P., see Santo, A.M.E. 198/199 (1999) 466

Moravec, P., see Franc, J. 197 (1999) 593

Moreland, K.T., see Stevens, A.M. 196 (1999) 350

Morello, G., see Bertone, D. 195 (1998) 624

Moreno, A., L.A. González-Ramírez, M. de los Angeles Hernández-Hernández, C. Oliver-Salvador, M. Soriano-García and A. Rodríguez-Romero, Investigations on gravity influence upon protein crystallization by the gel acupuncture technique 196 (1999) 587
Mori, A. and I.L. Maksimov, On the Temkin model of solid–liquid interface 200 (1999) 297
Mori, A., see Nishioka, K. 200 (1999) 592
Mori, K., H. Hatakeyama, K. Hamamoto, K. Komatsu, T. Sasaki and T. Matsumoto, Narrow-stripe selective growth of high-quality MQWs by atmospheric-pressure MOVPE 195 (1998) 466
Mori, M., see Honda, T. 195 (1998) 319
Mori, Y., see Furuya, H. 198/199 (1999) 560
Mori, Y., see Adachi, H. 198/199 (1999) 568
Mori, Y., see Yap, Y.K. 198/199 (1999) 1028
Mori, Y.H., see Ohmura, R. 196 (1999) 164
Moriguchi, K., see Ishimaru, M. 194 (1998) 178
Morikawa, T., see Osawa, S. 198/199 (1999) 444
Morikawa, T., see Katsumata, T. 198/199 (1999) 869
Morikoshi, H., see Sato, J. 191 (1998) 746
Morishima, Y., see Wang, J. 197 (1999) 48
Morita, D., see Inoue, R. 198/199 (1999) 1196
Moriwaki, Y., see Iijima, M. 193 (1998) 182
Moriwaki, Y., see Iijima, M. 194 (1998) 125
Moriwaki, Y., see Iijima, M. 198/199 (1999) 670
Morizot, A., A. Neville and T. Hodgkiess, Studies of the deposition of $CaCO_3$ on a stainless steel surface by a novel electrochemical technique 198/199 (1999) 738
Morooka, S., see Saito, T. 191 (1998) 723
Morris, R.C. and B.H.T. Chai, Imperfect low-angle boundaries and fracture in hydrothermally grown berlinite crystals 191 (1998) 108
Moses, T., see Lu, T., 193 (1998) 577
Mößner, R. and G. Gerbeth, Buoyant melt flows under the influence of steady and rotating magnetic fields 197 (1999) 341
Mota, M.A., A.A. Coelho, J.M.Z. Bejarano, S. Gama and R. Caram, Directional growth and characterization of Fe–Al–Nb eutectic alloys 198/199 (1999) 850
Motisuke, P., see Rappl, P.H.O. 191 (1998) 466
Motohisa, J., see Akabori, M. 195 (1998) 579
Motokawa, M., see Yanagiya, S.-i. 196 (1999) 319
Motooka, T., see Ishimaru, M. 194 (1998) 178
Moudden, H., see Ammerahl, U. 193 (1998) 55
Moulding, K.M., see Fleischer, S. 196 (1999) 53
Mühe, A., R. Backofen, J. Fainberg, G. Müller, E. Dornberger, E. Tomzig and W. Von Ammon, Oxygen distribution in silicon melt during a standard Czochralski process studied by sensor measurements and comparison to numerical simulation 198/199 (1999) 409
Mühlbauer, A., A. Muiznieks, G. Raming, H. Riemann and A. Lüdge, Numerical modelling of the microscopic inhomogeneities during FZ silicon growth 198/199 (1999) 107
Mühlbauer, A., see Gross, C. 198/199 (1999) 188
Mühlberg, M., see Dohnke, I. 198/199 (1999) 287
Muhlstein, N., see Métrat, G. 197 (1999) 883
Muiznieks, A., see Mühlbauer, A. 198/199 (1999) 107
Muiznieks, A., see Gross, C. 198/199 (1999) 188
Mujilatu, N., see Shimamura, K. 197 (1999) 896
Mujilatu, N., see Baldochi, S.L. 200 (1999) 521
Mukerji, S. and T. Kar, Etch pit study of different crystallographic faces of L-arginine hydrobromide monohydrate (LAHBr) in alcohols 200 (1999) 543
Mukovskii, Ya., see Shulyatev, D. 198/199 (1999) 511
Mula, G., see Bleuse, J. 197 (1999) 529
Müller, G., see Kurz, M. 198/199 (1999) 101
Müller, G., see Fischer, B. 198/199 (1999) 170
Müller, G., see Eisener, B. 198/199 (1999) 321
Müller, G., see Böttcher, K. 198/199 (1999) 349
Müller, G., see Amon, J. 198/199 (1999) 361
Müller, G., see Amon, J. 198/199 (1999) 367
Müller, G., see Mühe, A. 198/199 (1999) 409
Muller, J.C., see Angermeier, D. 191 (1998) 386
Müller, P. and R. Kern, Equilibrium shape of epitaxially strained crystals (Volmer–Weber case) 193 (1998) 257
Müller, St.G., see Hofmann, D. 198/199 (1999) 1005
Müller, T., see Schulz, D. 198/199 (1999) 1024
Müller-Vogt, G., see Scholz, K. 197 (1999) 586
Mullin, J.W., see Kubota, N. 197 (1999) 388
Mullins, J.T., see Aitken, N.M. 198/199 (1999) 984
Munekata, H., see Hirose, S. 194 (1998) 16
Munetoh, S., see Ishimaru, M. 194 (1998) 178
Munoz F., A., see Földvári, I. 198/199 (1999) 482
Muñoz, V., see Garcia, J.A. 191 (1998) 685
Muñoz, V., see Sochinskii, N.V. 192 (1998) 342
Muñoz, V., A. Lasbley, S. Klotz and R. Triboulet, Synthesis and growth of PbTe crystals at low temperature and their characterization 196 (1999) 71
Muñoz, V., see Martinez-Tomas, C. 197 (1999) 435
Muñoz, V., see Mora-Seró, I. 197 (1999) 497
Muñoz, V., see Reig, C. 197 (1999) 688
Muñoz, V., see Garcia, J.A. 197 (1999) 794
Muñoz, V., see Triboulet, R. 198/199 (1999) 968
Murakami, T., see Katsumata, T. 198/199 (1999) 1226

Murakami, Y., see Yonenaga, I. 191 (1998) 399
Muranevich, E., see Lisiansky, M. 197 (1999) 630
Murase, K., see Furuya, H. 198/199 (1999) 560
Murmann, L., see Kauerauf, B. 193 (1998) 701
Murthy, R.V.A., M. Ravikumar, A. Choubey, K. Lal, L. Kharachenko, V. Shleguel and V. Guerasimov, Growth and characterization of large-size bismuth germanate single crystals by low thermal gradient Czochralski method 197 (1999) 865
Mycielski, A., A. Szadkowski, E. Łusakowska, L. Kowalczyk, J. Domagała, J. Bąk-Misiuk and Z. Wilamowski, Parameters of substrates–single crystals of ZnTe and $Cd_{1-x}Zn_xTe$ ($x < 0.25$), obtained by physical vapor transport technique (PVT) 197 (1999) 423
Myers, T.H., see Ziemer, K.S. 191 (1998) 594
Myerson, A.S., see Izmailov, A.F. 196 (1999) 234

Nabetani, Y., K. Sawada, Y. Furukawa, A. Wakahara, S. Noda and A. Sasaki, Self-assembled InP islands grown on GaP substrate 193 (1998) 470
Nabot, J.P., see Boiton, P. 194 (1998) 43
Nabot, J.P., see Duffar, T. 198/199 (1999) 374
Nagai, M., see Tsukamoto, H. 191 (1998) 679
Nagai, Y., Y. Tsuboi, H. Miyasaka and A. Itaya, Effect of applied voltage on aggregate structure of microcrystals in vacuum-deposited films of mesogens 193 (1998) 732
Nagano, O., see Obara, K. 198/199 (1999) 894
Nagaraja, H.S., V. Upadhyaya, P. Mohan Rao, P. Sreeramana Aithal and A.P. Bhat, Organic nonlinear optical crystals of benzoyl glycine 193 (1998) 674
Nagasawa, H., see Yaguchi, H. 195 (1998) 323
Nagashio, K., Y. Takamura, K. Kuribayashi and Y. Shiohara, Microstructural control of $NdBa_2Cu_3O_{7-\delta}$ superconducting oxide from highly undercooled melt by containerless processing 200 (1999) 118
Nagata, K., see Chani, V.I. 194 (1998) 374
Nagatoshi, Y., see Sazaki, G. 196 (1999) 204
Nagornaya, L., S. Burachas, Yu. Vostretsov, V. Martynov and V. Ryzhikov, Studies of ways to reduce defects in $CdWO_4$ single crystals 198/199 (1999) 877
Nagornaya, L., see Burachas, S. 198/199 (1999) 881
Nahm, K.S., see Kim, K.C. 197 (1999) 841
Naik, M.B., S.K. Lakshmanan, R.H. Wentorf, R.R. Reeves and W.N. Gill, Thermal chemical vapor deposition of copper from hexafluoroacetylacetonate Cu(I) vinyltrimethylsilane: kinetic studies 193 (1998) 133
Nakada, T., see Sazaki, G. 196 (1999) 204
Nakada, T., see Kurihara, K. 196 (1999) 285
Nakada, T., see Yanagiya, S.-i. 196 (1999) 319
Nakada, T., G. Sazaki, S. Miyashita, S.D. Durbin and H. Komatsu, Direct AFM observations of impurity effects on a lysozyme crystal 196 (1999) 503
Nakada, T., see Kaito, C. 200 (1999) 271
Nakajima, K., see Kodama, S. 194 (1998) 166
Nakajima, K., see Nishijima, Y. 197 (1999) 769
Nakamura, F., S. Hashimoto, M. Hara, S. Imanaga, M. Ikeda and H. Kawai, AlN and AlGaN growth using low-pressure metalorganic chemical vapor deposition 195 (1998) 280
Nakamura, S., High-power InGaN-based blue laser diodes with a long lifetime 195 (1998) 242
Nakanishi, H., K. Nakazato, S. Asaba, K. Abe, S. Maeda and K. Terashima, Temperature dependence of density of molten germanium measured by a newly developed Archimedian technique 191 (1998) 711
Nakanishi, H., see Maeda, S. 192 (1998) 117
Nakanishi, H., see Maeda, S. 194 (1998) 70
Nakanishi, Y., see Niraula, M. 200 (1999) 90
Nakano, K., see Shimamura, K. 197 (1999) 896
Nakano, K., see Baldochi, S.L. 200 (1999) 521
Nakatsuji, S., see Anzai, H. 191 (1998) 148
Nakazato, K., see Nakanishi, H. 191 (1998) 711
Nam, S., B. O, K.-S. Lee and Y.D. Choi, Optimum growth and properties of ZnS/GaAs(1 0 0) epilayers by hot-wall epitaxy 194 (1998) 61
Namikawa, Y., see Fujiwara, S. 192 (1998) 328
Namikawa, Y., see Fujiwara, S. 196 (1999) 83
Nanev, C.N., see Tsekova, D. 196 (1999) 226
Naoi, Y., see Wang, J. 197 (1999) 48
Naoi, Y., see Wang, J. 200 (1999) 85
Narayanan, R., see Prasad, S.R. 198/199 (1999) 194
Narayanan, R., see Singh, N.B. 198/199 (1999) 588
Narimatsu, S., see Nishioka, K. 200 (1999) 592
Narine, S.S. and A.G. Marangoni, Microscopic and rheological studies of fat crystal networks 198/199 (1999) 1315
Narita, K., see Koukitu, A. 198/199 (1999) 1111
Naritsuka, S., see Yan, Z. 192 (1998) 11
Naritsuka, S., see Chang, Y.S. 192 (1998) 18
Naritsuka, S., see Yan, Z. 198/199 (1999) 1077

Naritsuka, S., Z. Yan and T. Nishinaga, Two-dimensional nucleation at stacking fault during InP microchannel epitaxy 198/199 (1999) 1082
Näser, A., see Dadgar, A. 195 (1998) 69
Nasibov, A.S., see Korostelin, Yu.V. 197 (1999) 449
Nastac, L., Analytical modeling of solute redistribution during the initial unsteady unidirectional solidification of binary dilute alloys 193 (1998) 271
Nastase, N., see Verardi, P. 197 (1999) 523
Nataf, G., B. Beaumont, A. Bouillé, S. Haffouz, M. Vaille and P. Gibart, Lateral overgrowth of high quality GaN layers on GaN/Al_2O_3 patterned substrates by halide vapour-phase epitaxy 192 (1998) 73
Naumann, W., see Franke, T. 193 (1998) 451
Navarro-Contreras, H., see Constantino, M.E. 194 (1998) 301
Navarro-Contreras, H., see Salazar-Hernández, B. 197 (1999) 783
Ndap, J.O., see Burger, A. 198/199 (1999) 872
Neal, B.L., D. Asthagiri, O.D. Velev, A.M. Lenhoff and E.W. Kaler, Why is the osmotic second virial coefficient related to protein crystallization? 196 (1999) 377
Negishi, A., see Anzai, H. 191 (1998) 148
Nemirovsky, Y., see Levy, M. 197 (1999) 626
Nemirovsky, Y., see Stolyarova, S. 198/199 (1999) 1157
Nemirovsky, Y., see Cohen, K. 198/199 (1999) 1174
Nemirovsky, Y., see Chack, A. 198/199 (1999) 1179
Nenow, D., see Iwanov, D. 198/199 (1999) 96
Nepomnyashchy, A.A., see Golovin, A.A. 198/199 (1999) 1245
Nepomnyashchy, A.A., see Rotstein, H.G. 198/199 (1999) 1262
Nering, J., see Tran, C.A. 195 (1998) 397
Nesnidal, M., see Mawst, L.J. 195 (1998) 609
Neubauer, B., see Gerthsen, D. 200 (1999) 353
Neubert, M., see Böttcher, K. 198/199 (1999) 349
Neumann, A.M., S.K. Bermingham, H.J.M. Kramer and G.M. van Rosmalen, The effect of the impeller speed on the product crystal size distribution (CSD) a 22 liter draft tube (DT) crystallizer 198/199 (1999) 723
Neumann, W., see Kappelt, M. 195 (1998) 552
Neumann, W., see Storm, S. 197 (1999) 517
Neumann, W., see Dohnke, I. 198/199 (1999) 287
Neumann, W., see Penzel, S. 198/199 (1999) 811
Neuroth, G. and F. Wallrafen, Czochralski growth and characterisation of pure and doped $YAlO_3$ single crystals 198/199 (1999) 435
Neville, A., see Morizot, A. 198/199 (1999) 738
Neville, A., see Hennessy, A.J. 198/199 (1999) 830
Ng, G.I., see Yoon, S.F. 193 (1998) 285
Ng, G.I., see Zheng, H.Q. 197 (1999) 762
Ng, J.D., see Sauter, C. 196 (1999) 365
Ngankam, P.A., P. Schaaf, J.C. Voegel and F.J.G. Cuisinier, Heterogeneous nucleation of calcium phosphate salts at a solid/liquid interface examined by scanning angle reflectometry 197 (1999) 927
Ni, W.-X, see Joelsson, K.B. 196 (1999) 97
Niehus, H., see Storm, S. 197 (1999) 517
Niimura, N., Y. Minezaki, I. Tanaka, S. Fujiwara and M. Ataka, Polar structure of lysozyme aggregates in unsaturated solution determined by small-angle neutron scattering – contrast variation method 200 (1999) 265
Nijdam, A.J., see Plomp, M. 193 (1998) 389
Nijdam, A.J., see van Suchtelen, J. 198/199 (1999) 17
Nijdam, A.J., J. van Suchtelen, J.W. Berenschot, J.G.E. Gardeniers and M. Elwenspoek, Etching of silicon in alkaline solutions: a critical look at the {1 1 1} minimum 198/199 (1999) 430
Nikitin, P.I., see Savchuk, A.I. 197 (1999) 698
Nikolov, V., see Manuilov, N. 196 (1999) 181
Ning Dong, see Zhao Qian 200 (1999) 603
Ning, Y., T. Zhou, B. Zhang, H. Jiang, S. Li, G. Yuan, Y. Tian and Y. Jin, Growth and characterization of InAs-rich GaInAsSb alloys on GaSb substrates by MOCVD 191 (1998) 39
Niraula, M., T. Aoki, Y. Nakanishi and Y. Hatanaka, Growth and doping studies of CdTe epilayers on GaAs substrates by low-pressure plasma-radical-assisted metal-organic chemical vapor deposition 200 (1999) 90
Nirk, T., see Lott, K. 197 (1999) 485
Nishida, T., N. Maeda, T. Akasaka and N. Kobayashi, Step-flow MOVPE of GaN on SiC substrates 195 (1998) 41
Nishida, T., T. Akasaka, Y. Yamauchi and N. Kobayashi, Step-free surface and interface by finite area metalorganic vapor phase epitaxy 195 (1998) 459
Nishigaki, T., see Inoue, R. 198/199 (1999) 1196
Nishijima, Y., K. Nakajima, K. Otsubo and H. Ishikawa, InGaAs single crystal using a GaAs seed grown with the vertical gradient freeze technique 197 (1999) 769
Nishinaga, T., see Bacchin, G. 191 (1998) 599
Nishinaga, T., see Yan, Z. 192 (1998) 11
Nishinaga, T., see Chang, Y.S. 192 (1998) 18
Nishinaga, T., see Yan, Z. 198/199 (1999) 1077

Nishinaga, T., see Naritsuka, S. 198/199 (1999) 1082
Nishinaga, T., see Masuda, M. 198/199 (1999) 1098
Nishinaga, T., see Kousai, S. 198/199 (1999) 1119
Nishinaga, T., see Yamashiki, A. 198/199 (1999) 1125
Nishinaga, T., see Bacchin, G. 198/199 (1999) 1130
Nishino, K., see Qhalid Fareed, R.S. 200 (1999) 348
Nishioka, K., see Li, J.-S. 198/199 (1999) 27
Nishioka, K., see Balykov, L.N. 198/199 (1999) 32
Nishioka, K., see Sanada, M. 198/199 (1999) 67
Nishioka, K., A. Mori, K.J. Takano, Y. Kaishita and S. Narimatsu, Pressure-dependence of the interfacial tension of a critical nucleus in the binary-ideal solution 200 (1999) 592
Nishiyama, Y., see Yokoyama, C. 191 (1998) 827
Nistor, S.V., see Stefan, M. 200 (1999) 148
Nitta, S., see Yamaguchi, S. 195 (1998) 309
Niu, P.J., see Li, Y.X. 191 (1998) 282
Niwa, E. and K. Masumoto, Growth of $AgGaS_2$ single crystals by a self-seeding vertical gradient freezing method 192 (1998) 354
Niwa, K., see Furukawa, Y. 197 (1999) 889
Noda, S., see Nabetani, Y. 193 (1998) 470
Noh, D., see Paek, J.-S. 200 (1999) 55
Noh, S.K., see Lee, C.-R. 193 (1998) 300
Noh, S.K., see Leem, J.-Y. 193 (1998) 491
Noh, S.K., see Lee, C.-R. 197 (1999) 78
Noh, S.K., see Leem, J.-Y. 197 (1999) 84
Nomura, T., see Shimizu, K. 191 (1998) 178
Nomura, T., see Shimizu, K. 191 (1998) 185
Nomura, T., see Shimizu, K. 197 (1999) 921
Nonaka, M., see Yonenaga, I. 191 (1998) 393
Nonat, A., see Garrault-Gauffinet, S. 200 (1999) 565
Nordby Jr., H.D., see Burk Jr., A.A. 200 (1999) 458
Nordén, H.V., see Koiranen, T. 198/199 (1999) 749
Notcovich, A.G., I. Braslavsky and S.G. Lipson, Imaging fields around growing crystals 198/199 (1999) 10
Nouaoura, M., see Breton, G. 200 (1999) 112
Novella, M.L., see Otálora, F. 196 (1999) 649
Novella, M.L., see Garcia-Ruiz, J.M. 196 (1999) 703
Novick-Cohen, A., see Rotstein, H.G. 198/199 (1999) 1256
Novick-Cohen, A., see Rotstein, H.G. 198/199 (1999) 1262
Novikov, S.V., see Orton, J.W. 197 (1999) 7
Novikov, S.V., see Cheng, T.S. 197 (1999) 12
Nowysz, K., see Hruban, A. 198/199 (1999) 282
Nozaki, K., see Anzai, H. 191 (1998) 148
Nozaki, M., see Wang, J. 197 (1999) 48
Nozaki, M., see Wang, J. 200 (1999) 85
N'tep, J.M., see Triboulet, R. 198/199 (1999) 968
Nur, O., see Zhao, Q.X. 193 (1998) 328
Nurmi, J., see Koiranen, T. 198/199 (1999) 749
Nurmikko, A.V., see Han, J. 195 (1998) 291
Ny, J.Le, see Leroux, S. 198/199 (1999) 911
Nykonyuk, Ye., see Panchuk, O. 197 (1999) 607
O, B., see Nam, S. 194 (1998) 61
O'Keefe, E.S., see Maxey, C.D. 197 (1999) 427
O'Loughlin, M.J., see Burk Jr., A.A. 200 (1999) 458
O'Palko, F.J., see Whipps, S. 192 (1998) 243
Oakley, D.C., see Wang, C.A. 195 (1998) 346
Oates, W.A. and H. Wenzl, Foreign atom thermodynamics in liquid gallium arsenide 191 (1998) 303
Obara, K. and T. Fukuyama, Experimental simulations of adsorbed particles and relations with crystal growth 198/199 (1999) 77
Obara, K., K.-i. Chiba, O. Nagano and P. YiJi, Monitoring the surface electronic states of crystals in vapor-phase growth processes under magnetic field 198/199 (1999) 894
Obara, K. and P. YiJi, Electronic structures of adsorbed buffer layer on metallic electrodes 198/199 (1999) 917
Obloh, H., K.H. Bachem, U. Kaufmann, M. Kunzer, M. Maier, A. Ramakrishnan and P. Schlotter, Self-compensation in Mg doped p-type GaN grown by MOCVD 195 (1998) 270
Ochimizu, H. and H. Tanaka, Si-doping into GaAs grown by metalorganic vapor phase epitaxy using bisdiisopropylaminosilane 195 (1998) 58
Oda, O., see Sato, K. 197 (1999) 413
Oda, Y. and T. Fukui, Natural formation of multiatomic steps on patterned vicinal substrates by MOVPE and application to GaAs QWR structures 195 (1998) 6
Oelgart, G., see Knauer, A. 195 (1998) 694
Oertel, J., K. Ellmer, W. Bohne, J. Röhrich and H. Tributsch, Growth of n-type polycrystalline pyrite (FeS_2) films by metalorganic chemical vapour deposition and their electrical characterization 198/199 (1999) 1205
Off, J., A. Kniest, C. Vorbeck, F. Scholz and O. Ambacher, Influence of buffer layers on the In-content of GaInN layers 195 (1998) 286
Ogata, K., Sz. Fujita and Sg. Fujita, Effects of photoirradiation energy and of underlying layers on ZnSe growth by photoassisted MOVPE 198/199 (1999) 1170
Ogawa, M., see Tachibana, H. 196 (1999) 41
Ogura, M., see Wang, X.-L. 195 (1998) 586
Ogura, T., see Kousai, S. 198/199 (1999) 1119
Oh, J. and C.H. Grein, Epitaxial growth simulations of CdTe(1 1 1)B on Si(0 0 1) 193 (1998) 241

Ohachi, T., see Koizumi, K. 198/199 (1999) 1136
Ohba, T., see Kurihara, K. 196 (1999) 285
Ohishi, M., see Inoue, R. 198/199 (1999) 1196
Ohiso, Y., see Amano, C. 193 (1998) 460
Ohki, K., see Kurihara, K. 196 (1999) 285
Ohkohchi, M., see Zhao, X. 198/199 (1999) 934
Ohmura, R., T. Shigetomi and Y.H. Mori, Formation, growth and dissociation of clathrate hydrate crystals in liquid water in contact with a hydrophobic hydrate-forming liquid 196 (1999) 164
Ohnoki, N., F. Koyama and K. Iga, Super-lattice AlAs/AlInAs for lateral-oxide current confinement in InP-based lasers 195 (1998) 603
Ohsaka, K. and E.H. Trinh, Apparatus for measuring the growth velocity of dendritic ice in undercooled water 194 (1998) 138
Ohsawa, T., see Otani, S. 200 (1999) 472
Ohshita, Y., M. Oshida, M. Seki and K. Watanabe, $TiSi_2$/Si interface instability in plasma-assisted chemical vapor deposition of titanium 193 (1998) 322
Ohtake, H., see Shimamura, K. 197 (1999) 896
Ohtani, K., see Jung, Y.-C. 196 (1999) 88
Ohtomo, A., see Honda, T. 195 (1998) 319
Ohtsuki, O., see Kodama, S. 194 (1998) 166
Okada, M., see Sekijima, T. 193 (1998) 446
Okada, Y., see Udono, H. 193 (1998) 39
Okada, Y., see Jang, K.-Y. 197 (1999) 54
Okada, Y., see Udono, H. 197 (1999) 466
Okamoto, A., see Sugiyama, N. 191 (1998) 84
Okamoto, H., see Yamamoto, N. 193 (1998) 16
Okamoto, Y., Theoretical study on the precursors of group-III nitrides 191 (1998) 405
Okamoto, Y., Theoretical study of the initial gas-phase reactions of TaN CVD 197 (1999) 236
Okazawa, K., see Kishida, Y. 198/199 (1999) 135
Okhrimenko, T.M., see Kuznetsov, V.A. 193 (1998) 164
Okumura, K., see Sugiyama, N. 191 (1998) 84
Okuyama, H., S. Kijima, Y. Sanaka and A. Ishibashi, Study of the growth mechanism of ZnCdSe by MBE using the mass spectrometer 193 (1998) 43
Oling, F., see Brisson, A. 196 (1999) 456
Oliver-Salvador, C., see Moreno, A. 196 (1999) 587
Olson, J.M., see Geisz, J.F. 195 (1998) 401
Olson, J.M., see Friedman, D.J. 195 (1998) 409
Olson, J.M., see Friedman, D.J. 195 (1998) 438
Olsson, E., see Joelsson, K.B. 196 (1999) 97
Olsthoorn, S.M., see Hageman, P.R. 194 (1998) 270
Omaev, A.K., see Ataev, B.M. 198/199 (1999) 1222
Omeltchouk, A.R., see Szczerbakow, A. 191 (1998) 673
Omino, A., see Miki, T. 200 (1999) 399
Onabe, K., see Yaguchi, H. 195 (1998) 323
Onabe, K., see Biwa, G. 195 (1998) 574
Onabe, K., see Wu, J. 197 (1999) 73
Ono, Y., see Ichimura, M. 198/199 (1999) 308
Oosterhof, H., R.M. Geertman, G.J. Witkamp and G.M. van Rosmalen, The growth of sodium nitrate from mixtures of water and isopropoxyethanol 198/199 (1999) 754
Opitz, R., see Mogilyanski, D. 198/199 (1999) 1070
Opolonin, A., see Ryzhikov, V. 197 (1999) 655
Ortner, B., see Kečkéš, J. 192 (1998) 84
Orton, J.W., C.T. Foxon, T.S. Cheng, S.E. Hooper, S.V. Novikov, B.Ya. Ber and Yu.A. Kudriavtsev, Incorporation of Mg in GaN grown by molecular beam epitaxy 197 (1999) 7
Osawa, S., T. Katsumata, T. Iyoda, Y. Enoki, S. Komuro and T. Morikawa, Effects of composition on the optical properties of doped and nondoped $GdVO_4$ 198/199 (1999) 444
Oshiba, Y., see Kawasaki, M. 198/199 (1999) 449
Oshida, M., see Ohshita, Y. 193 (1998) 322
Osinsky, A., see Tran, C.A. 195 (1998) 397
Ošťádal, I., see Sobotík, P. 197 (1999) 955
Oster, A., see Knauer, A. 195 (1998) 694
Ostheimer, V., T. Filz, J. Hamann, St. Lauer, Ch. Schmitz, D. Weber, H. Wolf and Th. Wichert, Doping of CdTe with radioactive ^{111}In during MOCVD growth 198/199 (1999) 1184
Ostrogorsky, A.G., see Dutta, P.S. 191 (1998) 904
Ostrogorsky, A.G., see Dutta, P.S. 194 (1998) 1
Ostrogorsky, A.G., see Dutta, P.S. 197 (1999) 1
Ostrogorsky, A.G., see Dutta, P.S. 197 (1999) 749
Ostrogorsky, A.G., see Dutta, P.S. 198/199 (1999) 384
Ota, H., see Migita, S. 200 (1999) 161
Otálora, F., J.-M. García-Ruiz, J.A. Gavira and B. Capelle, Topography and high resolution diffraction studies in tetragonal lysozyme 196 (1999) 546
Otálora, F., M.L. Novella, D. Rondón and J.-M. García-Ruiz, Growth of lysozyme crystals under microgravity conditions in the LMS (STS-78) mission 196 (1999) 649
Otálora, F., see García-Ruiz, J.-M. 196 (1999) 703
Otani, S., Preparation of CaB_6 crystals by the floating zone method 192 (1998) 346
Otani, S., M.M. Korsukova and T. Mitsuhashi, Floating zone growth and high-temperature hardness of NbB_2 and TaB_2 single crystals 194 (1998) 430

Otani, S. and T. Ohsawa, Floating zone growth and high-temperature hardness of CrB_2 single crystals 200 (1999) 472
Otoishi, S. and Y. Tange, Growth rate and morphology of silicon carbide whiskers from polycarbosilane 200 (1999) 467
Otsubo, K., see Nishijima, Y. 197 (1999) 769
Ougazzaden, A., see Sik, H. 195 (1998) 479
Ougazzaden, A., see Dumont, H. 197 (1999) 755
Ovanesyan, K.L., see Petrosyan, A.G. 198/199 (1999) 492
Ovanesyan, K.L., A.G. Petrosyan, G.O. Shirinyan, C. Pedrini and L. Zhang, Czochralski single crystal growth of Ce- and Pr-doped $LaLuO_3$ double oxide 198/199 (1999) 497
Özkar, S., see Tanrikulu, S.Ü. 194 (1998) 220
Ozoe, H., see Kakimoto, K. 198/199 (1999) 114

Paek, J.-S., K.-K. Kim, J.-M. Lee, D.-J. Kim, M.-S. Yi, D.Y. Noh, H.-G. Kim and S.-J. Park, Nitridation of sapphire substrate and its effect on the growth of GaN layer at low temperature 200 (1999) 55
Paganotto, N., see Siviniant, J. 197 (1999) 680
Pajaczkowska, A., A. Klos, D. Kasprowicz and M. Drozdowski, Influence of oxygen on the growth of some oxide crystals 198/199 (1999) 440
Pałczyńska, T., see Sangwal, K. 194 (1998) 214
Palosaari, S., see Sha, Z.L. 198/199 (1999) 692
Palosz, W., Diffusive gas losses from silica glass ampoules at elevated temperatures 191 (1998) 897
Palosz, W., see Su, C.-H. 192 (1998) 386
Pan, D., J. Xu and E. Towe, Insensitivity of self-formed quantum dots to substrate surface roughness 196 (1999) 23
Pan, J., see Yuan, Y. 193 (1998) 585
Pan, L., see Zhuang, Q.D. 200 (1999) 375
Pan Liang, see Zhou Hongwei 191 (1998) 361
Pan, Q., see Gallagher, D.T. 193 (1998) 665
Pan, Q.Y., see Feng, J. 197 (1999) 393
Pan, S., see Shi, W. 197 (1999) 905
Pan, S.-h., see Wang, R.-p. 200 (1999) 505
Pan, Z., see Jin, W. 191 (1998) 760
Pan, Z., see Miyamoto, T. 195 (1998) 421
Pan, Z., see Schlenker, D. 196 (1999) 67
Panchuk, O., see Fochuk, P. 197 (1999) 603
Panchuk, O., A. Savitskiy, P. Fochuk, Ye. Nykonyuk, O. Parfenyuk, L. Shcherbak, M. Ilashchuk, L. Yatsunyk and P. Feychuk, IV group dopant compensation effect in CdTe 197 (1999) 607
Panda, R.N. and N.S. Gajbhiye, Chemical synthesis and magnetic properties of nanocrystalline $FeMoN_2$ 191 (1998) 92
Panova, A.N., V.I. Goriletsky, T.B. Grinyova, K.V. Shakhova and E.L. Vinograd, Study of the growth atmosphere effect on optical and scintillation characteristics of large CsI(Tl) crystals 198/199 (1999) 865
Papaioannou, V., J. Stoemenos, L. Di Cioccio, D. David and C. Pudda, Study of 4H- and 6H-SiC films grown on off-oriented (0 0 0 1) SiC substrates 194 (1998) 342
Parello, J., see Declercq, J.-P. 196 (1999) 595
Parfenyuk, O.A., see Savitsky, A.V. 192 (1998) 196
Parfenyuk, O., see Panchuk, O. 197 (1999) 607
Parillaud, O., see Trassoudaine, A. 192 (1998) 402
Park, G.H., see Considine, L. 195 (1998) 192
Park, H.L., see Kim, T.W. 197 (1999) 799
Park, H.S., see Hong, S.K. 191 (1998) 275
Park, J., see Dupuis, R.D. 195 (1998) 340
Park, J.-W., C.M. Rouleau and D.H. Lowndes, Heteroepitaxial growth of n-type CdSe on GaAs(0 0 1) by pulsed laser deposition: studies of film–substrate interdiffusion and indium diffusion 193 (1998) 516
Park, S.-E., see Lee, C.-R. 193 (1998) 300
Park, S.-J., see Paek, J.-S. 200 (1999) 55
Park, Y., see Hong, S.K. 191 (1998) 275
Parkinson, G.M., see Rossiter, D.S. 191 (1998) 525
Parkinson, G.M., see Reyhani, M.M. 198/199 (1999) 258
Parkinson, G.M., see Lee, M.-y. 198/199 (1999) 270
Parsiegla, K.I. and J.L. Katz, Calcite growth inhibition by copper(II). I. Effect of supersaturation 200 (1999) 213
Partin, D.L., M. Pelczynski, P. Cooke, L. Green, J. Heremans and C.M. Thrush, The influence of stoichiometry on the growth of tellurium-doped indium antimonide for magnetic field sensors 195 (1998) 378
Pascal-Delannoy, F., see Boulouz, A. 194 (1998) 336
Passaseo, A., M. Longo, R. Rinaldi, R. Cingolani, M. Catalano, A. Taurino and L. Vasanelli, Influence of different V-grooved GaAs substrates on the geometrical shape of InGaAs/GaAs quantum wires 197 (1999) 777
Pastor, R.C., Crystal growth of metal fluorides for CO_2 laser operation. I. The necessity of the RAP approach 200 (1999) 510
Paszkowicz, W., see Miotkowska, S. 200 (1999) 483
Patel, C.J., see Zhao, Q.X. 193 (1998) 328
Patel, P.D., see Deshpande, M.P. 197 (1999) 833

Patriarche, G., see Sik, H. 195 (1998) 479
Patriarche, G., see Sagnes, I. 195 (1998) 524
Pattyn, H., see Jin, S. 194 (1998) 189
Paul, D.McK., see Gardner, J.S. 191 (1998) 740
Paul, N., C.M. Van Vliet and S. Mergui, Generation–recombination noise and photo-induced transient conductivity in epitaxial CdHgTe long wavelength infrared detectors 197 (1999) 547
Pautrat, J.-L., see Bleuse, J. 197 (1999) 529
Pauwels, B., D. Bernaerts, S. Amelinckx, G. Van Tendeloo, J. Joutsensaari and E.I. Kauppinen, Multiply twinned C_{60} and C_{70} nanoparticles 200 (1999) 126
Pavlović, T., see Čabrić, B. 200 (1999) 339
Pavlyuchenko, V.S., see Drebushchak, V.A. 193 (1998) 728
Pawlitz, J.L., see Stevens, A.M. 196 (1999) 350
Paxton, T.E., A. Sambanis and R.W. Rousseau, Mineral substrates as heterogeneous nucleants in the crystallization of proteins 198/199 (1999) 656
Peacock, C., see Johnstone, J. 198/199 (1999) 275
Peanasky, M.J., see Cederberg, J.G. 195 (1998) 63
Pecz, B., see di Forte-Poisson, M.A. 195 (1998) 314
Pedrini, C., see Petrosyan, A.G. 198/199 (1999) 492
Pedrini, C., see Ovanesyan, K.L. 198/199 (1999) 497
Pehrsson, P.E., see Lang, A.R. 200 (1999) 446
Pelczynski, M., see Partin, D.L. 195 (1998) 378
Pellegrino, J.G., see Gupta, J.A. 195 (1998) 34
Pelzmann, A., see Prystawko, P. 198/199 (1999) 1061
Pemble, M.E., see Yates, H.M. 193 (1998) 9
Pemble, M.E., see Yates, R.F. 195 (1998) 174
Penn, B.G., see Wang, W.S. 198/199 (1999) 578
Penzel, S. and W. Neumann, Growth of Bi–Sb gradient crystals for X-ray monochromators 198/199 (1999) 811
Pèpe, G., see Lin, C.H. 191 (1998) 791
Pèpe, G., see Seyssiecq, I. 196 (1999) 174
Pereira, E., see di Forte-Poisson, M.A. 195 (1998) 314
Peshev, P., see Manuilov, N. 196 (1999) 181
Péter, Á., see Földvári, I. 198/199 (1999) 482
Peters, P., see Sen, S. 193 (1998) 692
Pet'kov, I.S., see Borodin, A.V. 198/199 (1999) 215
Petravic, M., see Li, G. 191 (1998) 357
Petrich, G.S., see Koontz, E.M. 198/199 (1999) 1104
Petrosyan, A.G., G.O. Shirinyan, K.L. Ovanesyan, C. Pedrini and C. Dujardin, Bridgman single crystal growth of Ce-doped $(Lu_{1-x}Y_x)AlO_3$ 198/199 (1999) 492
Petrosyan, A.G., see Ovanesyan, K.L. 198/199 (1999) 497
Petruševski, Lj.S., see Mitrović, M.M. 198/199 (1999) 687
Pfeiffer, D., see Cederberg, J.G. 195 (1998) 105
Phillips, J.R., see McCaffrey, J.P. 200 (1999) 498
Phipps, A.G., see Christopher, G.K. 191 (1998) 820
Piataev, V., see Jochum, S. 195 (1998) 637
Piazza, R., Interactions in protein solutions near crystallisation: a colloid physics approach 196 (1999) 415
Piccoli, R., see Sica, F. 196 (1999) 305
Piechotka, M., E. Kaldis, G. Wetzel, H.-J. Schneider, W. Buff, M. Tardy and H. Stanna, Kinetics of physical vapor transport at low pressure under microgravity conditions. I. DCMF flight hardware and experimental conditions 193 (1998) 80
Piechotka, M., E. Kaldis, G. Wetzel and A. Flisch, Kinetics of physical vapour transport at low pressure under microgravity conditions. II. Results of the DCMF space experiment 193 (1998) 90
Pietzonka, I., T. Sass, R. Franzheld, G. Wagner and V. Gottschalch, Surface characterization of ordered (GaIn)P 195 (1998) 21
Pietzonka, I., R. Franzheld, T. Saß, G. Benndorf, R. Schwabe, M. Handschuh and V. Gottschalch, Metal organic vapour phase epitaxial growth and characterization of (GaIn)P layers grown with different P-containing precursors 196 (1999) 33
Pilkington, S.J. and M. Missous, The growth of epitaxial aluminium on As containing compound semiconductors 196 (1999) 1
Pines, V., A. Chait, M. Zlatkowski and C. Beckermann, Equiaxed dendritic solidification in supercooled melts 197 (1999) 355
Piqueras, J., see Plaza, J.L. 198/199 (1999) 379
Pistol, M.-E., see Carlsson, N. 191 (1998) 347
Pitt, A.D., see Lane, P.A. 192 (1998) 423
Placzek-Popko, E., see Szatkowski, J. 197 (1999) 684
Platen, J., see Pristovsek, M. 195 (1998) 1
Plaza, J.L., P. Hidalgo, B. Méndez, J. Piqueras, J.L. Castaño and E. Diéguez, Effect of Er dopant in GaSb bulk crystals grown by vertical Bridgman technique 198/199 (1999) 379
Pletser, V., J. Stapelmann, L. Potthast and R. Bosch, The Protein Crystallization Diagnostics Facility, a new European instrument to investigate biological macromolecular crystal growth on board the International Space Station 196 (1999) 638

Plomp, M., A.J. Nijdam and W.J.P. van Enckevort, The structure of coarse crystal surfaces: the (0 0 $\bar{1}$) face of $K_2Cr_2O_7$ crystals grown from aqueous solution as an example 193 (1998) 389

Plomp, M., K. Maiwa and W.J.P. van Enckevort, Atomic force microscopy observations of hollow cores on the {1 1 1} and {1 0 0} faces of barium nitrate 198/199 (1999) 246

Ploog, K., see Yang, Q.K. 192 (1998) 28

Pohl, U.W., R. Engelhardt, V. Türck and D. Bimberg, MOCVD of vertically stacked CdSe/ZnSSe quantum islands 195 (1998) 569

Poindessous, G., see Gabrielli, C. 200 (1999) 236

Poirier, D.R., see Felicelli, S.D. 191 (1998) 879

Polosan, S., see Vasile, E. 198/199 (1999) 806

Polovko, Yu.A., V.V. Sazonov and V.S. Yuferev, Effect of spacecraft rotation on convection and impurity segregation during the growth of crystals from a melt under microgravity 198/199 (1999) 182

Pompe, O. and M. Rettenmayr, Microstructural changes during quenching 192 (1998) 300

Popov, R.G., see Liszi, I. 198/199 (1999) 1330

Popp, M., see Kröner, P. 195 (1998) 660

Porowski, S., see Prystawko, P. 198/199 (1999) 1061

Porsche, J., A. Ruf, M. Geiger and F. Scholz, Size control of self-assembled InP/GaInP quantum islands 195 (1998) 591

Porteanu, H., see Lifshitz, E. 196 (1999) 126

Porteanu, H., see Litvin, I.D. 198/199 (1999) 313

Post, G., see Décobert, J. 195 (1998) 681

Postnova, L.I., see Yakimovich, V.N. 198/199 (1999) 975

Postnova, L.I., see Levchenko, V.I. 198/199 (1999) 980

Pötschke, J., see Busse, P. 193 (1998) 413

Potter, M.D.G., see Aitken, N.M. 198/199 (1999) 984

Potthast, L., see Pletser, V. 196 (1999) 638

Pracka, I., see Sokólska, I. 198/199 (1999) 521

Prasad, S.R., C. Mallika, T.J. Anderson and R. Narayanan, An electrochemical method to detect flow profiles during convection in liquid metals 198/199 (1999) 194

Prasad, V., see Zhang, T. 198/199 (1999) 141

Prasad, V., see Chen, Q.S. 198/199 (1999) 710

Prater, B.D., S.C. Tuller and L.J. Wilson, Simplex optimization of protein crystallization conditions 196 (1999) 674

Prause, J., see Flade, T. 198/199 (1999) 336

Pressel, K., see Dold, P. 192 (1998) 125

Prévot, I., see Sagnes, I. 195 (1998) 524

Price, M.W., R.N. Scripa, S.L. Lehoczky, F.R. Szofran and C.-H. Su, Directional solidification and characterization of $Hg_{0.89}Mn_{0.11}Te$ 198/199 (1999) 297

Price, M.W., R.N. Scripa, S.L. Lehoczky and F.R. Szofran, Differential thermal analysis of $Hg_{1-x}Mn_xTe$ alloys in the x = 0–0.3 range 198/199 (1999) 303

Prieto, M., see Fernández-González, A. 200 (1999) 227

Přikryl, P., see Ivlev, G. 198/199 (1999) 1066

Prince, K.E., see Li, G. 191 (1998) 357

Prince, R.H., see Chen, Y. 193 (1998) 342

Pristovsek, M., H. Menhal, T. Wehnert, J.-T. Zettler, T. Schmidtling, N. Esser, W. Richter, C. Setzer, J. Platen and K. Jacobi, Reconstructions of the GaAs (1 1 3) surface 195 (1998) 1

Pristovsek, M., see Zettler, J.-T. 195 (1998) 151

Pristovsek, M., see Hardtdegen, H. 195 (1998) 211

Prost, W., see Velling, P. 195 (1998) 117

Prost, W., see Velling, P. 195 (1998) 490

Protzmann, H., see Leu, S. 195 (1998) 91

Protzmann, H., see Beccard, R. 198/199 (1999) 1049

Prystawko, P., M. Leszczyński, A. Śliwiński, H. Teisseyre, T. Suski, M. Boćkowski, J. Domagała, C. Kirchner, A. Pelzmann, M. Schauler and M. Kamp, Epitaxy of ternary nitrides on GaN single crystals 198/199 (1999) 1061

Prywer, J., Theoretical analysis of changes in habit of growing crystals in response to variable growth rates of individual faces 197 (1999) 271

Pschorr-Schoberer, E., see Hahn, B. 191 (1998) 65

Pudda, C., see Papaioannou, V. 194 (1998) 342

Pusey, M.L., see Forsythe, E.L. 196 (1999) 332

Pushkarev, A.V., see Shiryaev, S.V. 198/199 (1999) 631

Pushkarev, A.V., see Barilo, S.N. 198/199 (1999) 636

Pusztai, A., see Kurz, M. 198/199 (1999) 101

Pusztai, A., see Böttcher, K. 198/199 (1999) 349

Püttjer, D., see Behres, A. 195 (1998) 373

Pylneva, N.A., N.G. Kononova, A.M. Yurkin, G.G. Bazarova and V.I. Danilov, Growth and non-linear optical properties of lithium triborate crystals 198/199 (1999) 546

Pysarevsky, V., see Zaginey, A. 194 (1998) 317

Qhalid Fareed, R.S., see Wang, J. 200 (1999) 85

Qhalid Fareed, R.S., S. Tottori, K. Nishino and S. Sakai, Surface morphology studies on sublimation grown GaN by atomic force microscopy 200 (1999) 348

Qi, M., see Chen, J.X. 193 (1998) 28

Qian, J.-J., see Liu, F.-Q. 197 (1999) 789

Qiu Rongsheng, see Xu Ke 193 (1998) 127
Qiu, W., see Zhu, D.-W. 196 (1999) 356
Qiu, X.H., see Gong, Q. 192 (1998) 376
Que, D., see Liu, C. 196 (1999) 111
Que, D.L., see Wu, H.Z. 191 (1998) 72
Quon, D.H.H., see Saghir, M.Z. 193 (1998) 623

Rabadanov, M.R., see Ataev, B.M. 198/199 (1999) 1222
Radamson, H.H., see Syväjärvi, M. 197 (1999) 147
Radhakrishnan, K., see Yoon, S.F. 191 (1998) 24
Radhakrishnan, K., see Yoon, S.F. 193 (1998) 285
Radhakrishnan, K., see Zheng, H.Q. 197 (1999) 762
Raghothamachar, B., see Dudley, M. 192 (1998) 1
Rai, R.N., see Rai, U.S. 191 (1998) 234
Rai, U.S. and R.N. Rai, Physical chemistry of the organic analog of metal–metal eutectic and monotectic alloys 191 (1998) 234
Rainforth, W.M., see Hawksworth, A. 197 (1999) 286
Raisch, P., see Winterhoff, R. 195 (1998) 132
Rak, D.M., see Luft, J.R. 196 (1999) 447
Rak, D.M., see Luft, J.R. 196 (1999) 450
Rak, M., see Kuznetsov, V.A. 193 (1998) 164
Rak, M., Influence of the back-stress effect on the interstep distance and on the surface supersaturation 193 (1998) 189
Rak, M., X. Gui and D. de Cogan, Transient analysis of surface supersaturation after crystal face submersion using the analytical and transmission-line matrix (TLM) methods 197 (1999) 944
Ramakrishna Reddy, K.T., see Miles, R.W. 198/199 (1999) 316
Ramakrishnan, A., see Obloh, H. 195 (1998) 270
Raman, A., see Shi, W. 197 (1999) 89
Ramasamy, P., see Senguttuvan, N. 191 (1998) 130
Ramasamy, P., see Sankaranarayanan, K. 193 (1998) 252
Ramasamy, P., see Shanthi, S. 194 (1998) 369
Ramasamy, P., see Kumaragurubaran, S. 197 (1999) 210
Ramasamy, P., see Ushasree, P.M. 197 (1999) 216
Ramasamy, P., see Shanthi, S. 197 (1999) 858
Ramasamy, P., see Kumaresan, R. 198/199 (1999) 1165
Ramasamy, P., see Mohan, P. 200 (1999) 96
Ramasamy, P., see Jeganathan, K. 200 (1999) 341
Ramaz, F., see Briat, B. 197 (1999) 724
Raming, G., see Mühlbauer, A. 198/199 (1999) 107
Ramírez-Piscina, L., see González-Cinca, R. 193 (1998) 712
Ramsland, P.A., see Edmundson, A.B. 196 (1999) 276
Rappl, P.H.O., H. Closs, S.O. Ferreira, E. Abramof, C. Boschetti, P. Motisuke, A.Y. Ueta and I.N. Bandeira, Molecular beam epitaxial growth of high quality $Pb_{1-x}Sn_xTe$ layers with $0 \leqslant x \leqslant 1$ 191 (1998) 466
Rappoli, B.J., see DeSisto, W.J. 191 (1998) 290
Raransky, M.D., see Korbutyak, D.V. 197 (1999) 659
Rasmuson, Å.C., see Holmbäck, X. 198/199 (1999) 780
Rasmuson, Å.C., see Granberg, R.A. 198/199 (1999) 1287
Rastegaev, V.P., see Avrov, D.D. 198/199 (1999) 1011
Ratajczak, J., see Strupiński, W. 195 (1998) 474
Ratke, L., see Alkemper, J. 191 (1998) 252
Raukas, M., see Lott, K. 197 (1999) 489
Ravikumar, M., see Murthy, R.V.A. 197 (1999) 865
Raz, O., see Shimony, Y. 198/199 (1999) 583
Rebey, A., L. Béji, B. El Jani and P. Gibart, Optical monitoring of the growth rate reduction by CCl_4 during metalorganic vapour-phase epitaxy deposition of carbon doped GaAs 191 (1998) 734
Rebey, A., A. Bchetnia and B. El Jani, Etching of GaAs by CCl_4 and VCl_4 in a metalorganic vapor-phase epitaxy reactor 194 (1998) 286
Rebey, A., A. Bchetnia, Ch. Benjeddou, B. El Jani and P. Gibart, New vanadium dopant precursor for GaAs growth by metalorganic vapor-phase epitaxy 194 (1998) 292
Recha, S., see Dold, P. 192 (1998) 125
Rechenberg, I., see Hofmann, L. 195 (1998) 485
Reedy, R., see Friedman, D.J. 195 (1998) 438
Reedy, Jr., R.C., see Bertness, K.A. 196 (1999) 13
Reeves, C.L., see Lane, P.A. 192 (1998) 423
Reeves, R.R., see Naik, M.B. 193 (1998) 133
Regal, R., see Zumbiehl, A. 197 (1999) 650
Regel, L.L., see Skudarnov, P.V. 193 (1998) 219
Regula, M., C. Ballif and F. Lévy, In situ TEM observation of nickel promoted WS_2 thin-film crystallization 193 (1998) 109
Reier, F.W., see Franke, D. 195 (1998) 112
Reig, C., see Sochinskii, N.V. 192 (1998) 342
Reig, C., N.V. Sochinskii and V. Muñoz, Low-pressure synthesis and Bridgman growth of $Hg_{1-x}Mn_xTe$ 197 (1999) 688
Reimann, K., see Haselhoff, M. 196 (1999) 135
Reinhold, Th., see Flade, T. 198/199 (1999) 336
Reinhold, Th., see Korb, J. 198/199 (1999) 343
Reinitz, I.M., see Lu, T. 193 (1998) 577
Reislöhner, U., N. Achtziger and W. Witthuhn, Investigation of indium-defect pairs in CdTe by PAC spectroscopy 197 (1999) 576
Reithmaier, J.P., see Höfling, E. 191 (1998) 607
Rek, Z.U., see Tanaka, T. 192 (1998) 141
Remón, A., see Garcia, J.A. 191 (1998) 685
Remón, A., see Garcia, J.A. 197 (1999) 794
Ren, B., see Liu, C. 196 (1999) 111
Ren, H.-W., see Lee, J.-S. 200 (1999) 77

Ren, Y.C., see Chen, J.X. 193 (1998) 28
Rettenmayr, M., see Pompe, O. 192 (1998) 300
Rettig, R., see Ellmers, C. 195 (1998) 630
Revcolevschi, A., see Ammerahl, U. 193 (1998) 55
Revcolevschi, A., see Ammerahl, U. 197 (1999) 825
Revcolevschi, A., U. Ammerahl and G. Dhalenne, Crystal growth of pure and substituted low-dimensionality cuprates $CuGeO_3$, La_2CuO_4, $SrCuO_2$, Sr_2CuO_3 and $Sr_{14}Cu_{24}O_{41}$ by the floating zone and travelling solvent zone methods 198/199 (1999) 593
Reviakine, I., see Brisson, A. 196 (1999) 456
Rex, S., see Kauerauf, B. 193 (1998) 701
Reyhani, M.M., S. Freij and G.M. Parkinson, In situ atomic force microscopy investigation of the growth of secondary nuclei produced by contact of different growth faces of potash alum crystals under supersaturated solutions 198/199 (1999) 258
Reynolds, Jr., C.L., see Henderson, R. 194 (1998) 8
Reza, A., see Shvanskaya, L. 198/199 (1999) 600
Reza, A., see Leonyuk, L. 198/199 (1999) 619
Reza, A., see Maltsev, V. 198/199 (1999) 626
Ricci, E., see Eustathopoulos, N. 191 (1998) 268
Rich, D.H., see Kobayashi, J.T. 195 (1998) 252
Richter, E., see Kurpas, P. 195 (1998) 217
Richter, S., see Lyahovitskaya, V. 197 (1999) 177
Richter, W., see Pristovsek, M. 195 (1998) 1
Richter, W., see Zettler, J.-T. 195 (1998) 151
Richter, W., see Hardtdegen, H. 195 (1998) 211
Richter, W., see Zorn, M. 195 (1998) 223
Richter, W., see Steimetz, E. 195 (1998) 530
Richter, W., see Schenk, H.P.D. 200 (1999) 45
Rieger, J., see Kröner, P. 195 (1998) 660
Riemann, H., see Mühlbauer, A. 198/199 (1999) 107
Riès-Kautt, M., see Tardieu, A. 196 (1999) 193
Riès-Kautt, M., see Fourme, R. 196 (1999) 535
Righi, L., see Koporulina, E.V. 198/199 (1999) 460
Rijkeboer, A., see Sweegers, C. 197 (1999) 244
Riman, R.E., see Gelabert, M.C. 197 (1999) 195
Rinaldi, R., see Passaseo, A. 197 (1999) 777
Ristic, R.I., see Takiyama, H. 192 (1998) 439
Ritter, S., K. Diederichs, I. Frey, A. Berg, J. Keul and M.W. Baumstark, Crystallization of human low density lipoprotein (LDL), a large lipid–protein complex. Collection of X-ray data at very low resolution 196 (1999) 344
Rivera-Alvarez, Z., see López-López, M. 193 (1998) 528
Rivière, A., see Lemasson, P. 197 (1999) 462
Rivoallant, A., see Duffar, T. 192 (1998) 63
Rizzi, A., see Gerthsen, D. 200 (1999) 353
Robert, M.C., see Vidal, O. 192 (1998) 257
Robert, M.C., see Vidal, O. 192 (1998) 271
Robert, M.C., see Vidal, O. 196 (1999) 559
Roberts, J.S., J.P.R. David, L. Smith and P.L. Tihanyi, The influence of trimethylindium impurities on the performance of InAlGaAs single quantum well lasers 195 (1998) 668
Roberts, K.J., see Johnstone, J. 198/199 (1999) 275
Roberts, K.J., see Hennessy, A.J. 198/199 (1999) 830
Robinson, B.J., see LaPierre, R.R. 191 (1998) 319
Rocabois, P., J. Lehmann, H. Gaye and M. Wintz, Kinetics of precipitation of non-metallic inclusions during solidification of steel 198/199 (1999) 838
Rodewald, M., see Buschmann, V. 191 (1998) 430
Rodgers, A., see Bretherton, T. 192 (1998) 448
Rodier, F., see Bancel, P.A. 191 (1998) 537
Rodier, F., see Bancel, P.A. 196 (1999) 685
Rodriguez-Clemente, R., see Domingo, C. 198/199 (1999) 760
Rodríguez-Romero, A., see Moreno, A. 196 (1999) 587
Rodriguez-Viejo, J., see Heine, J.R. 195 (1998) 564
Rogalla, M., see Fiederle, M. 197 (1999) 635
Roger, J.P., see Rzepka, E. 197 (1999) 480
Rogers, K.D., see Lane, D.W. 197 (1999) 743
Rogin, P., G. Huber and J. Hulliger, $LiYF_4$ liquid-phase epitaxy using an inverted slider geometry 198/199 (1999) 564
Röhrich, J., see Birkholz, M. 197 (1999) 571
Röhrich, J., see Oertel, J. 198/199 (1999) 1205
Rojo, J.C. and J.J. Derby, On the formation of rotational spoke patterns during the Czochralski growth of bismuth silicon oxide 198/199 (1999) 154
Rojo, J.C., E. Diéguez and J.J. Derby, A heat shield to control thermal gradients, melt convection, and interface shape during shouldering in Czochralski oxide growth 200 (1999) 329
Romani, S., see Lane, D.W. 197 (1999) 743
Romann, A., see di Forte-Poisson, M.A. 195 (1998) 314
Romeo, M., see Dentel, D. 191 (1998) 697
Rondeau, G., see Décobert, J. 195 (1998) 681
Rondón, D., see Otálora, F. 196 (1999) 649
Rongen, R.T.H., see Verschuren, C.A. 200 (1999) 19
Rosch, W., see Singh, N.B. 198/199 (1999) 588
Rosch, W., see Barber, P. 198/199 (1999) 815
Rosch, W., see Seidensticker, R.G. 198/199 (1999) 988
Rosch, W., see Singh, N.B. 198/199 (1999) 995
Rose, D., see Szczerbakow, A. 191 (1998) 673
Rose, J., see Carter, D.C. 196 (1999) 610
Rosemeier, R.D., see Burger, A. 198/199 (1999) 872
Rosenberg, J., see Carter, D.C. 196 (1999) 610
Rosenberger, F., see Vekilov, P.G. 196 (1999) 261
Rosenberger, F., see Carter, D.C. 196 (1999) 623
Rosov, N., see Barilo, S.N. 198/199 (1999) 636

Rosset, R., see Gabrielli, C. 200 (1999) 236
Rossiter, D.S., P.D. Fawell, D. Ilievski and G.M. Parkinson, Investigation of the unseeded nucleation of Gibbsite, $Al(OH)_3$, from synthetic bayer liquors 191 (1998) 525
Rossolenko, S.N., see Kurlov, V.N. 191 (1998) 520
Rossolenko, S.N., see Borodin, V.A. 198/199 (1999) 201
Rost, H.-J., see Schulz, D. 198/199 (1999) 1024
Rotstein, H.G., S. Brandon and A. Novick-Cohen, Hyperbolic flow by mean curvature 198/199 (1999) 1256
Rotstein, H.G., A. Nepomnyashchy and A. Novick-Cohen, Hyperbolic non-conserved phase field equations 198/199 (1999) 1262
Rouleau, C.M., see Park, J.-W. 193 (1998) 516
Rousseau, R.W., see Givand, J.C. 194 (1998) 228
Rousseau, R.W., see Paxton, T.E. 198/199 (1999) 656
Rousseau, R.W., see Givand, J.C. 198/199 (1999) 1340
Roussel, J.-M., A. Saúl, G. Tréglia and B. Legrand, Theoretical prediction of new dissolution modes during metal heteroepitaxy 198/199 (1999) 83
Route, R.K., see Lee, M. 193 (1998) 347
Rowen, M., see Tanaka, T. 192 (1998) 141
Roy, M.-O., see Boyer, M. 196 (1999) 185
Rozsa, R., see Zaitseva, N. 197 (1999) 911
Rubbo, M. and D. Aquilano, On the calculation of specific free energy of step edges in ionic crystals 194 (1998) 156
Ruble, J.R., see Carter, D.C. 196 (1999) 602
Ruble, J.R., see Carter, D.C. 196 (1999) 610
Ruble, J.R., see Carter, D.C. 196 (1999) 623
Ruda, H.E., see Mei, X. 193 (1998) 148
Rudenskaya, G.N., see Kuranova, I.P. 196 (1999) 313
Rudolph, P., see Sato, J. 191 (1998) 746
Rudolph, P. and M. Jurisch, Bulk growth of GaAs. An overview 198/199 (1999) 325
Rudolph, P., see Böttcher, K. 198/199 (1999) 349
Ruf, A., see Porsche, J. 195 (1998) 591
Rühle, W.W., see Ellmers, C. 195 (1998) 630
Runkel, M., see Zaitseva, N. 197 (1999) 911
Rybakov, V., see Leonyuk, L. 198/199 (1999) 619
Ryon, R., see Zaitseva, N. 197 (1999) 911
Ryu, G. and C.S. Yoon, Seeded supercooled melt growth and polar morphology of organic nonlinear optical crystal, meta-nitroaniline (mNA) 191 (1998) 190
Ryu, G., C.S. Yoon, T.P.J. Han and H.G. Gallagher, Growth and characterisation of $CsLiB_6O_{10}$ (CLBO) crystals 191 (1998) 492
Ryu, H., see Lee, H.J. 191 (1998) 621
Ryu, Y.-H., see Leem, J.-Y. 193 (1998) 491
Ryzhikov, V., see Atroshchenko, L.V. 197 (1999) 471
Ryzhikov, V., see Atroshchenko, L.V. 197 (1999) 475
Ryzhikov, V., V. Chernikov, L. Gal'chinetskii, S. Galkin, E. Lisetskaya, A. Opolonin and V. Volkov, The use of semiconductor scintillation crystals $A^{II}B^{VI}$ in radiation instruments 197 (1999) 655
Ryzhikov, V., see Atroshchenko, L. 198/199 (1999) 292
Ryzhikov, V., see Nagornaya, L. 198/199 (1999) 877
Ryzhikov, V., see Burachas, S. 198/199 (1999) 881
Rzepka, E., J.P. Roger, P. Lemasson and R. Triboulet, Optical transmission of ZnSe crystals grown by solid phase recrystallization 197 (1999) 480

Saad, M., see Weiss, T. 198/199 (1999) 1190
Sabharwal, S.C. and Sangeeta, Study of growth imperfections, optical absorption, thermoluminescence and radiation hardness of $CdWO_4$ crystals 200 (1999) 191
Sada, C., see Bermúdez, V. 191 (1998) 589
Saghir, M.Z., M.R. Islam, N. Maffei and D.H.H. Quon, Three-dimensional modeling of $Bi_{12}GeO_{20}$ using the float zone technique 193 (1998) 623
Sagnes, I., I. Prévot, G. Patriarche, G. Le Roux, B. Gayral, A. Lemaître and J.M. Gérard, High-quality InAs/GaAs quantum dots grown by low-pressure metalorganic vapor-phase epitaxy 195 (1998) 524
Saito, H., T. Makimoto and N. Kobayashi, MOVPE growth of strained InGaAsN/GaAs quantum wells 195 (1998) 416
Saito, H., see Inoue, R. 198/199 (1999) 1196
Saito, T., M. Kameta, K. Kusakabe, S. Morooka, H. Maeda, Y. Hayashi, T. Asano and A. Kawahara, Morphology and semiconducting properties of homoepitaxially grown phosphorus-doped (1 0 0) and (1 1 1) diamond films by microwave plasma-assisted chemical vapor deposition using triethylphosphine as a dopant source 191 (1998) 723
Saito, Y., see Kaito, C. 200 (1999) 271
Sakaguchi, H., see Shibata, M. 196 (1999) 47
Sakaguchi, T., see Honda, T. 195 (1998) 319
Sakai, H., see Kaigawa, K. 191 (1998) 119
Sakai, H., see Kodama, S. 194 (1998) 166
Sakai, R., see Katsumata, T. 198/199 (1999) 869
Sakai, S., see Wang, J. 197 (1999) 48
Sakai, S., see Wang, J. 200 (1999) 85

Sakai, S., see Migita, S. 200 (1999) 161
Sakai, S., see Qhalid Fareed, R.S. 200 (1999) 348
Sakakibara, N., see Ueno, Y. 197 (1999) 376
Sakamoto, H., see Lin, H. 192 (1998) 250
Sakamoto, H., see Hirose, F. 196 (1999) 115
Sakamoto, T., see Yoshimura, J. 191 (1998) 483
Sakata, Y., see Koui, T. 195 (1998) 503
Sakurazawa, S., T. Kubota and M. Ataka, Orientation of protein crystals grown in a magnetic field 196 (1999) 325
Salamanca-Riba, L., see Bhat, R. 195 (1998) 427
Salamatin, A.N., T. Hondoh, T. Uchida and V.Y. Lipenkov, Post-nucleation conversion of an air bubble to clathrate air–hydrate crystal in ice 193 (1998) 197
Salamone, A., see Sgualdino, G. 192 (1998) 290
Salazar-Hernández, B., see Constantino, M.E. 194 (1998) 301
Salazar-Hernández, B., M.A. Vidal, M.E. Constantino, H. Navarro-Contreras, R. Asomoza and A. Merkulov, Structural study of metastable $(GaAs)_{1-x}(Ge_2)_x$ thin films grown by RF magnetron sputtering 197 (1999) 783
Salviati, G., see Henderson, R. 194 (1998) 8
Salzmann, A., see Leu, S. 195 (1998) 98
Sambanis, A., see Paxton, T.E. 198/199 (1999) 656
Samojlenkov, S., see Kleptsyn, V. 196 (1999) 122
Samuelson, L., see Carlsson, N. 191 (1998) 347
Samuelson, L., see Johansson, J. 195 (1998) 546
Sanada, M., I.L. Maksimov and K. Nishioka, Transient kinetics of the runaway nucleation 198/199 (1999) 67
Sanaka, Y., see Okuyama, H. 193 (1998) 43
Sánchez, F., see Trtík, V. 192 (1998) 175
Sánchez, J.J., O. Marty, M. Hopkinson, I. Izpura, A. Guzmán and J.M.G. Tijero, Structural and morphological characteristics of InGaAs/GaAs quantum well structures on tilted (1 1 1)B GaAs grown by MBE 192 (1998) 363
Sandström, P., E.B. Svedberg, J. Birch and J.-E. Sundgren, Structure and surface morphology of epitaxial Ni films grown on MgO(1 1 1) substrates: growth of high quality single domain films 197 (1999) 849
Sangaletti, L., B. Allieri, L.E. Depero, M. Bettinelli, K. Lebbou and R. Moncorgé, Search for impurity phases of Nd^{3+}:YVO_4 crystals for laser and luminescence applications 198/199 (1999) 454
Sangaletti, L., see Depero, L.E. 198/199 (1999) 516
Sangaletti, L., L.E. Depero, G. Sberveglieri, B. Allieri, E. Bontempi and S. Groppelli, Growth of WO_3 crystals from W–Ti–O thin films 198/199 (1999) 1240
Sangeeta, see Sabharwal, S.C. 200 (1999) 191
Sangwal, K., On the mechanism of crystal growth from solutions 192 (1998) 200
Sangwal, K., J. Borc and T. Pałczyńska, On the growth hillock vicinality and normal growth rates of the (1 0 1) face of KDP crystals 194 (1998) 214
Sanjoh, A. and T. Tsukihara, Spatiotemporal protein crystal growth studies using microfluidic silicon devices 196 (1999) 691
Sankaranarayanan, K. and P. Ramasamy, Microtube-Czochralski technique (μT-CZ): a novel way of seeding the melt to grow bulk single crystal 193 (1998) 252
Santailler, J.L., see Boiton, P. 194 (1998) 43
Santailler, J.L., see Barvinschi, F. 198/199 (1999) 239
Santhanaraghavan, P., see Mohan, P. 200 (1999) 96
Santo, A.M.E., S.L. Baldochi and S.P. Morato, Zone-melting study of $LiSrAlF_6$ and $LiSrAlF_6:Cr^{3+}$ by thermal analysis 198/199 (1999) 466
Sanz-Hervás, A., S. Cho, J. Kim, A. Majerfeld, C. Villar and B.W. Kim, Effect of the growth parameters on the luminescence properties of high-quality GaAs/AlGaAs multiquantum wells on (1 1 1)A substrates by metal organic vapor phase epitaxy 195 (1998) 558
Saotome, K., see Honda, T. 195 (1998) 319
Sapundzhiev, Ts.J., see Liszi, I. 198/199 (1999) 1330
Saravanan, S., K. Jeganathan, K. Baskar, T. Jimbo, T. Soga and M. Umeno, Crystal growth of high quality hybrid GaAs heteroepitaxial layers on Si substrate by metalorganic chemical vapor deposition and liquid phase epitaxy 192 (1998) 23
Saravanan, S., see Jeganathan, K. 200 (1999) 341
Sarin Kumar A.K., see Watanabe, N. 195 (1998) 48
Sarti, D., see Dour, G. 193 (1998) 230
Sarukura, N., see Shimamura, K. 197 (1999) 896
Sasaki, A., see Nabetani, Y. 193 (1998) 470
Sasaki, H., see Soga, T. 196 (1999) 291
Sasaki, T., see Mori, K. 195 (1998) 466
Sasaki, T., see Furuya, H. 198/199 (1999) 560
Sasaki, T., see Adachi, H. 198/199 (1999) 568
Sasaki, T., see Yap, Y.K. 198/199 (1999) 1028
Sasaki, Y., see Koui, T. 195 (1998) 503
Sass, T., see Pietzonka, I. 195 (1998) 21
Sass, T., see Pietzonka, I. 196 (1999) 33
Sato, A., see Kubota, N. 196 (1999) 156

Sato, J., H. Takeda, H. Morikoshi, K. Shimamura, P. Rudolph and T. Fukuda, Czochralski growth of $RE_3Ga_5SiO_{14}$ (RE = La, Pr, Nd) single crystals for the analysis of the influence of rare earth substitution on piezoelectricity 191 (1998) 746
Sato, K., see Takiguchi, H. 193 (1998) 641
Sato, K., see Kaneko, N. 197 (1999) 263
Sato, K., Y. Seki, Y. Matsuda and O. Oda, Recent developments in II–VI substrates 197 (1999) 413
Sato, K., see Ueno, S. 198/199 (1999) 1326
Sato, M. and M. Uwaha, Change of wandering pattern with anisotropy in step kinetics 198/199 (1999) 38
Sato, S. and S. Satoh, Metalorganic chemical vapor deposition of GaInNAs lattice matched to GaAs for long-wavelength laser diodes 192 (1998) 381
Sato, S., see Miyamoto, T. 195 (1998) 421
Sato, T.J., T. Hirano and A.P. Tsai, Single-crystal growth of the decagonal Al–Ni–Co quasicrystal 191 (1998) 545
Sato, T.J., see Guo, J.Q. 197 (1999) 963
Satoh, H., see Sekijima, T. 193 (1998) 446
Satoh, S., see Sato, S. 192 (1998) 381
Satre, P., see Mansori, M. 197 (1999) 141
Saúl, A., see Roussel, J.-M. 198/199 (1999) 83
Sauter, C., J.D. Ng, B. Lorber, G. Keith, P. Brion, M.W. Hosseini, J.-M. Lehn and R. Giegé, Additives for the crystallization of proteins and nucleic acids 196 (1999) 365
Savage, D.E., see Li, J. 195 (1998) 617
Savchuk, A.I., V.I. Fediv, V.M. Frasunyak, I.D. Stolyarchuk and P.I. Nikitin, Enhancement of magneto-optical effects in ZnHgMnTe solid solutions 197 (1999) 698
Savitskiy, A., see Panchuk, O. 197 (1999) 607
Savitsky, A.V., M.I. Ilashchuk, O.A. Parfenyuk, R.D. Ivanchuk, D.D. Ivanchuk, K.S. Ulyanytsky and V.R. Burachek, Improvement of quality of $Cd_{1-x}Mn_xTe$ crystals by special annealing 192 (1998) 196
Savitsky, V., see Zaginey, A. 194 (1998) 317
Sawada, K., see Nabetani, Y. 193 (1998) 470
Sawada, T., K. Takemura, K. Shigematsu, S. Yoda and K. Kawasaki, Effects of gravity on a free dendrite of NH_4Cl grown by dynamic pressure control 191 (1998) 225
Sazaki, G., Y. Nagatoshi, Y. Suzuki, S.D. Durbin, S. Miyashita, T. Nakada and H. Komatsu, Solubility of tetragonal and orthorhombic lysozyme crystals under high pressure 196 (1999) 204
Sazaki, G., see Kurihara, K. 196 (1999) 285
Sazaki, G., see Yanagiya, S.-i. 196 (1999) 319
Sazaki, G., see Nakada, T. 196 (1999) 503
Sazonov, V.V., see Polovko, Yu.A. 198/199 (1999) 182
Sberveglieri, G., see Sangaletti, L. 198/199 (1999) 1240
Scalbert, D., see Siviniant, J. 197 (1999) 680
Schaaf, P., see Ngankam, P.A. 197 (1999) 927
Schäffer, C., see Buschmann, V. 191 (1998) 430
Schauler, M., see Prystawko, P. 198/199 (1999) 1061
Scheel, H.J., see Klemenz, C. 200 (1999) 435
Schelkin, Yu.F., see Lakeenkov, V.M. 197 (1999) 443
Schenk, H.P.D., G.D. Kipshidze, U. Kaiser, A. Fissel, J. Kräußlich, J. Schulze and Wo. Richter, Investigation of two-dimensional growth of AlN(0 0 0 1) on Si(1 1 1) by plasma-assisted molecular beam epitaxy 200 (1999) 45
Scherback, L., see Vacková, S. 197 (1999) 599
Schetzina, J.F., see Yu, Z. 195 (1998) 333
Schikora, D., see Lima, A.P. 197 (1999) 31
Schimmel, Th., see Belenchuk, A. 198/199 (1999) 1216
Schineller, B., A. Guttzeit, P.H. Lim, M. Schwambera, K. Heime, O. Schön and M. Heuken, The influence of Mg-concentration and carrier gas on the electrical and optical properties of GaN : Mg grown by MOVPE 195 (1998) 274
Schineller, B., see Schoen, O. 195 (1998) 297
Schlenker, D., see Miyamoto, T. 195 (1998) 421
Schlenker, D., T. Miyamoto, Z. Pan, F. Koyama and K. Iga, Miscibility gap calculation for $Ga_{1-x}In_xN_yAs_{1-y}$ including strain effects 196 (1999) 67
Schlotter, P., see Obloh, H. 195 (1998) 270
Schmidt, K., see Boeck, T. 198/199 (1999) 420
Schmidt, K., see Teubner, T. 198/199 (1999) 425
Schmidt, R., M. v.d. Ahe, Ch. Dieker, D. Gauer, H. Hardtdegen, T. Hauck, M. Luysberg, D. Meertens and D. Schmitz, Contributions to understanding the optical properties of partially ordered $(Al_{0.3}Ga_{0.7})_{0.52}In_{0.48}P$ 195 (1998) 124
Schmidtling, T., see Pristovsek, M. 195 (1998) 1
Schmitt, E., see Hofmann, D. 198/199 (1999) 1005
Schmitz, Ch., see Ostheimer, V. 198/199 (1999) 1184
Schmitz, D., see Schmidt, R. 195 (1998) 124
Schmitz, D., see Hardtdegen, H. 195 (1998) 211
Schmitz, D., see Schoen, O. 195 (1998) 297
Schmitz, D., see Beccard, R. 198/199 (1999) 1049
Schneider, H.-J., see Piechotka, M. 193 (1998) 80

Schneider, R., see Brecht, E. 191 (1998) 421
Schoen, O., M. Schwambera, B. Schineller, D. Schmitz, M. Heuken and H. Juergensen, High quality III-nitride material grown in mass production MOCVD systems 195 (1998) 297
Scholz, F., see Winterhoff, R. 195 (1998) 132
Scholz, F., see Off, J. 195 (1998) 286
Scholz, F., see Porsche, J. 195 (1998) 591
Scholz, K., H. Stiens and G. Müller-Vogt, Investigations on the effect of contacts on p-type CdTe DLTS-measurements 197 (1999) 586
Schön, O., see Schineller, B. 195 (1998) 274
Schönherr, E. and M. Freiberg, In situ observation of twin formation during the growth of ZnSe single crystals from the vapor phase 197 (1999) 455
Schönherr, E., see Lauck, R. 197 (1999) 513
Schöttker, B., see Lima, A.P. 197 (1999) 31
Schoutsen, M., see van Hoof, P.J.C.M. 192 (1998) 307
Schoutsen, M., see van Hoof, P.J.C.M. 193 (1998) 679
Schultz, L., see Behr, G. 198/199 (1999) 642
Schulz, D., G. Wagner, J. Dolle, K. Irmscher, T. Müller, H.-J. Rost, D.Siche and J. Wollweber, Impurity incorporation during sublimation growth of 6H bulk SiC 198/199 (1999) 1024
Schulz, O., see Gross, C. 198/199 (1999) 188
Schulze, J., see Schenk, H.P.D. 200 (1999) 45
Schumann, H., see Dadgar, A. 195 (1998) 69
Schunk, P., see Belenchuk, A. 198/199 (1999) 1216
Schurman, M., see Tran, C.A. 195 (1998) 397
Schwabe, R., see Pietzonka, I. 196 (1999) 33
Schwambera, M., see Schineller, B. 195 (1998) 274
Schwambera, M., see Schoen, O. 195 (1998) 297
Schweizer, M., see Cröll, A. 191 (1998) 365
Scripa, R.N., see Price, M.W. 198/199 (1999) 297
Scripa, R.N., see Price, M.W. 198/199 (1999) 303
Scripa, R.N., B. Wang, A. Gonzalez and R.R. Holmes, Chemical compatibility of vacuum plasma sprayed (VPS) metal cartridges with various semiconductor materials 198/199 (1999) 825
Sebaoun, A., see Mansori, M. 197 (1999) 141
Sebastian, J., see Bugge, F. 195 (1998) 676
Secu, M., see Iliescu, B. 198/199 (1999) 507
Segato, F., see Bermúdez, V. 191 (1998) 589
Segawa, Y., see Yaguchi, H. 195 (1998) 323
Seidensticker, R.G., W.R. Rosch, R. Mazelsky, R.H. Hopkins, N.B. Singh, S.R. Coriell, W.M.B. Duval and C. Batur, Active control of interface shape during the crystal growth of lead bromide 198/199 (1999) 988
Seifert, W., see Carlsson, N. 191 (1998) 347
Seifert, W., see Johansson, J. 195 (1998) 546
Seifert, W., J. Johansson, N. Carlsson, A. Gustafsson and J.-O. Malm, Continuous and discontinuous metal-organic vapour phase epitaxy of coherent self-assembled islands: effects on size homogeneity 197 (1999) 19
Seipel, K., see Ferguson, I.T. 195 (1998) 648
Sekerka, R.F., see Coriell, S.R. 191 (1998) 573
Sekerka, R.F., see Coriell, S.R. 200 (1999) 276
Seki, H., see Koukitu, A. 197 (1999) 99
Seki, H., see Koukitu, A. 198/199 (1999) 1111
Seki, M., see Ohshita, Y. 193 (1998) 322
Seki, Y., see Sato, K. 197 (1999) 413
Sekijima, T., H. Satoh, K. Tahara, T. Fujii, K. Wakino and M. Okada, Growth of fibrous YIG single crystals by the self-adjusting solvent FZ method 193 (1998) 446
Semenov, V.N., see Moest, B. 192 (1998) 410
Sen, S., B.K. Dhindaw, P.A. Curreri, P. Peters and W.F. Kaukler, Measurement of interfacial undercooling in a dilute Pb–Sn alloy near the regime of morphological instability 193 (1998) 692
Sénateur, J.P., see Abrutis, A. 191 (1998) 79
Senchenkov, A.S., I.V. Barmin, A.S. Tomson and V.V. Krapukhin, Seedless THM growth of $Cd_xHg_{1-x}Te$ ($x \approx 0.2$) single crystals within rotating magnetic field 197 (1999) 552
Senguttuvan, N., P. Mohan, S.M. Babu and P. Ramasamy, A study of the optical and mechanical properties of $PbWO_4$ single crystals 191 (1998) 130
Senguttuvan, N., see Mohan, P. 200 (1999) 96
Seo, A., see Shindo, H. 198/199 (1999) 253
Seo, W.S., see Lin, H. 192 (1998) 250
Seong, S., see Hwang, J. 200 (1999) 63
Serrano, M.D., see Duffar, T. 192 (1998) 63
Serrano, M.D., see Bermúdez, V. 198/199 (1999) 526
Serrano, M.D., see Bermúdez, V. 200 (1999) 185
Serrano, M.L., see Barata, P.A. 194 (1998) 101
Serrano, M.L., see Barata, P.A. 194 (1998) 109
Setzer, C., see Pristovsek, M. 195 (1998) 1
Seyssiecq, I., S. Veesler, G. Pèpe and R. Boistelle, The influence of additives on the crystal habit of gibbsite 196 (1999) 174
Sgualdino, G., D. Aquilano, G. Vaccari, G. Mantovani and A. Salamone, Growth morphology of sucrose crystals. The role of glucose and fructose as habit-modifiers 192 (1998) 290
Sha, Z.L., H. Alatalo, M. Louhi-Kultanen and S. Palosaari, Purification by crystallization from solutions of various viscosities 198/199 (1999) 692

Shakhova, K.V., see Panova, A.N. 198/199 (1999) 865
Shakirov, E.V., see Kuranova, I.P. 196 (1999) 313
Shang, G.Y., see Gong, Q. 192 (1998) 376
Shanthi, S., H. Anuratha, C. Subramanian and P. Ramasamy, Effect of fluorine doping on structural, electrical and optical properties of sprayed SnO_2 thin films 194 (1998) 369
Shanthi, S., C. Subramanian and P. Ramasamy, Growth and characterization of antimony doped tin oxide thin films 197 (1999) 858
Shapkin, P.V., see Korostelin, Yu.V. 197 (1999) 449
Shapoval, O., see Belenchuk, A. 198/199 (1999) 1216
Shcherbak, L., Pre-transition phenomena in CdTe near the melting point 197 (1999) 397
Shcherbak, L., see Panchuk, O. 197 (1999) 607
Shcherbin, K., see Briat, B. 197 (1999) 724
Shealy, J.R., see Wankerl, A. 191 (1998) 8
Sheintuch, M., see Efremenko, I. 198/199 (1999) 951
Shekunov, B.Yu., P. Taylor and J.G. Grossmann, Structural phenomena in hydrogel–drug systems 198/199 (1999) 1335
Shekunov, B.Yu., M. Hanna and P. York, Crystallization process in turbulent supercritical flows 198/199 (1999) 1345
Shen, D., see Yu, G. 196 (1999) 77
Shen, H.M., see Lu, C.J. 191 (1998) 113
Shen Xingda, see Zhang Shoudu 197 (1999) 901
Sher, A., see Mainzer, N. 197 (1999) 542
Sherwood, J.N., see Takiyama, H. 192 (1998) 439
Shevtsov, N.I., see Atroshchenko, L.V. 197 (1999) 471
Shevtsov, N.I., see Atroshchenko, L.W. 198/199 (1999) 292
Shi, B.Q. and C.W. Tu, Modeling study of silicon incorporation from $SiBr_4$ in GaAs layers grown by chemical beam epitaxy 195 (1998) 740
Shi, L.P., T.C. Chong and X.W. Xu, Growth and characteristics of Fe-doped $KTiOPO_4$ crystals 198/199 (1999) 551
Shi, W., D.H. Zhang, H.Q. Zheng, S.F. Yoon, C.H. Kam and A. Raman, Effects of arsenic beam equivalent pressure on InGaAsP grown by solid source molecular beam epitaxy with continuous white phosphorous production 197 (1999) 89
Shi, W., Z. Chen, N. Liu, Y. Zhou and S. Pan, Self-organized growth of complex oxide Ce : $BaTiO_3$ nano-islands on (1 0 0)MgO by pulsed laser ablation 197 (1999) 905
Shi, W., see Zhang, D.H. 198/199 (1999) 1141
Shiba, T., see Takemi, M. 191 (1998) 18
Shibata, M., T. Furuya, H. Sakaguchi and S. Kuma, Synthesis of gallium nitride by ammonia injection into gallium melt 196 (1999) 47
Shields, A.D., see Wang, W.S. 198/199 (1999) 578
Shigematsu, K., see Sawada, T. 191 (1998) 225
Shigetomi, T., see Ohmura, R. 196 (1999) 164
Shigley, J., see Lu, T., 193 (1998) 577
Shih, I., see Wang, H.P. 200 (1999) 137
Shilo, D., see Avrahami, Y. 198/199 (1999) 264
Shima, R., M. Folman, I. Brown and A. Hoffman, Effect of Ti ion implantation, abrasion with particles, and thin film evaporation on the formation of CVD diamond on Si substrates 198/199 (1999) 957
Shimamura, K., see Sato, J. 191 (1998) 746
Shimamura, K., see Ko, J.M. 192 (1998) 157
Shimamura, K., V.V. Kochurikhin, H. Takeda and T. Fukuda, Growth of Gd–Yb–Ga garnet single crystals with large lattice parameters as substrates for optical isolators 194 (1998) 203
Shimamura, K., H. Tabata, H. Takeda, V.V. Kochurikhin and T. Fukuda, Growth and characterization of $(La,Sr)(Al,Ta)O_3$ single crystals as substrates for GaN epitaxial growth 194 (1998) 209
Shimamura, K., see Takeda, H. 197 (1999) 204
Shimamura, K., N. Mujilatu, K. Nakano, S.L. Baldochi, Z. Liu, H. Ohtake, N. Sarukura and T. Fukuda, Growth and characterization of Ce-doped $LiCaAlF_6$ single crystals 197 (1999) 896
Shimamura, K., see Epelbaum, B.M. 198/199 (1999) 471
Shimamura, K., see Baldochi, S.L. 200 (1999) 521
Shimazu, T., see Tachibana, M. 198/199 (1999) 661
Shimizu, K., T. Nomura and K. Takahashi, Crystal size distribution of aluminum potassium sulfate in a batch crystallizer equipped with different types of impeller 191 (1998) 178
Shimizu, K., T. Nomura and K. Takahashi, Crystal size distribution of aluminum potassium sulfate in a profiled, a dished, or a flat bottom crystallizer equipped with a pitched paddle 191 (1998) 185
Shimizu, K., K. Takahashi, E. Suzuki and T. Nomura, Effect of baffle geometries on crystal size distribution of aluminum potassium sulfate in a seeded batch crystallizer 197 (1999) 921
Shimizu, M., see Tachibana, M. 198/199 (1999) 665

Shimokozono, M., see Kubota, E. 191 (1998) 501
Shimony, Y., G. Kimmel, O. Raz and M.P. Dariel, X-ray diffraction analysis of melt-grown $ZnGeP_2$ (ZGP) 198/199 (1999) 583
Shimoyama, H., see Zhao, X. 198/199 (1999) 934
Shin, Y.J., see Lee, H. 191 (1998) 59
Shindo, H., K. Shitagami, S. Kondo and A. Seo, Atomic force microscopic observation of directional layer growth and dissolution on surfaces of sulfate minerals 198/199 (1999) 253
Shinmura, M., see Aswal, D.K. 193 (1998) 61
Shinmura, M., see Aswal, D.K. 197 (1999) 379
Shinmura, M., see Aswal, D.K. 200 (1999) 427
Shintani, A., see Ishimaru, M. 194 (1998) 178
Shiohara, Y., see Nagashio, K. 200 (1999) 118
Shiraki, Y., see Yaguchi, H. 195 (1998) 323
Shiraki, Y., see Biwa, G. 195 (1998) 574
Shiraki, Y., see Wu, J. 197 (1999) 73
Shirasawa, T., see Honda, T. 195 (1998) 319
Shirinyan, G.O., see Petrosyan, A.G. 198/199 (1999) 492
Shirinyan, G.O., see Ovanesyan, K.L. 198/199 (1999) 497
Shiryaev, S.V., see Zhigunov, D.I. 198/199 (1999) 605
Shiryaev, S.V., S.N. Barilo, D.I. Zhigunov, V.V. Fedotova, A.V. Pushkarev, L.A. Kurochkin and A.G. Soldatov, Investigation of nucleation and epitaxial growth of $Ba_{1-x}K_xBiO_3$ films 198/199 (1999) 631
Shiryaev, S.V., see Barilo, S.N. 198/199 (1999) 636
Shiryaev, S.V., see Barilo, S.N. 198/199 (1999) 716
Shitagami, K., see Shindo, H. 198/199 (1999) 253
Shleguel, V., see Murthy, R.V.A. 197 (1999) 865
Shmatov, N.I., see Lakeenkov, V.M. 197 (1999) 443
Shneiderman, I.A., see Fedorov, A.G. 198/199 (1999) 1211
Shong, T.-W., see Chang, L.-B. 198/199 (1999) 1092
Shou, X., see Wu, H.Z. 191 (1998) 72
Shu, Z.-Y., H.-Y. Gong and R.-C. Bi, In situ measurement and dynamic control of the evaporation rate in vapor diffusion crystallization of proteins 192 (1998) 282
Shukri, Z.A. and C.H. Champness, Effect of nonstoichiometry on conductivity type in Bridgman-grown $CuInSe_2$ 191 (1998) 97
Shulyatev, D., S. Karabashev, A. Arsenov and Ya. Mukovskii, Growth and investigation of doped rare earth manganite single crystals 198/199 (1999) 511
Shvanskaya, L., L. Leonyuk, G.-J. Babonas and A. Reza, Structural features in Zn-doped 123-type single crystals 198/199 (1999) 600
Sica, F., S. Adinolfi, R. Berisio, C. De Lorenzo, L. Mazzarella, R. Piccoli, L. Vitagliano and A. Zagari, Crystallization of multiple forms of bovine seminal ribonuclease in the liganded and unliganded state 196 (1999) 305
Siche, D., see Schulz, D. 198/199 (1999) 1024
Sidorov, M.V., see Gao, Y. 191 (1998) 439
Sidorov, V.V., see Borodin, V.A. 198/199 (1999) 201
Sidorov, V.V., see Borodin, A.V. 198/199 (1999) 215
Sieranski, K., see Szatkowski, J. 197 (1999) 684
Siffert, P., see Fougères, P. 197 (1999) 641
Siffert, P., see Zerrai, A. 197 (1999) 646
Siffert, P., see Zumbiehl, A. 197 (1999) 650
Siffert, P., see Zumbiehl, A. 197 (1999) 670
Sigov, A.S., see Melnikov, A.A. 197 (1999) 666
Sik, H., Y. Le Bellego, P. Win, S. Bouchoule, G. Patriarche, P. Boulet, G. Le Mestreallan and A. Ougazzaden, Planar selective regrowth of high resistivity semi-insulating InP(Fe) by LP-MOVPE for buried lasers using TBP 195 (1998) 479
Silfvenius, C. and G. Landgren, Design, growth and performance of different QW structures for improved 1300 nm InGaAsP lasers 195 (1998) 700
Silier, I., see Konuma, M. 198/199 (1999) 1045
Silin, V.I., see Atroshchenko, L.V. 197 (1999) 471
Silin, V.I., see Atroshchenko, L.V. 197 (1999) 475
Silin, V.I., see Atroshchenko, L.V. 198/199 (1999) 292
Simonnet, A., see Brisson, O. 193 (1998) 597
Singh, N.B., D.R. Suhre, W. Rosch, R. Meyer, M. Marable, N.C. Fernelius, F.K. Hopkins, D.E. Zelmon and R. Narayanan, Modified GaSe crystals for mid-IR applications 198/199 (1999) 588
Singh, N.B., see Seidensticker, R.G. 198/199 (1999) 988
Singh, N.B., T. Henningsen, D.R. Suhre, W. Rosch, R.H. Hopkins, R. Mazelsky, S.R. Coriell and W.M.B. Duval, Hg_2Cl_2 crystals for efficient birefringence etalon filters 198/199 (1999) 995
Sipatov, A.Yu., see Fedorov, A.G. 198/199 (1999) 1211
Sirota, M., see Lifshitz, E. 196 (1999) 126
Şişman, H., see Bayender, B. 194 (1998) 119
Sitter, H., see Franc, J. 197 (1999) 593
Siviniant, J., N. Paganotto, A.V. Kavokin, D. Coquillat, D. Scalbert, J-P. Lascaray and J. Cibert, Negatively charged exciton formation in an asymmetric double CdTe/(Cd,Mn)Te QWs 197 (1999) 680
Skanthakumar, S., see Barilo, S.N. 198/199 (1999) 636
Skauli, T., see Maxey, C.D. 197 (1999) 427
Skoulika, S., see Domopoulou, A. 191 (1998) 166
Skudarnov, P.V., L.L. Regel and W.R. Wilcox, Visualization of convection in a simulated gradient freeze cell during centrifugation 193 (1998) 219

Slaoui, A., see Angermeier, D. 191 (1998) 386
Śliwiński, A., see Prystawko, P. 198/199 (1999) 1061
Smakhtin, L.A., see Zhigunov, D.I. 198/199 (1999) 605
Smeets, W.J.J., see ten Grotenhuis, E. 191 (1998) 834
Smirnitski, V.B., see Bugge, F. 195 (1998) 676
Smirnova, T.V., see Barilo, S.N. 198/199 (1999) 716
Smith, G.W., see Mizuno, K. 198/199 (1999) 1146
Smith, H.I., see Koontz, E.M. 198/199 (1999) 1104
Smith, L., see Roberts, J.S. 195 (1998) 668
Smith, T.L., see Fleischer, S. 196 (1999) 53
Smolsky, I., see Zaitseva, N. 197 (1999) 911
Snell, E.H., see Forsythe, E.L. 196 (1999) 332
Soares, L.S.M., M.A. Cotta, C.A.C. Mendonça, K.M. Ito-Landers and M.M.G. de Carvalho, Equilibrium shape and nucleation on InP(0 0 1) surfaces: effect of surface steps 191 (1998) 44
Sobotík, P. and I. Ošťádal, Temperature induced change of surface roughness of Au(1 1 1) epitaxial films on mica 197 (1999) 955
Sochinskii, N.V., C. Reig, V. Muñoz and J. Alamo, Vapor phase epitaxy of $Hg_{1-x}Cd_xI_2$ on sapphire 192 (1998) 342
Sochinskii, N.V., see Reig, C. 197 (1999) 688
Södervall, U., see Zhao, Q.X. 193 (1998) 328
Soerensen, G., see Gupta, J.A. 195 (1998) 205
Soga, T., see Saravanan, S. 192 (1998) 23
Soga, T., H. Sasaki, M. Tanokura and M. Ataka, Crystal growth and solubility studies of *Aspergillus niger* acid proteinase A in the presence of both a salt and an organic solvent 196 (1999) 291
Sohn, S.H., Interface Madelung constants for isoelectronic impurities: generalized Madelung constants 191 (1998) 143
Sokólska, I., I. Pracka and T. Łukasiewicz, Growth and spectroscopic properties of $LiNbO_3$ single crystals doped with Nd^{3+} and Yb^{3+} ions 198/199 (1999) 521
Soldatov, A.G., see Shiryaev, S.V. 198/199 (1999) 631
Solnyshkin, D.D., see Kovalenko, S.I. 191 (1998) 553
Son, J.-S., see Leem, J.-Y. 197 (1999) 84
Son, N.T., see Syväjärvi, M. 197 (1999) 147
Son, S.-J., see Lee, C.-R. 193 (1998) 300
Son, S.-J., see Leem, J.-Y. 193 (1998) 491
Son, S.-J., see Lee, C.-R. 197 (1999) 78
Song, J.-H., see Kim, Y.K. 192 (1998) 109
Song, J.J., see Considine, L. 195 (1998) 192
Song, Y.K., see Han, J. 195 (1998) 291
Song Youting, Zhang Daofan, Liu Hongbin, Zhou Tang, Fan Feidi, Yang Changxi, Zhu Yong and Wu Xing, Growth and characterization of $K_3Li_{2-x}Nb_{5+x}O_{15+2x}$ single crystals obtained by the edge-defined film-fed growth technique 194 (1998) 379
Song, Z., see Zeng, J. 197 (1999) 874
Sonin, V.M., see Chepurov, A.I. 198/199 (1999) 963
Soriano-García, M., see Moreno, A. 196 (1999) 587
Soto Urueta, J.A., see Jiménez-González, A.E. 192 (1998) 430
Souliere, V., see Dumont, H. 197 (1999) 755
Sous, S., see Alkemper, J. 191 (1998) 252
Spanos, N. and P.G. Koutsoukos, The transformation of vaterite to calcite: effect of the conditions of the solutions in contact with the mineral phase 191 (1998) 783
Speck, J.S., see Marchand, H. 195 (1998) 328
Spek, A.L., see ten Grotenhuis, E. 191 (1998) 834
Spencer, B.J. and H.E. Huppert, The relationship between dendrite tip characteristics and dendrite spacings in alloy directional solidification 200 (1999) 287
Spruytte, S., see Huang, T.F. 200 (1999) 362
Sreeramana Aithal, P., see Nagaraja, H.S. 193 (1998) 674
Srolovitz, D.J., see Battaile, C.C. 194 (1998) 353
Stafford, A., see Irvine, S.J.C. 197 (1999) 616
Stall, R., see Tran, C.A. 195 (1998) 397
Stall, R., see Ferguson, I.T. 195 (1998) 648
Stallings, W.C., see Stevens, A.M. 196 (1999) 350
Stallings, W.C., see Carter, D.C. 196 (1999) 610
Stampe, P.A. and R.J. Kennedy, X-ray characterization of MgO thin films grown by laser ablation on yttria-stabilized zirconia 191 (1998) 472
Stampe, P.A. and R.J. Kennedy, X-ray characterization of MgO thin films grown by laser ablation on $SrTiO_3$ and $LaAlO_3$ 191 (1998) 478
Stanculescu, A., F. Stanculescu and H. Alexandru, Melt growth and characterization of pure and doped meta-dinitrobenzene crystals 198/199 (1999) 572
Stanculescu, F., see Stanculescu, A. 198/199 (1999) 572
Stanna, H., see Piechotka, M. 193 (1998) 80
Stapelmann, J., see Pletser, V. 196 (1999) 638
Starostin, M.Yu., see Gurjiyants, P.A. 198/199 (1999) 227
Stefan, M., S.V. Nistor, D.C. Mateescu and A.M. Abakumov, Growth of pure and doped Rb_2ZnCl_4 and K_2ZnCl_4 single crystals by Czochralski technique 200 (1999) 148
Stegeman, R.A., see Stevens, A.M. 196 (1999) 350
Steimetz, E., T. Wehnert, K. Haberland, J.-T. Zettler and W. Richter, GaAs cap layer growth and In-segregation effects on self-assembled InAs-quantum dots monitored by optical techniques 195 (1998) 530

Steinkirchner, J., see Leu, S. 195 (1998) 91
Stenzel, C., see Gross, C. 198/199 (1999) 188
Stenzel, O., see Dadgar, A. 195 (1998) 69
Stepanov, S.I., see Cheng, T.S. 197 (1999) 12
Steriopolo, T.A., see Borodin, V.A. 198/199 (1999) 201
Stevens, A.M., J.L. Pawlitz, R.G. Kurumbail, J.K. Gierse, K.T. Moreland, R.A. Stegeman, J.Y. Loduca and W.C. Stallings, Crystallization of recombinant cyclo-oxygenase-2 196 (1999) 350
Stevens, A.M., see Carter, D.C. 196 (1999) 610
Stewart, P.D.S. and P.F.M. Baldock, Practical experimental design techniques for automatic and manual protein crystallization 196 (1999) 665
Stiens, H., see Scholz, K. 197 (1999) 586
Stier, O., see Heinrichsdorff, F. 195 (1998) 540
Stinespring, C.D., see Ziemer, K.S. 191 (1998) 594
Stöcker, C., see Alkemper, J. 191 (1998) 252
Stockman, S.A., see Cederberg, J.G. 195 (1998) 63
Stoemenos, J., see Papaioannou, V. 194 (1998) 342
Stolyarchuk, I.D., see Savchuk, A.I. 197 (1999) 698
Stolyarova, S., N. Amir and Y. Nemirovsky, Rapid thermal processing of epitaxial II–VI heterostructures 198/199 (1999) 1157
Stolyarova, S., see Cohen, K. 198/199 (1999) 1174
Stolyarova, S., see Chack, A. 198/199 (1999) 1179
Stolz, W., see Dadgar, A. 195 (1998) 69
Stolz, W., see Leu, S. 195 (1998) 91
Stolz, W., see Leu, S. 195 (1998) 98
Stolz, W., see Höhnsdorf, F. 195 (1998) 391
Stolz, W., see Ellmers, C. 195 (1998) 630
Storchum, O., see Zaginey, A. 194 (1998) 317
Storm, S., W. Neumann and H. Niehus, Preparation of (0 0 1) ZnSe surfaces for homoepitaxy 197 (1999) 517
Straßburg, M., see Dadgar, A. 195 (1998) 69
Strauch, G., see Beccard, R. 198/199 (1999) 1049
Stringfellow, G.B., see Liu, Z. 191 (1998) 1
Stringfellow, G.B., see Hsu, T.C. 193 (1998) 1
Stringfellow, G.B., see Lee, S.H. 195 (1998) 13
Strupiński, W., A. Małąg and J. Ratajczak, Selective area metalorganic vapor phase epitaxy growth of prism- shaped GaAs resonators for folded cavity surface emitting lasers 195 (1998) 474
Strzelecka, S., see Hruban, A. 198/199 (1999) 282
Stura, E.A., J.-B. Charbonnier and M.J. Taussig, Epitaxial jumps 196 (1999) 250
Su, C.-H., see Chattopadhyay, K. 191 (1998) 377
Su, C.-H., W. Palosz, S. Feth and S.L. Lehoczky, Heat treatments of ZnSe starting materials for physical vapor transport 192 (1998) 386
Su, C.-H., see Price, M.W. 198/199 (1999) 297
Su Genbo, see Yang Shangfeng 197 (1999) 383
Suárez-Parra, R., see Jiménez-González, A.E. 192 (1998) 430
Subramanian, C., see Shanthi, S. 194 (1998) 369
Subramanian, C., see Kumaragurubaran, S. 197 (1999) 210
Subramanian, C., see Ushasree, P.M. 197 (1999) 216
Subramanian, C., see Shanthi, S. 197 (1999) 858
Sudijono, J.L., see Holmes, D.M. 192 (1998) 33
Suemasu, T., see Tsuchiya, H. 198/199 (1999) 1056
Sugawara, T., R. Komatsu and S. Uda, Growth and characterization of lithium tetraborate crystals grown in phase-matching directions 193 (1998) 364
Sugisaki, M., see Lee, J.-S. 200 (1999) 77
Sugiura, H., M. Mitsuhara, S. Kondo and Y. Suzaki, Thermal cleaning of air-exposed p-type InGaAs films and CBE regrowth of carbon-doped InGaAs layers for optical device applications 200 (1999) 13
Sugiyama, N., A. Okamoto, K. Okumura, T. Tani and N. Kamiya, Step structures and dislocations of SiC single crystals grown by modified Lely method 191 (1998) 84
Sugiyama, N., T. Tezuka and A. Kurobe, Fabrication of nano-crystal silicon on SiO_2 using the agglomeration process 192 (1998) 395
Sugou, S., see Lee, J.-S. 200 (1999) 77
Suh, E.-K., see Joo, H.-B. 194 (1998) 161
Suh, E.-K., see Kim, K.C. 197 (1999) 841
Suh, S.-H., see Kim, Y.K. 192 (1998) 109
Suhre, D.R., see Singh, N.B. 198/199 (1999) 588
Suhre, D.R., see Singh, N.B. 198/199 (1999) 995
Sun, D., see Li, X. 191 (1998) 31
Sun, D., see Li, X. 191 (1998) 34
Sun, D.-Z., see Zhang, J.-P. 192 (1998) 93
Sun, D.-Z., see Zhang, J.-P. 192 (1998) 471
Sun, D.Z., see Liu, J.P. 193 (1998) 535
Sun, D.Z., see Liu, J.P. 194 (1998) 426
Sun, D.-Z., see Zhang, J.-P. 197 (1999) 368
Sun, D.Z., see Liu, J.P. 200 (1999) 613
Sun, D.Z., see Liu, J.P. 200 (1999) 617
Sun, J., L. Zhang and T.F. Kuech, In situ thermal nitridation of GaAs using metalorganic vapor phase epitaxy 195 (1998) 711
Sun, L., see Zhang, H. 200 (1999) 335
Sun, R., see Fan, S. 198/199 (1999) 542
Sunaba, K., see Tsuchiya, H. 198/199 (1999) 1056
Sundgren, J.-E., see Sandström, P. 197 (1999) 849
Surya, C., see Fleischer, S. 196 (1999) 53
Suski, T., see Prystawko, P. 198/199 (1999) 1061

Suvorova, E.I. and H.E. Lundager Madsen, Observation by HRTEM the hydroxyapatite–octacalcium phosphate interface in crystals grown from aqueous solutions 198/199 (1999) 677
Suzaki, Y., see Sugiura, H. 200 (1999) 13
Suzdal, V.S., see Zaslavsky, B.G. 198/199 (1999) 856
Suzuki, E., see Furukawa, Y. 197 (1999) 889
Suzuki, E., see Shimizu, K. 197 (1999) 921
Suzuki, H., see Kaito, C. 200 (1999) 271
Suzuki, J., see Yoshida, S. 191 (1998) 279
Suzuki, K., see Epelbaum, B.M. 198/199 (1999) 471
Suzuki, T., see Mamiya, M. 198/199 (1999) 611
Suzuki, Y., see Kodama, S. 194 (1998) 166
Suzuki, Y., see Sazaki, G. 196 (1999) 204
Svedberg, E.B., see Sandström, P. 197 (1999) 849
Svedberg, E.B., see McCaffrey, J.P. 200 (1999) 498
Svensson, B.G., see Joelsson, K.B. 196 (1999) 97
Swaminathan, V., see Henderson, R. 194 (1998) 8
Sweegers, C., W.J.P. van Enckevort, H. Meekes, P. Bennema, I.D.K. Hiralal and A. Rijkeboer, The impact of twinning on the morphology of γ-$Al(OH)_3$ crystals 197 (1999) 244
Swiatek, Z., see Ciach, R. 197 (1999) 675
Syono, Y., see Mansori, M. 197 (1999) 141
Sys, C., see D'Hondt, M. 195 (1998) 655
Syväjärvi, M., see Tuominen, M. 193 (1998) 101
Syväjärvi, M., R. Yakimova, H.H. Radamson, N.T. Son, Q. Wahab, I.G. Ivanov and E. Janzén, Liquid phase epitaxial growth of SiC 197 (1999) 147
Syväjärvi, M., R. Yakimova, M. Tuominen, A. Kakanakova-Georgieva, M.F. MacMillan, A. Henry, Q. Wahab and E. Janzén, Growth of 6H and 4H–SiC by sublimation epitaxy 197 (1999) 155
Syväjärvi, M., R. Yakimova, P.-A. Glans, A. Henry, M.F. MacMillan, L.I. Johansson and E. Janzén, Morphology and polytype disturbances in sublimation growth of SiC epitaxial layers 198/199 (1999) 1019
Szadkowski, A., see Mycielski, A. 197 (1999) 423
Szakács, O., see Földvári, I. 198/199 (1999) 482
Szatkowski, J., E. Placzek-Popko, K. Sieranski and B. Bieg, Defect studies in $Cd_{0.95}Mn_{0.05}$: Ga by DLTS 197 (1999) 684
Szczerbakow, A., J. Domagala, D. Rose, K. Durose, V.Yu. Ivanov and A.R. Omeltchouk, Structural defects and compositional uniformity in CdTe and $Cd_{1-x}Zn_xTe$ crystals grown by a vapour transport technique 191 (1998) 673
Szczerbakow, A., see Miotkowska, S. 200 (1999) 483
Szekeres, A., D. Gogova and K. Gesheva, Optical properties of thin CVD-tungsten oxide films by spectroscopic ellipsometry 198/199 (1999) 1235
Szofran, F.R., see Price, M.W. 198/199 (1999) 297
Szofran, F.R., see Price, M.W. 198/199 (1999) 303
Szymczak, H., see Barilo, S.N. 198/199 (1999) 636
Szymczak, R., see Barilo, S.N. 198/199 (1999) 636

Tabata, H., see Shimamura, K. 194 (1998) 209
Tabata, T., see Miyazawa, S. 191 (1998) 512
Tachibana, H., T. Ishido, M. Ogawa, M. Funato, Sz. Fujita and Sg. Fujita, Relation between GaAs surface morphology and incorporation of hexagonal GaN into cubic GaN 196 (1999) 41
Tachibana, M., Y. Kobayashi, T. Shimazu, M. Ataka and K. Kojima, Growth and mechanical properties of lysozyme crystals 198/199 (1999) 661
Tachibana, M., K. Kono, M. Shimizu and K. Kojima, Growth and dislocation characteristics of organic molecular crystals: 2,3-dimethylnaphthalene 198/199 (1999) 665
Taguchi, R., see Kuriyama, K. 198/199 (1999) 802
Tahara, K., see Sekijima, T. 193 (1998) 446
Tairov, Yu.M., see Avrov, D.D. 198/199 (1999) 1011
Tairov, Yu.M., see Bakin, A.S. 198/199 (1999) 1015
Takada, A., see Inatomi, Y. 198/199 (1999) 176
Takagi, A., J.-G. Wen, I. Hirabayashi and U. Mizutani, Growth mode dependence of microstructures and superconducting properties of $Nd_{1+x}Ba_{2-x}Cu_3O_y$ thick films prepared by liquid-phase epitaxy 193 (1998) 71
Takahashi, K., see Shimizu, K. 191 (1998) 178
Takahashi, K., see Shimizu, K. 191 (1998) 185
Takahashi, K., see Shimizu, K. 197 (1999) 921
Takahashi, N., see Koukitu, A. 197 (1999) 99
Takahashi, Y., see Adachi, H. 198/199 (1999) 568
Takamiya, S., see Miyashita, M. 192 (1998) 79
Takamura, Y., see Nagashio, K. 200 (1999) 118
Takano, K.J., see Nishioka, K. 200 (1999) 592
Takasaki, S., see Anzai, H. 191 (1998) 148
Takeda, H., see Sato, J. 191 (1998) 746
Takeda, H., see Shimamura, K. 194 (1998) 203
Takeda, H., see Shimamura, K. 194 (1998) 209
Takeda, H., K. Shimamura, V.I. Chani and T. Fukuda, Effect of starting melt composition on crystal growth of $La_3Ga_5SiO_{14}$ 197 (1999) 204
Takei, H., see Mamiya, M. 198/199 (1999) 611
Takei, H., see Tanaka, T. 200 (1999) 155
Takekawa, S., see Kaneko, N. 197 (1999) 818

Takemi, M., Y. Mihashi, T. Shiba and M. Aiga, High-resolution X-ray diffraction studies on growth interrupted heterointerfaces grown by metalorganic vapor-phase epitaxy 191 (1998) 18
Takemura, K., see Sawada, T. 191 (1998) 225
Takenouchi, H., see Amano, C. 193 (1998) 460
Takeuchi, K., see Maeda, S. 194 (1998) 70
Takeuchi, K., see Miyamoto, T. 197 (1999) 67
Takeuchi, T., see Yamaguchi, S. 195 (1998) 309
Taki, T., see Koukitu, A. 197 (1999) 99
Taki, T., see Koukitu, A. 198/199 (1999) 1111
Takiguchi, H., K. Iida, S. Ueno, J. Yano and K. Sato, Heterogeneous nucleation of n-alcohol crystals from solution assisted by vapor-deposited thin films of fatty acids 193 (1998) 641
Takiguchi, H., see Yoshida, Y. 198/199 (1999) 923
Takiyama, H., N. Tezuka, M. Matsuoka, R.I. Ristic and J.N. Sherwood, Growth rate enhancement by microcrystals and the quality of resulting potash alum crystals 192 (1998) 439
Takiyama, H., see Matsuoka, M. 198/199 (1999) 1299
Takizawa, T., see Matsushita, H. 191 (1998) 455
Takizawa, T., see Matsushita, H. 197 (1999) 169
Taleb, M., C. Didierjean, C. Jelsch, J.P. Mangeot, B. Capelle and A. Aubry, Crystallization of proteins under an external electric field 200 (1999) 575
Talham, D.R., see Whipps, S. 192 (1998) 243
Tamamura, K., see Tsukamoto, H. 191 (1998) 679
Tamamura, T., see Temmyo, J. 195 (1998) 516
Tamulaitis, G., see Burachas, S. 198/199 (1999) 881
Tamura, S., see Dąbkowski, A. 197 (1999) 879
Tamura, S., see Imanaka, N. 200 (1999) 169
Tamura, Y., see Yokoyama, C. 191 (1998) 827
Tanaka, H., see Ochimizu, H. 195 (1998) 58
Tanaka, I., see Niimura, N. 200 (1999) 265
Tanaka, S., see Anzai, H. 191 (1998) 148
Tanaka, S., see Hwang, J. 200 (1999) 63
Tanaka, S.-i., see Hovakimian, L.B. 198/199 (1999) 900
Tanaka, T., Z.U. Rek, J. Wong and M. Rowen, FZ crystal growth of monochromator-grade YB_{66} single crystals as guided by topographic and double-crystal diffraction characterization 192 (1998) 141
Tanaka, T., H. Takei and C. Uyeda, Flux growth of $(Mg_{1-x}Fe_x)SiO_3$ orthoenstatite crystals 200 (1999) 155
Tandon, A. and R.M. Cohen, Highly p-type carbon-doped InGaAs grown by atmospheric pressure organometallic vapor-phase epitaxy 192 (1998) 47
Tanemura, S., see Jin, P. 191 (1998) 285
Tang, C., see Wu, G. 192 (1998) 417
Tang, C.C., see Li, Y.X. 191 (1998) 282
Tang, D., see Hong, X. 193 (1998) 610
Tang, Y.H., see Zhang, Y.F. 197 (1999) 136
Tang, Z.M. and W.R. Hu, A simulation model of a floating half zone 192 (1998) 335
Tange, Y., see Otoishi, S. 200 (1999) 467
Tani, T., see Sugiyama, N. 191 (1998) 84
Tanigaki, N., see Yoshida, Y. 198/199 (1999) 923
Tanner, B.K., see Duffar, T. 192 (1998) 63
Tanner, B.K., see Aitken, N.M. 198/199 (1999) 984
Tanner, B.K., see Mizuno, K. 198/199 (1999) 1146
Tanokura, M., see Soga, T. 196 (1999) 291
Tanrikulu, S.Ü., I. Eroğlu, A.N. Bulutcu and S. Özkar, The growth and dissolution of ammonium perchlorate crystals in a fluidized bed crystallizer 194 (1998) 220
Tardieu, A., see Boyer, M. 196 (1999) 185
Tardieu, A., A. Le Verge, M. Malfois, F. Bonneté, S. Finet, M. Riès-Kautt and L. Belloni, Proteins in solution: from X-ray scattering intensities to interaction potentials 196 (1999) 193
Tardieu, A., see Budayova, M. 196 (1999) 210
Tardieu, A., see Bonneté, F. 196 (1999) 403
Tardy, M., see Piechotka, M. 193 (1998) 80
Tashiro, K., see Kaneko, F. 198/199 (1999) 1352
Tateno, K., see Amano, C. 193 (1998) 460
Tateuchi, M., see Koizumi, K. 198/199 (1999) 1136
Taudt, W., J. Xu, A. Hardt, H. Körfer, Q. Liu, H. Hamadeh, H. Lakner, J. Woitok and M. Heuken, Optimization of pre-epitaxial processes to obtain high-quality ZnSe/GaAs heterointerfaces grown in a low-pressure metalorganic vapour-phase epitaxy system 191 (1998) 663
Taudt, W., see Liu, Q. 197 (1999) 507
Taurino, A., see Passaseo, A. 197 (1999) 777
Taussig, M.J., see Stura, E.A. 196 (1999) 250
Tavare, N.S. and V.K. Jadhav, Separation through crystallization and hydrotropy: the 6-aminopenicillanic acid (6-APA) and phenoxyacetic acid (PAA) system 198/199 (1999) 1320
Taylor, P., see Shekunov, B.Yu. 198/199 (1999) 1335
Tazawa, M., see Jin, P. 191 (1998) 285
Tédenac, J.C., see Tomasini, P. 193 (1998) 572
Tegetmeier, A., see Cröll, A. 191 (1998) 365
Tegude, F.J., see Velling, P. 195 (1998) 117
Tegude, F.J., see Velling, P. 195 (1998) 490
Teiserskis, A., see Abrutis, A. 191 (1998) 79
Teisseyre, H., see Prystawko, P. 198/199 (1999) 1061
Teja, A.S., see Givand, J.C. 198/199 (1999) 1340

Temmyo, J., E. Kuramochi, H. Kamada and T. Tamamura, Resonant self-organization in semiconductor growth 195 (1998) 516

Ten Grotenhuis, E., A.W. Marsman, F.J. Hoogesteger, J.C. van Miltenburg, J.P. van der Eerden, L.W. Jenneskens, W.J. Smeets and A.L. Spek, Solid state structures in spin-coated assemblies of oligo(cyclohexylidene) oxime derivatives and (partly) saturated analogues: an atomic force microscopy study 191 (1998) 834

Teng, X., see Duan, S. 195 (1998) 304

Teng, X.-G., see Yang, H.-F. 193 (1998) 478

Tennenhouse, L.A., see LaCombe, J.C. 194 (1998) 143

Ter Horst, J.H., R.M. Geertman, A.E. van der Heijden and G.M. van Rosmalen, The influence of a solvent on the crystal morphology of RDX 198/199 (1999) 773

Terada, Y., see Ko, J.M. 192 (1998) 157

Terada, Y., see Ferriol, M. 197 (1999) 221

Terashima, K., see Nakanishi, H. 191 (1998) 711

Terashima, K., see Maeda, S. 192 (1998) 117

Terashima, K., see Maeda, S. 194 (1998) 70

Tessaro, G. and P. Mascher, Point defect characterization of Zn- and Cd-based semiconductors using positron lifetime spectroscopy 197 (1999) 581

Teubner, T., see Boeck, T. 198/199 (1999) 420

Teubner, T., T. Boeck and K. Schmidt, Modelling of solution growth of silicon from small indium droplets – homogeneous nucleation 198/199 (1999) 425

Tezuka, N., see Takiyama, H. 192 (1998) 439

Tezuka, N., see Matsuoka, M. 198/199 (1999) 1299

Tezuka, T., see Sugiyama, N. 192 (1998) 395

Theodore, F., see Krymov, V.M. 198/199 (1999) 210

Theodore, F., see Gurjiyants, P.A. 198/199 (1999) 227

Theodore, F., T. Duffar and F. Louchet, Modelling plastic stress relaxation in shaped sapphire crystal growth 198/199 (1999) 232

Thiandoume, C., O. Ka, A. Lusson and O. Gorochov, MOVPE growth of ZnS on (1 0 0)GaAs using dimethylzinc and ditertiarybutyl sulphide precursors 197 (1999) 805

Thiyagarajan, P., see Marone, P.A. 191 (1998) 811

Thomas, B.R., see Vekilov, P.G. 196 (1999) 261

Thomas, B.R., see Carter, D.C. 196 (1999) 623

Thomas, S.G., see Liu, J.L. 200 (1999) 106

Thompson, A.G., see Ferguson, I.T. 195 (1998) 648

Thompson, D.A., see LaPierre, R.R. 191 (1998) 319

Thorne, R.E., see Dobrianov, I. 196 (1999) 511

Thrush, C.M., see Partin, D.L. 195 (1998) 378

Thrush, E.J., see Considine, L. 195 (1998) 192

Thrush, E.J., see Vanhollebeke, K. 195 (1998) 644

Tiaden, J., Phase field simulations of the peritectic solidification of Fe–C 198/199 (1999) 1275

Tian, L., see Guan, Q. 197 (1999) 1012

Tian, Y., see Ning, Y. 191 (1998) 39

Tiede, D.M., see Marone, P.A. 191 (1998) 811

Tihanyi, P.L., see Roberts, J.S. 195 (1998) 668

Tijero, J.M.G., see Sánchez, J.J. 192 (1998) 363

Tirrell, D.A., see Gower, L.A. 191 (1998) 153

Tiwari, A.N., see Furlong, M.J. 193 (1998) 114

Tkachuk, P.M., see Korbutyak, D.V. 197 (1999) 659

Tkachuk, V.I., see Korbutyak, D.V. 197 (1999) 659

Togawa, S., see Guo, Z. 194 (1998) 321

Tok, E.S., see Holmes, D.M. 192 (1998) 33

Tomasini, P., A. Haidoux, J.C. Tédenac and M. Maurin, Methylpentacarbonylmanganese as organometallic precursor for the epitaxial growth of manganese selenide heterostructures 193 (1998) 572

Tomilenko, A.A., see Chepurov, A.I. 198/199 (1999) 963

Tomson, A.S., see Senchenkov, A.S. 197 (1999) 552

Tomzig, E., see Mühe, A. 198/199 (1999) 409

Tönhardt, R. and G. Amberg, Phase-field simulation of dendritic growth in a shear flow 194 (1998) 406

Topa, V., see Vasile, E. 198/199 (1999) 806

Topalova, L.I., see Melnikov, A.A. 197 (1999) 666

Tordjman, M., see di Forte-Poisson, M.A. 195 (1998) 314

Torii, K., see Yamamoto, M. 197 (1999) 967

Toth, A.L., see Franc, J. 197 (1999) 593

Tóth-Katona, T., see González-Cinca, R. 193 (1998) 712

Tottori, S., see Qhalid Fareed, R.S. 200 (1999) 348

Touhari, F., see Breton, G. 200 (1999) 112

Tournié, E., see Bousquet, V. 192 (1998) 102

Towe, E., see Pan, D. 196 (1999) 23

Towe, E., see Xu, J. 196 (1999) 26

Tracy, S.L., C.J.P. François and H.M. Jennings, The growth of calcite spherulites from solution I. Experimental design techniques 193 (1998) 374

Tracy, S.L., D.A. Williams and H.M. Jennings, The growth of calcite spherulites from solution. II. Kinetics of formation 193 (1998) 382

Trætholt, C., see Brecht, E. 191 (1998) 421

Tran, C.A., R.F. Karlicek Jr., M. Schurman, A. Osinsky, V. Merai, Y. Li, I. Eliashevich, M.G. Brown, J. Nering, I. Ferguson and R. Stall, Phase separation in InGaN/GaN multiple quantum wells and its relation to brightness of blue and green LEDs 195 (1998) 397

Trassoudaine, A., O. Parillaud, E. Goumet, D. Castelluci, E. Gil-Lafon and R. Cadoret, Kinetic study of Si incorporation in InP by the hydride vapour phase epitaxy 192 (1998) 402
Tréglia, G., see Roussel, J.-M. 198/199 (1999) 83
Trepk, T., see Zorn, M. 195 (1998) 223
Triboulet, R., see Garcia, J.A. 191 (1998) 685
Triboulet, R., see Munoz, V. 196 (1999) 71
Triboulet, R., see Martinez-Tomas, C. 197 (1999) 435
Triboulet, R., see Lemasson, P. 197 (1999) 462
Triboulet, R., see Rzepka, E. 197 (1999) 480
Triboulet, R., see Mora-Seró, I. 197 (1999) 497
Triboulet, R., see Zerrai, A. 197 (1999) 729
Triboulet, R., see Garcia, J.A. 197 (1999) 794
Triboulet, R., J.M. N'tep, M. Barbe, P. Lemasson, I. Mora-Seró and V. Munoz, Some fundamentals of the vapor and solution growth of ZnSe and ZnO 198/199 (1999) 968
Tributsch, H., see Oertel, J. 198/199 (1999) 1205
Trinh, E.H., see Ohsaka, K. 194 (1998) 138
Trinh, E.H., see Chung, S.K. 194 (1998) 384
Trivedi, S., see Burger, A. 198/199 (1999) 872
Tromson-Carli, A., see Lemasson, P. 197 (1999) 462
Trtik, V., R. Aguiar, F. Sánchez, C. Ferrater and M. Varela, Study of the epitaxial growth of CeO_2(0 0 1) on yttria-stabilized zirconia/Si(0 0 1) 192 (1998) 175
Tsai, A.P., see Sato, T.J. 191 (1998) 545
Tsai, A.P., see Guo, J.Q. 197 (1999) 963
Tsekova, D., S. Dimitrova and C.N. Nanev, Heterogeneous nucleation (and adhesion) of lysozyme crystals 196 (1999) 226
Tsuboi, Y., see Nagai, Y. 193 (1998) 732
Tsuchiya, H., K. Sunaba, T. Suemasu and F. Hasegawa, Growth of thick and pure cubic GaN on (0 0 1) GaAs by halide VPE 198/199 (1999) 1056
Tsuda, N., see Kaito, C. 200 (1999) 271
Tsugami, M., see Miyashita, M. 192 (1998) 79
Tsukada, T., see Hahn, S.-H. 191 (1998) 413
Tsukamoto, H., K. Tamamura, M. Nagai, Futoshi Hiei and M. Ikeda, Optical characteristics of ZnCdSe/ZnSSe single quantum wells 191 (1998) 679
Tsukihara, T., see Sanjoh, A. 196 (1999) 691
Tsvetkov, D.V., see Cheng, T.S. 197 (1999) 12
Tsvetovsky, V.B., see Golyshev, V.D. 198/199 (1999) 501
Tu, C.W., see Bhat, R. 195 (1998) 427
Tu, C.W., see Shi, B.Q. 195 (1998) 740
Tuller, S.C., see Prater, B.D. 196 (1999) 674
Tuominen, M., R. Yakimova, A. Kakanakova-Georgieva, M.F. MacMillan, M. Syväjärvi and E. Janzén, Investigation of domain evolution in sublimation epitaxy of SiC 193 (1998) 101
Tuominen, M., see Syväjärvi, M. 197 (1999) 155
Türck, V., see Kappelt, M. 195 (1998) 552
Türck, V., see Pohl, U.W. 195 (1998) 569
Türn, L., see Lott, K. 197 (1999) 493
Twigg, M.E., B.R. Bennett and R. Magno, Morphological instability in InAs/GaSb heterostructures 191 (1998) 651
Twigg, P.D., see Carter, D.C. 196 (1999) 602
Twigg, P.D., see Carter, D.C. 196 (1999) 610
Twigg, P.D., see Carter, D.C. 196 (1999) 623

Uchida, T., see Salamatin, A.N. 193 (1998) 197
Uda, S., see Sugawara, T. 193 (1998) 364
Uda, S., see Lan, C.W. 193 (1998) 552
Udono, H., I. Kikuma and Y. Okada, Lattice parameter of ZnSe crystals grown from melt under Zn partial pressure 193 (1998) 39
Udono, H., I. Kikuma and Y. Okada, Dependence of lattice parameter of melt-grown ZnSe on Zn partial pressure during in situ annealing 197 (1999) 466
Ueno, S., see Takiguchi, H. 193 (1998) 641
Ueno, S., see Kaneko, N. 197 (1999) 263
Ueno, S., A. Minato, J. Yano and K. Sato, Synchrotron radiation X-ray diffraction study of polymorphic crystallization of SOS from liquid phase 198/199 (1999) 1326
Ueno, Y., N. Sakakibara and H. Hoshizaki, Dependence of the surface resistance on the microdefects in $YBa_2Cu_3O_{7-x}$ films 197 (1999) 376
Ueta, A.Y., see Rappl, P.H.O. 191 (1998) 466
Ufimtsev, V.B., see Lakeenkov, V.M. 197 (1999) 443
Ulyanytsky, K.S., see Savitsky, A.V. 192 (1998) 196
Umeno, M., see Saravanan, S. 192 (1998) 23
Upadhyaya, V., see Nagaraja, H.S. 193 (1998) 674
Uppal, K., see Kim, I. 193 (1998) 293
U'Ren, G.D., see Koontz, E.M. 198/199 (1999) 1104
Urmann, G., see Künzel, H. 192 (1998) 56
Ushasree, P.M., R. Jayavel, C. Subramanian and P. Ramasamy, Growth of zinc thiourea sulfate (ZTS) single crystals: a potential semiorganic NLO material 197 (1999) 216
Ushiyama, K., see Kuriyama, K. 198/199 (1999) 802
Usui, S., see Yoshimura, J. 191 (1998) 483
Uwaha, M., see Sato, M. 198/199 (1999) 38
Uyeda, C., see Tanaka, T. 200 (1999) 155

Vaccari, G., see Sgualdino, G. 192 (1998) 290
Vaccaro, P.O., see Koizumi, K. 198/199 (1999) 1136
Vacek, K., see Vacková, S. 197 (1999) 599

Vachette, P., see Budayova, M. 196 (1999) 210

Vacková, S., K. Ždánský, K. Vacek, L. Scherback, P. Feichouk and M. Ilaschouk, Conductivity change of Au/p-CdTe/Au as a function of the temperature gradient 197 (1999) 599

Vaille, M., see Nataf, G. 192 (1998) 73

Van den Berg, E.P.G., G. Bögels and G.J. Arkenbout, Growth of ε-caprolactam crystals from the melt: the influence of cyclohexanone on the $\{1\,1\,\bar{1}\}$ and $\{1\,1\,0\}$ forms 191 (1998) 169

Van den Bogaert, N., see Gondet, S. 198/199 (1999) 129

Van der Eerden, J.P., see ten Grotenhuis, E. 191 (1998) 834

Van der Ham, F., G.J. Witkamp, J. de Graauw and G.M. van Rosmalen, Eutectic freeze crystallization simultaneous formation and separation of two solid phases 198/199 (1999) 744

Van der Heijden, A.E., see ter Horst, J.H. 198/199 (1999) 773

Van der Stricht, W., see Considine, L. 195 (1998) 192

Van Dongen, T., see van Geelen, A. 195 (1998) 79

Van Enckevort, W.J.P., see van Hoof, P.J.C.M. 191 (1998) 861

Van Enckevort, W.J.P., see Plomp, M. 193 (1998) 389

Van Enckevort, W.J.P., see van Hoof, P.J.C.M. 193 (1998) 679

Van Enckevort, W.J.P., see de Theije, F.K. 197 (1999) 37

Van Enckevort, W.J.P. see Sweegers, C. 197 (1999) 244

Van Enckevort, W.J.P., see van Veenendaal, E. 198/199 (1999) 22

Van Enckevort, W.J.P., see Plomp, M. 198/199 (1999) 246

Van Geelen, A., T.M.F. de Smet, T. van Dongen and W.M.E.M. van Gils, Zinc doping of InP by metal organic vapour phase diffusion (MOVPD) 195 (1998) 79

Van Gils, W.M.E.M., see van Geelen, A. 195 (1998) 79

Van Hoof, P.J.C.M., see Vogels, L.J.P. 191 (1998) 563

Van Hoof, P.J.C.M., see Grimbergen, R.F.P. 191 (1998) 846

Van Hoof, P.J.C.M., R.F.P. Grimbergen, H. Meekes, W.J.P. van Enckevort and P. Bennema, Morphology of orthorhombic n-paraffin crystals: a comparison between theory and experiments 191 (1998) 861

Van Hoof, P.J.C.M., M. Schoutsen and P. Bennema, Solvent effect on the roughening transition and wetting of n-paraffin crystals 192 (1998) 307

Van Hoof, P.J.C.M., W.J.P. van Enckevort and M. Schoutsen, The growth of extremely thin crystals: a Monte Carlo study and an application to n-paraffins 193 (1998) 679

Van Hoof, P.J.C.M., see van Veenendaal, E. 198/199 (1999) 22

Van Miltenburg, J.C., see ten Grotenhuis, E. 191 (1998) 834

Van Rosmalen, G.M., see Neumann, A.M. 198/199 (1999) 723

Van Rosmalen, G.M., see Kramer, H.J.M. 198/199 (1999) 729

Van Rosmalen, G.M., see van der Ham, F. 198/199 (1999) 744

Van Rosmalen, G.M., see Oosterhof, H. 198/199 (1999) 754

Van Rosmalen, G.M., see Domingo, C. 198/199 (1999) 760

Van Rosmalen, G.M., see Wubbolts, F.E. 198/199 (1999) 767

Van Rosmalen, G.M., see ter Horst, J.H. 198/199 (1999) 773

Van Rosmalen, G.M., see Zijlema, T.G. 198/199 (1999) 789

Van Suchtelen, J., A.J. Nijdam and E. van Veenendaal, The velocity source concept 198/199 (1999) 17

Van Suchtelen, J., see van Veenendaal, E. 198/199 (1999) 22

Van Suchtelen, J., see Nijdam, A.J. 198/199 (1999) 430

Van Tendeloo, G., see Buschmann, V. 191 (1998) 430

Van Tendeloo, G., see Pauwels, B. 200 (1999) 126

Van Veenendaal, E., see van Suchtelen, J. 198/199 (1999) 17

Van Veenendaal, E., P.J.C.M. van Hoof, J. van Suchtelen, W.J.P. van Enckevort and P. Bennema, Kinetic roughening of the Kossel (1 0 0) surface 198/199 (1999) 22

Van Vliet, C.M., see Paul, N. 197 (1999) 547

Vanderschaeve, G., see Levade, C. 197 (1999) 565

Vandewalle, N., M. Ausloos and R. Cloots, Collective effects during crystal growth in the presence of mobile nonreactive impurities: experiments and simulations 197 (1999) 317

Vang, T.A., see Mawst, L.J. 195 (1998) 609

Vanhollebeke, K., L. Considine, I. Moerman, P. Demeester, E.J. Thrush and J.A. Crawley, Highly uniform AlAs/GaAs, InGa(Al)P/GaAs and InGaAs(P)/InP structures grown in a three 2″ wafer close-spaced vertical rotating disk reactor 195 (1998) 644

Vantomme, A., see Jin, S. 194 (1998) 189

Varela, M., see Trtík, V. 192 (1998) 175

Vařenka, J., see Kubínek, R. 193 (1998) 174
Vasanelli, L., see Passaseo, A. 197 (1999) 777
Vasetsky, S.I., see Zaslavsky, B.G. 198/199 (1999) 856
Vashi, M.N., see Deshpande, M.P. 197 (1999) 833
Vashuk, V.V., see Zhigunov, D.I. 198/199 (1999) 605
Vasile, E., M. Datcu, S. Polosan, E. Apostol and V. Topa, Silver nanocrystals obtained by the ionization of Ag^--ions in KCl 198/199 (1999) 806
Vasiliu, F., see Iliescu, B. 198/199 (1999) 507
Vasiljević, R., see Blagojević, I. 200 (1999) 558
Vázquez, L., see Yates, H.M. 193 (1998) 9
Veesler, S., see Seyssiecq, I. 196 (1999) 174
Veesler, S., see Budayova, M. 196 (1999) 297
Veesler, S., see Badens, E. 198/199 (1999) 704
Veesler, S., see Garcia, E. 198/199 (1999) 1360
Veignant, F., M. Gandais, P. Aubert and G. Garry, Structural evolution of lithium niobate deposited on sapphire (0 0 0 1): from early islands to continuous films 196 (1999) 141
Vekilov, P.G., F. Rosenberger, H. Lin and B.R. Thomas, Nonlinear dynamics of layer growth and consequences for protein crystal perfection 196 (1999) 261
Vekilov, P.G., see Carter, D.C. 196 (1999) 623
Velev, O.D., see Neal, B.L. 196 (1999) 377
Velling, P., G. Janßen, M. Agethen, W. Prost and F.J. Tegude, InGaP/GaAs hole barrier asymmetry determined by (0 0 2) X-ray reflections and p-type DB-RTD hole transport 195 (1998) 117
Velling, P., W. Fix, W. Geißelbrecht, W. Prost, G.H. Döhler and F.-J. Tegude, InGaP/GaAs shadow-mask for optoelectronic integration and MBE regrowth 195 (1998) 490
Vengalis, B., see Kleptsyn, V. 196 (1999) 122
Verardi, P., N. Nastase, C. Gherasim, C. Ghica, M. Dinescu, R. Dinu and C. Flueraru, Scanning force microscopy and electron microscopy studies of pulsed laser deposited ZnO thin films: application to the bulk acoustic waves (BAW) devices 197 (1999) 523
Verbeeck, A., see Millan, A. 192 (1998) 215
Vereda, F., see Fedorov, V.A. 194 (1998) 94
Verkhovtseva, E.T., see Kovalenko, S.I. 191 (1998) 553
Verschuren, C.A., M.R. Leys, R.T.H. Rongen, H. Vonk and J.H. Wolter, Morphology of homo-epitaxial vicinal (1 0 0) III–V surfaces 200 (1999) 19
Vescan, L., Lateral ordering of Ge islands along facets 194 (1998) 173
Vetkin, A., see Leonyuk, L. 198/199 (1999) 619
Vetkin, A., see Maltsev, V. 198/199 (1999) 626
Veuhoff, E., Exploitation of surface selective growth in metalorganic growth technologies for device applications 195 (1998) 444
Veuhoff, E., see Kröner, P. 195 (1998) 660
Vidal, M.A., see Constantino, M.E. 194 (1998) 301
Vidal, M.A., see Salazar-Hernández, B. 197 (1999) 783
Vidal, O., M.C. Robert and F. Boué, Gel growth of lysozyme crystals studied by small angle neutron scattering: case of agarose gel, a nucleation promotor 192 (1998) 257
Vidal, O., M.C. Robert and F. Boué, Gel growth of lysozyme crystals studied by small angle neutron scattering: case of silica gel, a nucleation inhibitor 192 (1998) 271
Vidal, O., M.C. Robert, B. Arnoux and B. Capelle, Crystalline quality of lysozyme crystals grown in agarose and silica gels studied by X-ray diffraction techniques 196 (1999) 559
Vigdergauz, S. and D. Givoli, Thermoelastic stresses in a crystal with weak anisotropy 198/199 (1999) 125
Villar, C., see Sanz-Hervás, A. 195 (1998) 558
Vineis, C.J., C.A. Wang, K.F. Jensen and W.G. Breiland, In situ monitoring of GaSb, GaInAsSb, and AlGaAsSb 195 (1998) 181
Vinograd, E.L., see Panova, A.N. 198/199 (1999) 865
Virchenko, V.A., see Korzun, B.V. 198/199 (1999) 821
Virozub, A. and S. Brandon, Radiative heat transport during the vertical Bridgman growth of oxide single crystals: slabs versus cylinders 193 (1998) 592
Vishnjakov, A., see Lott, K. 197 (1999) 489
Vitagliano, L., see Sica, F. 196 (1999) 305
Voegel, J.C., see Ngankam, P.A. 197 (1999) 927
Vogels, L.J.P., P.J.C.M. van Hoof and R.F.P. Grimbergen, On the roughening transition of anisotropic and (pseudo) hexagonal lattices 191 (1998) 563
Volkov, V., see Ryzhikov, V. 197 (1999) 655
Voller, V.R., A semi-analytical model of microsegregation in a binary alloy 197 (1999) 325
Voller, V.R., A semi-analytical model of microsegregation and coarsening in a binary alloy 197 (1999) 333
Von Ammon, W., E. Dornberger and P.O. Hansson, Bulk properties of very large diameter silicon single crystals 198/199 (1999) 390
Von Ammon, W., see Mühe, A. 198/199 (1999) 409

Von Bardeleben, H.J., T. Arnoux and J.C. Launay, Intrinsic defects in photorefractive bulk CdTe and ZnCdTe 197 (1999) 718
Von Bardeleben, H.J., see Briat, B. 197 (1999) 724
Vonk, H., see Verschuren, C.A. 200 (1999) 19
Vorbeck, C., see Off, J. 195 (1998) 286
Voronkov, V.V. and R. Falster, Vacancy-type microdefect formation in Czochralski silicon 194 (1998) 76
Voronkov, V.V. and R. Falster, Nucleation and growth of faceted voids in silicon crystals 198/199 (1999) 399
Vorotilov, K.A., see Melnikov, A.A. 197 (1999) 666
Vostretsov, Yu., see Nagornaya, L. 198/199 (1999) 877

Wagner, A.M., see Marone, P.A. 191 (1998) 811
Wagner, G., see Pietzonka, I. 195 (1998) 21
Wagner, G., see Schulz, D. 198/199 (1999) 1024
Wagner, M., see Eisener, B. 198/199 (1999) 321
Wagner, V., see Dinger, A. 200 (1999) 391
Wagner, W., see Winterhoff, R. 195 (1998) 132
Wahab, Q., see Syväjärvi, M. 197 (1999) 147
Wahab, Q., see Syväjärvi, M. 197 (1999) 155
Wakahara, A., see Nabetani, Y. 193 (1998) 470
Wakamatsu, N., see Iijima, M. 193 (1998) 182
Wakayama, N.I., Quantitative study of crystallization kinetics of hen egg-white lysozyme using magnetic orientation 191 (1998) 199
Wakino, K., see Sekijima, T. 193 (1998) 446
Waku, Y., see Epelbaum, B.M. 198/199 (1999) 471
Walker, J.S., Bridgman crystal growth with a strong, low-frequency, rotating magnetic field 192 (1998) 318
Walker, P.J., see Allwood, D.A. 195 (1998) 163
Walker, P.J., see Klipstein, P.C. 195 (1998) 168
Wallnöfer, W., P.W. Krempl, F. Krispel and V. Willfurth, Segregation forming and growth defect characterization by heat treatment of hydrothermally grown $GaPO_4$ 198/199 (1999) 487
Wallrafen, F., see Neuroth, G. 198/199 (1999) 435
Walters, F., see Henderson, R. 194 (1998) 8
Walther, T. and C.J. Humphreys, A quantitative study of compositional profiles of chemical vapour-deposited strained silicon–germanium/silicon layers by transmission electron microscopy 197 (1999) 113
Wang, B., see Scripa, R.N. 198/199 (1999) 825
Wang, B.C., see Carter, D.C. 196 (1999) 610
Wang, C., see Zhang, H. 193 (1998) 370
Wang, C., see Lima, A.P. 197 (1999) 31
Wang, C., see Meng, X. 200 (1999) 199
Wang, C.A., OMVPE growth of GaInAsSb in the 2–2.4 μm range 191 (1998) 631
Wang, C.A., see Vineis, C.J. 195 (1998) 181
Wang, C.A., H.K. Choi, D.C. Oakley and G.W. Charache, Recent progress in GaInAsSb thermophotovoltaics grown by organometallic vapor-phase epitaxy 195 (1998) 346
Wang, C.A., see Hitchcock, C.W. 195 (1998) 363
Wang, D., see Liu, X. 193 (1998) 23
Wang, D., see Wang, L. 193 (1998) 484
Wang, F.L., see Wang, Z.M. 192 (1998) 97
Wang, G.-X., see Zhang, T. 198/199 (1999) 141
Wang, H., Y. Zeng, H. Zhou and M. Kong, Triclinic deformation and anisotropic strain relaxation of an InAs film on a GaAs(0 0 1) substrate measured by a series of symmetric double crystal X-ray diffraction 191 (1998) 627
Wang, H., see Liu, C. 196 (1999) 111
Wang, H., see Zhu, H. 197 (1999) 372
Wang, H., see Zheng, H.Q. 197 (1999) 762
Wang, H., see Feng, Q.L. 200 (1999) 550
Wang, H.M., see Li, Y.X. 191 (1998) 282
Wang, H.P., W.W. Lam and I. Shih, Crystal growth of $Cu(In_{1-x}Ga_x)_3Se_5$ by horizontal Bridgman method 200 (1999) 137
Wang, H.-T., see Chang, L.-B. 198/199 (1999) 1092
Wang Haobing, see Zhang Shoudu 197 (1999) 901
Wang Hongmei, see Zhou Hongwei 191 (1998) 361
Wang, J., see Lu, L. 194 (1998) 25
Wang, J., M. Nozaki, Y. Ishikawa, M.S. Hao, Y. Morishima, T. Wang, Y. Naoi and S. Sakai, Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth 197 (1999) 48
Wang, J., see Guan, Q. 197 (1999) 1012
Wang, J., see Xu, H. 200 (1999) 70
Wang, J., M. Nozaki, M. Lachab, R.S. Qhalid Fareed, Y. Ishikawa, T. Wang, Y. Naoi and S. Sakai, Formation and optical properties of InGaN/GaN nano-structures grown on amorphous Si substrates by MOCVD 200 (1999) 85
Wang, J.F., see Miki, T. 200 (1999) 399
Wang, J.H., D.H. Kim and H.-D. Yoo, Two-dimensional analysis of axial segregation in batchwise and coninuous Czochralski process 198/199 (1999) 120
Wang, K.L., see Liu, J.L. 200 (1999) 106
Wang, J.-S., see Liu, J.-S. 192 (1998) 372
Wang, L., see Liu, X. 193 (1998) 23
Wang, L., X. Liu, Y. Zan, D. Wang, D.-C. Lu, Z. Wang, Y. Wang, L. Cheng and Z. Zhang, The growth and characterization of GaN grown on an Al_2O_3 coated (0 0 1) Si substrate by metalorganic vapor phase epitaxy 193 (1998) 484

Wang, L., see Zeng, J. 197 (1999) 874
Wang, N., see Zhang, Y.F. 197 (1999) 136
Wang, P., see Zhang, H. 193 (1998) 370
Wang, P., see Zhang, H. 200 (1999) 335
Wang, Q., see Liu, C. 196 (1999) 111
Wang, R.-p., S.-h. Pan, Y.-l. Zhou, G.-w. Zhou, N.-n. Liu, K. Xie and H.-b. Lu, Fabrication and characteristics of CeO_2 films on Si(1 0 0) substrates by pulsed laser deposition 200 (1999) 505
Wang Siting, see Zhou Guoqing 191 (1998) 517
Wang Siting, see Zhang Shoudu 197 (1999) 901
Wang, T., see Wang, J. 197 (1999) 48
Wang, T., see Wang, J. 200 (1999) 85
Wang, W.S., M.D. Aggarwal, J. Choi, T. Gebre, A.D. Shields, B.G. Penn and D.O. Frazier, Solvent effects and polymorphic transformation of organic nonlinear optical crystal L-pyroglutamic acid in solution growth processes I. Solvent effects and growth morphology 198/199 (1999) 578
Wang, X., see Liu, X. 193 (1998) 23
Wang, X.J., see Xu, D.P. 191 (1998) 646
Wang, X.-L., see Zhang, J.-P. 192 (1998) 93
Wang, X.-L., see Zhang, J.-P. 192 (1998) 471
Wang, X.-L., M. Ogura and H. Matsuhata, Self-limiting effects of flow rate modulation epitaxy of GaAs on patterned substrate 195 (1998) 586
Wang, X.-L., see Zhang, J.-P. 197 (1999) 368
Wang, Y., see Wang, L. 193 (1998) 484
Wang, Y.N., see Lu, C.J. 191 (1998) 113
Wang, Z., see Wang, L. 193 (1998) 484
Wang, Z., see Zhu, H. 197 (1999) 372
Wang, Z., see Xu, H. 200 (1999) 70
Wang, Z., see Li, H. 200 (1999) 321
Wang, Z.G., see Gong, Q. 192 (1998) 376
Wang, Z.G., see Wu, J. 197 (1999) 95
Wang, Z.G., see Liu, F.-Q. 197 (1999) 789
Wang, Z.G., see Zhou, W. 200 (1999) 608
Wang, Z.M., S.L. Feng, X.P. Yang, Z.D. Lu, Z.Y. Xu, H.Z. Zheng, F.L. Wang, P.D. Han and X.F. Duan, Effects of growth interruption on self-assembled InAs/GaAs islands 192 (1998) 97
Wang Zhiming, see Zhao Qian 200 (1999) 603
Wankerl, A., D.T. Emerson, M.J. Cook and J.R. Shealy, Wavelength dependence of UV laser selective $Al_xGa_{1-x}As$ growth via adlayer stimulation in OMVPE 191 (1998) 8
Warddrip, M.L., see Kappers, M.J. 191 (1998) 332
Warddrip, M.L., see Begarney, M.J. 193 (1998) 305
Wardell, M., see Carter, D.C. 196 (1999) 610
Warren, J.A., see Boettinger, W.J. 200 (1999) 583
Watanabe, K., see Ohshita, Y. 193 (1998) 322
Watanabe, K., see Yanagiya, S.-i. 196 (1999) 319
Watanabe, M., M. Eguchi and T. Hibiya, Flow and temperature field in molten silicon during Czochralski crystal growth in a cusp magnetic field 193 (1998) 402
Watanabe, N., Sarin Kumar A.K., S. Yamahata and T. Kobayashi, Annealing effect on C-doped InGaAs grown by metalorganic chemical vapor deposition 195 (1998) 48
Watanabe, N., S. Yamahata and T. Kobayashi, Hydrogen removal by annealing from C-doped InGaAs grown on InP by metalorganic chemical vapor deposition 200 (1999) 599
Watanabe, Y., see Fujiwara, S. 192 (1998) 328
Watkins, S.P., see Gupta, J.A. 195 (1998) 34
Watkins, S.P., see Gupta, J.A. 195 (1998) 205
Watkins, S.P., see Arès, R. 195 (1998) 234
Watkins, S.P., see Xu, X.G. 195 (1998) 687
Weber, A., see Hofmann, D. 198/199 (1999) 1005
Weber, D., see Ostheimer, V. 198/199 (1999) 1184
Weber, H.-J., see Haselhoff, M. 196 (1999) 135
Wehnert, T., see Pristovsek, M. 195 (1998) 1
Wehnert, T., see Steimetz, E. 195 (1998) 530
Wei, J., see Guan, Q. 197 (1999) 1012
Weil, R., see Lisiansky, M. 197 (1999) 630
Weil, R., see Cohen, K. 198/199 (1999) 1174
Weil, R., see Chack, A. 198/199 (1999) 1179
Weimann, H., see Fischer, B. 198/199 (1999) 170
Weinert, B., see Flade, T. 198/199 (1999) 336
Weinert, B., see Korb, J. 198/199 (1999) 343
Weinert, B., see Gärtner, G. 198/199 (1999) 355
Weise, B., see Dinger, A. 200 (1999) 391
Weiss, F., see Abrutis, A. 191 (1998) 79
Weiss, T., M. Birkholz, M. Saad, S. Bleyhl, M. Kunst, A. Jäger-Waldau and M.Ch. Lux-Steiner, Ag-doped $CuGaSe_2$ as a precursor for thin film solar cells 198/199 (1999) 1190
Wells, M., see McPherson, A. 196 (1999) 572
Wen, J.-G., see Takagi, A. 193 (1998) 71
Wentorf, R.H., see Naik, M.B. 193 (1998) 133
Wenzl, H., see Oates, W.A. 191 (1998) 303
Werckmann, J., see Dentel, D. 191 (1998) 697
Wery, J.-P., see Carter, D.C. 196 (1999) 610
Wessels, B.W., Ferroelectric oxide epitaxial thin films: synthesis and nonlinear optical properties 195 (1998) 706
Westphalen, R., see Keiper, D. 197 (1999) 25
Wetzel, C., see Yamaguchi, S. 195 (1998) 309
Wetzel, G., see Piechotka, M. 193 (1998) 80
Wetzel, G., see Piechotka, M. 193 (1998) 90
Weyers, M., see Zettler, J.-T. 195 (1998) 151
Weyers, M., see Kurpas, P. 195 (1998) 217

Weyers, M., see Zorn, M. 195 (1998) 223
Weyers, M., see Hofmann, L. 195 (1998) 485
Weyers, M., see Bugge, F. 195 (1998) 676
Weyers, M., see Knauer, A. 195 (1998) 694
Whelan, M.J., see Mitura, Z. 198/199 (1999) 905
Whipps, S., S.R. Khan, F. Jeffrey O'Palko, R. Backov and D.R. Talham, Growth of calcium oxalate monohydrate at phospholipid Langmuir monolayers 192 (1998) 243
White, M., see Carter, D.C. 196 (1999) 602
White, M., see Carter, D.C. 196 (1999) 610
Whitehouse, C.R., see Mizuno, K. 198/199 (1999) 1146
Wichert, Th., see Ostheimer, V. 198/199 (1999) 1184
Wiencek, J.M., see Darcy, P.A. 196 (1999) 243
Wilamowski, Z., see Mycielski, A. 197 (1999) 423
Wilcox, W.R., see Skudarnov, P.V. 193 (1998) 219
Wilde, P.-M., see Boeck, T. 198/199 (1999) 420
Willander, M., see Zhao, Q.X. 193 (1998) 328
Willfurth, V., see Wallnöfer, W. 198/199 (1999) 487
Williams, D.A., see Tracy, S.L. 193 (1998) 382
Wilson, L.J., see Prater, B.D. 196 (1999) 674
Wilson, W.W., see Guo, B. 196 (1999) 424
Win, P., see Sik, H. 195 (1998) 479
Winnacker, A., see Hofmann, D. 198/199 (1999) 1005
Winsa, E.A., see LaCombe, J.C. 194 (1998) 143
Winter, C.H., see Cederberg, J.G. 195 (1998) 105
Winterhoff, R., P. Raisch, V. Frey, W. Wagner and F. Scholz, Control of dopant distribution profiles in GaInP laser diodes with Mg- and Se-doped AlInP cladding layers 195 (1998) 132
Wintz, M., see Rocabois, P. 198/199 (1999) 838
Witkamp, G.J., see van der Ham, F. 198/199 (1999) 744
Witkamp, G.J., see Oosterhof, H. 198/199 (1999) 754
Witkamp, G.J., see Zijlema, T.G. 198/199 (1999) 789
Witkowska, B., see Miotkowska, S. 200 (1999) 483
Witthuhn, W., see Reislöhner, U. 197 (1999) 576
Witz, J., see Bancel, P.A. 191 (1998) 537
Woicik, J.C., see Gupta, J.A. 195 (1998) 34
Woitok, J., see Taudt, W. 191 (1998) 663
Wolf, D., see Eisener, B. 198/199 (1999) 321
Wolf, H., see Ostheimer, V. 198/199 (1999) 1184
Wollweber, J., see Schulz, D. 198/199 (1999) 1024
Wolter, J.H., see Verschuren, C.A. 200 (1999) 19
Wong, J., see Tanaka, T. 192 (1998) 141
Wood, D.A., see Lane, D.W. 197 (1999) 743
Wright, B.S., see Declercq, J.-P. 196 (1999) 595
Wright, B.S., see Carter, D.C. 196 (1999) 602
Wright, B.S., see Carter, D.C. 196 (1999) 610
Wright, B.S., see Carter, D.C. 196 (1999) 623
Wright, P.J., see Lane, P.A. 192 (1998) 423
Wu, D., see Wu, J. 197 (1999) 95
Wu, G., B. Hu, S. Gao, Y. Li, J. Du, C. Tang, K. Jia and W. Zhan, Growth and spin reorientation transition of $Tb(Fe,Ti)_{12}$ single crystal 192 (1998) 417
Wu, G.H., see Li, Y.X. 191 (1998) 282
Wu, H.Z., J.Y. Huang, Z.Z. Ye, X.B. Jiang, X. Shou and D.L. Que, Strain relaxation in graded SiGe grown by ultra-high vacuum chemical vapor deposition (UHVCVD) 191 (1998) 72
Wu, J., see Yaguchi, H. 195 (1998) 323
Wu, J., H. Yaguchi, K. Onabe and Y. Shiraki, Stimulated emission from optically pumped cubic GaN/AlGaN double heterostructures 197 (1999) 73
Wu, J., B. Xu, H.X. Li, Q.W. Mo, Z.G. Wang, X.M. Zhao and D. Wu, $InAs/In_{0.52}Al_{0.48}As$ quantum wire structure with the specific layer-ordering orientation on InP(0 0 1) 197 (1999) 95
Wu, J., see Liu, F.-Q. 197 (1999) 789
Wu, J., see Fan, S. 198/199 (1999) 542
Wu, M.-C., see Yang, C.-C. 200 (1999) 32
Wu, M.-C., see Yang, C.-C. 200 (1999) 39
Wu, M.-C., see Lee, C.-Y. 200 (1999) 382
Wu, M.F., see Jin, S. 194 (1998) 189
Wu, R.H., see Xu, D.P. 191 (1998) 646
Wu, W., see Mo, Y. 191 (1998) 459
Wu Xing, see Song Youting 194 (1998) 379
Wu, Z., see Fu, Z. 193 (1998) 316
Wubbolts, F.E., see Domingo, C. 198/199 (1999) 760
Wubbolts, F.E., O.S.L. Bruinsma and G.M. van Rosmalen, Dry-spraying of ascorbic acid or acetaminophen solutions with supercritical carbon dioxide 198/199 (1999) 767

Xia, Y., see Mo, Y. 191 (1998) 459
Xie, B.-X., see Zhu, D.-W. 196 (1999) 356
Xie, J., see Zou, X. 200 (1999) 441
Xie, K., see Wang, R.-p. 200 (1999) 505
Xie, Z.-P., see Xu, G.-Y. 200 (1999) 143
Xu, B., see Gong, Q. 192 (1998) 376
Xu, B., see Wu, J. 197 (1999) 95
Xu, B., see Liu, F.-Q. 197 (1999) 789
Xu, B., see Xu, H. 200 (1999) 70
Xu, B., see Zhou, W. 200 (1999) 608
Xu, D., see Ma, W.J. 193 (1998) 430
Xu, D.P., H. Yang, L.X. Zheng, X.J. Wang, L.H. Duan and R.H. Wu, Gallium diffusion through cubic GaN films grown on GaAs(1 0 0) at high-temperature using low-pressure MOVPE 191 (1998) 646
Xu, G.-Y., J.-B. Li, Y. Huang and Z.-P. Xie, Fabrication and morphology of different color NbC_x whiskers 200 (1999) 143

Xu, H., Q. Gong, B. Xu, W. Jiang, J. Wang, W. Zhou and Z. Wang, Structural and optical characteristics of self-organized InAs quantum dots grown on GaAs (3 1 1)A substrates 200 (1999) 70

Xu, H.Z., see Zhou, W. 200 (1999) 608

Xu, J., see Taudt, W. 191 (1998) 663

Xu, J., X.J. Cheng, A. Behres and K. Heime, Calculation of lateral distribution of lattice constant for horizontal MOVPE grown quaternary alloys 193 (1998) 50

Xu, J. and X.J. Cheng, Analysis compositional homogeneity for MOVPE grown ternary alloys in the horizontal reactor with a rotating susceptor 193 (1998) 636

Xu, J., X.J. Cheng, A. Behres and K. Heime, Erratum to "Calculation of lateral distributions of lattice constant for horizontal MOVPE grown quaternary alloys". [J. Crystal Growth 193 (1998) 50] 193 (1998) 738

Xu, J., see Pan, D. 196 (1999) 23

Xu, J., E. Towe, Q. Yuan and R. Hull, Beryllium doping and silicon amphotericity in (1 1 0) GaAs-based heterostructures: structural and optical properties 196 (1999) 26

Xu, J.-J. and D.-S. Yu, Examinations of dendritic growth theories with some latest numerical simulations and experimental data 198/199 (1999) 43

Xu, J.-J., see Yu, D.-S. 198/199 (1999) 49

Xu Jianwei, Zhou Yongzong, Zhou Guoqing, Xu Ke, Deng Peizhen and Xu Jun, Growth of large-sized sapphire boules by temperature gradient technique (TGT) 193 (1998) 123

Xu Jun, see Zhou Guoqing 191 (1998) 517

Xu Jun, see Xu Jianwei 193 (1998) 123

Xu Jun, see Xu Ke 193 (1998) 127

Xu Jun, see Zhang Shoudu 197 (1999) 901

Xu Ke, see Zhou Guoqing 191 (1998) 517

Xu Ke, see Xu Jianwei 193 (1998) 123

Xu Ke, Xu Jun, Deng Peizhen, Zhou Yongzong, Zhou Guoqing, Qiu Rongsheng and Fang Zujie, γ-$LiAlO_2$ single crystal: a novel substrate for GaN epitaxy 193 (1998) 127

Xu, L.B., The formation of an inhomogeneous distribution of oxygen in CZ-Si crystal. An investigation with quantum reaction–diffusion equation 193 (1998) 541

Xu, L.B., A statistical thermodynamic model for oxygen segregation during Czochralski growth of silicon single crystals 200 (1999) 414

Xu Shao-hong, see Jiang Xue-yin 191 (1998) 692

Xu, W., see Ma, D. 194 (1998) 398

Xu, X.G., Ch. Giesen, R. Hövel, M. Heuken and K. Heime, Surface morphology and growth rate variation of InP on patterned substrates using tertiarybutylphosphine 191 (1998) 341

Xu, X.G., see Giesen, Ch. 195 (1998) 85

Xu, X.G., S. McLaughlin, J. Hu, S.P. Watkins and C.R. Bolognesi, Comparison of single- and double-barrier pseudomorphic InGaP/InGaAs HFETs 195 (1998) 687

Xu, X.W., T.C. Chong, L. Li, H. Kumagai and M. Hirano, Top seeded solution growth and characterisation of ferroelectric potassium lithium niobate crystals 198/199 (1999) 536

Xu, X.W., see Shi, L.P. 198/199 (1999) 551

Xu, Y., see Liu, C. 196 (1999) 111

Xu, Z.Y., see Wang, Z.M. 192 (1998) 97

Yablonski, G.P., see Yakimovich, V.N. 198/199 (1999) 975

Yabuzaki, J., see Adachi, H. 198/199 (1999) 568

Yaguchi, H., J. Wu, B. Zhang, Y. Segawa, H. Nagasawa, K. Onabe and Y. Shiraki, Micro Raman and micro photoluminescence study of cubic GaN grown on 3C-SiC(0 0 1) substrates by metalorganic vapor phase epitaxy 195 (1998) 323

Yaguchi, H., see Biwa, G. 195 (1998) 574

Yaguchi, H., see Wu, J. 197 (1999) 73

Yakimova, R., see Tuominen, M. 193 (1998) 101

Yakimova, R., see Syväjärvi, M. 197 (1999) 147

Yakimova, R., see Syväjärvi, M. 197 (1999) 155

Yakimova, R., see Syväjärvi, M. 198/199 (1999) 1019

Yakimovich, V.N., see Korzun, B.V. 198/199 (1999) 821

Yakimovich, V.N., V.I. Levchenko, G.P. Yablonski, V.I. Konstantinov, L.I. Postnova and A.A. Kutas, Vapour growth of bulk ZnSe single crystals 198/199 (1999) 975

Yakimovich, V.N., see Levchenko, V.I. 198/199 (1999) 980

Yalovets, T.N., see Borodin, V.A. 198/199 (1999) 201

Yamada, J.-i., see Anzai, H. 191 (1998) 148

Yamada, K., see Kaneko, N. 197 (1999) 818

Yamaguchi, S., M. Kariya, S. Nitta, H. Kato, T. Takeuchi, C. Wetzel, H. Amano and I. Akasaki, Structural and optical properties of AlInN and AlGaInN on GaN grown by metalorganic vapor phase epitaxy 195 (1998) 309

Yamahata, S., see Watanabe, N. 195 (1998) 48
Yamahata, S., see Watanabe, N. 200 (1999) 599
Yamamoto, K., see Kawaguchi, T. 191 (1998) 125
Yamamoto, M. and K. Torii, Evaluation of the onset of oscillatory thermocapillary convection in liquid bridge with empirical correlations in terms of a modified Marangoni number 197 (1999) 967
Yamamoto, N., K. Kishi, Y. Kondo, S. Matsumoto, R. Iga, Y. Kadota, H. Okamoto and H. Mawatari, Ammonium sulfide combined etching (ACE): an effective treatment for reducing impurities prior to MOVPE InP regrowth in a process using hydrocarbon gas reactive ion etching (RIE) 193 (1998) 16
Yamanobe, M., see Matsuoka, M. 198/199 (1999) 1299
Yamaoka, S., see Hong, S.M. 200 (1999) 326
Yamashiki, A., see Kousai, S. 198/199 (1999) 1119
Yamashiki, A. and T. Nishinaga, Arsenic pressure dependence of incorporation diffusion length on (0 0 1) and (1 1 0) surfaces and inter-surface diffusion in MBE of GaAs 198/199 (1999) 1125
Yamashita, Y., see Irie, S. 198/199 (1999) 939
Yamauchi, Y. and H. Horikawa, Doping characteristics of n-type InP using phenylsilane and TBP by MOVPE 195 (1998) 74
Yamauchi, Y., see Nishida, T. 195 (1998) 459
Yamaura, M., see Hirose, S. 194 (1998) 16
Yan, Z., S. Naritsuka and T. Nishinaga, Step sources in microchannel epitaxy of InP 192 (1998) 11
Yan, Z., S. Naritsuka and T. Nishinaga, Interface supersaturation dependence of step velocity in liquid-phase epitaxy of InP 198/199 (1999) 1077
Yan, Z., see Naritsuka, S. 198/199 (1999) 1082
Yanagiya, S.-i., G. Sazaki, S.D. Durbin, S. Miyashita, T. Nakada, H. Komatsu, K. Watanabe and M. Motokawa, Effect of a magnetic field on the orientation of hen egg-white lysozyme crystals 196 (1999) 319
Yang, B., see Yang, Q.K. 192 (1998) 28
Yang, B.J., see Yu, G. 196 (1999) 77
Yang, C.-C., G.-C. Chi, C.-K. Huang and M.-C. Wu, The improvement of GaN epitaxial layer quality by the design of reactor chamber spacing 200 (1999) 32
Yang, C.-C., C.-K. Huang, G.-C. Chi and M.-C. Wu, Growth and characterization of GaN by atomsphere pressure metalorganic chemical-vapor deposition with a novel separate-flow reactor 200 (1999) 39
Yang Changxi, see Song Youting 194 (1998) 379
Yang, G., see Lu, L. 194 (1998) 25
Yang, G.C., see Li, J.F. 192 (1998) 462
Yang, G.M., see Joo, H.-B. 194 (1998) 161
Yang, H., see Xu, D.P. 191 (1998) 646
Yang, H., see Mawst, L.J. 195 (1998) 609
Yang, H.-F., P.-D. Han, L.-S. Cheng, Z. Zhang, S.-K. Duan and X.-G. Teng, Microstructure evolution of GaN buffer layer on $MgAl_2O_4$ substrate 193 (1998) 478
Yang, P., see Cheng, J. 194 (1998) 89
Yang, Q., J. Chen and A. Li, Photoluminescence study of InGaAs/InAlAs single and multiple quantum wells 194 (1998) 31
Yang, Q.K., A.Z. Li, Y.G. Zhang, B. Yang, O. Brandt and K. Ploog, Growth and mosaic model of GaN grown directly on 6H–SiC(0 0 0 1) by direct current plasma assisted molecular beam epitaxy 192 (1998) 28
Yang, Q.K., see Chen, J.X. 193 (1998) 28
Yang Shangfeng, Su Genbo, Li Zhengdong and Jiang Rihong, Rapid growth of KH_2PO_4 crystals with additives 197 (1999) 383
Yang, X.P., see Wang, Z.M. 192 (1998) 97
Yang, Y., see Zhang, W. 194 (1998) 263
Yang, Z., see Cheng, L. 191 (1998) 641
Yano, J., see Takiguchi, H. 193 (1998) 641
Yano, J., see Kaneko, N. 197 (1999) 263
Yano, J., see Ueno, S. 198/199 (1999) 1326
Yao, T., see Ko, J.M. 192 (1998) 157
Yap, Y.K., Y. Mori, S. Kida, T. Aoyama and T. Sasaki, Carbon nitride thin films synthesized at high temperature by using RF-plasma PLD 198/199 (1999) 1028
Yase, K., see Yoshida, Y. 198/199 (1999) 923
Yashiro, H., see Kubota, N. 196 (1999) 156
Yasuhiro, S., see Jing, C.J. 200 (1999) 204
Yates, H.M., M.E. Pemble, H. Míguez, A. Blanco, C. López, F. Meseguer and L. Vázquez, Atmospheric pressure MOCVD growth of crystalline InP in opals 193 (1998) 9
Yates, H.M., see Yates, R.F. 195 (1998) 174
Yates, R.F., H.M. Yates and M.E. Pemble, Surface photoabsorption interferometry studies of the growth of InP and GaP on glass 195 (1998) 174
Yatsunyk, L., see Panchuk, O. 197 (1999) 607
Ye, Q. and B.H.T. Chai, Crystal growth of $YCa_4O(BO_3)_3$ and its orientation 197 (1999) 228

Ye, Z.Z., see Wu, H.Z. 191 (1998) 72

Yeckel, A., Y. Zhou, M. Dennis and J.J. Derby, Three-dimensional computations of solution hydrodynamics during the growth of potassium dihydrogen phosphate. II. Spin down 191 (1998) 206

Yelisseyev, A.P., L.I. Isaenko, A.I. Belov and A.A. Merkulov, Yb^{3+} doping of nonlinear $KTiOAsO_4$ (KTA) single crystals 198/199 (1999) 555

Yen, W.M., see Jia, W. 200 (1999) 179

Yeo, P., see Arès, R. 195 (1998) 234

Yi, M.-S., see Paek, J.-S. 200 (1999) 55

YiJi, P., see Obara, K. 198/199 (1999) 894

YiJi, P., see Obara, K. 198/199 (1999) 917

Yoda, S., see Sawada, T. 191 (1998) 225

Yokota, M., see Kubota, N. 196 (1999) 156

Yokota, M., see Kubota, N. 197 (1999) 388

Yokoyama, C., Y. Tamura and Y. Nishiyama, Crystal growth rates of tricaprin and trilaurin under high pressures 191 (1998) 827

Yonenaga, I. and M. Nonaka, Czochralski growth of bulk crystals of $Ge_{1-x}Si_x$ alloys. II. Si-rich alloys 191 (1998) 393

Yonenaga, I. and Y. Murakami, Segregation during the seeding process in the Czochralski growth of GeSi alloys 191 (1998) 399

Yonenaga, I., Czochralski growth of GeSi bulk alloy crystals 198/199 (1999) 404

Yoo, H.-D., see Hoe Wang, J. 198/199 (1999) 120

Yoo, T.K., see Kim, S.T. 194 (1998) 37

Yoon, C.S., see Ryu, G. 191 (1998) 190

Yoon, C.S., see Ryu, G. 191 (1998) 492

Yoon, J.K., see Kang, G.Y. 193 (1998) 615

Yoon, S.F., P.H. Zhang, H.Q. Zheng and K. Radhakrishnan, The effects of arsenic pressure on the properties of $In_{1-x-y}Ga_xAl_yAs$ layers grown by molecular beam epitaxy 191 (1998) 24

Yoon, S.F., K.W. Mah, H.Q. Zheng and P.H. Zhang, Effects of substrate temperature on the properties of $In_{0.48}Ga_{0.52}P$ grown by molecular-beam epitaxy using a valved phosphorus cracker cell 191 (1998) 613

Yoon, S.F., P.H. Zhang, H.Q. Zheng, K. Radhakrishnan and G.I. Ng, The effects of beryllium doping in InGaAlAs layers grown by molecular beam epitaxy 193 (1998) 285

Yoon, S.F., P.Y. Lui and H.Q. Zheng, Characterization of solid source MBE-grown $In_{0.48}Ga_{0.52}P/In_{0.2}Ga_{0.8}As/GaAs$ structures using X-ray reflectivity technique 197 (1999) 59

Yoon, S.F., see Shi, W. 197 (1999) 89

Yoon, S.F., see Zheng, H.Q. 197 (1999) 762

Yoon, S.F., see Zhang, D.H. 198/199 (1999) 1141

Yoon, S.Y., see Hong, S.K. 191 (1998) 275

Yoon, Y.S., see Kim, T.W. 193 (1998) 496

York, P., see Shekunov, B.Yu. 198/199 (1999) 1345

Yoshida, A., see Hirose, S. 194 (1998) 16

Yoshida, S. and J. Suzuki, High quality GaN grown by a gas-source molecular-beam epitaxy and its electrical property 191 (1998) 279

Yoshida, Y., H. Takiguchi, T. Hanada, N. Tanigaki, E.-M. Han and K. Yase, Control of growth mechanism and optical properties of p-sexiphenyl thin films on ionic crystal substrates 198/199 (1999) 923

Yoshikawa, A., see Epelbaum, B.M. 198/199 (1999) 471

Yoshimura, J., T. Sakamoto, S. Usui and S. Kimura, X-ray perfection study of Verneuil-grown $SrTiO_3$ crystals 191 (1998) 483

Yoshimura, M., see Furuya, H. 198/199 (1999) 560

Yoshino, T., see Kawaguchi, T. 191 (1998) 125

Yoshioka, Y., T. Matsui, M. Kasuga and T. Irisawa, Effects of impurities on lateral growth of crystals 198/199 (1999) 71

Youn, C.J., see Lee, H. 191 (1998) 59

Young, C.-C., see Chen, J.-C. 198/199 (1999) 476

Yu, D., see Zhou, G. 197 (1999) 129

Yu, D.-S., see Xu, J.-J. 198/199 (1999) 43

Yu, D.-S. and J.-J. Xu, Dendritic growth with external flow: interfacial wave theory and its comparison with experiments 198/199 (1999) 49

Yu, F., Structure study of $Hg_{1-x}Cd_xTe$–HgTe superlattice and CdTe/ZnTe/GaAs heterojunctions 197 (1999) 1003

Yu, G., X.W. Fan, J.Y. Zhang, B.J. Yang, X. Zhao, D. Shen and Y.M. Lu, The growth of ZnSe by photo-assisted metalorganic chemical vapor deposition (MOCVD) 196 (1999) 77

Yu, P.Y., see Lee, H. 191 (1998) 59

Yu, Z., M.A.L. Johnson, J.D. Brown, N.A. El-Masry, J.W. Cook Jr. and J.F. Schetzina, Study of the epitaxial–lateral-overgrowth (ELO) process for GaN on sapphire 195 (1998) 333

Yu, Z.-Q., see D'Hondt, M. 195 (1998) 655

Yuan, G., see Ning, Y. 191 (1998) 39

Yuan, H., see Jia, W. 200 (1999) 179

Yuan, Q., see Xu, J. 196 (1999) 26

Yuan, S., see Li, G. 195 (1998) 54

Yuan, Y. and J. Pan, The effect of vapor phase on the growth of TiC whiskers prepared by chemical vapor deposition 193 (1998) 585
Yuferev, V.S., see Polovko, Yu.A. 198/199 (1999) 182
Yurkin, A.M., see Pylneva, N.A. 198/199 (1999) 546

Zaccai, G., see Ebel, C. 196 (1999) 395
Zacher, Th., see Franke, T. 193 (1998) 451
Zagari, A., see Sica, F. 196 (1999) 305
Zaginey, A., B. Kotlyarchuk, V. Savitsky, O. Storchun and V. Pysarevsky, Modification of CdTe–HgTe defect substructure and carrier concentration by laser irradiation 194 (1998) 317
Zaitseva, N., J. Atherton, R. Rozsa, L. Carman, I. Smolsky, M. Runkel, R. Ryon and L. James, Design and benefits of continuous filtration in rapid growth of large KDP and DKDP crystals 197 (1999) 911
Zaleski, A., see Bryja, L. 197 (1999) 694
Zan, Y., see Wang, L. 193 (1998) 484
Zarudi, I., see Lereah, Y. 198/199 (1999) 62
Zaslavsky, B.G., B.V. Grinyov, V.S. Suzdal, A.M. Kudin, I.I. Kisil, S.I. Vasetsky and A.I. Mitichkin, Automated growing of large alkali halide single crystals 198/199 (1999) 856
Zaslavsky, B.G., Automated pulling of large-diameter alkali halide scintillation single crystals from the melt 200 (1999) 476
Zauner, A.R.A., see de Theije, F.K. 197 (1999) 37
Ždánský, K., see Vacková, S. 197 (1999) 599
Zeimer, U., see Bugge, F. 195 (1998) 676
Žekić, A.A., see Mitrović, M.M. 198/199 (1999) 687
Zelmon, D.E., see Singh, N.B. 198/199 (1999) 588
Zeng, H., see Fu, Y.-J. 198/199 (1999) 682
Zeng, H.C., see Balakumar, S. 194 (1998) 195
Zeng, H.C., see Balakumar, S. 197 (1999) 186
Zeng, J., L. Wang, J. Gao, Z. Song, X. Zhu and C. Lin, Structural and electrical characteristics of oriented $Pb(Zr_{0.52}Ti_{0.48})O_3$ ferroelectric thin films deposited on diamond substrates by a simple sol–gel process 197 (1999) 874
Zeng, Y., see Wang, H. 191 (1998) 627
Zeng, Y.-P., see Zhang, J.-P. 192 (1998) 471
Zeng, Y.-P., see Zhang, J.-P. 197 (1999) 368
Zeng, Y.P., see Zhuang, Q.D. 200 (1999) 375
Zeng Yiping, see Zhou Hongwei 191 (1998) 361
Zerrai, A., K. Cherkaoui, G. Marrakchi, G. Brémond, P. Fougères, M. Hage-Ali, J.M. Koebel and P. Siffert, Influence of deep levels on CdZnTe nuclear detectors 197 (1999) 646
Zerrai, A., see Zumbiehl, A. 197 (1999) 670
Zerrai, A., M. Dammak, G. Marrakchi, G. Brémond, R. Triboulet and Y. Marfaing, Investigation of deep levels in vanadium-doped CdTe and CdZnTe 197 (1999) 729
Zettler, J.-T., see Pristovsek, M. 195 (1998) 1
Zettler, J.-T., K. Haberland, M. Zorn, M. Pristovsek, W. Richter, P. Kurpas and M. Weyers, Real-time monitoring of MOVPE device growth by reflectance anisotropy spectroscopy and related optical techniques 195 (1998) 151
Zettler, J.-T., see Hardtdegen, H. 195 (1998) 211
Zettler, J.-T., see Zorn, M. 195 (1998) 223
Zettler, J.-T., see Steimetz, E. 195 (1998) 530
Zhan, W., see Wu, G. 192 (1998) 417
Zhang, B., see Ning, Y. 191 (1998) 39
Zhang, B., see Yaguchi, H. 195 (1998) 323
Zhang, D.H., see Shi, W. 197 (1999) 89
Zhang, D.H., W. Shi and S.F. Yoon, Characterisation of p-doped InGaAs/GaAs quantum wells for infrared photodetector application 198/199 (1999) 1141
Zhang Daofan, see Song Youting 194 (1998) 379
Zhang, G., see Cheng, L. 191 (1998) 641
Zhang, H., see Zheng, L.L. 191 (1998) 243
Zhang, H., see Zhang, H. 193 (1998) 370
Zhang, H., X. Meng, L. Zhu, C. Wang, P. Wang, H. Zhang, Y.T. Chow and J. Dawes, Growth and laser properties of laser crystal $Nd:Gd_{0.8}La_{0.2}VO_4$ 193 (1998) 370
Zhang, H., see Zhang, T. 198/199 (1999) 141
Zhang, H., see Meng, X. 200 (1999) 199
Zhang, H., X. Meng, L. Zhu, P. Wang, X. Liu, R. Cheng, J. Dawes, P. Dekker, S. Zhang and L. Sun, Growth and laser properties of $Yb:Ca_4YO(BO_3)_3$crystal 200 (1999) 335
Zhang, J., see Li, X. 191 (1998) 31
Zhang, J., see Li, X. 191 (1998) 34
Zhang, J.-P., D.-Z. Sun, X.-B. Li, X.-L. Wang, R.-H. Fu and M.-Y. Kong, The growth of an AlGaN/GaN modulation-doped heterostructure by NH_3 source molecular beam epitaxy 192 (1998) 93
Zhang, J.-P., D.-Z. Sun, X.-L. Wang, X.-B. Li, M.-Y. Kong, Y.-P. Zeng, J.-M. Li and L.-Y. Lin, The effect of buried $Al_xGa_{1-x}N$ isolating layers on the transport properties of GaN deposited on sapphire substrate by molecular beam epitaxy using NH_3 192 (1998) 471

Zhang, J.-P., D.-Z. Sun, X.-L. Wang, M.-Y. Kong, Y.-P. Zeng, J.-M. Li and L.-Y. Lin, p-Type co-doping study of GaN by photoluminescence 197 (1999) 368
Zhang, J.Y., see Yu, G. 196 (1999) 77
Zhang, L., see Sun, J. 195 (1998) 711
Zhang, L., see Ovanesyan, K.L. 198/199 (1999) 497
Zhang, L.T., see Chen, C.-M. 191 (1998) 873
Zhang, P.H., see Yoon, S.F. 191 (1998) 24
Zhang, P.H., see Yoon, S.F. 191 (1998) 613
Zhang, P.H., see Yoon, S.F. 193 (1998) 285
Zhang, P.H., see Zheng, H.Q. 197 (1999) 762
Zhang, S., see Zhang, H. 200 (1999) 335
Zhang Shoudu, Wang Siting, Shen Xingda, Wang Haobing, Zhong Heyu, Zhang Shunxing and Xu Jun, Czochralski growth of rare-earth orthosilicates–Y_2SiO_5 single crystals 197 (1999) 901
Zhang Shunxing, see Zhang Shoudou 197 (1999) 901
Zhang, T., G.-X. Wang, H. Zhang, F. Ladeinde and V. Prasad, Turbulent transport of oxygen in the Czochralski growth of large silicon crystals 198/199 (1999) 141
Zhang, W., H. Fu, Y. Yang and Z. Hu, A numerical model for spacing selection of lamellar eutectics grown from flowing liquids 194 (1998) 263
Zhang, X., see Kobayashi, J.T. 195 (1998) 252
Zhang, Y., see Lu, L. 194 (1998) 25
Zhang, Y.F., Y.H. Tang, N. Wang, C.S. Lee, I. Bello and S.T. Lee, One-dimensional growth mechanism of crystalline silicon nanowires 197 (1999) 136
Zhang, Y.G., see Yang, Q.K. 192 (1998) 28
Zhang, Z., see Cheng, L. 191 (1998) 641
Zhang, Z., see Yang, H.-F. 193 (1998) 478
Zhang, Z., see Wang, L. 193 (1998) 484
Zhang, Z., see Zhou, G. 197 (1999) 129
Zhang Zhi-lin, see Jiang Xue-yin 191 (1998) 692
Zhao, Q.X., O. Nur, U. Södervall, C.J. Patel, M. Willander, P.O. Holtz and W.B. de Boer, Optical study of APCVD-grown $Si_{1-x}Ge_x/Si$ quantum well structures under different post-growth annealing conditions 193 (1998) 328
Zhao Qian, Feng Songlin, Ning Dong, Zhu Haijun, Wang Zhiming and Deng Yuanming, Si doping effect on self-organized InAs/GaAs quantum dots 200 (1999) 603
Zhao, X., see Yu, G. 196 (1999) 77
Zhao, X., M. Ohkohchi, H. Shimoyama and Y. Ando, Morphology of carbon allotropes prepared by hydrogen arc discharge 198/199 (1999) 934
Zhao, X.M., see Wu, J. 197 (1999) 95
Zhavoronkov, N.V., see Melnikov, A.A. 197 (1999) 666
Zhdanov, A.V., see Borodin, A.V. 198/199 (1999) 220
Zheng, H.Q., see Yoon, S.F. 191 (1998) 24
Zheng, H.Q., see Yoon, S.F. 191 (1998) 613
Zheng, H.Q., see Yoon, S.F. 193 (1998) 285
Zheng, H.Q., see Yoon, S.F. 197 (1999) 59
Zheng, H.Q., see Shi, W. 197 (1999) 89
Zheng, H.Q., K. Radhakrishnan, H. Wang, P.H. Zhang, S.F. Yoon and G.I. Ng, Characterization of beryllium doped $Al_{0.33}Ga_{0.67}As$ layers grown by molecular beam epitaxy 197 (1999) 762
Zheng, H.Z., see Wang, Z.M. 192 (1998) 97
Zheng, L.L., D.J. Larson Jr. and H. Zhang, Role of thermotransport (Soret effect) in macrosegregation during eutectic/off-eutectic directional solidification 191 (1998) 243
Zheng, L.X., see Xu, D.P. 191 (1998) 646
Zhigunov, D.I., S.V. Shiryaev, L.A. Kurnevich, N.A. Kalanda, L.A. Kurochkin, S.N. Barilo, V.V. Vashuk and L.A. Smakhtin, Growth and chemical analysis of bulk $Nd_{2-x}Ce_xCuO_y$ single crystals 198/199 (1999) 605
Zhigunov, D.I., see Shiryaev, S.V. 198/199 (1999) 631
Zhigunov, D.I., see Barilo, S.N. 198/199 (1999) 636
Zhong Heyu, see Zhou Guoqing 191 (1998) 517
Zhong Heyu, see Zhang Shoudu 197 (1999) 901
Zhong, X., see Lin, L. 191 (1998) 586
Zhou, G., Z. Zhang and D. Yu, Growth morphology and micro-structural aspects of Si nanowires synthesized by laser ablation 197 (1999) 129
Zhou, G.-w., see Wang, R.-p. 200 (1999) 505
Zhou Guoqing, Xu Jun, Chen Xingda, Zhong Heyu, Wang Siting, Xu Ke, Deng Peizhen and Gan Fuxi, Growth and spectrum of a novel birefringent α-BaB_2O_4 crystal 191 (1998) 517
Zhou Guoqing, see Xu Jianwei 193 (1998) 123
Zhou Guoqing, see Xu Ke 193 (1998) 127
Zhou, H., see Wang, H. 191 (1998) 627
Zhou Hongwei, Zeng Yiping, Wang Hongmei, Dong Jianrong, Zhu Zhanping, Pan Liang and Kong Meiying, Growth and transport properties of InAs thin films on GaAs 191 (1998) 361
Zhou, J.M., see Cai, L.C. 197 (1999) 364
Zhou, T., see Ning, Y. 191 (1998) 39
Zhou Tang, see Song Youting 194 (1998) 379
Zhou, W., see Gong, Q. 192 (1998) 376

Zhou, W., see Liu, F.-Q. 197 (1999) 789
Zhou, W., see Xu, H. 200 (1999) 70
Zhou, W., Z.M. Zhu, F.Q. Liu, B. Xu, H.Z. Xu and Z.G. Wang, Substrate surface atomic structure influence on the growth of InAlAs quantum dots 200 (1999) 608
Zhou, W.C., see Chen, C.-M. 191 (1998) 873
Zhou, Y., see Yeckel, A. 191 (1998) 206
Zhou, Y., see Shi, W. 197 (1999) 905
Zhou, Y.-H., see Cang, H.-X. 192 (1998) 236
Zhou, Y.H., see Li, J.F. 192 (1998) 462
Zhou, Y.H., see Feng, J. 197 (1999) 393
Zhou, Y.-l., see Wang, R.-p. 200 (1999) 505
Zhou Yongzong, see Xu Jianwei 193 (1998) 123
Zhou Yongzong, see Xu Ke 193 (1998) 127
Zhu, D.-W., Q. Han, W. Qiu, R.L. Campbell, B.-X. Xie, A. Azzi and S.-X. Lin, Human 17β-hydroxysteroid dehydrogenase-ligand complexes: crystals of different space groups with various cations and combined seeding and co-crystallization 196 (1999) 356
Zhu, H., Z. Wang, H. Wang, L. Cui and S. Feng, Uniformity enhancement of the self-organized InAs quantum dots 197 (1999) 372
Zhu Haijun, see Zhao Qian 200 (1999) 603
Zhu, L., see Zhang, H. 193 (1998) 370
Zhu, L., see Meng, X. 200 (1999) 199
Zhu, L., see Zhang, H. 200 (1999) 335
Zhu, S., see Li, X. 191 (1998) 34
Zhu, S., see Zou, X. 200 (1999) 441
Zhu, X., see Zeng, J. 197 (1999) 874
Zhu Yong, see Song Youting 194 (1998) 379
Zhu, Z.M., see Zhou, W. 200 (1999) 608
Zhu Zhanping, see Zhou Hongwei 191 (1998) 361
Zhuang, Q.D., J.M. Li, Y.P. Zeng, L. Pan, H.X. Li, M.Y. Kong and L.Y. Lin, Structural characterization of InGaAs/GaAs quantum dots superlattice infrared photodetector structures 200 (1999) 375
Ziemer, K.S., C.D. Stinespring, L.S. Hirsch and T.H. Myers, Characterization of atomic hydrogen-etched HgCdTe surfaces 191 (1998) 594
Zijlema, T.G., R.J.A.J. Hollman, G.J. Witkamp and G.M. Van Rosmalen, The production of pure NaCl by the antisolvent crystallisation of $NaCl \cdot 2H_2O$ and a consecutive recrystallisation step 198/199 (1999) 789
Zimmermann, G., see Kauerauf, B. 193 (1998) 701
Zlatkowski, M., see Pines, V. 197 (1999) 355
Zocchi, M., see Depero, L.E. 198/199 (1999) 516
Zogg, H., see Furlong, M.J. 193 (1998) 114
Zolotoyabko, E., see Mainzer, N. 197 (1999) 542
Zolotoyabko, E., see Avrahami, Y. 198/199 (1999) 264
Zolotoyabko, E., see Ahilea, T. 198/199 (1999) 414
Zorn, M., see Zettler, J.-T. 195 (1998) 151
Zorn, M., T. Trepk, P. Kurpas, M. Weyers, J.-T. Zettler and W. Richter, In situ monitoring and control of InGaP growth on GaAs in MOVPE 195 (1998) 223
Zou, X., S. Zhu, J. Xie and J. Feng, Low-temperature synthesis of C_{60} thin films by ionized cluster beam deposition technique 200 (1999) 441
Zumbiehl, A., see Fougères, P. 197 (1999) 641
Zumbiehl, A., M. Hage-Ali, P. Fougeres, J.M. Koebel, R. Regal and P. Siffert, Electric field distribution in CdTe and $Cd_{1-x}Zn_xTe$ nuclear detectors 197 (1999) 650
Zumbiehl, A., P. Fougeres, M. Hage-Ali, J.M. Koebel, P. Siffert, A. Zerrai, K. Cherkaoui, G. Marrakchi and G. Bremond, Resistivity simulation of CZT materials 197 (1999) 670

ELSEVIER

Journal of Crystal Growth 200 (1999) 709–720

JOURNAL OF CRYSTAL GROWTH

Subject index to volumes 191–200

Apparatus
- for crucibleless method **198/199** (1999) 501
- for crystallization of ammonium perchlorate **194** (1998) 220
- for crystallization of lysozyme **200** (1999) 575
- for determining substrate orientation **192** (1998) 456
- for directional solidification **191** (1998) 252; **193** (1998) 701
- for environmental near-edge X-ray absorption fine structure spectroscopy **198/199** (1999) 275
- for epitaxy growth **200** (1999) 32, 39
- for forced flow growth **196** (1999) 261
- for forced stirring Czochralski of melt growth **191** (1998) 774
- for gallium nitride synthesis **196** (1999) 47
- for gravity influence on protein crystallization **196** (1999) 587
- for high pressure optical vessel **191** (1998) 827
- for in situ observation of crystallization **193** (1998) 61
- for in situ time resolved reflectance measurement **195** (1998) 205
- for industrial crystallizers **198/199** (1999) 729
- for laser manipulating of seeding **196** (1999) 685
- for levitated containerless growth of protein droplets **194** (1998) 384
- for measuring temperature field **198/199** (1999) 56
- for melt growth under microgravity **200** (1999) 1
- for microbatch crystallization **196** (1999) 450, 665
- for microgravity crystal growth **196** (1999) 572
- for multi-zone Mellen furnace **191** (1998) 904
- for physical vapor transport rate **193** (1998) 80
- for polythermal microbatch growth **196** (1999) 447
- for protein diagnostics **196** (1999) 638
- for protein growth **191** (1998) 537; **192** (1998) 282; **196** (1999) 602, 610
- for pyrochlore anti-ferromagnet growth of $Tb_2Ti_2O_7$ **191** (1998) 740
- for solubility measurements under high pressure **196** (1999) 204
- for supercritical precipitation **198/199** (1999) 760
- for III–V compounds **198/199** (1999) 1049
- for vertical Bridgman with submerged heater **191** (1998) 904
- for zone melting **192** (1998) 410

Biological aspects
- of antibody recognition **193** (1998) 656

Cellular growth
- of alloys **200** (1999) 583
- of aluminum zinc alloys **197** (1999) 393
- of diamond **198/199** (1999) 963
- of lead tin alloys **193** (1998) 692
- of transparent alloys **193** (1998) 701

Computer simulation
- of alpha-glycine **191** (1998) 791
- of atomic scale processes **198/199** (1999) 1
- of binary solutions **200** (1999) 592
- of buoyant melt flow **197** (1999) 341
- of chemical vapor deposition reactor **200** (1999) 527
- of convection **191** (1998) 206
- of crystal growth **194** (1998) 178
- of crystal lattices **196** (1999) 276
- of defect equilibrium **197** (1999) 493
- of dislocation density **196** (1999) 62
- of dissolution modes **198/199** (1999) 83
- of dissolution of sucrose **198/199** (1999) 749
- of ductile solidification **191** (1998) 261
- of effective mass theory growth
- – of chemical vapor deposition on diamond **194** (1998) 353
- – of gallium selenide **194** (1998) 331
- – of zinc selenide **194** (1998) 331
- of gamma-aminobutyric acid **191** (1998) 803
- of heat transfer **191** (1998) 413; **194** (1998) 321; **197** (1999) 435; **198/199** (1999) 101, 349, 710
- of impurity effect **198/199** (1999) 71
- of Kossel (100) surface **198/199** (1999) 22
- of lithium niobate melt flow **200** (1999) 204
- of liquid–liquid diffusion **196** (1999) 442
- of low supersaturation nucleation **193** (1998) 426
- of melt growth **193** (1998) 592
- of micro-pulling down process **193** (1998) 552
- of molecular dynamics **198/199** (1999) 114
- of molecular orbitals in gas phase **191** (1998) 405
- of nonplanar epitaxy **195** (1998) 596
- of Ostwald ripening **197** (1999) 973
- of oxygen doping in silicon **193** (1998) 541
- of phase field model **193** (1998) 712
- of plastic stress relaxation **198/199** (1999) 232
- of solid–liquid interface **194** (1998) 149
- of solute transport **194** (1998) 133

0022-0248/99/$ – see front matter © 1999 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(99)00166-9

- of strain relaxation **200** (1999) 421
- of sugar crystallization **198/199** (1999) 1294
- of thermocapillary convection **192** (1998) 335
- of thermotransport **191** (1998) 243
- of thin crystal growth **193** (1998) 679
- of two-dimensional impure systems **197** (1999) 317
- of vacancy aggregation **198/199** (1999) 399
- of vertical Bridgman **197** (1999) 983
- of wave theory **198/199** (1999) 17
- of X-ray diffraction **191** (1998) 161

Constitutional supercooling
- for solidification and melt **200** (1999) 276
- of alloys **197** (1999) 992
- of barium borate **193** (1998) 610
- of cadmium telluride **197** (1999) 397
- of dilute binary alloys **193** (1998) 271
- of flux melt **198/199** (1999) 716
- of lead tin alloys **193** (1998) 692
- of germanium silicon **192** (1998) 125
- of planar solidifying interface **191** (1998) 889

Convection **191** (1998) 206, 225, 760, 774, 879; **192** (1998) 63, 328, 335; **193** (1998) 90, 133, 219, 552, 692, 701; **194** (1998) 43, 247, 263, 379, 406; **196** (1999) 83, 261, 572, 623, 703; **197** (1999) 210, 297, 307, 341, 552, 749, 811, 967; **198/199** (1999) 67, 107, 129, 141, 147, 154, 161, 174, 182, 194, 297, 716
- of lithium borate **200** (1999) 172, 204

Defects
- modification by laser irradiation
- - of cadmium telluride/mercury telluride **194** (1998) 317

Dendritic growth
- of alloys **197** (1999) 992
- of aluminum copper alloy **192** (1998) 300
- of aluminum zinc alloys **197** (1999) 393
- of ammonium chloride **198/199** (1999) 10
- of ferrite **198/199** (1999) 1275
- of germanium **198/199** (1999) 62
- of ice **194** (1998) 138; **198/199** (1999) 10, 56
- of liquid crystals **193** (1998) 712
- of metal in quartz **198/199** (1999) 507
- of neodymium barium cuprate **193** (1998) 61; **200** (1999) 118
- of nickel **194** (1998) 406
- of nickel copper alloy **192** (1998) 462
- of ODS-alloys **193** (1998) 413
- of rapidly solidified alloys **198/199** (1999) 1256
- of sodium chloride **193** (1998) 174
- of succinonitrile **194** (1998) 143; **198/199** (1999) 43

Device characterization
- diodes **195** (1998) 79, 117, 409, 490, 617, 668; **197** (1999) 537, 557, 576, 586, 858; **198/199** (1999) 1092; **200** (1999) 382
- electro-optics **195** (1998) 706
- electroluminescent displays **194** (1998) 53
- electronic materials **191** (1998) 97, 746; **192** (1998) 84, 89, 430; **193** (1998) 9, 39, 491; **194** (1998) 317, 369; **195** (1998) 69, 91, 117, 223, 274, 490, 438, 499, 687; **196** (1999) 97; **197** (1999) 106, 177, 507, 547, 571, 576, 581, 593, 599, 630, 646, 650, 663, 670, 675, 684, 707, 858, 865, 874, 905; **198/199** (1999) 264, 414, 542, 821, 1179; **200** (1999) 441
- ferroelectric materials **191** (1998) 113
- heterojunction–bipolar–transistors **195** (1998) 217
- heterojunctions **194** (1998) 25; **195** (1998) 280, 297, 444, 660, 681; **197** (1999) 507, 675, 858; **200** (1999) 101
- heterostructures **191** (1998) 466
- infrared detectors **197** (1999) 547
- lasers **191** (1998) 275; **192** (1998) 56, 381, 448; **194** (1998) 25; **195** (1998) 242, 479, 495, 503, 603, 609, 624, 655, 660, 668, 676, 700; **197** (1999) 507, 529; **200** (1999) 13
- nanoparticles **193** (1998) 335
- quantum dots and wires **191** (1998) 347; **192** (1998) 89; **195** (1998) 6, 524, 530, 546, 552, 564, 569, 579; **196** (1999) 23; **197** (1999) 372, 680; **200** (1999) 77, 603, 608
- quantum wells **191** (1998) 679; **192** (1998) 363; **193** (1998) 328; **194** (1998) 8, 25, 31; **195** (1998) 6, 117, 297, 373, 444, 466, 558, 617, 660, 668, 676, 700; **197** (1999) 113, 507, 799; **198/199** (1999) 1141; **200** (1999) 77, 603, 608
- scintillators **197** (1999) 471, 475; **198/199** (1999) 292, 492
- solar cells **196** (1999) 13; **197** (1999) 733, 833
- superlattices **195** (1998) 117
- thermophotovoltaic **195** (1998) 346, 363
- transistor **195** (1998) 681

Diffusional control
- of beryllium in indium gallium arsenide **194** (1998) 297
- of cadmium selenide **193** (1998) 516
- of crystal growth **192** (1998) 185, 225
- of doping **197** (1999) 537
- of gallium nitride **191** (1998) 646
- of germanium in silicon–germanium **193** (1998) 328
- of heat flow control **192** (1998) 328
- of hen egg white lysozyme **196** (1999) 623, 703
- of lithium borate **200** (1999) 172, 276
- of protein crystal growth **196** (1999) 572
- of segregation **197** (1999) 749
- of solid growth **193** (1998) 197
- of tellurium in gallium antimonide **191** (1998) 904
- of vapor growth **197** (1999) 513
- of zinc **195** (1998) 79, 112

Diodes, see Device characterization

Dissolution of
- ammonium perchlorate **194** (1998) 220
- lead titanate **197** (1999) 195
- neodymium barium cuprate **193** (1998) 61
- potassium sulphate **197** (1999) 388
- proteins under high pressure **196** (1999) 204

Doping
- of silicon and carbon in III–V compounds **195** (1998) 54
- of zinc in gallium arsenide **191** (1998) 357

Electronic materials, see Device characterization

Epitaxy, see Thin film growth

Etching
- chemical **191** (1998) 153, 275, 589, 594; **192** (1998) 1, 63, 410, 417; **193** (1998) 16, 305, 510; **194** (1998) 43, 286, 379; **195** (1998) 199, 490, 495, 624; **196** (1999) 1; **197** (1999) 449, 475,

517, 702, 1012; **198/199** (1999) 17, 430, 526, 975; **200** (1999) 96, 185, 543
- electrochemical **198/199** (1999) 815
- gas **194** (1998) 277
- of low-angle boundaries **191** (1998) 108
- photolithographic **193** (1998) 510; **195** (1998) 495
- thermal **198/199** (1999) 471

Eutectic growth
- of aluminum–copper **194** (1998) 398
- of Al–$CuAl_2$ **191** (1998) 558
- of aluminum–silicon **191** (1998) 252
- of binary systems **194** (1998) 263
- of iron–aluminum–niobium **198/199** (1999) 850
- of LaB_6–ZnB_2 **191** (1998) 873
- of nickel–silicon alloys **198/199** (1999) 844
- of succinonitrile–carbontetrabromide system **191** (1998) 234

Heat flow control **198/199** (1999) 147, 165; **200** (1999) 329
- of closed-spaced growth **195** (1998) 725
- of Czochralski growth of silicon **191** (1998) 413
- of interface control **197** (1999) 552
- of numerical simulation **193** (1998) 430
- of vapor growth system **193** (1998) 426

Heterojunctions, see Device characterization
Heterostructures, see Device characterization
Hydrodynamics, see Convection

Kinetics
- of aggregation **200** (1999) 265
- of defects **197** (1999) 565
- of dendritic growth **191** (1998) 298
- of diffusion **195** (1998) 112; **197** (1999) 743
- of dissolution **198/199** (1999) 27, 32, 83
- of doping **195** (1998) 740
- of etching **198/199** (1999) 430
- of growth **191** (1998) 24, 34, 44, 166, 169, 178, 185, 199, 553, 651, 697, 760, 811, 827, 834, 861; **192** (1998) 18, 33, 97, 185, 200, 225, 300, 402, 430, 439, 448; **193** (1998) 80, 90, 114, 156, 164, 182, 189, 305, 342, 374, 382, 430, 470, 510, 528, 535, 577, 610; **194** (1998) 101, 109, 178, 214, 220, 292, 336, 353, 398, 426; **195** (1998) 58, 174, 187, 228, 234, 328, 459, 596, 718, 733; **196** (1999) 1, 115, 156, 220, 261, 285, 297, 471, 503, 623, 649, 703; **197** (1999) 7, 37, 78, 84, 147, 155, 244, 271, 286, 317, 355, 497, 616, 789, 805, 874, 905, 944, 973, 992; **198/199** (1999) 1, 10, 22, 32, 56, 62, 71, 77, 176, 270, 349, 516, 687, 723, 729, 738, 744, 754, 838, 1032, 1174, 1245, 1251, 1267, 1275, 1326; **200** (1999) 19, 32, 39, 213, 236, 251, 287, 297, 368, 583, 617
- of growth element shaped method **191** (1998) 779
- of impurity effects **197** (1999) 263
- of interface control **191** (1998) 18, 143, 166, 178, 282, 347; **192** (1998) 56; **194** (1998) 138; **195** (1998) 459, 516, 596; **196** (1999) 41, 261, 524; **197** (1999) 789; **198/199** (1999) 96, 165, 885, 900, 988; **200** (1999) 13, 341
- of nucleation **191** (1998) 178, 185, 421, 525, 811; **192** (1998) 395, 448; **193** (1998) 156, 257, 426, 510, 610, 641; **194** (1998) 16, 109, 239; **195** (1998) 174, 459; **196** (1999) 1, 220, 226, 243, 388, 471, 524, 649; **197** (1999) 155, 263, 789, 927; **198/199** (1999) 27, 67, 414, 631, 723, 729, 738; **200** (1999) 236
- of particle engulfment **193** (1998) 413
- of precursor analysis **191** (1998) 1
- of sedimentation **191** (1998) 199
- of surface processes **193** (1998) 451
- of thin film formation **193** (1998) 133
- of transformation **191** (1998) 783

Lasers, see Device characterization
Lasers, crystals for **198/199** (1999) 435, 454, 466, 482, 546, 555, 564, 980
- alumina **191** (1998) 520
- gadolinium ytterbium gallium garnet **194** (1998) 203
- holmium:yttrium aluminum borate **191** (1998) 767
- metal fluorides **200** (1999) 510
- nonlinear optical crystals **191** (1998) 135
- potassium gadolinium tungstate **196** (1999) 181
- sapphire **191** (1998) 779
- silicon nanowires **197** (1999) 129, 136
- silver gallium selenide **193** (1998) 597
- ultraviolet **193** (1998) 364, 370
- yttrium calcium oxaborate **200** (1999) 335

Lysozyme **191** (1998) 199; **194** (1998) 384; **196** (1999) 193, 204, 226, 243, 261, 285, 319, 332, 403, 503, 511, 535, 546, 559, 649, 674, 691, 703; **197** (1999) 257; **198/199** (1999) 661; **200** (1999) 265, 575

Melt growth technique
- by axial gradient solidification **198/199** (1999) 860
- by Bridgman–Stockbarger method
  - of aluminum–cerium systems **197** (1999) 286
  - of aluminum–lanthanum systems **197** (1999) 286
  - of aluminum–neodymium systems **197** (1999) 286
  - of BSCCO **192** (1998) 136
  - of cadmium manganese telluride **198/199** (1999) 872
  - of cadmium selenide **197** (1999) 655
  - of cadmium telluride **197** (1999) 406, 603, 607, 659, 707, 718, 724, 729
  - of cadmium zinc manganese telluride **197** (1999) 694
  - of cadmium zinc telluride **192** (1998) 196; **197** (1999) 427, 443, 635, 707, 718, 729
  - of copper indium diselenide **197** (1999) 169
  - of copper indium gallium selenide **200** (1999) 137
  - of copper indium selenide **198/199** (1999) 321
  - of copper zinc diselenide **191** (1998) 97
  - of epsilon-caprolactam **191** (1998) 169
  - of gallium antimonide **192** (1998) 63; **194** (1998) 43, 149; **197** (1999) 1, 749; **198/199** (1999) 379
  - of gallium arsenide **198/199** (1999) 325, 374
  - of germanium silicon **192** (1998) 125
  - of indium antimonide **200** (1999) 96
  - of indium arsenide **197** (1999) 1
  - of indium arsenide/gallium antimonide **198/199** (1999) 384
  - of lanthanum lutetium oxide **198/199** (1999) 497
  - of lead barium niobate **193** (1998) 347, 355
  - of lead potassium niobate **198/199** (1999) 542

– – of lead tin manganese telluride **200** (1999) 483
– – of lutetium ortho-aluminate **198/199** (1999) 492
– – of manganese bismuth **191** (1998) 243
– – of mercury manganese telluride **197** (1999) 688; **198/199** (1999) 297
– – of silver gallium selenide **193** (1998) 597
– – of succinonitrile **193** (1998) 701
– – of 2,3-dimethyl naphthalene **198/199** (1999) 665
– – of zinc mercury manganese telluride **197** (1999) 698
– – of zinc selenide **193** (1998) 39; **197** (1999) 466, 655; **198/199** (1999) 292
– – theory
– – – of growth under strong, low frequency rotating magnetic field **192** (1998) 318
– – – of heat flow **193** (1998) 430, 592
– – – of solidification **194** (1998) 247
– by cold traveling heater method
– – of zinc telluride **191** (1998) 685
– by crucibleless method **198/199** (1999) 501
– by Czochralski method
– – of alkali halides **200** (1999) 476
– – of alpha-barium borate **191** (1998) 517
– – of aluminum tungstate **200** (1999) 169
– – of aluminum tungstate oxide **197** (1999) 879
– – of barium borate **198/199** (1999) 161
– – of barium yttrium europium chloride **200** (1999) 515
– – of benzil **193** (1998) 252
– – of bismuth germanate **197** (1999) 865
– – of bismuth silicate **200** (1999) 329
– – of bismuth silicon oxide **198/199** (1999) 154
– – of bismuth telluride **198/199** (1999) 482
– – of bismuth tellurite **197** (1999) 210
– – of cadmium tungstate **198/199** (1999) 877; **200** (1999) 191
– – of calcium gadolinium alumate **196** (1999) 122
– – of cesium iodide **198/199** (1999) 865
– – of europium lithium niobate **200** (1999) 185
– – of gadolinium lanthanum vanadate **193** (1998) 370
– – of gadolinium ytterbium gallium garnet **194** (1998) 203
– – of gallium arsenide **191** (1998) 303; **198/199** (1999) 125, 325, 336, 343, 349, 355, 361
– – of germanium **193** (1998) 720
– – of germanium silicon **198/199** (1999) 404
– – of indium antimonide **193** (1998) 443
– – of indium phosphide **192** (1998) 1; **198/199** (1999) 129
– – of lanthanum galate **197** (1999) 204
– – of lanthanum strontium aluminum tantalate **194** (1998) 209
– – of large alkali halide **198/199** (1999) 856
– – of lead tungstate **191** (1998) 130; **198/199** (1999) 881
– – of lithium calcium aluminum fluoride **197** (1999) 896
– – of lithium niobate **191** (1998) 589; **198/199** (1999) 521
– – of lithium tantalate **197** (1999) 889
– – of lithium tetraborate **193** (1998) 364
– – of neodymium yttrium vanadate **200** (1999) 199
– – of potassium zinc chloride **200** (1999) 148
– – of rare earth gallium silicon dioxide **191** (1998) 746
– – of rubidium zinc chloride **200** (1999) 148
– – of scandium tungstate **200** (1999) 169
– – of silicon **191** (1998) 413; **192** (1998) 117; **193** (1998) 402, 541, 720; **194** (1998) 70, 76; **196** (1999) 111; **198/199** (1999) 120, 135, 141, 390, 409
– – of silicon germanium **191** (1998) 393, 399
– – of $Tb(Fe,Ti)_{12}$ **192** (1998) 417
– – of ytterbium lithium niobate **200** (1999) 185
– – of yttrium aluminum oxide **198/199** (1999) 435
– – of yttrium calcium oxyborate **197** (1999) 228
– – of yttrium orthosilicate **197** (1999) 901
– – theory of convection **197** (1999) 297, 307
– by edge-defined film-fed method
– – of alumina **191** (1998) 520
– – of potassium lithium niobate **194** (1998) 379
– by emulsification **197** (1999) 263
– by floating zone method **200** (1999) 1, 179
– – of barium aluminate **198/199** (1999) 869
– – of calcium aluminate **198/199** (1999) 869
– – of calcium boron **192** (1998) 346
– – of calcium lanthanum cuprate **197** (1999) 825
– – of chromium borate **200** (1999) 472
– – of decagonal aluminum–nickel–cobalt **191** (1998) 545
– – of fibrous yttrium iron garnet **193** (1998) 446
– – of gallium antimonide **191** (1998) 365
– – of gallium arsenide **198/199** (1999) 170
– – of lanthanum manganite **198/199** (1999) 511
– – of niobium dibromide **194** (1998) 430
– – of palladium **192** (1998) 410
– – of perovskite manganites **191** (1998) 294
– – of silicon **194** (1998) 76, 321; **198/199** (1999) 107
– – of strontium aluminate **198/199** (1999) 869
– – of strontium calcium cuprate **193** (1998) 55
– – of thallium dibromide **194** (1998) 430
– – of YB_{66} **192** (1998) 141
– – theory of convection **197** (1999) 967
– by gradient freezing method **192** (1998) 354
– by gradient projection method
– – of bismuth antimony **198/199** (1999) 811
– by high pressure Bridgman
– – of cadmium zinc telluride **197** (1999) 641
– by induction cold crucible
– – of silicon **193** (1998) 230
– by laser heated pedestal
– – of bismuth silicon oxide **198/199** (1999) 476
– – of lithium niobate **198/199** (1999) 531
– – of strontium hafnium oxide **200** (1999) 483
– by micro-pulling down method **198/199** (1999) 471
– – of potassium lithium niobate **194** (1998) 374
– – of potassium lithium tantalate niobate **194** (1998) 374
– – of silicon germanium **193** (1998) 552
– by plasma vertical gradient freeze
– – of calcium fluoride **198/199** (1999) 999
– – of lithium fluoride **198/199** (1999) 999
– by pressure
– – of succinonitrile **194** (1998) 143
– by self-seeding technique
– – of cadmium telluride **194** (1998) 309
– – of cadmium zinc telluride **194** (1998) 309

- by Skull melting **198/199** (1999) 188
- by Stepanov method **198/199** (1999) 201, 210, 215, 220, 227, 232
- by submerged heater method
- - of gallium antimonide **191** (1998) 904
- - of indium gallium antimonide **194** (1998) 1
- by supercooled solution
- - of cesium lithium hexaborate **191** (1998) 492
- - of meta-nitroaniline **191** (1998) 190
- by top seeded solution
- - of zinc magnesium yttrium quasicrystals **192** (1998) 152
- by travelling heater method
- - of copper indium diselenide **197** (1999) 177
- - of mercury cadmium telluride **197** (1999) 552
- - of quasicrystals **197** (1999) 963
- - of zinc telluride **197** (1999) 794
- by uniaxial solidification **198/199** (1999) 629; **200** (1999) 629
- - of alpha-aluminum oxide **193** (1998) 123, 127
- - of aluminum–silicon **191** (1998) 252
- - of binary alloys **193** (1998) 271; **200** (1999) 305
- - of gallium arsenide **198/199** (1999) 170
- - of lead–tin **191** (1998) 879
- - of neodymium barium cuprate **200** (1999) 118
- - theory of convection **193** (1998) 271
- by Verneuil method
- - of strontium titanate **191** (1998) 483
- by vertical gradient freeze method
- - of cadmium telluride **197** (1999) 413
- - of cadmium zinc telluride **197** (1999) 593
- - of indium gallium arsenide **197** (1999) 769
- - of mercury cadmium telluride **197** (1999) 593
- - of zinc selenide **197** (1999) 413
- - of zinc telluride **197** (1999) 413
- by zone melting **198/199** (1999) 466
- - of bismuth germanate **193** (1998) 623
- - of tellurium-doped zinc selenide **197** (1999) 471, 475
- general properties
- - density dependence on temperature **191** (1998) 711
- technical methods
- - of gas losses through silica glass **191** (1998) 897
- theory of microsolvability **198/199** (1999) 56

Microgravity, growth under **198/199** (1999) 182; **200** (1999) 182
- high pressure **196** (1999) 204
- of aluminum gallium arsenide **194** (1998) 166
- of ammonium chloride **191** (1998) 225
- of bismuth germanate **193** (1998) 623
- of gallium antimonide **191** (1998) 365; **192** (1998) 63; **200** (1999) 1
- of gallium arsenide **191** (1998) 586; **198/199** (1999) 170
- of horizontal growth **192** (1998) 328
- of lead tin alloys **193** (1998) 692
- of lysozyme **196** (1999) 319, 524, 623, 649, 703
- of manganese bismuth **191** (1998) 243
- of mercuric iodide **193** (1998) 80, 90
- of parvalbumin **196** (1999) 595
- of proteins **194** (1998) 133; **196** (1999) 261, 325, 442, 572, 602, 610, 638
- of semiconductors **198/199** (1999) 825
- of simulated conditions **194** (1998) 384
- of succinonitrile **194** (1998) 143; **198/199** (1999) 43
- of supercooled melts **197** (1999) 355
- of zirconia **198/199** (1999) 188
- theory of convection in floating zone **197** (1999) 967

Morphological stability **200** (1999) 276
- of aluminum copper alloy **192** (1998) 300
- of binary alloys **193** (1998) 271, 701; **200** (1999) 305
- of cadmium sulphide **197** (1999) 612
- of cadmium telluride on gallium arsenide **192** (1998) 109
- of calcite **198/199** (1999) 697
- of calcium carbonate **200** (1999) 236
- of clathrate hydrate **196** (1999) 164
- of crystal faces **191** (1998) 563
- of dendritic crystals **192** (1998) 462
- of DL-methionine **198/199** (1999) 1299
- of fat **198/199** (1999) 1315, 1352
- of gallium arsenide **195** (1998) 28
- of gallium nitride **195** (1998) 192
- of germanium **200** (1999) 617
- of germanium–germanium silicon interface **192** (1998) 125
- of gypsum **198/199** (1999) 704
- of indium arsenide/gallium antimonide **191** (1998) 651
- of interfaces **197** (1999) 31
- of L-glutamic acid **192** (1998) 225
- of L-isoleucine **194** (1998) 228
- of lead tin alloys **193** (1998) 692
- of macromolecular crystallization **196** (1999) 471
- of molybdate **194** (1998) 195
- of n-paraffin **198/199** (1999) 1281
- of neodymium yttrium vanadate **200** (1999) 199
- of niobium carbide **200** (1999) 143
- of protein crystals **193** (1998) 665
- of silicides **194** (1998) 189
- of silicon carbide **198/199** (1999) 1005
- of silicon germanium surfaces **193** (1998) 720
- of silver bromide **192** (1998) 215
- of spherulitic calcite **193** (1998) 374, 382
- of step kinetics **198/199** (1999) 38
- of strained crystals **193** (1998) 257
- of strontium lanthanum gallate **198/199** (1999) 440
- of titanium carbide whiskers **193** (1998) 585
- of vicinal (100) surfaces **200** (1999) 19
- of zinc selenide **196** (1999) 83

Nanoparticles, see Device characterization

Nucleation
- of abecarnil **198/199** (1999) 1307
- of aluminum–copper chloride **191** (1998) 558
- of aluminum nitride **200** (1999) 45
- of aluminum trihydrate **200** (1999) 558
- of apatites **197** (1999) 927
- of barium chromate **200** (1999) 227
- of barium sulphate **200** (1999) 227
- of benzoic crystals **198/199** (1999) 780
- of binary solutions **200** (1999) 592

- of binary systems **198/199** (1999) 27
- of cadmium sulphide **197** (1999) 616
- of cadmium telluride **193** (1998) 426
- of calcium carbonate **198/199** (1999) 738, 796
- of calcium oxalate **192** (1998) 448
- of calcium oxalate monohydrate **192** (1998) 243
- of calcium silicate hydrate **200** (1999) 565
- of cuprous chloride nanocrystals **196** (1999) 135
- of detergent solutions **191** (1998) 811
- of diamond **191** (1998) 459; **200** (1999) 326
- of ethanohexanol vapor **194** (1998) 239
- of fractures **191** (1998) 108
- of gallium nitride **195** (1998) 192; **197** (1999) 37; **200** (1999) 32, 39, 55
- of gibbsite **191** (1998) 525; **196** (1999) 174
- of grains **198/199** (1999) 374
- of gypsum **198/199** (1999) 704
- of ice **194** (1998) 138
- of ice and salt **198/199** (1999) 744
- of indium phosphide **191** (1998) 44
- of lysozyme **192** (1998) 257, 271; **196** (1999) 220, 226, 243, 649; **197** (1999) 257
- of macromolecular crystals **196** (1999) 250
- of n-hexadecane **197** (1999) 263
- of n-paraffin **191** (1998) 861
- of nanocrystals **191** (1998) 161
- of neodymium barium cuprate **193** (1998) 61; **200** (1999) 427
- of organic materials **198/199** (1999) 1345
- of paracetamol **198/199** (1999) 1297
- of poly-ethylene oxide **198/199** (1999) 1335
- of potassium chloride **198/199** (1999) 1330
- of primary seed **198/199** (1999) 605
- of proteins **196** (1999) 185, 325, 356, 365, 377, 388, 395, 415, 434, 456, 489; **198/199** (1999) 649, 656
- of secondary contact **198/199** (1999) 258
- of silicon **191** (1998) 459; **198/199** (1999) 425
- of titanium nitride **198/199** (1999) 838
- of triacylglycerol **198/199** (1999) 1326
- of tungsten silicide **197** (1999) 163
- of twins **197** (1999) 455
- of voids **198/199** (1999) 399
- of wax **198/199** (1999) 830
- of yttrium barium copper oxide **197** (1999) 379

Numbers
- Grashof **192** (1998) 328; **193** (1998) 430; **195** (1998) 725; **197** (1999) 297, 307; **198/199** (1999) 129, 147, 710, 754; **200** (1999) 204
- Hartman **192** (1998) 318; **197** (1999) 307, 341
- Marangoni **191** (1998) 365; **192** (1998) 335; **193** (1998) 552; **197** (1999) 811, 967; **198/199** (1999) 531; **200** (1999) 204
- Nusselt **191** (1998) 298
- Peclet **193** (1998) 133; **194** (1998) 398, 406; **196** (1999) 649, 261
- Prandtl **194** (1998) 406
- Rayleigh **194** (1998) 247; **197** (1999) 297, 307, 341, 983; **198/199** (1999) 147, 154
- Reynolds **191** (1998) 206; **194** (1998) 398; **195** (1998) 725; **197** (1999) 811
- Rossby **197** (1999) 297
- Sherwood **192** (1998) 328
- Taylor **197** (1999) 341

Phase diagrams, of
- aluminum nitride **200** (1999) 45
- bismuth based superconductors **198/199** (1999) 611
- bismuth oxide/titanium oxide **191** (1998) 512
- Bi–Pb–Sr–Ca cuprate **197** (1999) 141
- cadmium selenide telluride **197** (1999) 485
- cadmium sulphide/cadmium telluride **197** (1999) 743
- cadmium telluride **197** (1999) 406
- copper gallium diselenide/copper indium diselenide **191** (1998) 455
- endoglucanase-A **196** (1999) 297
- gadolinium vanadate **198/199** (1999) 444
- gallium arsenide **191** (1998) 303; **195** (1998) 28
- growth direction **198/199** (1999) 56
- iron aluminum niobium **198/199** (1999) 850
- iron–nickel–sulphur **193** (1998) 728
- LaB_6–ZnO_2 **191** (1998) 873
- lanthanum galate **197** (1999) 204
- lead titanate **197** (1999) 195
- lysozyme **196** (1999) 193, 332
- mercury telluride/manganese telluride **198/199** (1999) 303
- neodymium barium cuprate **193** (1998) 61; **200** (1999) 427
- nickel silicon alloys **198/199** (1999) 844
- phase transitions **191** (1998) 113
- potassium sulphate **198/199** (1999) 692
- proteins **196** (1999) 185, 204, 388, 415, 424; **198/199** (1999) 656, 911
- silver copper alloys **198/199** (1999) 911
- sodium chloride **198/199** (1999) 789
- succinonitrile–carbontetrabromide system **191** (1998) 234
- surface stoichiometry **195** (1998) 228
- $Tb(Fe,Ti)_{12}$ **192** (1998) 417
- tin selenide/zinc selenide **198/199** (1999) 287
- tricaprin **191** (1998) 827
- trilaurin **191** (1998) 827
- water and isoproxyethanol **198/199** (1999) 754
- zinc magnesium sulphide **198/199** (1999) 1196
- zinc sulphide **197** (1999) 485, 489

Precursor, for
- aluminum gallium arsenide **192** (1998) 79
- aluminum nitride **195** (1998) 733
- arsenic **195** (1998) 391
- arsenic trichloride **195** (1998) 199
- biological apatite **193** (1998) 182
- calcite **191** (1998) 153
- erbium **195** (1998) 105
- gallium nitride **191** (1998) 1; **195** (1998) 733
- magnesium selenide **193** (1998) 572
- metalorganic vapor phase epitaxy **195** (1998) 21, 58, 69, 85, 98, 105, 280, 391, 479, 733
- nanocrystalline ferrous molybdenum nitride **191** (1998) 92
- nickel zinc ferrite **192** (1998) 423
- nitrogen **195** (1998) 391

- oxygen **195** (1998) 63
- phosphine **196** (1999) 33
- ruthenium **195** (1998) 69
- silicon carbide **193** (1998) 335
- silicon doping **195** (1998) 91
- tantalum nitride **197** (1999) 236
- III–V compounds **195** (1998) 98, 630
- III-nitrides **191** (1998) 405
- YBCO **191** (1998) 290

Purification
- of epsilon-caprolactam **191** (1998) 169
- of gases **195** (1998) 314
- of glutamic acid specific protease **196** (1999) 313
- of palladium **192** (1998) 410
- of pentlandite **193** (1998) 728
- of proteins **196** (1999) 674
- of succinonitrile **193** (1998) 701
- of tertiarybutylarsine **195** (1998) 98
- of zinc selenide **197** (1999) 513

Quantum dots and wires, see Device characterization
Quantum wells, see Device characterization

Solid growth technique
- by phase separation
  - of cuprous chloride **196** (1999) 135
- by recapitalisation
  - of iron molybdenum nitride **191** (1998) 92
- by recrystallization
  - of calcium phosphate **197** (1999) 939
  - of tungsten sulphide **193** (1998) 109
  - of zinc selenide **197** (1999) 462, 480
- theory of heterogeneity **197** (1999) 317

Solution growth technique
- by batch crystallization
  - of endoglucanase-A **196** (1999) 297
  - of gibbsite **196** (1999) 174
  - of lysozyme **196** (1999) 220
- by benzene thermal growth
  - of gallium phosphide **192** (1998) 89
- by cold travelling heater method
  - of lead telluride **196** (1999) 71
- by constant evaporation
  - of benzoyl amino acetic acid **193** (1998) 674
- by electrochemistry
  - of calcium carbonate **200** (1999) 236
- by electrocrystallization
  - of organic superconductor $(TMTSF)_2ClO_4$ **191** (1998) 148
- by electrodeposition **198/199** (1999) 636
- by flux method
  - of barium borate **198/199** (1999) 161
  - of beta-barium borate **191** (1998) 774
  - of cadmium sulphide **198/199** (1999) 313
  - of copper gallium arsenide **198/199** (1999) 1190
  - of diamond **200** (1999) 326
  - of emeralds **193** (1998) 648
  - of gallium phosphide **198/199** (1999) 176
  - of lithium triborate **198/199** (1999) 546
  - of meta-nitroaniline **192** (1998) 236
  - of microbatch macromolecular growth **196** (1999) 447
  - of molybdate **194** (1998) 195
  - of neodymium barium cuprate **193** (1998) 61, 71
  - of neodymium boron carbonate **200** (1999) 435
  - of neodymium cerium cuprate **198/199** (1999) 605
  - of ortho-enstatite crystals **200** (1999) 155
  - of potassium gadolinium tungstate **196** (1999) 181
  - of potassium lithium niobate **193** (1998) 615; **198/199** (1999) 536
  - of potassium lithium tantalate niobate **197** (1999) 1012
  - of potassium titanil arsenate **198/199** (1999) 555
  - of potassium titanil phosphate **198/199** (1999) 551
  - of rare earth aluminum borate **191** (1998) 135
  - of strontium calcium cuprate **193** (1998) 55
  - of strontium sulphide **197** (1999) 504
  - of thulium vanadate **198/199** (1999) 449
  - of tungsten sulphide **193** (1998) 109
  - of yttrium barium copper oxide **197** (1999) 379
  - of yttrium barium cuprate **198/199** (1999) 600
- by gel method
  - of barium chromate **200** (1999) 227
  - of barium sulphate **200** (1999) 227
  - of collagen **196** (1999) 535
  - of fullerene nanoprecipitates **200** (1999) 126
  - of lysozyme **192** (1998) 257, 271
  - of octacalcium phosphate **194** (1998) 125; **198/199** (1999) 670
  - of zinc oxide **192** (1998) 430
- by high temperature method
  - of holmium:yttrium aluminum borate **191** (1998) 767
- by hydrothermal growth
  - of aluminum phosphate **191** (1998) 108
  - of blue quartz **196** (1999) 151
  - of calcite **192** (1998) 350
  - of lead titanate **197** (1999) 195
- by laser heated pedestal growth
  - of zinc lithium niobate **197** (1999) 221
- by low temperature method
  - of aluminum potassium sulphate **197** (1999) 921
  - of aluminum trihydroxide **197** (1999) 244
  - of amino acids **198/199** (1999) 1340
  - of aspartame **198/199** (1999) 1365
  - of cadmium sulphide **193** (1998) 114
  - of calcite **191** (1998) 783; **200** (1999) 213
  - of calcium phosphate **200** (1999) 550
  - of calcium spherulites **193** (1998) 374, 382
  - of calcium sulphate dihydrate **193** (1998) 150
  - of copper indium diselenide **193** (1998) 114
  - of cyclo-oxygenase-2 **196** (1999) 350
  - of endoglucanase **196** (1999) 297
  - of gibbsite **191** (1998) 525
  - of hen egg white lysozyme **200** (1999) 265
  - of hydroxyapatite **193** (1998) 182
  - of hydroxyapatite octacalcium **198/199** (1999) 677
  - of lead sulphide **191** (1998) 161

– – of lepidocrocite **192** (1998) 250
– – of L-glutamic acid **192** (1998) 225
– – of L-pyroglutamic acid **198/199** (1999) 578
– – of lysozyme **196** (1999) 261, 511, 623
– – of magnetite **192** (1998) 250
– – of manganese-doped zinc sulphide **191** (1998) 692
– – of n-alcohol crystals **193** (1998) 641
– – of n-paraffin **192** (1998) 307
– – of octacalcium phosphate **193** (1998) 182
– – of organic nonlinear crystals **198/199** (1999) 568
– – of pharmaceutical compounds **198/199** (1999) 1360
– – of potassium acid phthalate **193** (1998) 164
– – of potassium bichromate **193** (1998) 389
– – of potassium dihydrogen phosphate **193** (1998) 164; **194** (1998) 101, 109, 214; **197** (1999) 383; **198/199** (1999) 682, 687
– – of potassium niobate **191** (1998) 760
– – of potassium orthophosphate **197** (1999) 911
– – of potassium sulphate **196** (1999) 156
– – of proteinase-A **196** (1999) 291
– – of proteins **191** (1998) 820; **196** (1999) 442, 511
– – of silver nanocrystals **198/199** (1999) 806
– – of sucrose **192** (1998) 290
– – of unstable molecular compounds **191** (1998) 166
– – of yttrium potassium tungstate **197** (1999) 883
– – of zinc thiourea sulphate **197** (1999) 216
– – theory of growth kinetics **193** (1998) 189
– by magnetic field
– – of lysozyme **196** (1999) 319
– by polymer solvent
– – of lead sulphide nanocrystals **196** (1999) 126
– by precipitation
– – of silver bromide **191** (1998) 446
– by protein supersaturation
– – of subtilisin **193** (1998) 665
– by salt
– – of polyethylene glycol **196** (1999) 210
– – of proteins **196** (1999) 395
– by sedimentation
– – of hen egg white lysozyme **191** (1998) 199
– by sol–gel
– – of ferroelectrics **197** (1999) 874
– by top seeded solution growth
– – of bismuth titanium oxides **191** (1998) 512
– by vapor diffusion
– – of bovine seminal ribonuclease **196** (1999) 305
– – of human low density lipoprotein **196** (1999) 344
– – of lysozyme **192** (1998) 282
– – of proteins **196** (1999) 332, 365, 434, 665
– – of trichosanthin **192** (1998) 282
– – of urokinase **197** (1999) 254
– theory
– – of crystal morphology **192** (1998) 236
– – of crystal packing **196** (1999) 276
– – of growth **194** (1998) 214; **197** (1999) 944
Statistical mechanics, molecular theory
– of metals **191** (1998) 268
– of miscibility gap calculations **196** (1999) 67
– of nucleation **196** (1999) 234
– of protein interacting potentials **196** (1999) 193, 377, 415
– of segregation **200** (1999) 414
– of solid–liquid interface **200** (1999) 297
Stefan problem or moving boundary problem
– of dendritic array **200** (1999) 287
– of impure grains **197** (1999) 317
– of indium antimonide **198/199** (1999) 1066
– of indium phosphide **191** (1998) 341
– of liquid–solid interface **198/199** (1999) 1256, 1262
– of microsegregation of binary alloys **197** (1999) 325, 333, 355
– of poly-silicon **191** (1998) 386
– of porous media **198/199** (1999) 89
– of solidification and melt **200** (1999) 276
– of solidification of binary alloys **198/199** (1999) 1267
– of step kinetics **198/199** (1999) 38
– of vertical Bridgman **197** (1999) 983
Superconductivity materials, high T_c
– bulk
– – of BSCCO **192** (1998) 136
– film
– – of Bi–Pb–Sr–Ca cuprate **197** (1999) 141
– – of BSCCO **191** (1998) 421; **196** (1999) 122
– – of LBCO **196** (1999) 122
– – of PrCeCO **197** (1999) 818
– – of YBCO **191** (1998) 79, 290; **197** (1999) 376
Superlattices, multilayers
– of aluminum arsenide/gallium arsenide **195** (1998) 630
– of cadmium sulphide **200** (1999) 391
– of cadmium telluride/zinc telluride/gallium arsenide **197** (1999) 1003
– of gallium arsenide/gallium aluminum arsenide **196** (1999) 53
– of gallium arsenide/indium arsenide **195** (1998) 205
– of gallium indium nitride arsenide/gallium arsenide **195** (1998) 391
– of gallium indium phosphide/gallium arsenide **195** (1998) 117
– of gallium nitride/indium gallium nitride **195** (1998) 258
– of indium gallium arsenide/gallium arsenide on boron **192** (1998) 363
– of indium gallium arsenide phosphide **195** (1998) 637
– of indium selenide/gallium selenide **194** (1998) 331
– of lead selenide **198/199** (1999) 1211
– of lead telluride **198/199** (1999) 1211, 1216
– of mercury cadmium telluride/mercury telluride **197** (1999) 1003
– of nitrides **200** (1999) 353
– of semi-magnetic II–VI compounds **193** (1998) 572
– of silicon germanium/silicon **194** (1998) 426
– of zinc sulphide **200** (1999) 391
Surface energy, determination
– of ammonium chloride **198/199** (1999) 10
– of ionic crystals **194** (1998) 156
– of L-glutamic acid **192** (1998) 225
– of n-paraffin **193** (1998) 679
– of solid–liquid interface of pivalic acid **194** (1998) 119
Surface structure, of
– alpha-glycine **191** (1998) 791

- aluminum gallium arsenide **195** (1998) 596
- aluminum trihydrate **200** (1999) 558
- ammonium dihydrogen phosphate **192** (1998) 200
- barium nitrate **198/199** (1999) 246
- calcium europium fluoride **200** (1999) 490
- calcium neodymium fluoride **200** (1999) 490
- camphene **198/199** (1999) 96
- cellular solid/liquid interface **193** (1998) 701
- clathrate hydrate **196** (1999) 164
- coarse crystal faces **193** (1998) 389
- diamond **194** (1998) 353
- epsilon-caprolactam **191** (1998) 169
- gallium antimonide **195** (1998) 163
- gallium arsenide **193** (1998) 451; **194** (1998) 277; **195** (1998) 1, 21, 163, 228
- gallium indium arsenide/gallium phosphide arsenide **195** (1998) 630
- gallium indium phosphide **193** (1998) 1; **195** (1998) 13, 21, 117
- gallium nitride **195** (1998) 41, 192, 328; **197** (1999) 37; **200** (1999) 348
- gamma-aminobutyric acid **191** (1998) 803
- germanium silicon heterostructures **200** (1999) 407
- indium aluminum arsenide **200** (1999) 608
- indium antimonide **192** (1998) 84; **195** (1998) 163
- indium arsenide **195** (1998) 163
- lead tin telluride **198/199** (1999) 815
- mercury cadmium telluride **198/199** (1999) 1162
- n-paraffin **192** (1998) 307
- palladium **192** (1998) 410
- potash alum **198/199** (1999) 258
- proteins **196** (1999) 388
- silicon **200** (1999) 112, 613
- silicon carbide **194** (1998) 342
- subtilisin **193** (1998) 665
- sulphate minerals **198/199** (1999) 253
- II–VI compounds **197** (1999) 571

Theory
- of dendrite growth **198/199** (1999) 49

Thin film growth, epitaxy
- by atomic hydrogen assisted epitaxy **191** (1998) 319
- by atomic layer epitaxy
  - of gallium arsenide **195** (1998) 34; **198/199** (1999) 1111
  - of indium arsenide **195** (1998) 34, 234
  - of zinc sulphide selenide **193** (1998) 33
  - theory of electrostatic potentials **191** (1998) 143
- by chemical beam epitaxy
  - of indium phosphide **191** (1998) 44
- by direct current magnetron sputtering
  - of BSCCO **196** (1999) 122
  - of LBCO **196** (1999) 122
- by directional ion beam deposition
  - of poly-silicon **191** (1998) 718
- by electron beam deposition
  - of zinc sulphide **194** (1998) 53
- by gas source molecular beam epitaxy
  - of gallium nitride **191** (1998) 31, 34, 279
  - of indium aluminum arsenide **194** (1998) 31
  - of indium gallium arsenide **194** (1998) 31
  - of silicon **196** (1999) 115
- by hot wall epitaxy
  - of zinc sulphide **194** (1998) 61
- by hydride method
  - of gallium arsenide on silicon **192** (1998) 23
  - of indium phosphide **192** (1998) 402
- by liquid phase epitaxy
  - of aluminum gallium arsenide **194** (1998) 166
  - of aluminum nitride **200** (1999) 45
  - of barium potassium bismuthetes **198/199** (1999) 631
  - of gallium arsenide **192** (1998) 18, 23; **198/199** (1999) 1087, 1092; **200** (1999) 341
  - of gallium phosphide **193** (1998) 148
  - of indium gallium arsenide **200** (1999) 368
  - of indium phosphide **192** (1998) 11; **198/199** (1999) 1077, 1082
  - of lepidocrocite **192** (1998) 250
  - of lithium niobate **193** (1998) 605; **198/199** (1999) 526
  - of lithium niobate tantalate **193** (1998) 605
  - of lithium niobium tantalate **191** (1998) 119, 125
  - of lithium yttrium fluoride **198/199** (1999) 564
  - of magnetite **192** (1998) 250
  - of neodymium barium cuprate **193** (1998) 71
  - of neodymium YBCO **200** (1999) 435
  - of oligo(cyclohexylidene) oximes **191** (1998) 834
  - of silicon **198/199** (1999) 1045
  - of silicon carbide **197** (1999) 147
  - of yttrium iron garnet **191** (1998) 754
  - of yttrium lutetium indium gallium garnet **191** (1998) 501
  - of zinc gallium arsenide **194** (1998) 25
- by magnetron sputtering **200** (1999) 498
- by metalorganic molecular beam epitaxy
  - of gallium aluminum arsenide **194** (1998) 161; **195** (1998) 516
  - of gallium arsenide **194** (1998) 161; **195** (1998) 151; **197** (1999) 67
  - of gallium indium arsenide **195** (1998) 151, 516
  - of gallium indium arsenide phosphide **195** (1998) 510, 660
  - of gallium indium phosphide **195** (1998) 151
  - of gallium nitride **198/199** (1999) 1061
  - of gallium phosphide nitride arsenide **195** (1998) 574
  - of indium antimonide **195** (1998) 378
  - of indium gallium arsenide **194** (1998) 161; **200** (1999) 368, 375
  - of indium gallium nitride arsenide **197** (1999) 67
  - of indium gallium phosphide **193** (1998) 510
  - of indium phosphide **192** (1998) 56; **193** (1998) 470
  - of silicon germanium **193** (1998) 535
  - of III-N compounds **195** (1998) 248
  - theory of growth kinetics **193** (1998) 28
  - thermodynamic theory of III-nitrides **197** (1999) 99
- by molecular beam epitaxy
  - of aluminum **196** (1999) 1
  - of aluminum gallium arsenide **197** (1999) 54, 762
  - of aluminum gallium nitride **192** (1998) 93, 471

– – of aluminum oxide **196** (1999) 88
– – of boron titanium oxide **200** (1999) 161
– – of calcium europium fluoride **200** (1999) 490
– – of calcium neodymium fluoride **200** (1999) 490
– – of cobalt disilicide **191** (1998) 430
– – of gallium aluminum arsenide **196** (1999) 53; **198/199** (1999) 1136
– – of gallium antimonide **191** (1998) 651
– – of gallium arsenide **192** (1998) 33, 97, 363; **195** (1998) 1, 490, 740; **196** (1999) 1, 26, 53; **197** (1999) 364, 372; **198/199** (1999) 1098, 1119, 1125, 1130
– – of gallium nitride **192** (1998) 28, 93; **197** (1999) 7, 12, 31, 368
– – of germanium silicon **200** (1999) 407
– – of indium aluminum arsenide **200** (1999) 608
– – of indium arsenide **191** (1998) 361, 627, 651; **192** (1998) 97, 376; **197** (1999) 364, 372; **200** (1999) 70, 321, 603
– – of indium gallium aluminum arsenide **191** (1998) 24; **193** (1998) 285
– – of indium gallium arsenide **194** (1998) 297; **196** (1999) 1, 23; **197** (1999) 59, 84; **198/199** (1999) 1141, 1146
– – of indium gallium arsenide phosphide **197** (1999) 89, 95; **198/199** (1999) 1104
– – of indium gallium phosphide **191** (1998) 613; **195** (1998) 490; **197** (1999) 59
– – of indium phosphide **197** (1999) 789; **198/199** (1999) 1104
– – of lead tin telluride **191** (1998) 466
– – of mercury cadmium telluride **200** (1999) 102
– – of mercury cadmium zinc telluride **197** (1999) 529
– – of neodymium fluoride **192** (1998) 157
– – of nitrides **200** (1999) 353
– – of p-sexiphenyl **198/199** (1999) 923
– – of silicon **194** (1998) 426; **196** (1999) 88, 97; **200** (1999) 106, 112, 613
– – of silicon germanium **191** (1998) 697; **194** (1998) 426; **196** (1999) 97
– – of thallium phosphide **192** (1998) 372
– – of II–VI compounds **197** (1999) 557, 616
– – of zinc cadmium selenide **193** (1998) 43
– – of zinc cadmium selenide/zinc sulphur selenide **191** (1998) 679
– – of zinc gallium arsenide **194** (1998) 25
– – of zinc selenide **192** (1998) 102; **193** (1998) 528; **194** (1998) 301; **197** (1999) 557
– – theory
– – – of cadmium telluride growth simulation **193** (1998) 241
– – – of dislocation density **192** (1998) 28
– – – of doping **195** (1998) 740
– – – of mole fraction and growth rate **193** (1998) 43
– by pulsed laser deposition
– – of cerium oxide **192** (1998) 175
– – of lithium niobate **196** (1999) 141
– – of magnesium oxide **191** (1998) 472, 478
– – of zinc oxide **197** (1999) 523
– by rapid thermal chemical vapor deposition
– – of poly-silicon **191** (1998) 386
– by spray pyrolysis
– – of tin oxide **194** (1998) 369
– – of II–VI compounds **197** (1999) 858
– by sputtering
– – of BSCCO **191** (1998) 421
– – of lead zirconium titanate **191** (1998) 113
– – of platinum on magnesium oxide **192** (1998) 164
– – of YBCO **197** (1999) 376
– by vapor diffusion
– – of zinc-doped lithium niobate **194** (1998) 94
– by vapor phase epitaxy
– – theory of growth **193** (1998) 636
– – through chemical vapor deposition
– – – of diamond **191** (1998) 459, 723; **194** (1998) 353
– – – of gallium nitride **191** (1998) 641
– – – of germanium **194** (1998) 173
– – – of silicon carbide **191** (1998) 439; **193** (1998) 335; **194** (1998) 342
– – – of silicon germanium **191** (1998) 72; **193** (1998) 328; **197** (1999) 113
– – – of titanium **193** (1998) 322
– – through evaporation and condensation
– – – of gallium arsenide **193** (1998) 451
– – – of gallium indium phosphide **196** (1999) 33
– – – of mercury cadmium iodide **192** (1998) 342
– – – of silicon carbide **197** (1999) 155
– – – of silver on indium phosphide **193** (1998) 496
– – through metalorganic chemical vapor deposition
– – – of aluminum arsenide **193** (1998) 460; **194** (1998) 16; **195** (1998) 630, 644
– – – of aluminum arsenide antimonide **195** (1998) 85, 356
– – – of aluminum gallium arsenide **191** (1998) 8, 599; **192** (1998) 79; **193** (1998) 460; **195** (1998) 54, 98, 199, 459, 474, 485, 495, 558, 596, 617, 648
– – – of aluminum gallium indium phosphide **195** (1998) 124, 644
– – – of aluminum gallium nitride **195** (1998) 280, 291; **197** (1999) 73
– – – of aluminum indium arsenide **195** (1998) 603, 681
– – – of aluminum indium arsenide antimonide **195** (1998) 363
– – – of aluminum indium gallium nitride **195** (1998) 309
– – – of aluminum indium nitride **195** (1998) 309
– – – of aluminum indium phosphide **196** (1999) 13
– – – of aluminum nitride **195** (1998) 280, 733
– – – of barium titanate **195** (1998) 706
– – – of bismuth telluride **194** (1998) 336
– – – of cadmium selenide **195** (1998) 564, 569
– – – of cadmium sulphide **195** (1998) 718
– – – of cadmium telluride **192** (1998) 109; **195** (1998) 718
– – – of cadmium zinc telluride **191** (1998) 51; **197** (1999) 626
– – – of gallium aluminum arsenide antimonide **195** (1998) 181
– – – of gallium aluminum indium arsenide **195** (1998) 668
– – – of gallium aluminum indium phosphide **191** (1998) 313
– – – of gallium antimonide **195** (1998) 163, 168, 181, 363, 385
– – – of gallium arsenide **191** (1998) 357, 734; **192** (1998) 23; **193** (1998) 460, 501; **194** (1998) 277, 286, 292; **195** (1998) 1, 6, 21, 28, 58, 91, 98, 105, 117, 163, 168, 199, 205, 211, 217, 228, 416, 427, 459, 474, 524, 530, 540, 546, 558, 579, 586, 596, 617, 630, 648, 655, 711; **196** (1999) 41; **197** (1999) 777

– – – of gallium arsenide antimonide **195** (1998) 356
– – – of gallium arsenide phosphide **195** (1998) 630
– – – of gallium indium antimonide **195** (1998) 363, 385
– – – of gallium indium arsenide **195** (1998) 48, 112, 144, 217, 421, 540, 617, 630, 648, 655, 676, 687, 681
– – – of gallium indium arsenide antimonide **191** (1998) 39, 631; **195** (1998) 181, 346, 363
– – – of gallium indium arsenide nitride **195** (1998) 391, 401, 409, 416, 421, 438
– – – of gallium indium arsenide phosphide **195** (1998) 444, 466, 609, 624, 637, 644, 660, 694, 700
– – – of gallium indium phosphide **193** (1998) 1; **194** (1998) 272; **195** (1998) 13, 21, 117, 132, 217, 223, 591, 609
– – – of gallium nitride **191** (1998) 1, 275, 621, 646; **193** (1998) 23, 127, 300, 478, 484, 491; **195** (1998) 41, 187, 192, 228, 258, 265, 270, 274, 280, 304, 314, 319, 323, 328, 333, 340, 427, 459,733; **196** (1999) 41; **197** (1999) 37, 73
– – – of gallium phosphide **195** (1998) 174, 574
– – – of indium aluminum gallium phosphide **195** (1998) 63
– – – of indium antimonide **195** (1998) 163
– – – of indium arsenide **195** (1998) 28, 163, 168, 205, 234, 356, 373, 524, 530
– – – of indium arsenide antimonide **195** (1998) 356, 373
– – – of indium arsenide phosphide **191** (1998) 347; **195** (1998) 356, 373, 552
– – – of indium gallium arsenide **191** (1998) 332, 607; **192** (1998) 47; **197** (1999) 25, 755, 777
– – – of indium gallium arsenide nitride **192** (1998) 381
– – – of indium gallium arsenide phosphide **193** (1998) 293; **194** (1998) 8
– – – of indium gallium nitride **195** (1998) 242, 252, 258, 286, 297, 397; nitride **197** (1999) 48, 78
– – – of indium phosphide **191** (1998) 18, 341; **193** (1998) 9, 16; **195** (1998) 48, 69, 74, 91, 138, 174, 444, 459, 479, 503, 546, 603, 624, 660, 681; **197** (1999) 19
– – – of indium phosphide antimonide **193** (1998) 50
– – – of iron oxide **192** (1998) 423
– – – of lithium aluminate **193** (1998) 127
– – – of magnesium selenide **193** (1998) 572
– – – of mercury cadmium telluride **191** (1998) 594; **197** (1999) 542, 547
– – – of nickel ferrite **192** (1998) 423
– – – of nickel oxide **192** (1998) 423
– – – of nickel zinc ferrite **192** (1998) 423
– – – of III–V compounds **193** (1998) 305
– – – of YBCO **191** (1998) 79, 290
– – – of zinc arsenide **196** (1999) 77
– – – of zinc ferrite **192** (1998) 423
– – – of zinc magnesium sulphide selenide **193** (1998) 50
– – – of zinc oxide **192** (1998) 423
– – – of zinc selenide **191** (1998) 65, 663; **197** (1999) 507
– – – of zinc sulphide **195** (1998) 564; **197** (1999) 805
– – – of zinc sulphide selenide **195** (1998) 569
– – through pulsed laser deposition
– – – of cadmium selenide **193** (1998) 516
– – through sputtering
– – – of gallium arsenide germanium **197** (1999) 783
– – – of magnesium oxide **197** (1999) 849
– – – of zinc oxide **193** (1998) 316

Vapor growth technique
– by arc discharge
– – of carbon nanotubes **198/199** (1999) 934
– by chemical transport
– – of cadmium telluride **191** (1998) 377
– – of gallium nitride **192** (1998) 73; **194** (1998) 37
– – of titania **200** (1999) 527
– – of zinc oxide **198/199** (1999) 968
– – of zinc selenide **196** (1999) 83; **197** (1999) 449; **198/199** (1999) 968
– by chemical vapor deposition
– – of copper **193** (1998) 133
– – of diamond **200** (1999) 446
– – of gallium nitride **198/199** (1999) 1056; **200** (1999) 55
– – of germanium silicon alloys **198/199** (1999) 1032
– – of potassium tungsten oxide bronze **197** (1999) 1008
– – of silicon **198/199** (1999) 1039
– – of silicon carbide **197** (1999) 841; **200** (1999) 458
– – of III–V compounds **200** (1999) 19
– – of tungsten oxide **198/199** (1999) 1130, 1235, 1240
– – of zinc oxide **198/199** (1999) 1122
– by close-space vapor transport
– – of cadmium sulphide **197** (1999) 733
– – of cadmium telluride **197** (1999) 733
– – of cadmium zinc telluride **197** (1999) 799
– – of gold **197** (1999) 955
– – of zinc selenide **197** (1999) 497
– by direct reaction
– – of lithium zinc nitride **198/199** (1999) 802
– by direct vapor transport
– – of tungsten selenide **197** (1999) 833
– by evaporation and condensation
– – of alpha-hexathiophene **193** (1998) 563
– – of alpha-quaterthiophene **193** (1998) 563
– – of barium titanate **197** (1999) 905
– – of cadmium telluride **191** (1998) 673; **198/199** (1999) 984
– – of cadmium zinc telluride **191** (1998) 673; **197** (1999) 423, 663, 666
– – of C_{60} **200** (1999) 441
– – of copper indium selenide **198/199** (1999) 316
– – of gallium arsenide **193** (1998) 451
– – of graphite **198/199** (1999) 939
– – of indium gallium phosphide **196** (1999) 33
– – of lysozyme **194** (1998) 384
– – of mercuric iodide **193** (1998) 80, 90
– – of mercurous iodide **198/199** (1999) 995
– – of mercury cadmium iodide **192** (1998) 342
– – of molybdenum trioxide **197** (1999) 186
– – of neodymium acetylacetonate **198/199** (1999) 1226
– – of organic films **193** (1998) 732
– – of oxide **198/199** (1999) 1226
– – of paraffin crystals **191** (1998) 563
– – of proteins **196** (1999) 356, 674
– – of samarium monosulphide **191** (1998) 285

– – of silicon carbide **191** (1998) 84; **193** (1998) 101; **197** (1999) 155; **198/199** (1999) 1011, 1015, 1019
– – of thaumatin **194** (1998) 384
– – of titanium dioxide **198/199** (1999) 894
– – of yttrium acetylacetonate **198/199** (1999) 1226
– – of yttrium oxide **198/199** (1999) 1226
– – of zinc selenide **192** (1998) 386; **197** (1999) 449, 455, 513; **198/199** (1999) 980
– – of zinc telluride **197** (1999) 423
– by hot wall epitaxy
– – of platinum/magnesium oxide/silicon multilayers **194** (1998) 89
– by Markov method
– – of zinc selenide **197** (1999) 517
– by metalorganic chemical vapor deposition
– – of aluminum gallium indium phosphide **200** (1999) 382
– – of cadmium telluride **198/199** (1999) 1184; **200** (1999) 90
– – of cadmium zinc telluride **198/199** (1999) 1174, 1179
– – of gallium nitride **200** (1999) 63, 85
– – of indium gallium arsenide **200** (1999) 77, 559
– – of indium gallium nitride **200** (1999) 85
– – of lead telluride **198/199** (1999) 1216
– – of mercury cadmium telluride **198/199** (1999) 1165
– – of II–VI compounds **198/199** (1999) 1151, 1157
– – of zinc magnesium sulphide **198/199** (1999) 1196
– – of zinc selenide **198/199** (1999) 1170; **200** (1999) 399
– by physical vapor transport
– – of silicon carbide **198/199** (1999) 1005
– by plasma assisted chemical vapor deposition
– – of graphitic nanofibres **193** (1998) 342
– by pulsed laser deposition
– – of cerium oxide **200** (1999) 505
– – of cadmium selenide **193** (1998) 516
– – of carbon nitride **198/199** (1999) 1028
– – of gallium nitride **200** (1999) 362
– by sputtering
– – of zinc oxide **193** (1998) 316
– by sublimation
– – of silicon carbide **198/199** (1999) 1024
– – of zinc selenide **191** (1998) 59
– by vapor diffusion
– – of lysozyme **196** (1999) 332
– – of polyethylene glycol **196** (1999) 250
– theory
– – of nucleation **193** (1998) 426
– – of transient binary nucleation **194** (1998) 239

Vapor–liquid–solid growth
– of n-paraffin **191** (1998) 861
– of pentlandite **193** (1998) 728
– of proteins **196** (1999) 434
– of titanium carbide whiskers **193** (1998) 585
– of zinc selenide whiskers **193** (1998) 528

Whiskers growth
– of niobium carbide **200** (1999) 143
– of silicon **200** (1999) 106
– of silicon carbide **200** (1999) 467
– of silicon nanowires **197** (1999) 136
– of titanium carbide **193** (1998) 585
– of zinc selenide **193** (1998) 528

Journal of Crystal Growth

Instructions to Authors (short version)

Submission of papers

Manuscripts (one original + two copies) should be sent to a member of the Editorial Board or preferably to an appropriate subject Associate Editor. Priority communications should be sent to L.F. Schneemeyer. News or announcements should be submitted through the Principal Editor; a duplicate should be sent directly to Elsevier Science B.V., address given below.

Original material. Submission of a manuscript implies it is not being simultaneously considered for publication elsewhere and that the authors have obtained the necessary authority for publication.

Types of contributions

Original research papers and Priority communications are welcome. They should contain an Abstract (of up to 200 words) and a Conclusions section, which particularly in the case of theoretical papers translates the results into terms readily accessible to most readers.

As a guideline: *experimental papers* should not be longer than 16 double-spaced typed pages, and 8 figures + tables; for *theoretical papers* a maximum of 20 pages and 10 figures + tables is suggested.

Priority communications should not be longer than 5 double-spaced typed pages, and 3 figures + tables. They will be given priority in both the refereeing and production processes. The faster production schedule may preclude sending proofs of Priority communications to authors.

Manuscript preparation

All manuscripts should be written in good English. The paper copies of the text should be prepared with double line spacing and wide margins, on numbered sheets.

Structure. Please adhere to the following order of presentation: Article title, Author(s), Affiliation(s), Abstract, PACS codes and keywords, Main text, Acknowledgements, Appendices, References, Figure captions, Tables.

Corresponding author. The name, complete postal address, telephone and fax numbers and the e-mail address of the corresponding author should be given on the first page of the manuscript.

Classification codes/keywords. Please supply one to four classification codes (PACS and/or MSC) and up to six keywords of your own choice that describe the content of your article in more detail.

References. References to other work should be consecutively numbered in the text using square brackets and listed by number in the Reference list. Please refer to the more detailed instructions for examples.

Illustrations

Illustrations should also be submitted in triplicate: one master set and two sets of copies. The *line drawings* in the master set should be original laser printer or plotter output or drawn in black india ink, with careful lettering, large enough (3–5 mm) to remain legible after reduction for printing. The *photographs* should be originals, with somewhat more contrast than is required in the printed version. They should be unmounted unless part of a composite figure. Any scale markers should be inserted on the photograph itself, not drawn below it.

Colour plates. Figures may be published in colour, if this is judged essential by the Editor. The Publisher and the author will each bear part of the extra costs involved. Further information is available from the Publisher.

After acceptance

Important. When page proofs of the accepted manuscripts are made and sent out to authors, this is in order to check that no undetected errors have arisen in the typesetting (or file conversion) process. At the proof stage only printer's errors may be corrected. No changes in, or additions to, the edited manuscript will be accepted.

Notification. The authors will receive the final answer of acceptance or rejection from the Editorial Board or Associate Editor and will be invited to supply an electronic version of the accepted text, if this is not already available.

Copyright transfer. In the course of the production process you will be asked to transfer the copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.

Electronic manuscripts

The Publisher welcomes the receipt of an electronic version of your accepted manuscript. If there is not already a copy of this (on diskette) with the journal editor at the time the manuscript is being refereed, you will be asked to send a file with the text of the accepted manuscript directly to the Publisher by e-mail or on diskette (allowed formats 3.5″ or 5.25″ MS-DOS, or 3.5″ Macintosh) to the address given below. (When e-mailing a non-ASCII word-processor file, you should encode it, e.g. with UUENCODE or BinHex, so as to retain all formatting codes.) The name and version of the word-processing program and the type of operating system should always be indicated. Please note that no deviations from the version accepted by the Editor of the journal are permissible without the prior and explicit approval by the Editor. Such changes should be clearly indicated on an accompanying printout of the file.

Author benefits

No page charges. Publishing in Journal of Crystal Growth is free.

Free offprints. The corresponding author will receive 25 offprints free of charge. An offprint order form will be supplied by the Publisher for ordering any additional paid offprints.

Discount. Contributors to Elsevier Science journals are entitled to a 30% discount on all Elsevier Science books.

Further information (after acceptance)

Elsevier Science B.V., J. Crystal Growth
Issue Management
Physics and Astronomy
P.O. Box 2759, 1000 CT Amsterdam
The Netherlands
Fax: +31 20 485 2319/ +31 20 485 2704
E-mail: a.koch@elsevier.nl

North-Holland, an imprint of Elsevier Science

JOURNAL OF
CRYSTAL GROWTH

Abstracted/Indexed in: Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineered Materials Abstracts; Engineering Index: INSPEC; Metals Abstracts

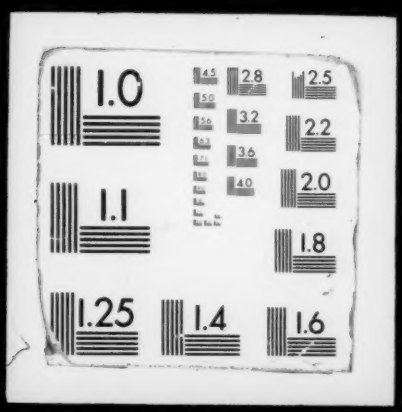
CONTENTS

Author index to volumes 191–200 635
Subject index to volumes 191–200 709

CONTENTS DIRECT

This journal is part of **ContentsDirect,** the ***free*** alerting service which sends tables of contents by e-mail for Elsevier Science books and journals. The quickest way to register for **ContentsDirect** is via the World Wide Web at: **www.elsevier.nl/locate/ContentsDirect.**
If you don't have access to the WWW you can register for this service by sending an e-mail message to cdsubs@elsevier.co.uk specifying the title of the publication you wish to register for. The tables of contents are also available on the Elsevier Science website at: www.elsevier.nl or www.elsevier.com or www.elsevier.co.jp.

0022-0248(1999)200;1-V


1.0
1.1
1.25
1.4
1.6
1.8
2.0
2.2
2.5
2.8
3.2
3.6
4.0
4.5
5.0
5.6
6.3
7.1
8.0
9.0
10.0